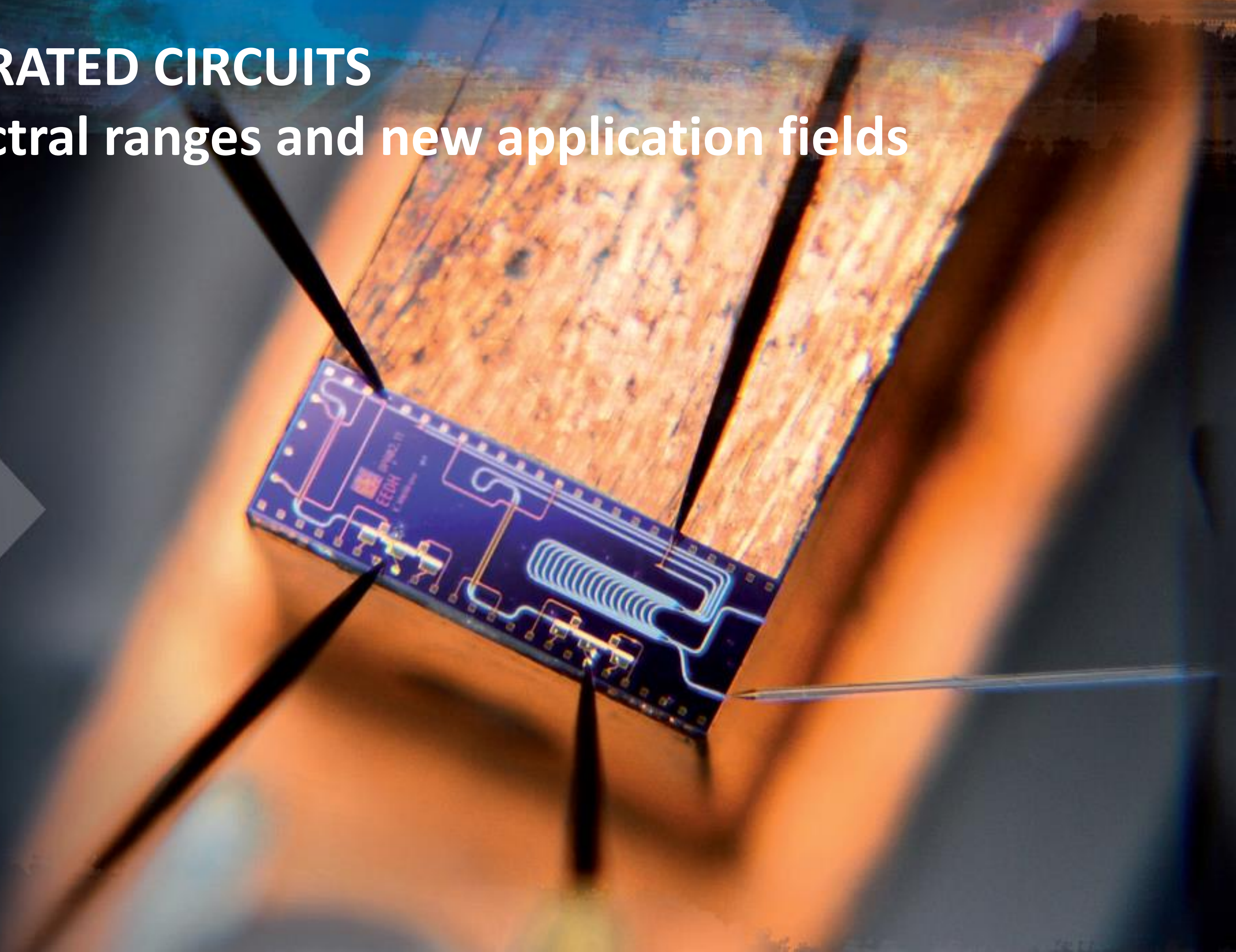


PHOTONIC INTEGRATED CIRCUITS

- toward new spectral ranges and new application fields

Ryszard Piramidowicz



PHOTONIC INTEGRATED CIRCUITS

- toward new spectral ranges and new application fields

Ryszard Piramidowicz

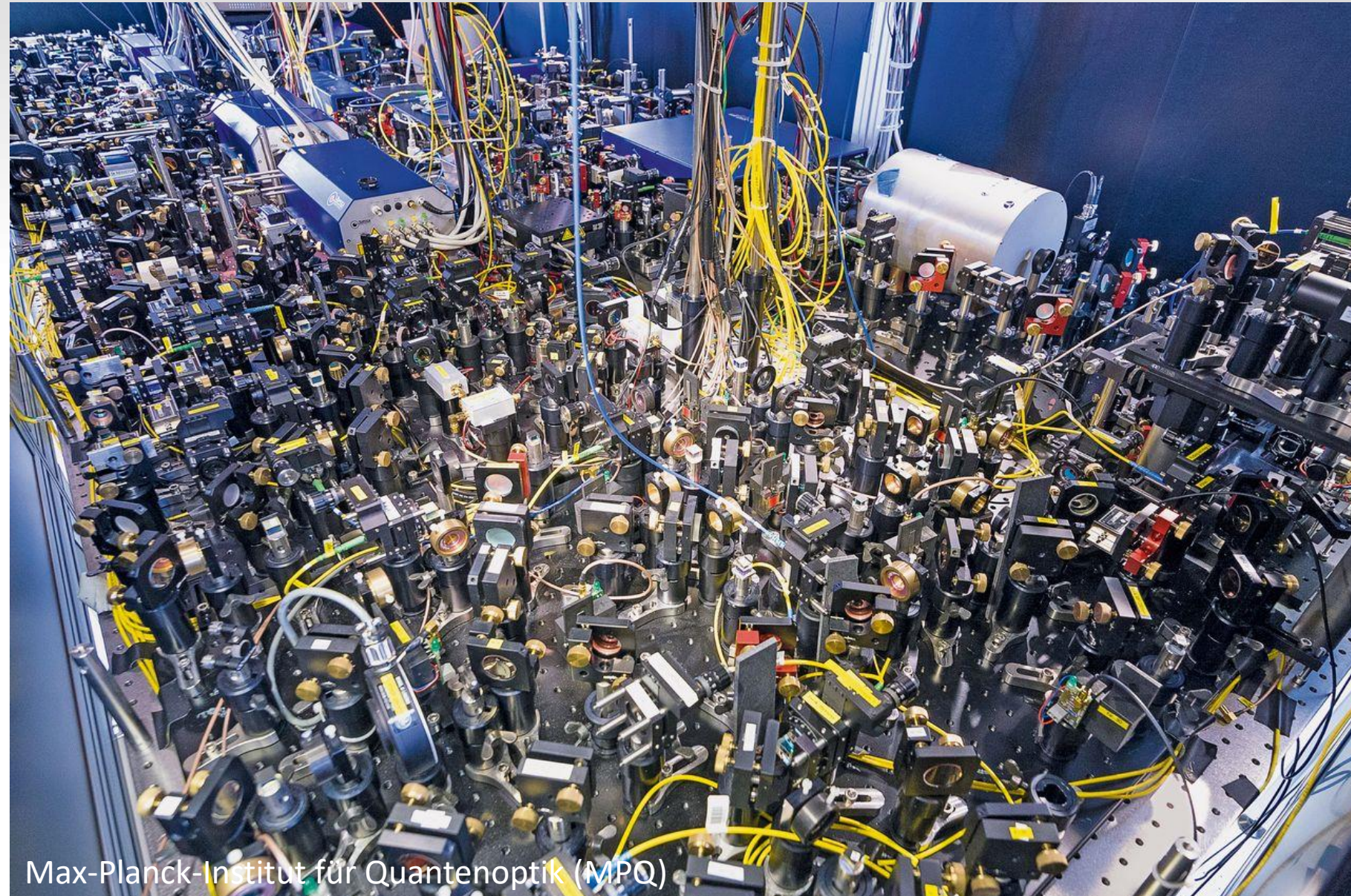


*S. STOPIŃSKI, K. ANDERS, A. JUSZA, M. LELIT, A. POŁATYŃSKI,
A. BIENIEK-KACZOREK, A. PAŚNIKOWSKA,
P. WIŚNIEWSKI, M. SŁOWIKOWSKI, M. JUCHNIEWICZ,
J. JUREŃCZYK, M. LIEBERT, K. PIERŚCIŃSKI, D. PIERŚCIŃSKA*



What is integrated photonics about?



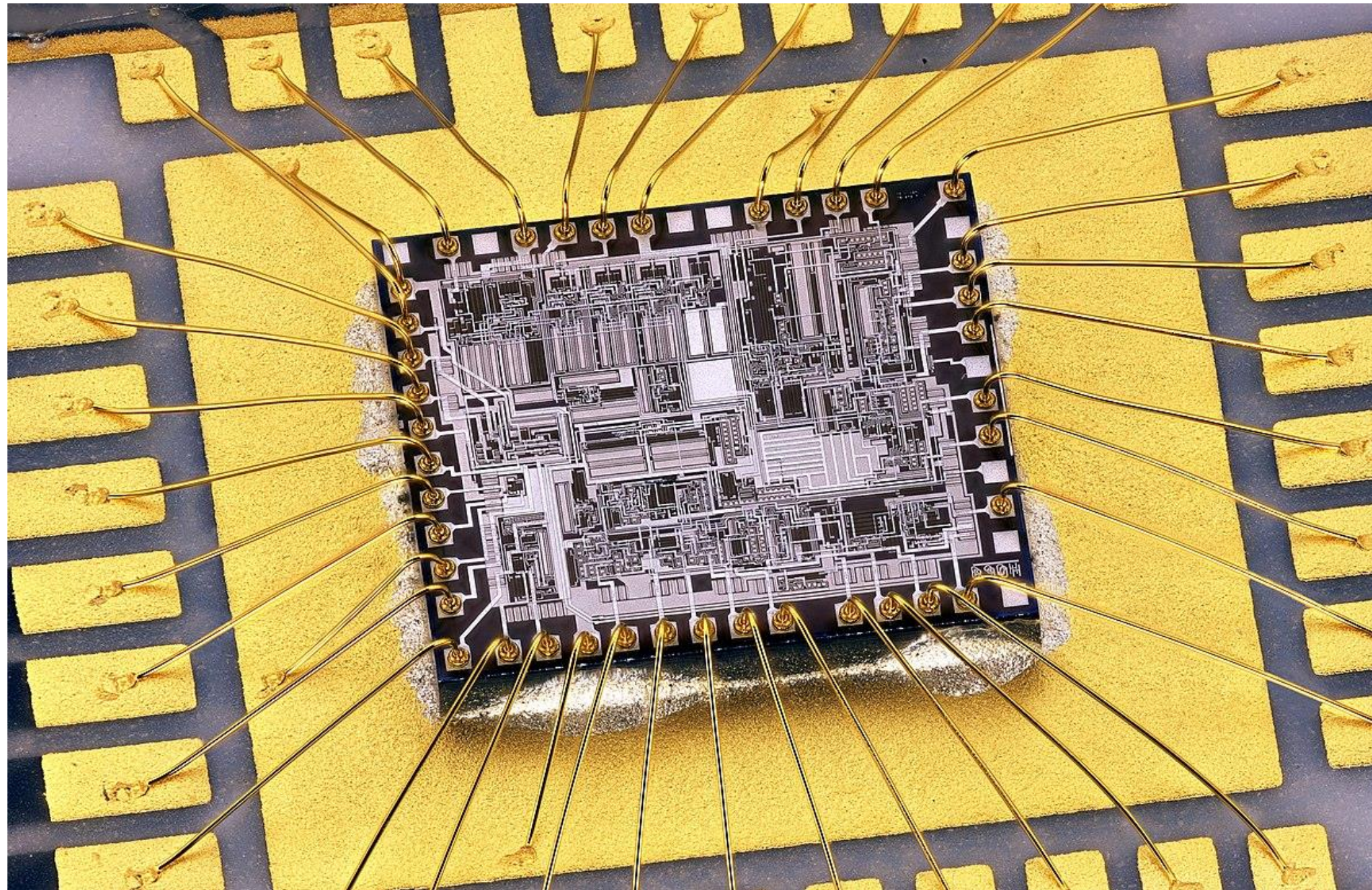


Advantages:

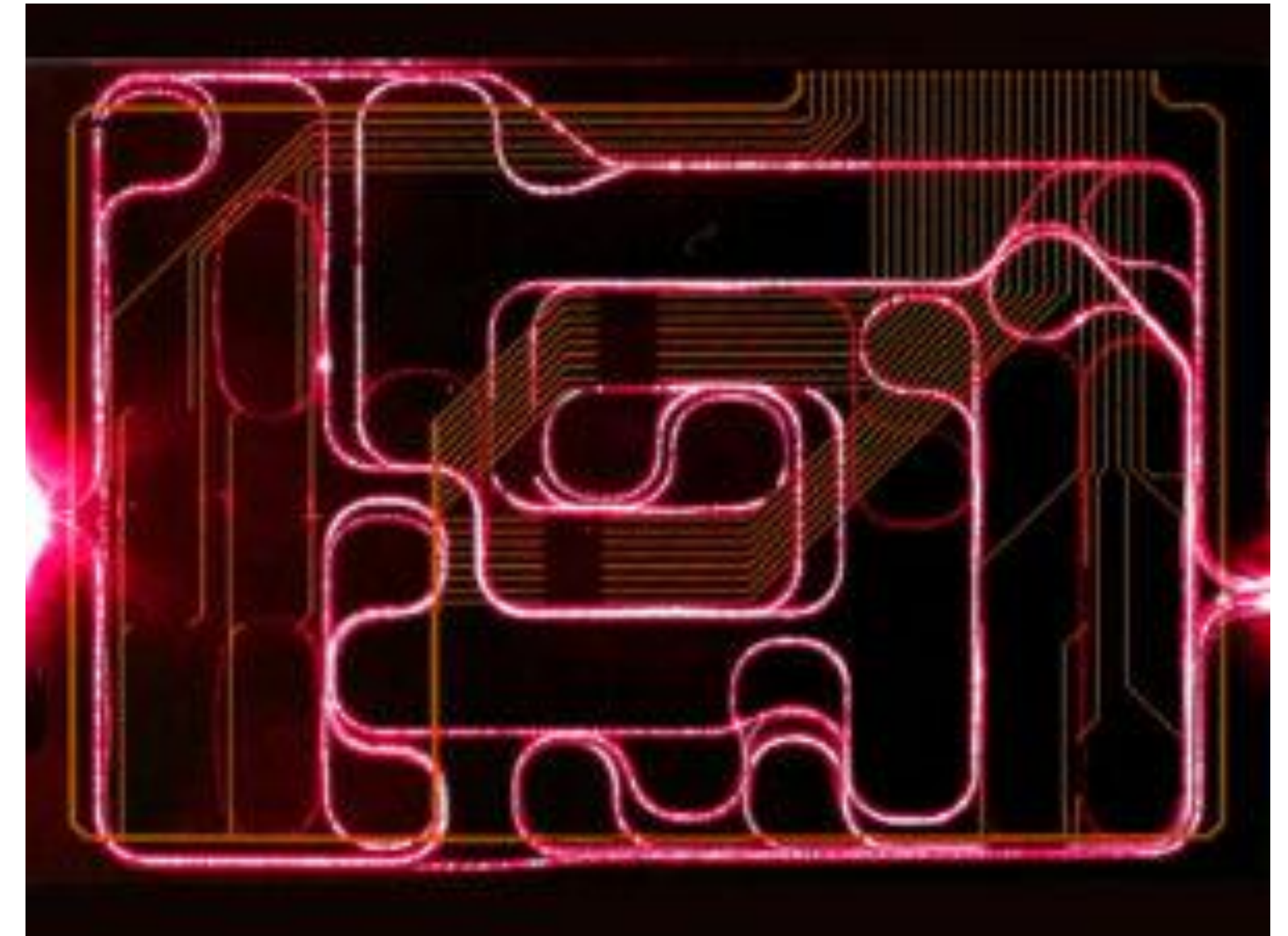
- compactness
- low power consumption
- high reliability
- reduction of packaging costs
- low manufacturing and exploitation costs

Integrated Photonics at glance

Integrated Electronics



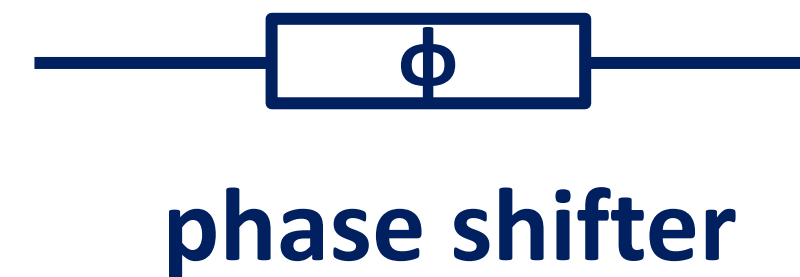
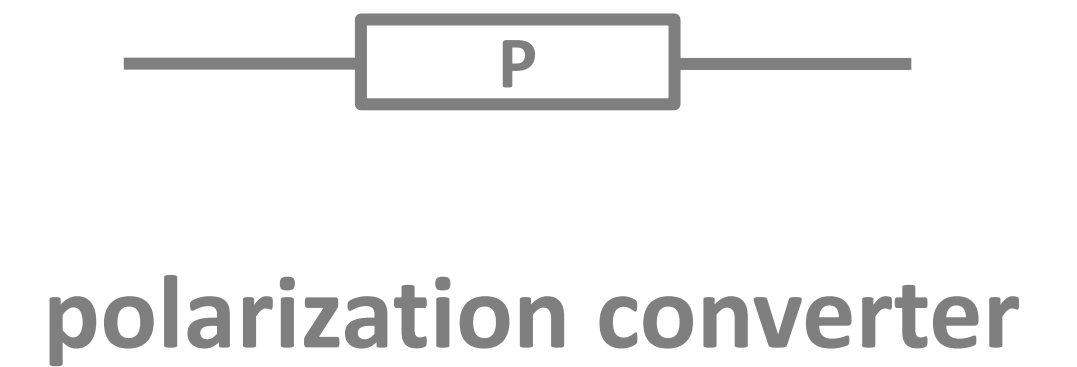
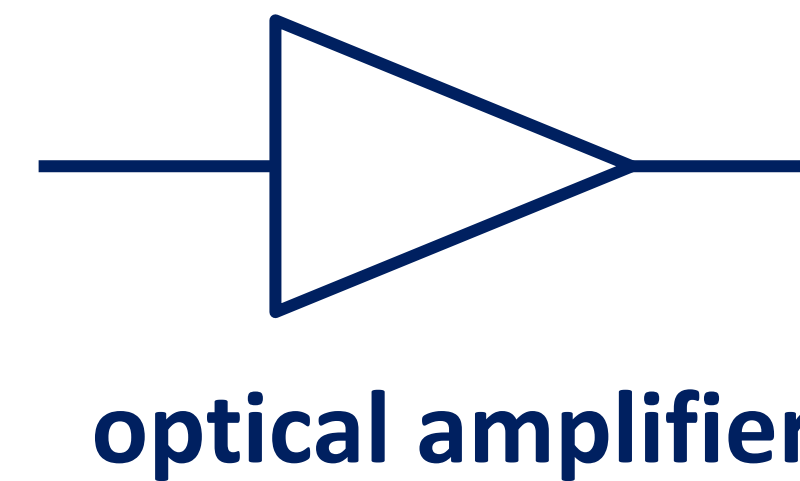
Integrated Photonics



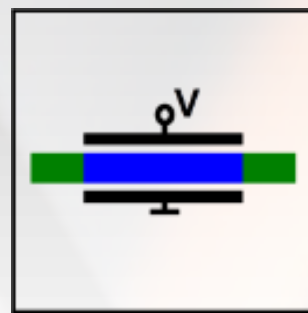
Electronic Building Blocks



Photonic Building Blocks



Generic integration technology



MMI-couplers and filters



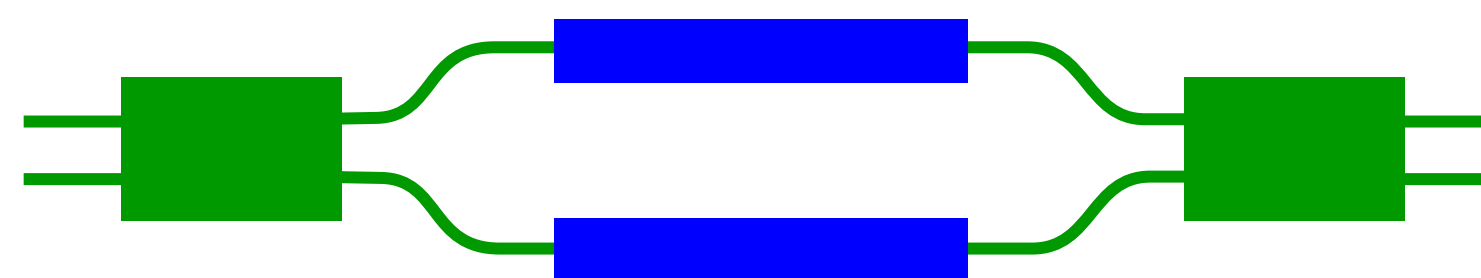
amplitude modulator



Fabry-Perot lasers



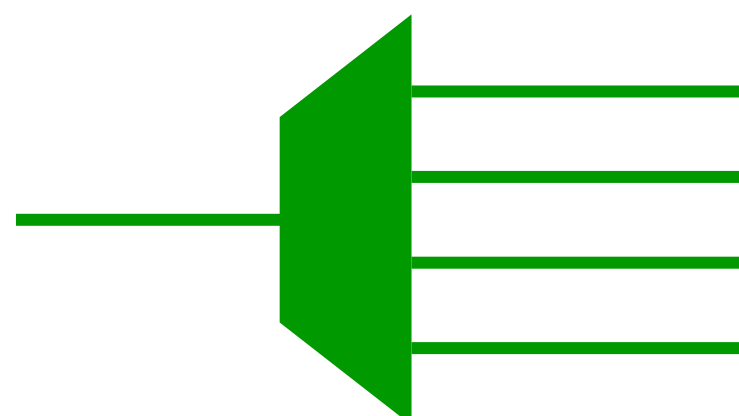
MMI-reflectors



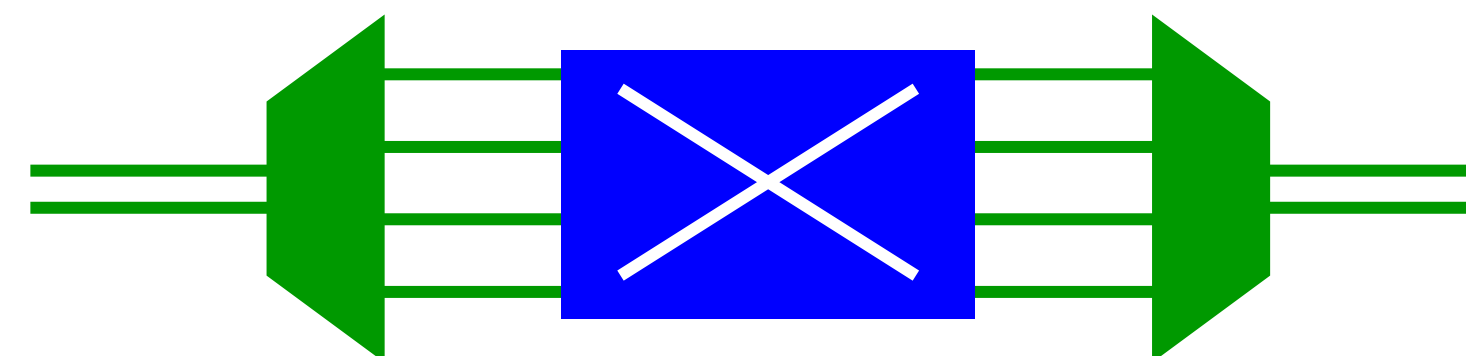
fast space switch



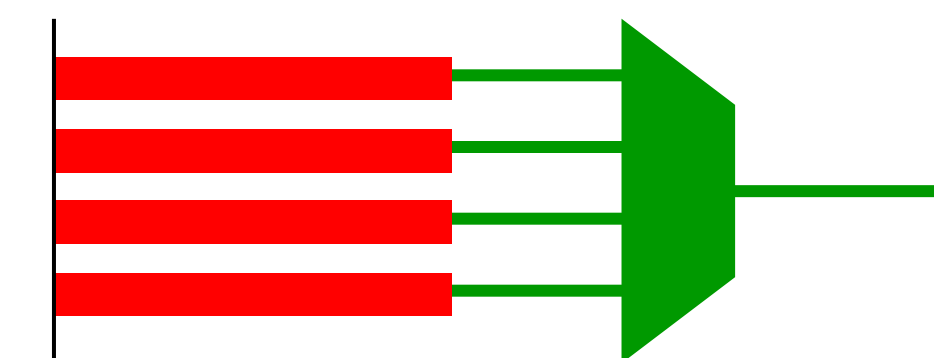
tunable DBR lasers



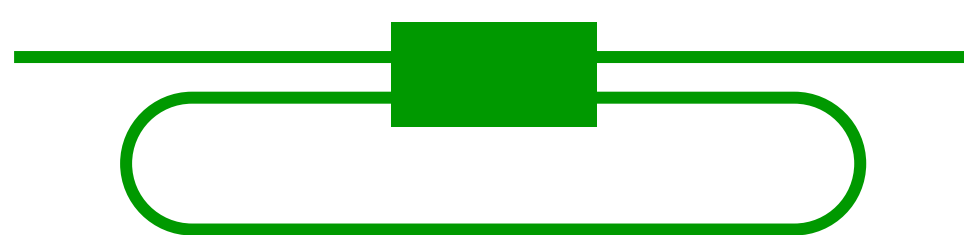
AWG-demux



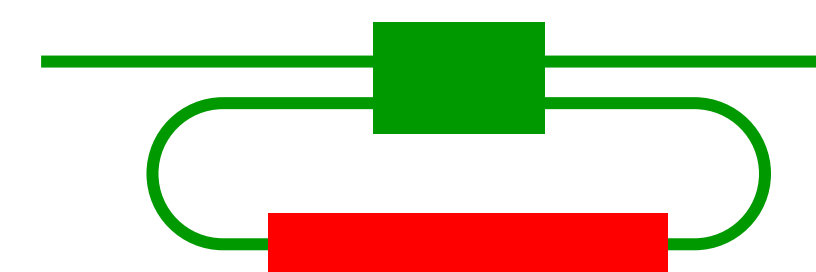
WDM cross-connect
WDM add-drop



multiwavelength lasers



ring filters



ring lasers

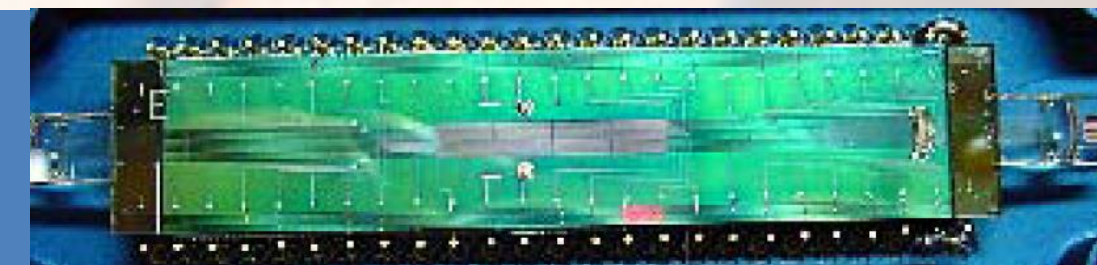
Technological platforms of integrated photonics



PIC

Si (silicon photonics)

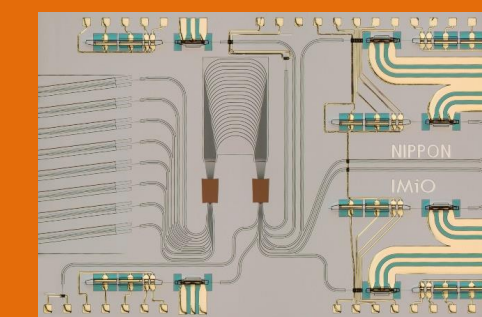
passive components and devices



Si Multichannel modulator

InP and related materials (InGaAsP)

active for 900–1800 nm window



InP multichannel transmitter

Si₃N₄ on SiO₂

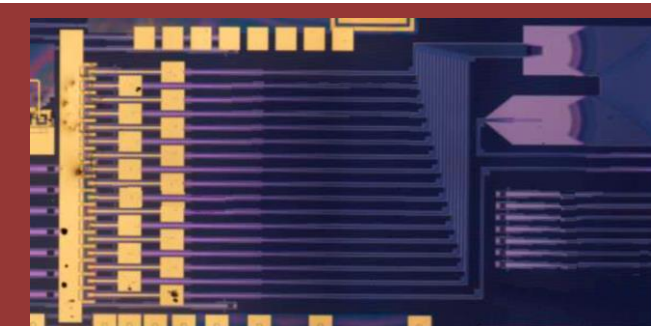
passive



Si₃N₄ on SiO₂ optical ring resonator

Hybrid/heterogeneous

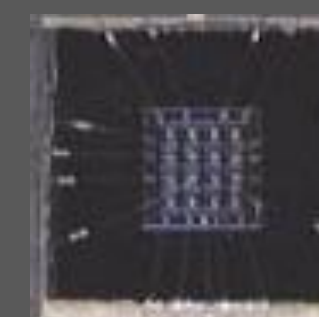
combined potential of various platforms



Si photonic AWG with integrated photodetectors

GaAs

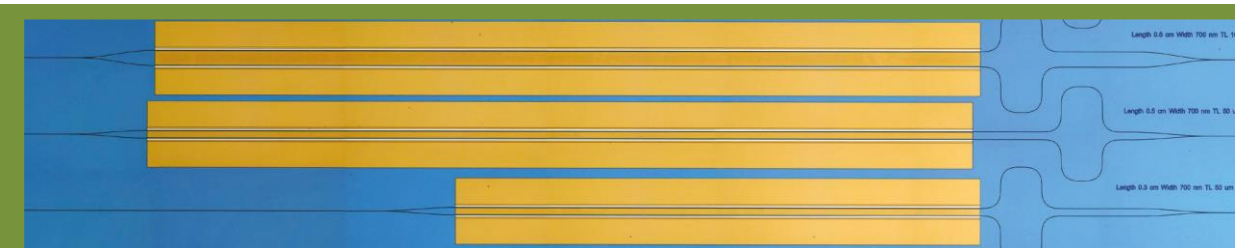
active for 600–900 nm window



GaAs chip for cancer diagnose

Dielectric

(e.g. LiNbO₃; RE³⁺-doped)



LiNbO₃ modulators

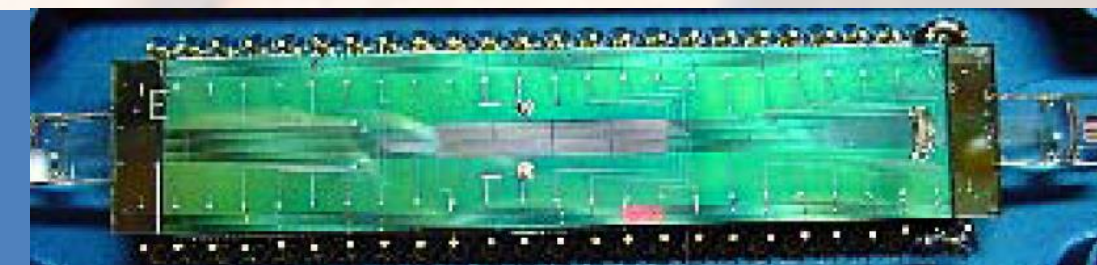
Technological platforms of integrated photonics



PIC

Si (silicon photonics)

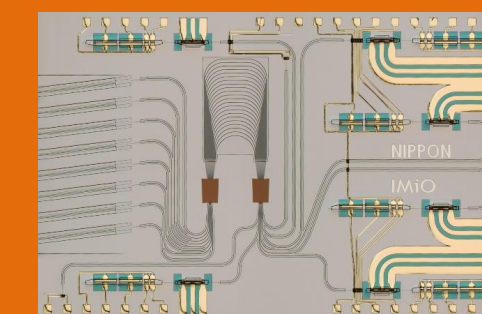
passive components and devices



Si Multichannel modulator

InP and related materials (InGaAsP)

active for 900–1800 nm window



InP multichannel transmitter

Si₃N₄ on SiO₂

passive



Si₃N₄ on SiO₂ optical ring resonator

Hybrid/heterogeneous

combined potential of various platforms



Si photonic AWG with integrated photodetectors

GaAs

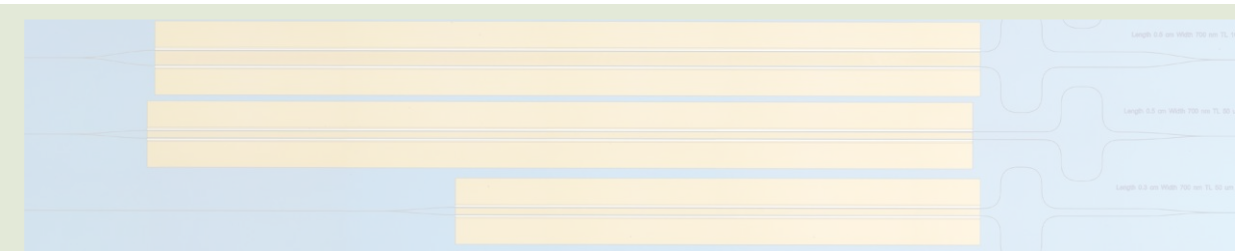
active for 600–900 nm window



GaAs chip for cancer diagnose

Dielectric

(e.g. LiNbO₃; RE³⁺-doped)



LiNbO₃ modulators

Technological platforms of integrated photonics

	Indium phosphide (InP)	Silicon (SOI)	Silicon nitride (Si ₃ N ₄)
Light generation and amplification	Yes	No (hybrid integration)	No (hybrid integration)
Light modulation	Electro-optic effect Carrier injection/depletion Electro-absorption Thermo-optic	No electro-optic effect Carrier injection/depletion Electro-absorption Thermo-optic	No electro-optic effect No carrier injection/depletion No electro-absorption Thermo-optic
Light detection @1550 nm	InGaAs/InGaAsP PIN photodiodes	Ge photodiodes	No
Index contrast	Low (large bending radii)	High (small bending radii)	Moderate (moderate bending radii)
Propagation loss @1550 nm	~1-2 dB/cm	0.1-0.5 dB/cm	0.02-0.5 dB/cm
Wavelength range	0.9 – 1.7 μm	1.2 – 3.7 μm	0.4 – 3.7 μm

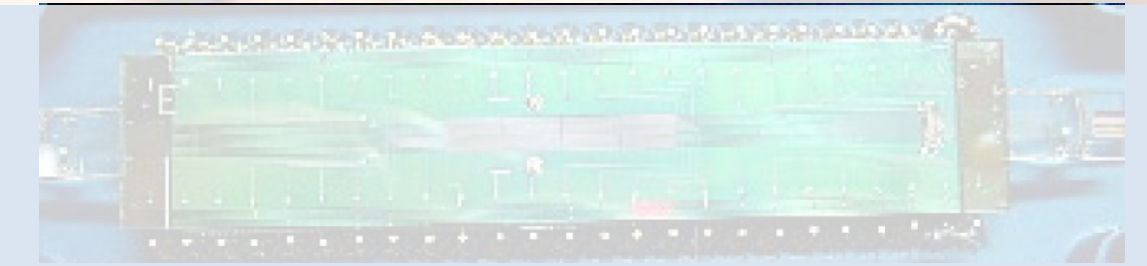
Technological platforms of integrated photonics



PIC

Si (silicon photonics)

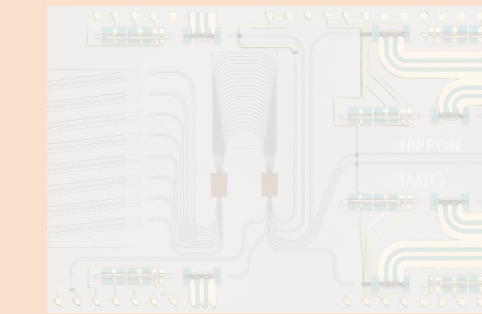
passive components and devices



Si Multichannel modulator

InP and related materials (InGaAsP)

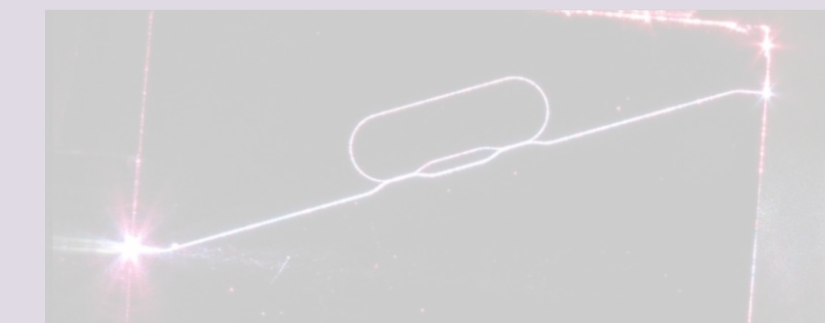
active for 900–1800 nm window



InP multichannel transmitter

Si₃N₄ on SiO₂

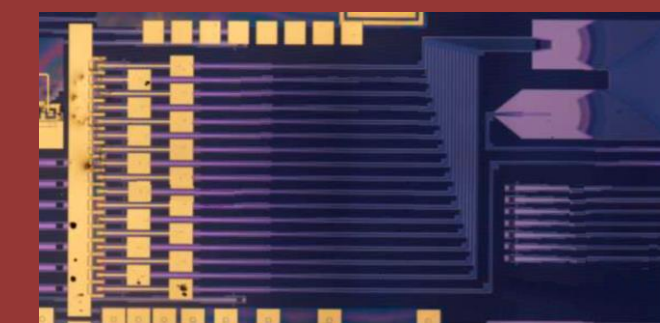
passive



Si₃N₄ on SiO₂ optical ring resonator

Hybrid/heterogeneous

combined potential of various platforms



Si photonic AWG with integrated photodetectors

GaAs

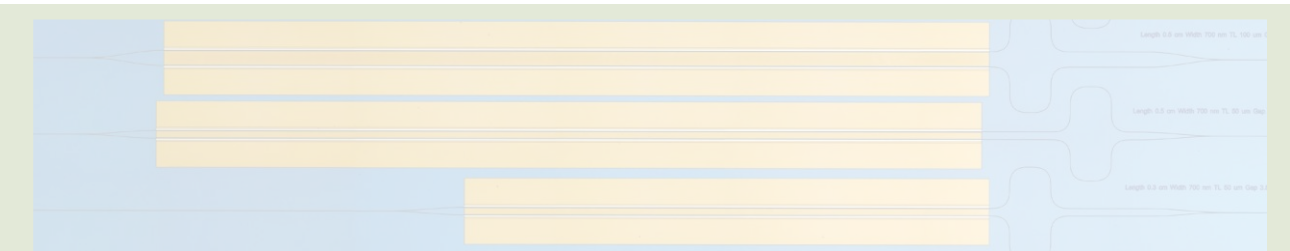
active for 600–900 nm window



GaAs chip for cancer diagnose

Dielectric

(e.g. LiNbO₃; RE³⁺-doped)



LiNbO₃ modulators

Technological platforms of integrated photonics



PIC

Si (silicon photonics)

passive components and devices

InP and related materials (InGaAs)

active for 900–1800 nm window

Si₃N₄ on SiO₂

passive

Hybrid/heterogeneous

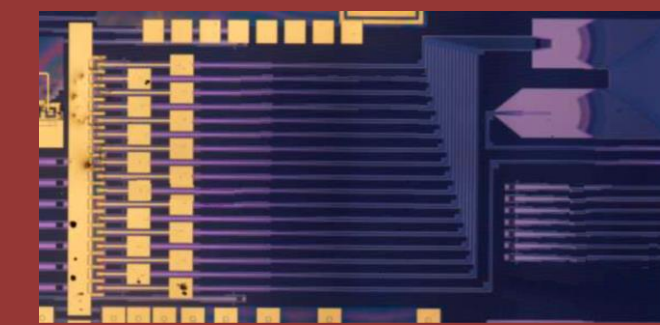
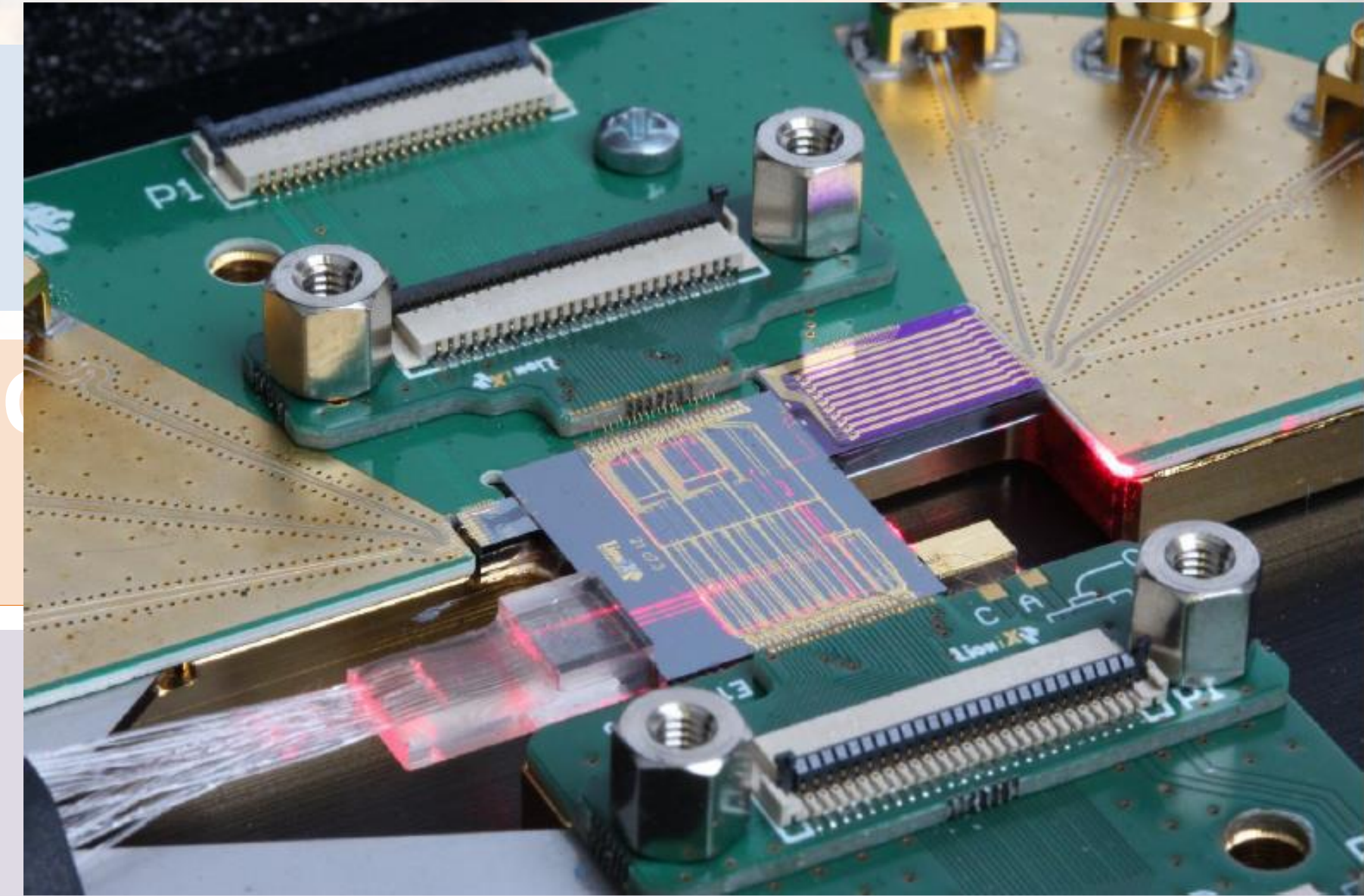
combined potential of various platforms

GaAs

active for 600–900 nm window

Dielectric

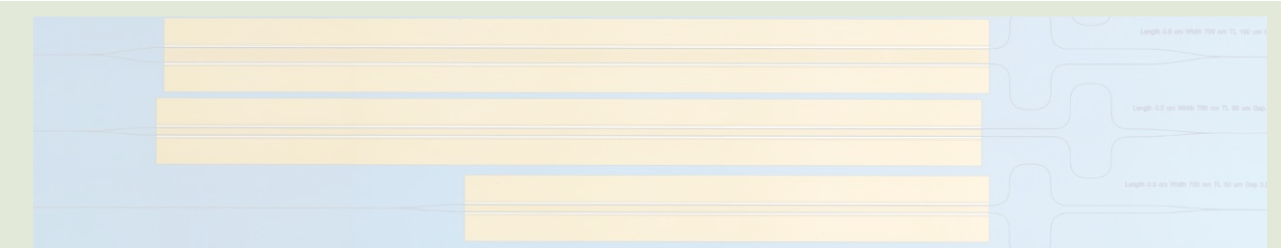
(e.g. LiNbO₃; RE³⁺-doped)



Si photonic AWG with integrated photodetectors



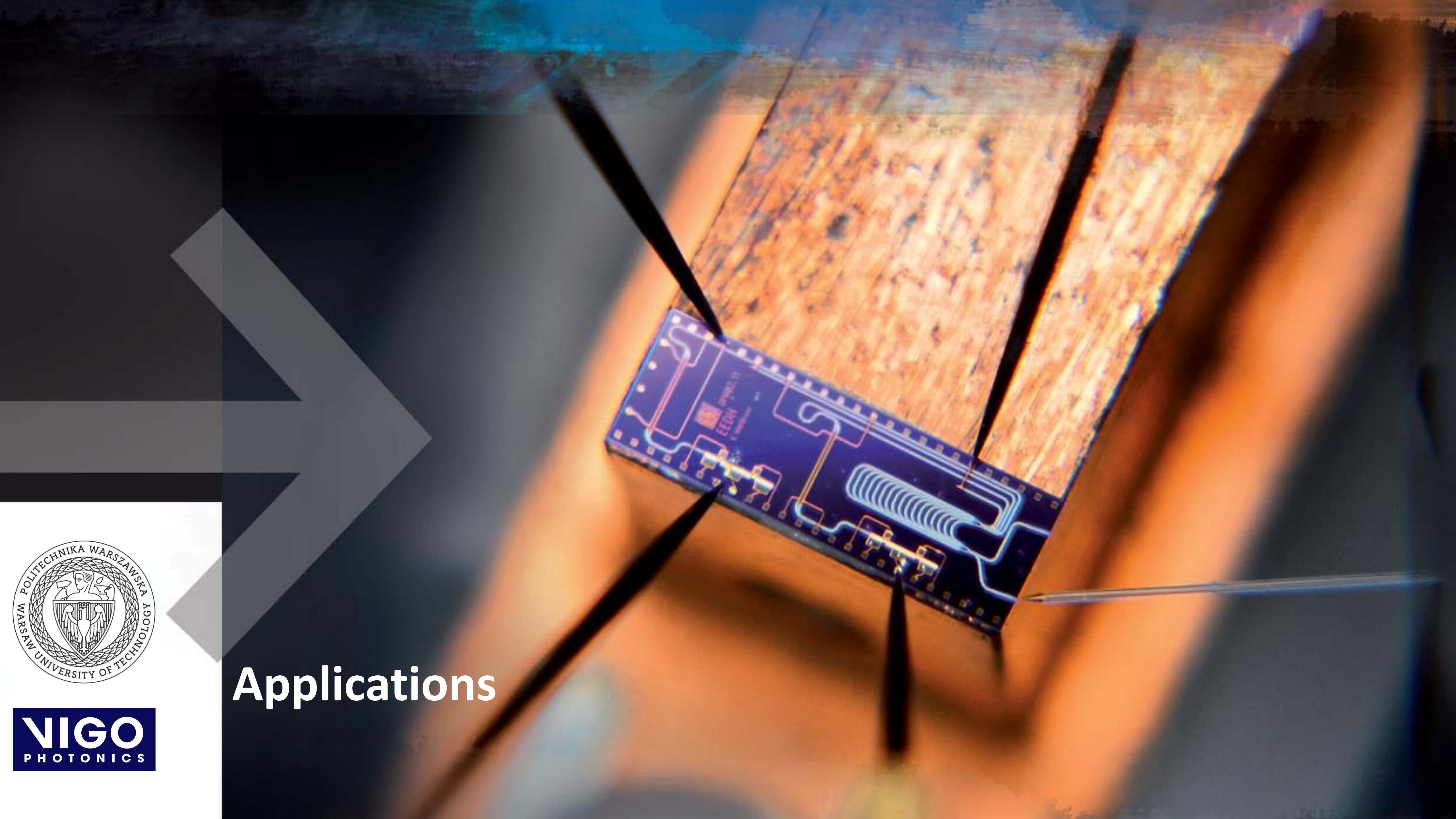
GaAs chip for cancer diagnose



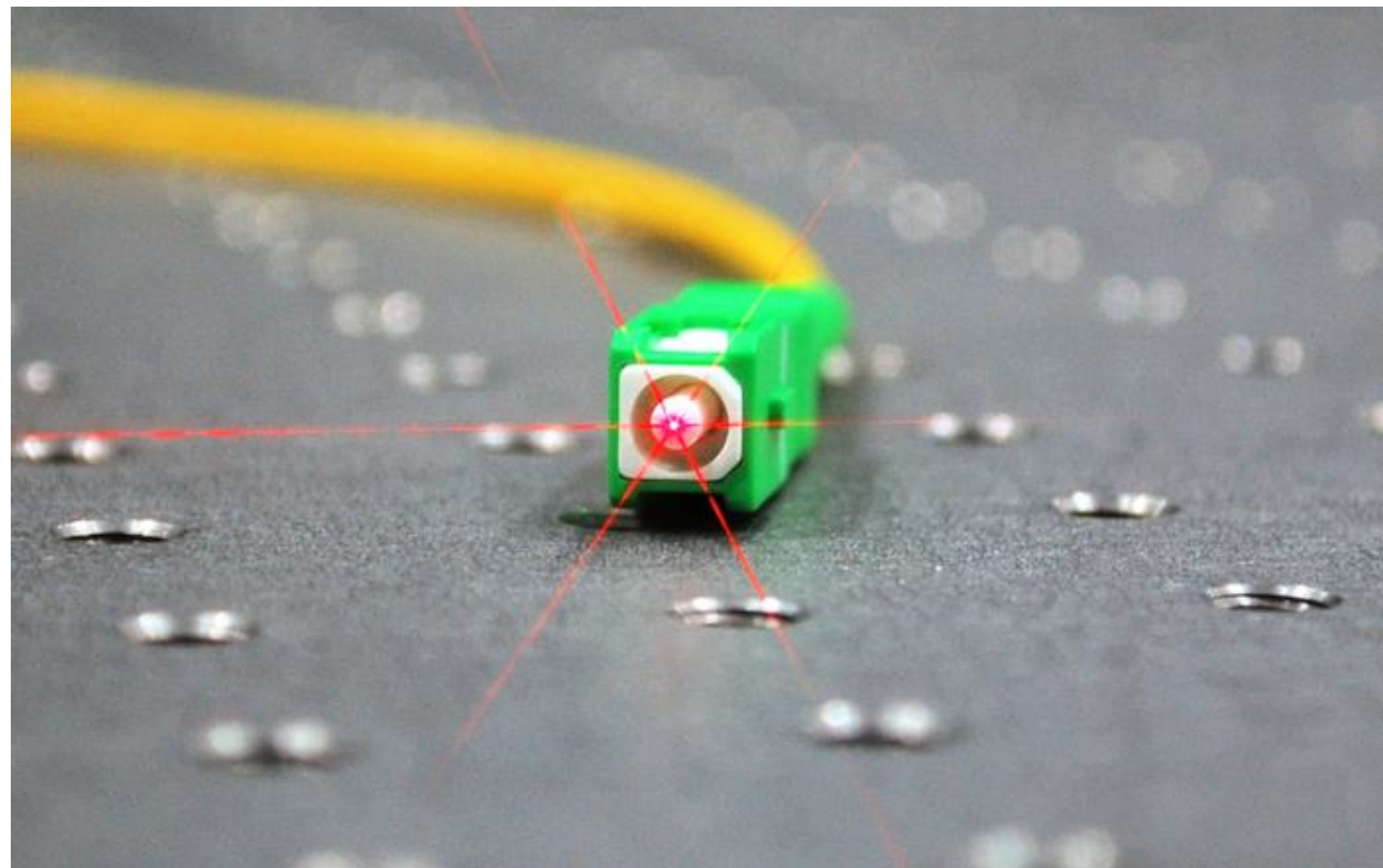
LiNbO₃ modulators



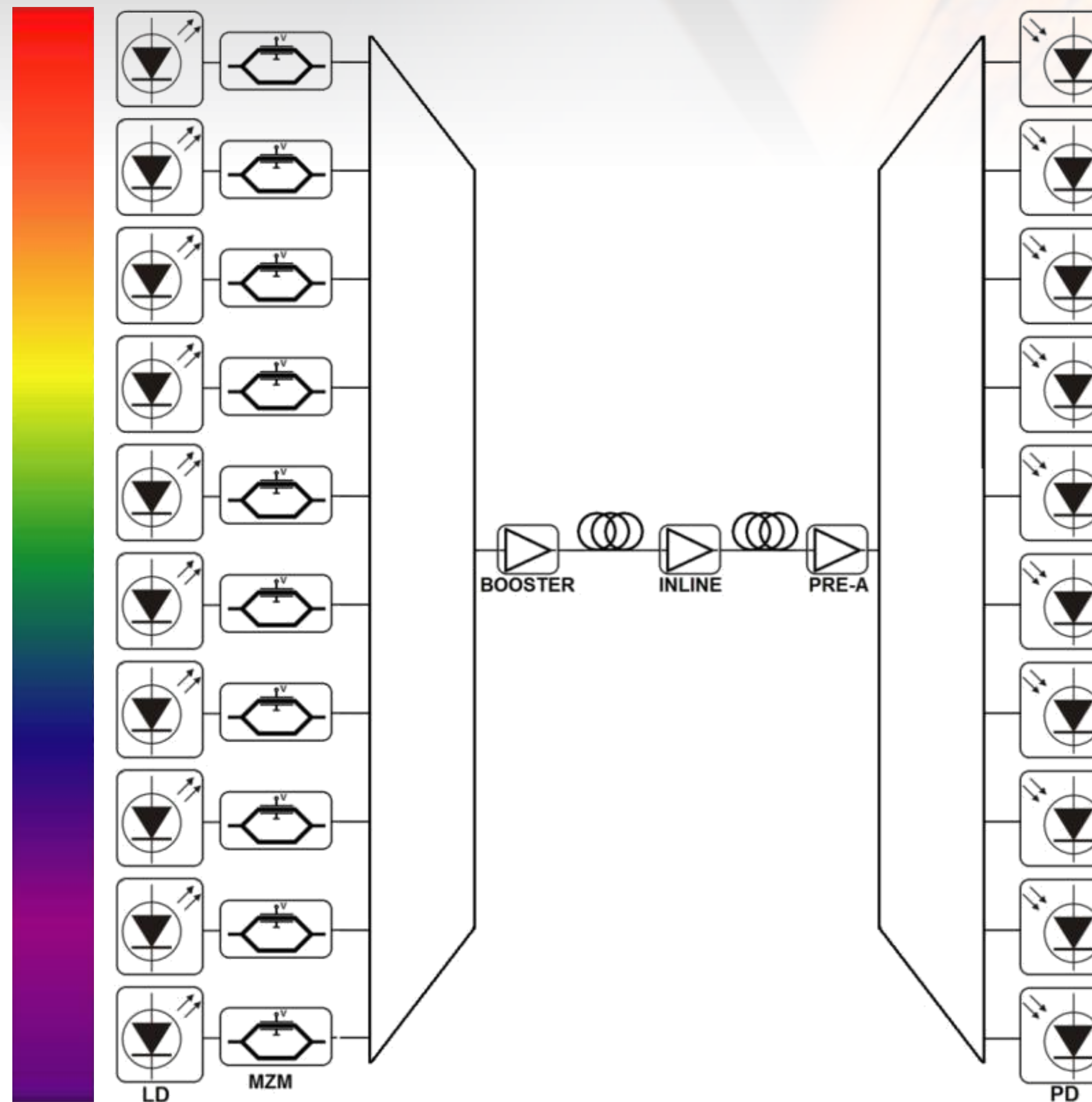
Applications



- **optical communication (fiber-optic communication systems)**
- **data communication (data centers)**
- **others**



2003 - the proposal that changed the telecom market forever...



10 wavelengths

Tx module:

10 Laser diodes (InGaAsP)

10 modulators (LiNbO₃)

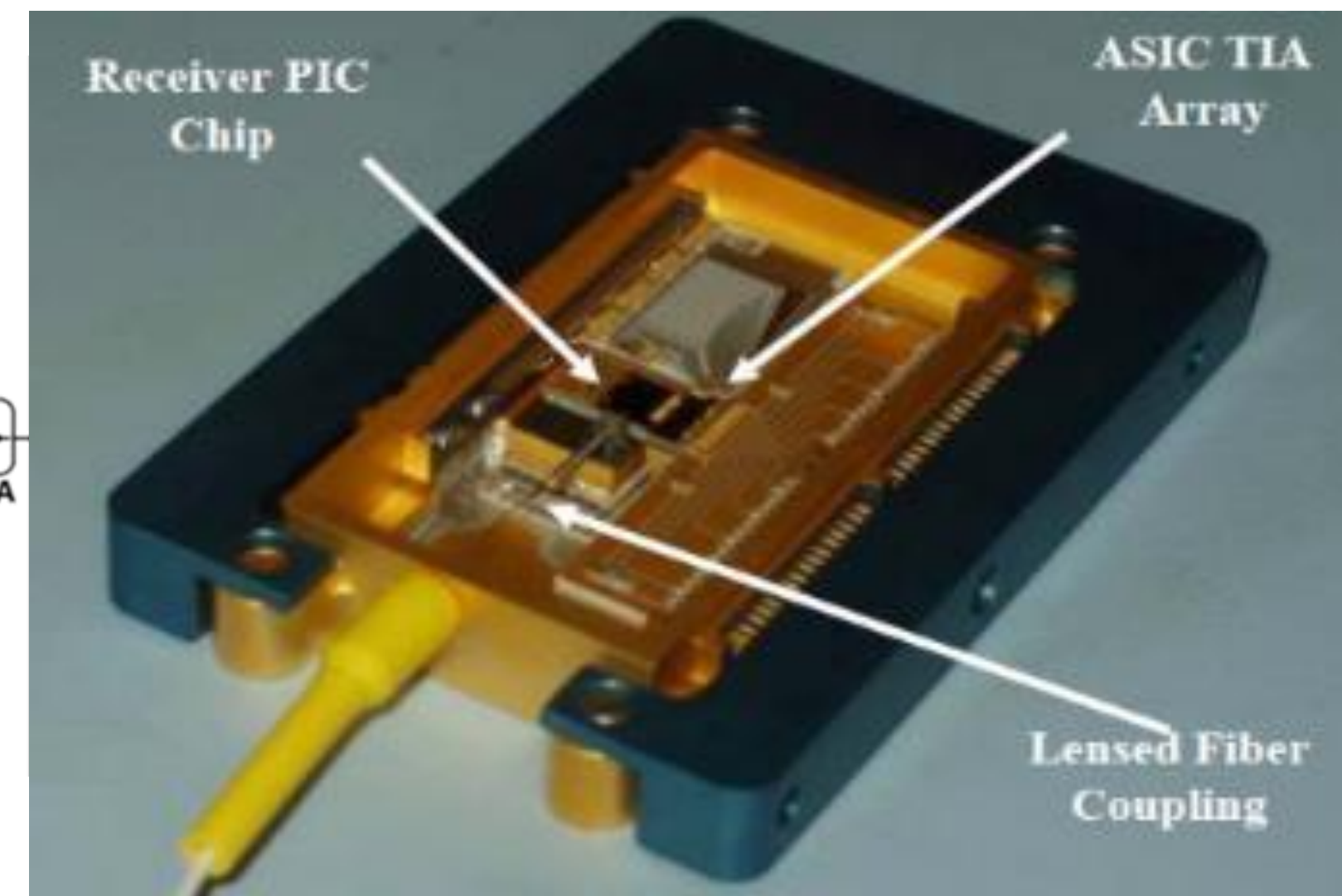
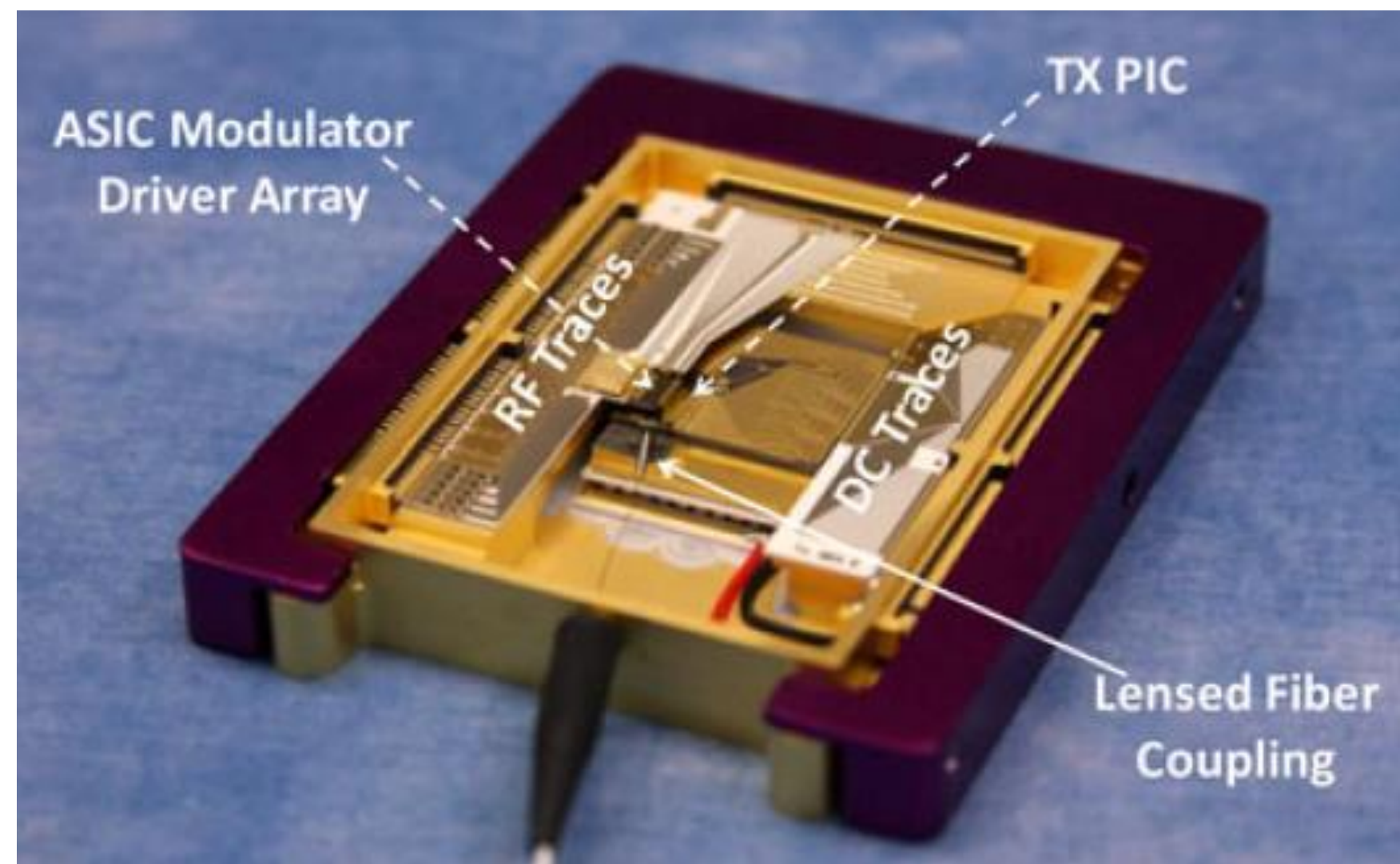
Booster amplifier (EDFA or InGaAsP SOA)

Rx module:

Pre-amplifier (EDFA or InGaAsP SOA)

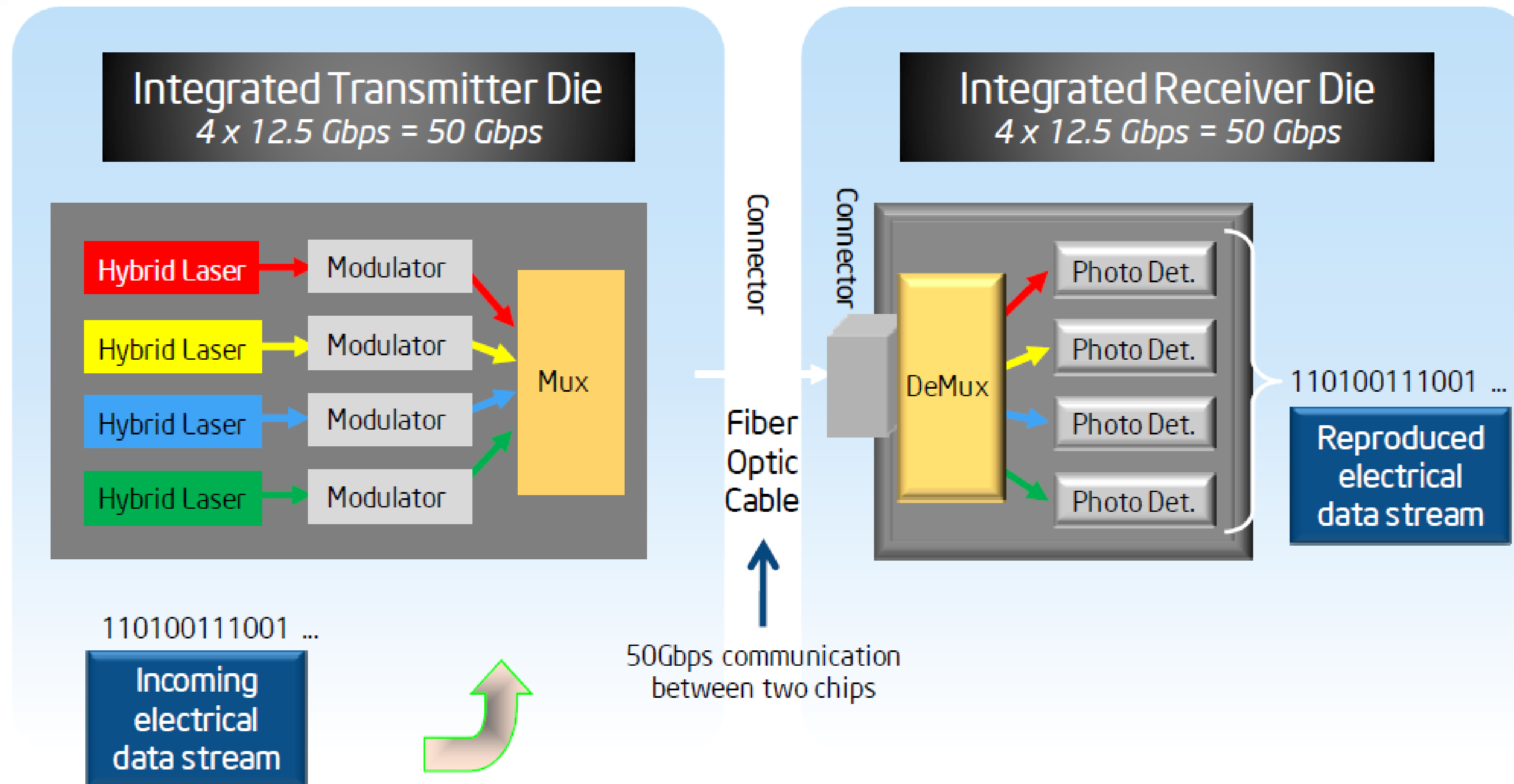
10 photodiodes (InGaAs)

WDM system in a size of matchbox (InP technology) 2006



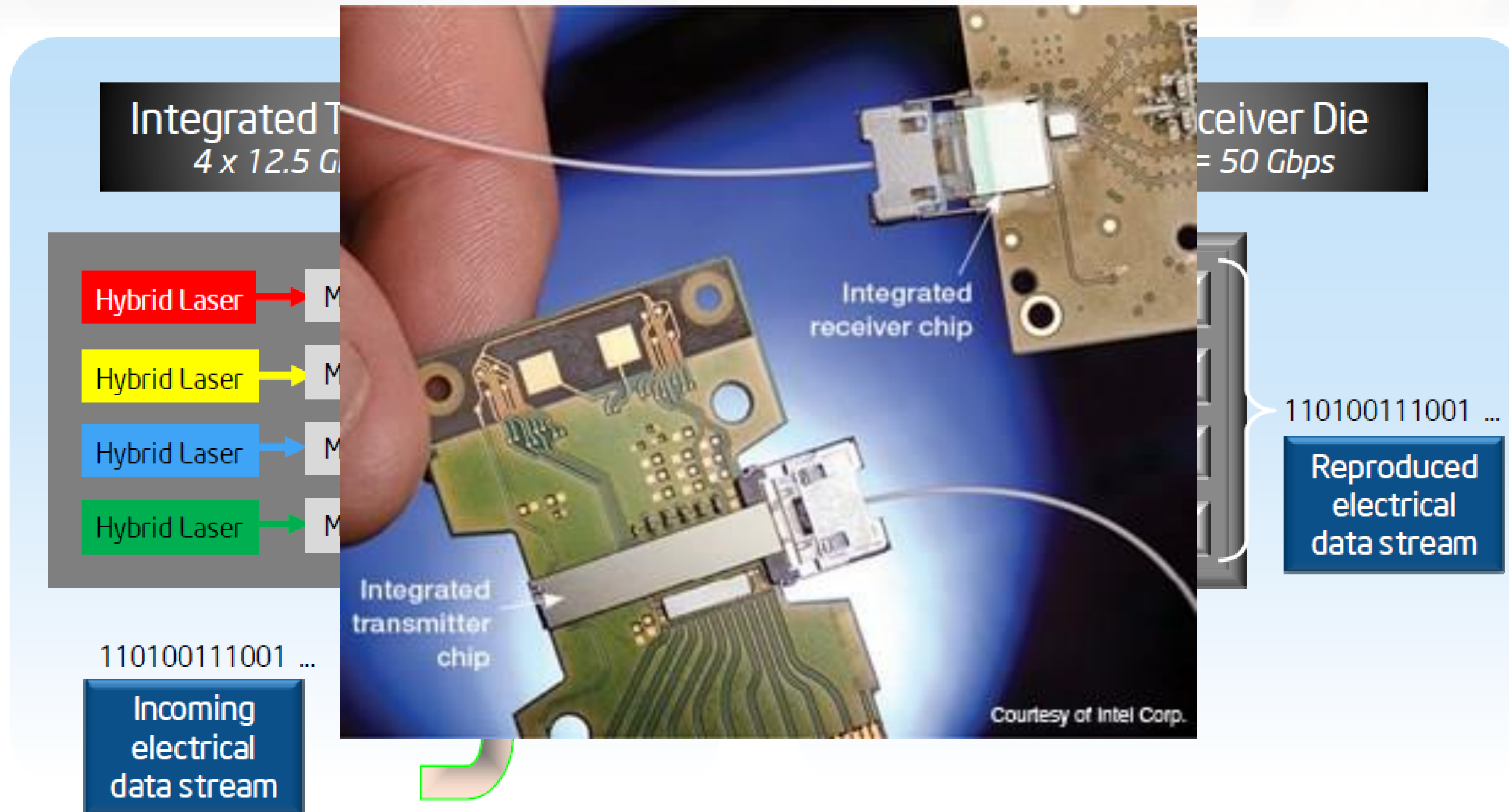
Early followers - data communication (silicon photonics)

Intel WDM data link - 50 Gb/s (2010)



Early followers - data communication (silicon photonics)

Intel WDM data link - 50 Gb/s (2010)



Datacom (2020) – integrated SFP modules



100 Gb/s



100 Gb/s



100-400 Gb/s



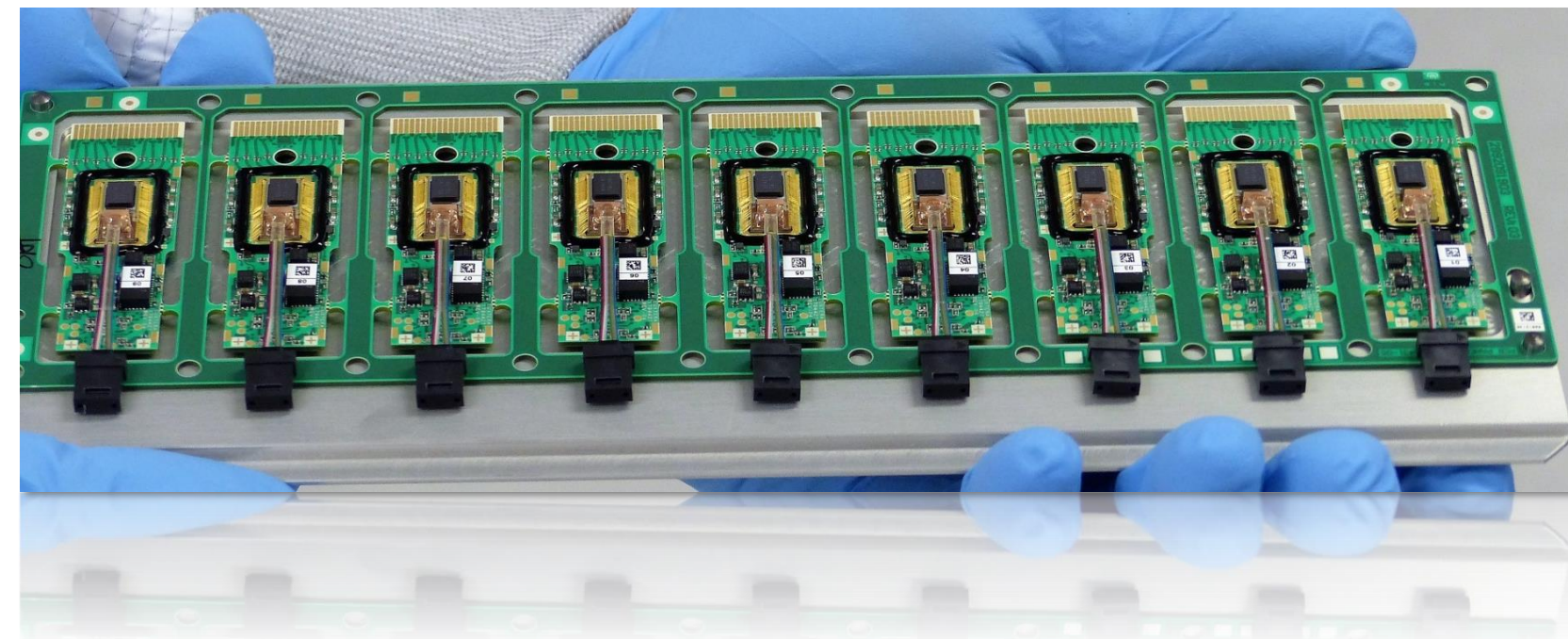
100G QSFP28 CWDM4 Transceiver



100G QSFP28 4WDM-10 Transceiver



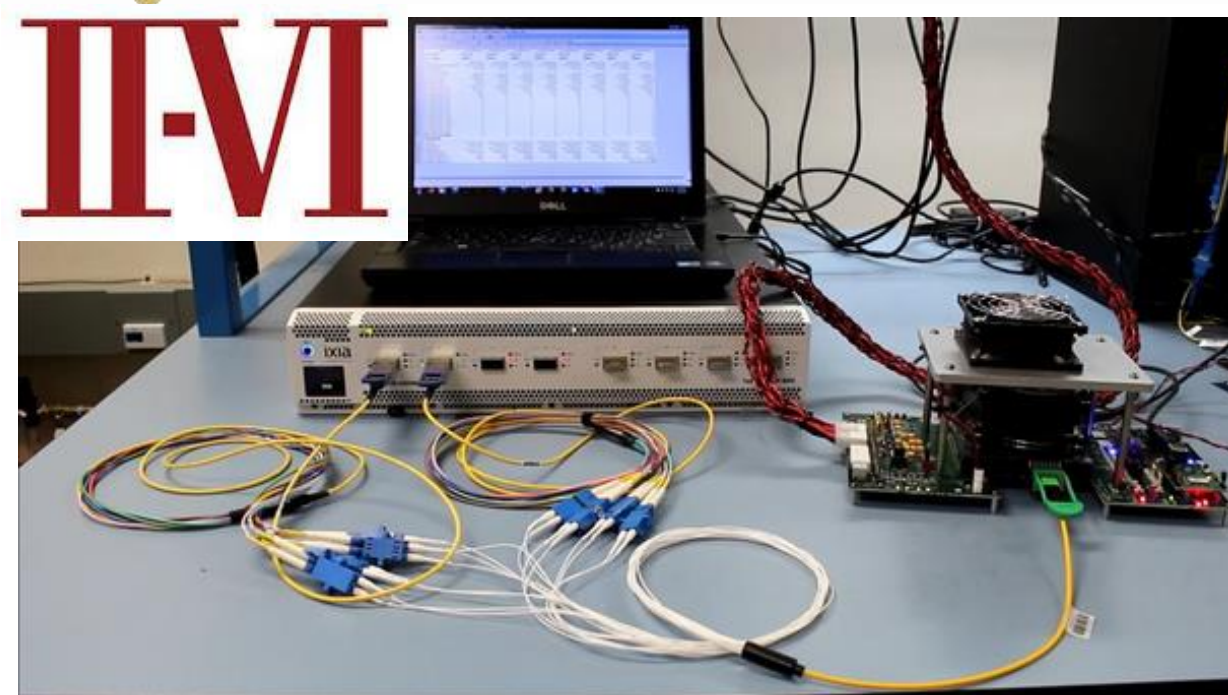
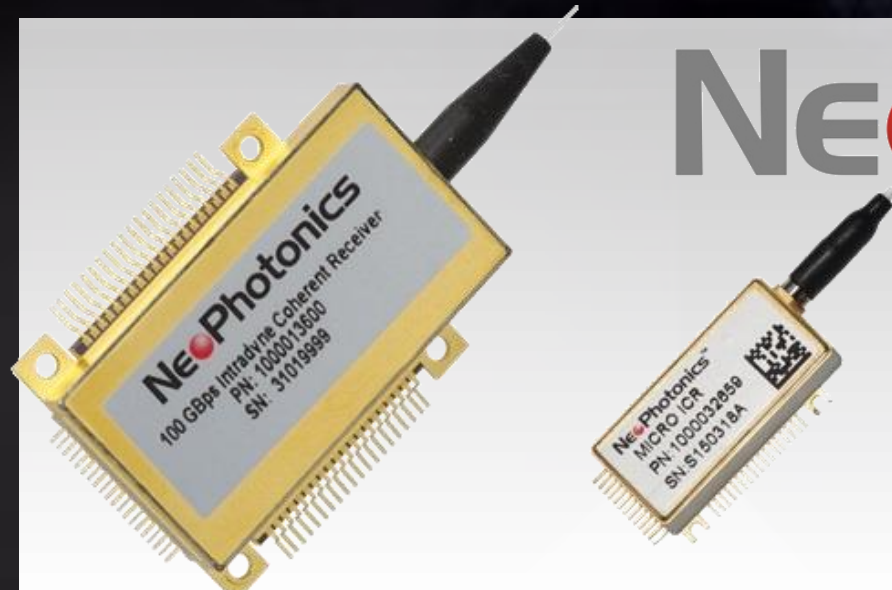
200G QSFP56 FR4 Transceiver (Roadmap)



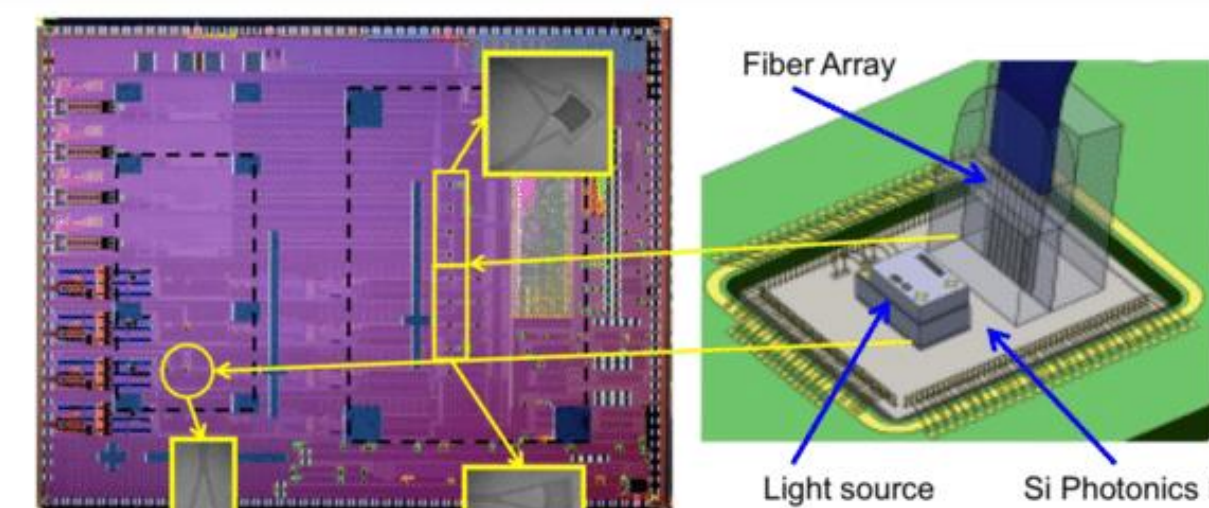
400G QSFP-DD FR4 Transceiver (Roadmap)

Telecom and datacom integrated photonic market

NeoPhotonics



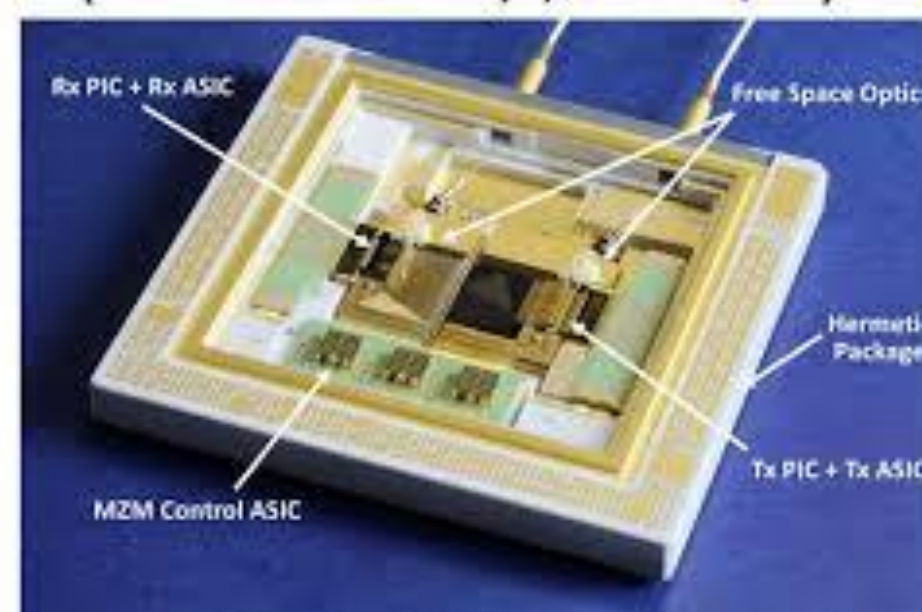
400/800G Transceivers for NG
25.6/51.2T Datacenter Switches



Transceivers 10G

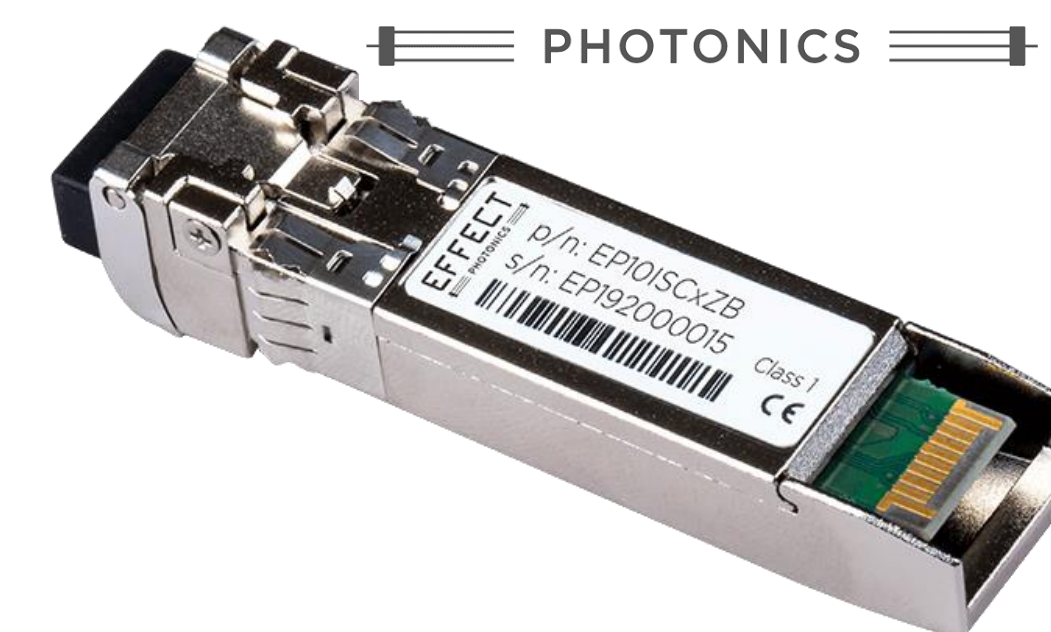
infinera

1.2 Tb/s Coherent Transceiver Module
(6 channels x 200 Gb/s, PM 16-QAM)



CFP2 and
QSFP-DD

EFFECT
PHOTONICS



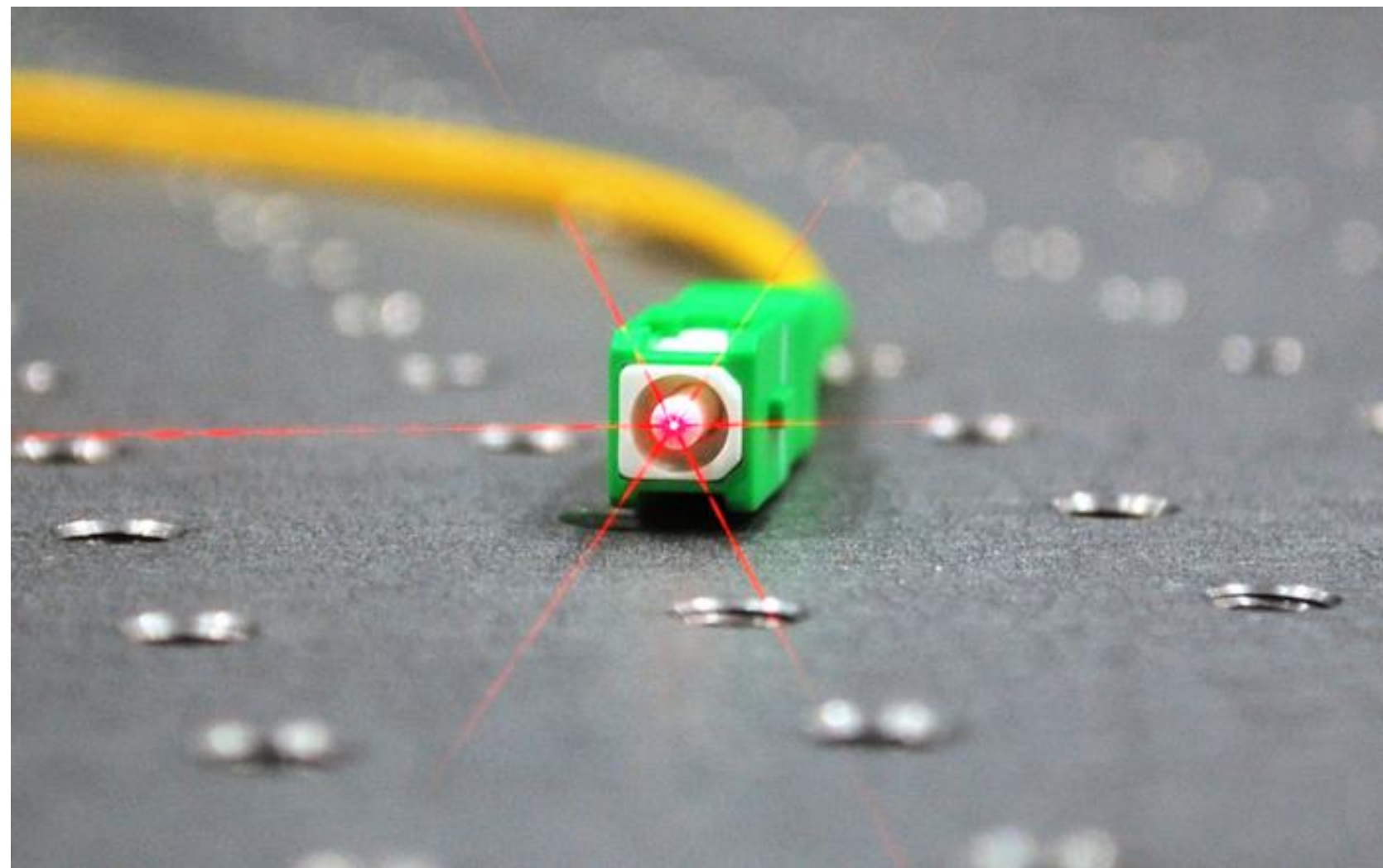
MIRAE X



ColorChip
SystemOnGlass™



- optical communication (fiber-optic communication systems)
- data communication (data centers)
- others



- **High-Performance Computing**
in-system optical interconnects, neuromorphic and quantum computing
- **Agrifood and Natural Resources**
various types of PIC-based **sensors** for detecting potentially harmful molecules and substances
- **Safety and Security**
monitoring of critical infrastructure and civil infrastructure objects, **detection** of explosives, chemical weapons, etc.
- **Industrial Sensing and Automation**
sensors and imaging systems monitoring gases, liquids and solid materials, measuring thicknesses of thin films, shapes and roughness of surfaces, distances, speeds, accelerations, temperatures, pressures etc.



White Paper on Integrated Photonics

authored by a Joint Focus Group of the
European Association on Smart Systems Integration (EPoSS)
and
Photonics21

Michael Scholles, Michael J. Wale, Timo Aalto, Mohand Achouche, Luc Augustin, David Bitauld, Sonia Garcia Blanco, Patrick Cogez, Marcus Dahlem, Paul van Dijk, Gerhard Domann, Amir Ghadimi, Martijn Heck, Thomas Hessler, Andreas Klug, Renaud de Langlade, Martin Martens, Christian Meyne, Clifford Murray, Sybille Niemeier, Ruud Oldenbeuving, Mehmet Cengiz Onbaşlı, Joseph Pankert, Ryszard Piramidowicz, Abdul Rahim, Graham Reed, Jelmer Renema, Ewit Roos, Martin Schell, Elisabeth Steinmetz, Martin Strassburg, Bertrand Szelag, Tolga Tekin, Dao Thang Duy, Dries van Thourhout, Marija Trajkovic, Gintaras Valusis, Lennart de Vreede, Markus Wilkens, Martina Wisniewski, Benjamin Wohlfeil, Lars Zimmermann

April 2023

- **Health and Wellbeing**
medical optical imaging (e.g., highly integrated endoscopes), photonic **biosensors**, continuous **monitoring** of patients' health status to detect diseases at an early stage or to continuously **monitor** the progression of illnesses outside a medical environment
- **Mobility and Space**
with future mobility concepts that require advanced environmental **sensing**, in particular, components for **LiDAR** systems, communication systems, etc.
- **Consumer electronics**
digital health **monitoring**, wearable systems (smartbends, smartwatches, smartphones etc. equipped with **PIC sensors**)

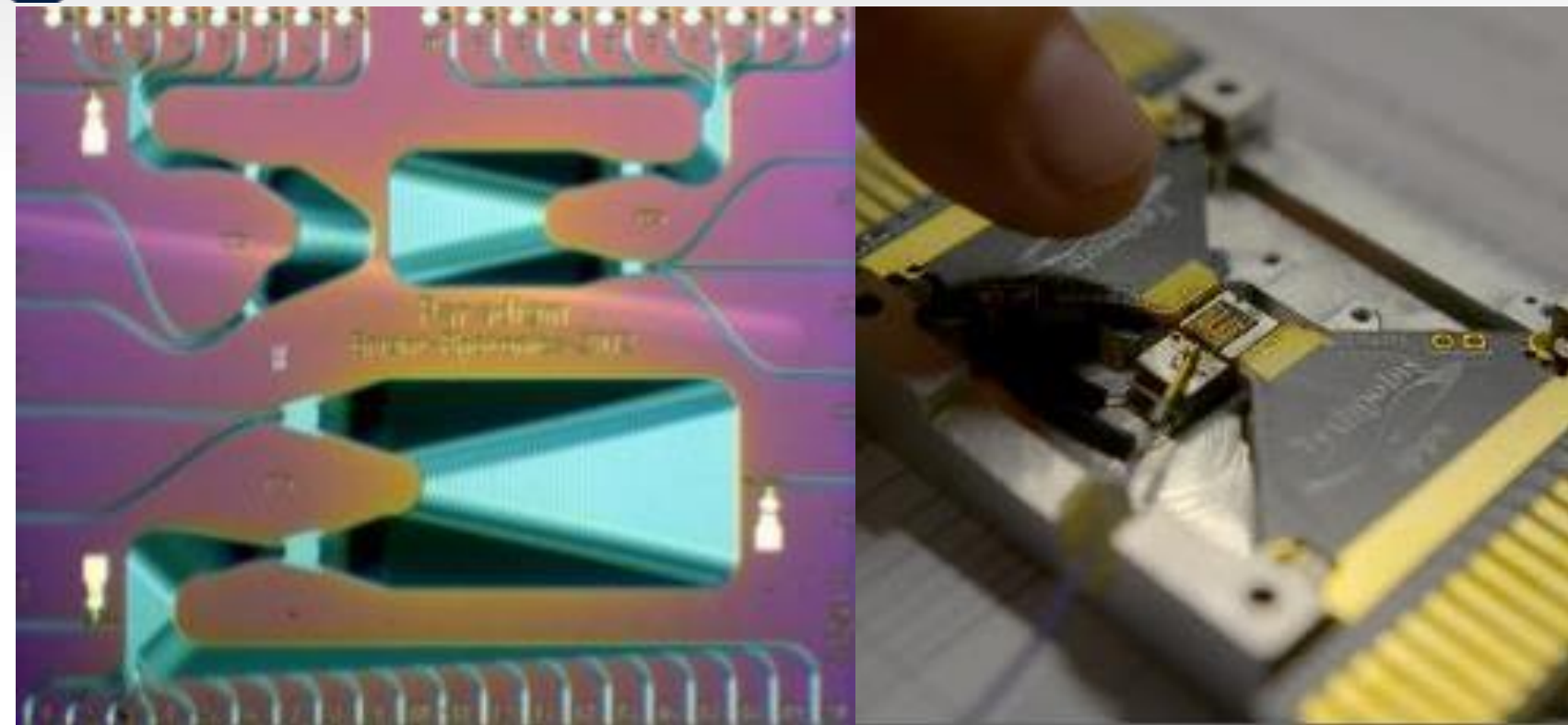


White Paper on Integrated Photonics

authored by a Joint Focus Group of the
European Association on Smart Systems Integration (EPoSS)
and
Photonics21

Michael Scholles, Michael J. Wale, Timo Aalto, Mohand Achouche, Luc Augustin, David Bitauld, Sonia Garcia Blanco, Patrick Cogez, Marcus Dahlem, Paul van Dijk, Gerhard Domann, Amir Ghadimi, Martijn Heck, Thomas Hessler, Andreas Klug, Renaud de Langlade, Martin Martens, Christian Meyne, Clifford Murray, Sybille Niemeier, Ruud Oldenbeuving, Mehmet Cengiz Onbaşlı, Joseph Pankert, Ryszard Piramidowicz, Abdul Rahim, Graham Reed, Jelmer Renema, Ewit Roos, Martin Schell, Elisabeth Steinmetz, Martin Strassburg, Bertrand Szelag, Tolga Tekin, Dao Thang Duy, Dries van Thourhout, Marija Trajkovic, Gintaras Valusis, Lennart de Vreede, Markus Wilkens, Martina Wisniewski, Benjamin Wohlfeil, Lars Zimmermann

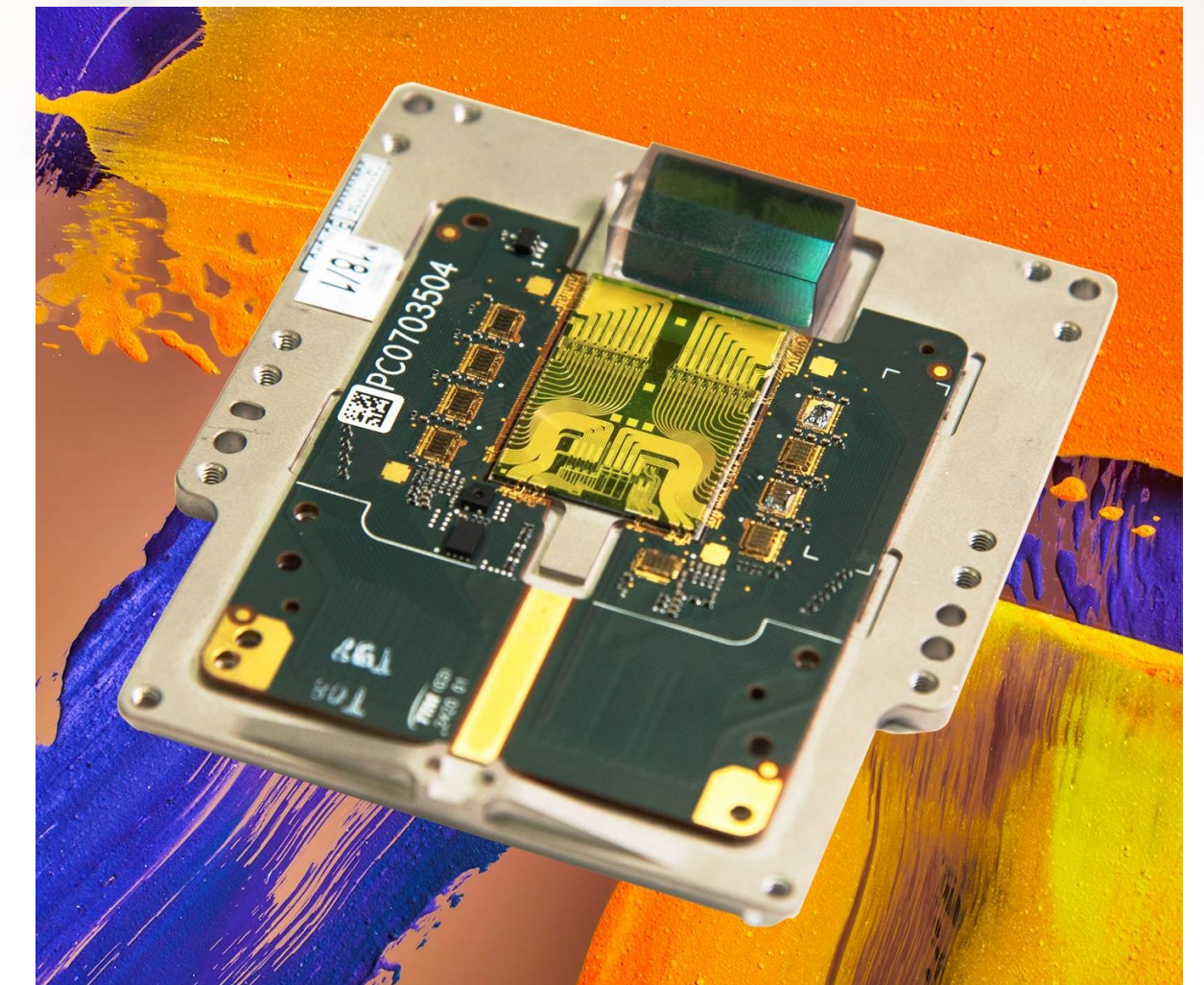
April 2023



optical interrogators



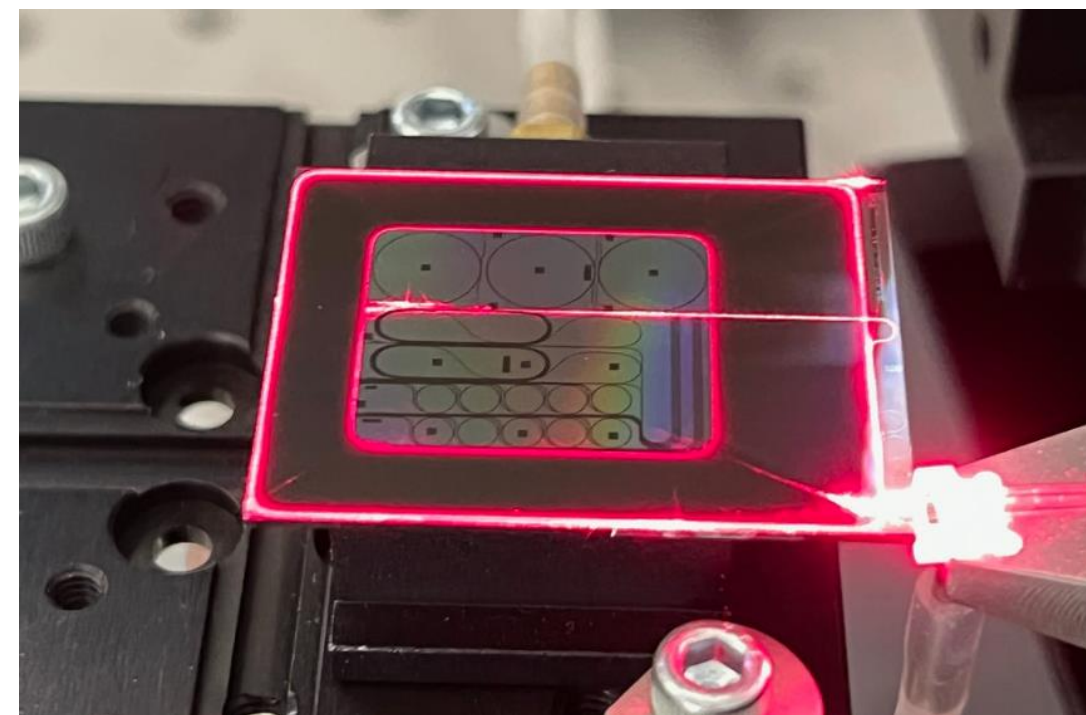
SARS-CoV-2 detection



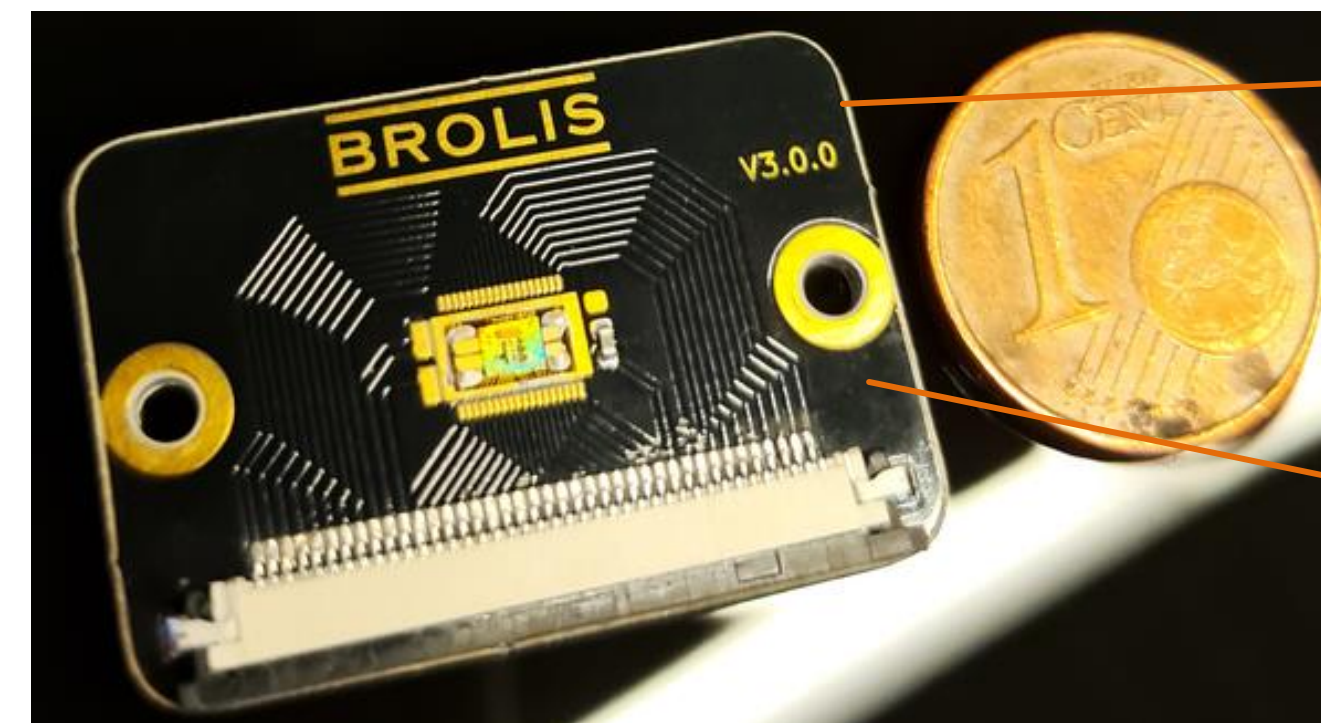
Lidar System-On-Chip



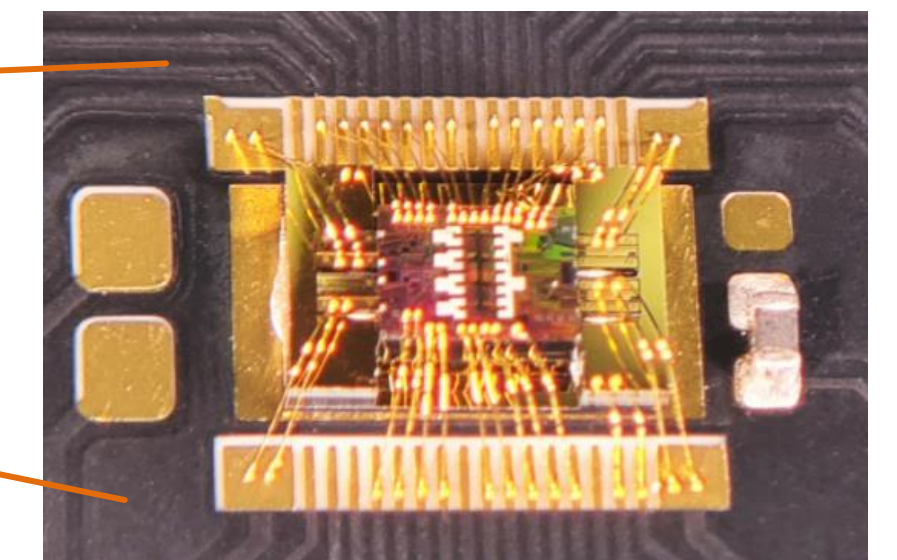
biosensor-array module
for drug screening



SIPHOG™ – optical gyro



spectrometer-on-a-chip





Challenges and perspectives

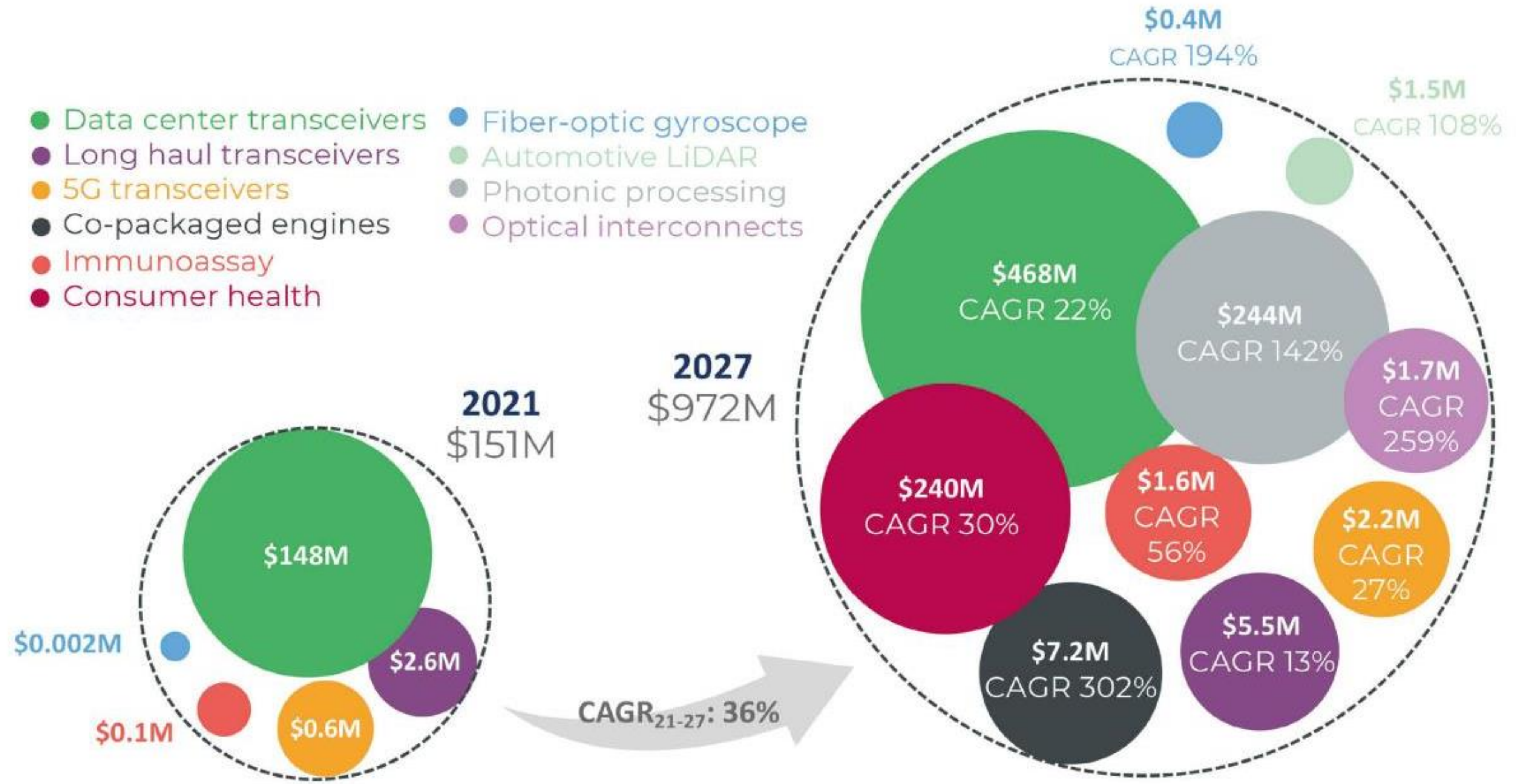


Integrated photonics is among the most important technologies of the information society, already revolutionizing the telecom and datacom market.

Major challenges:

- **scaling-up manufacturing resources,**
- **mass-scale generic packaging,**
- **electronic-photonic integration,**
- **new application fields and new markets!**

Silicon photonic 2021-2027 market forecast



Integrated photonics is among the most important technologies of the information society, already revolutionizing the telecom and datacom market.

Major challenges:

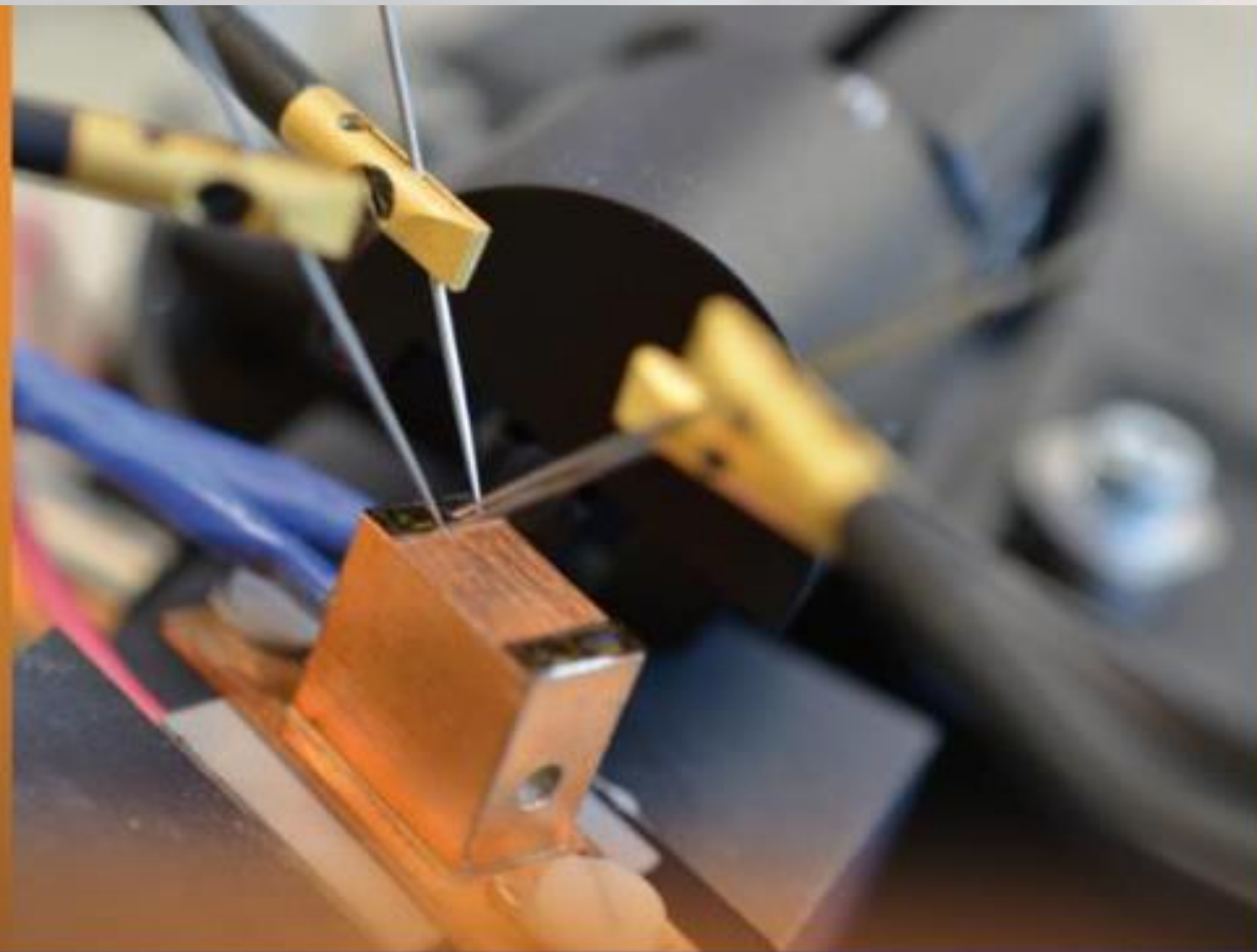
- **scaling-up manufacturing resources,**
- **mass-scale generic packaging,**
- **electronic-photonic integration,**
- **new application fields and new markets!**

Extension of spectral range (towards VIS and MIR) is a must!



POLISH PERSPECTIVE

Integrated photonics @ WUT – design and technology



Eastern Europe
DESIGN HUB



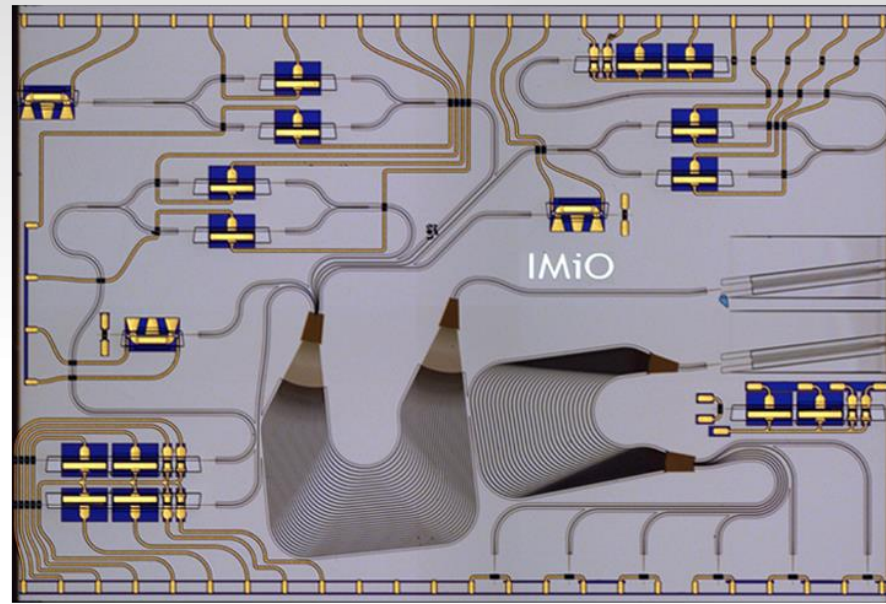
ASPICS: APPLICATION SPECIFIC
PHOTONIC INTEGRATED CIRCUITS
Warsaw University of Technology

- established in 2011
- first ASPIC designed in 2012
- characterization lab finalized in 2014
- first ASPIC characterized in 2013
- first technological trials in 2019 (CEZAMAT WUT)
- first Polish Design House **LightHouse** established in 2022

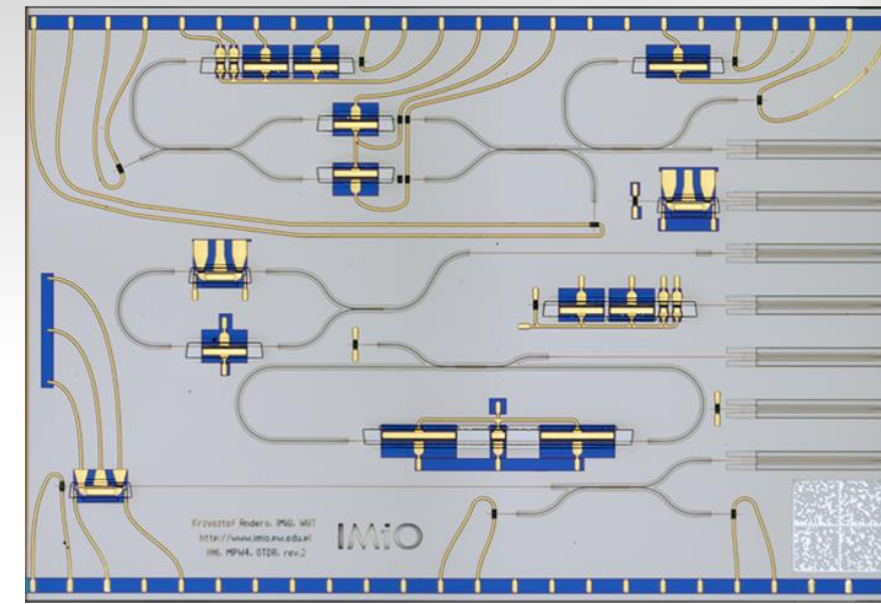


Eastern Europe Design Hub & LightHouse

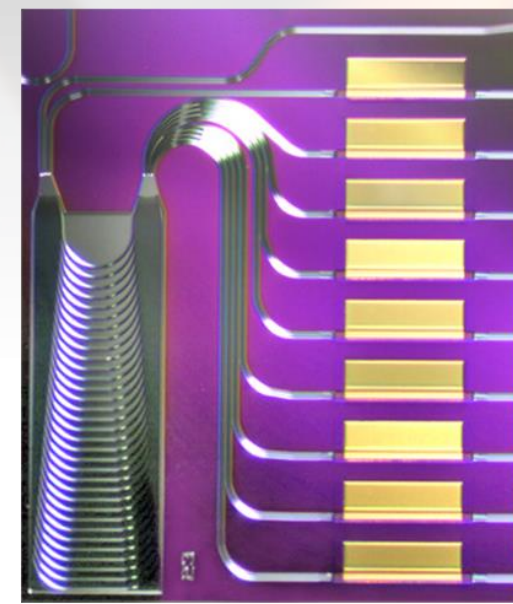
120+ ASPIC circuits designed by EEDH, manufactured by generic foundries



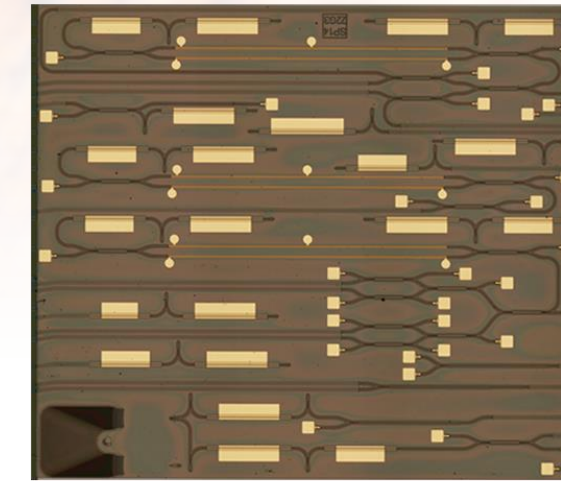
Multi-channel transceiver for free space optics



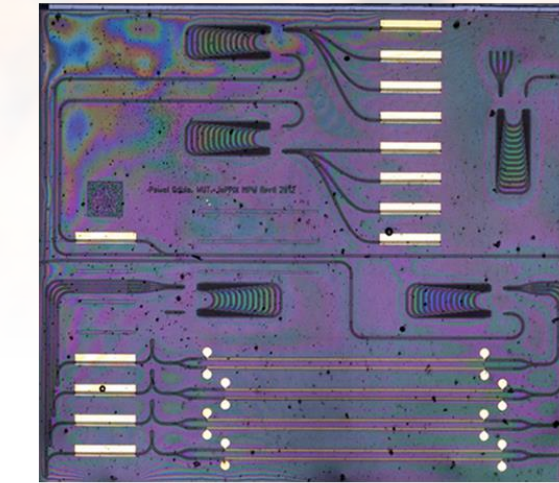
Optical time domain reflectometer



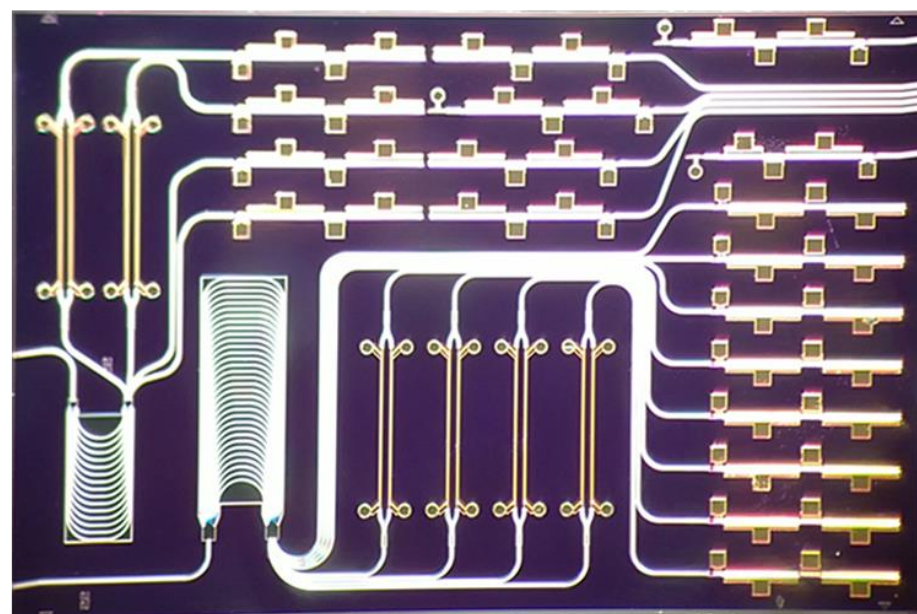
Multi-wavelength laser



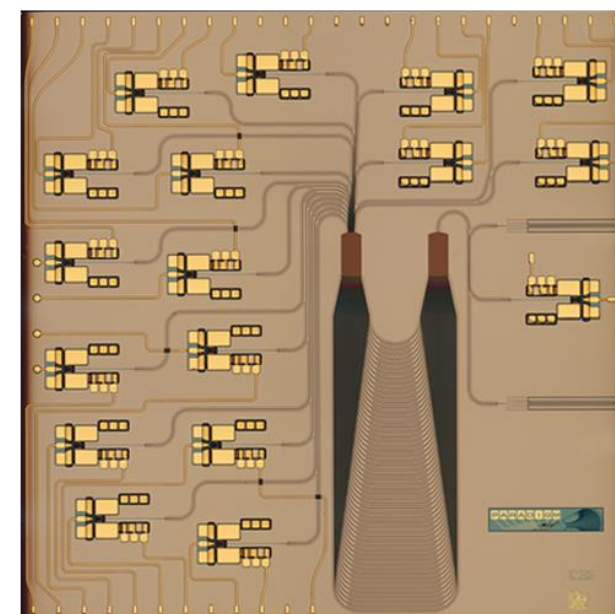
Multi-channel optical time domain reflectometer



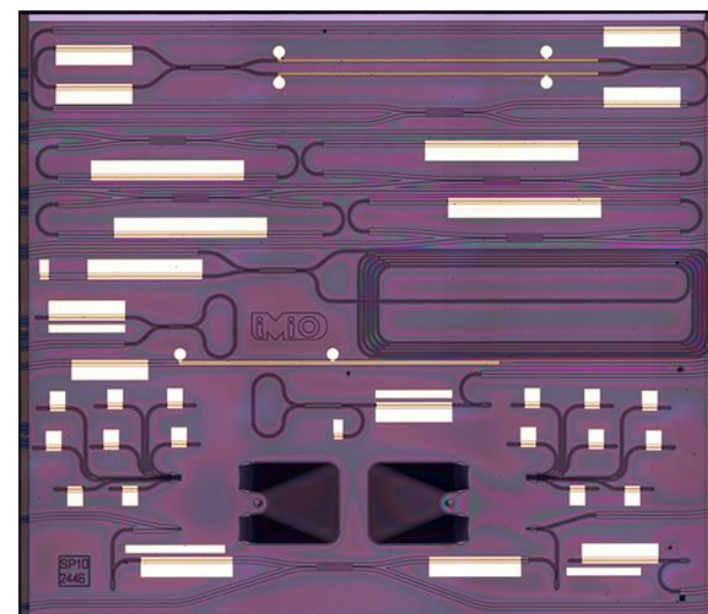
Multi-channel transmitter for FTTH networks



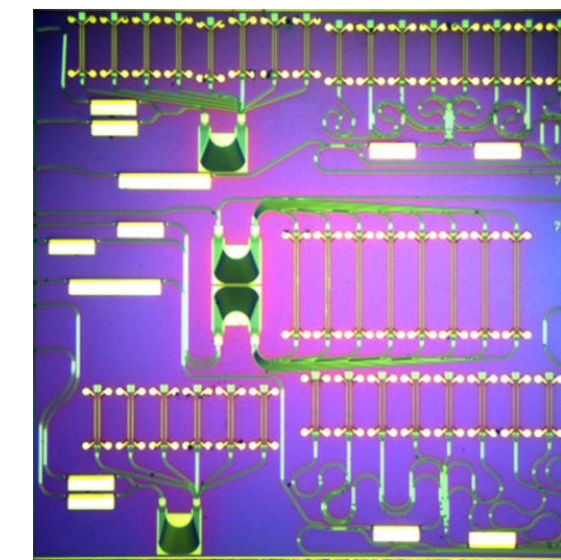
Multi-channel transmitter for FTTH networks



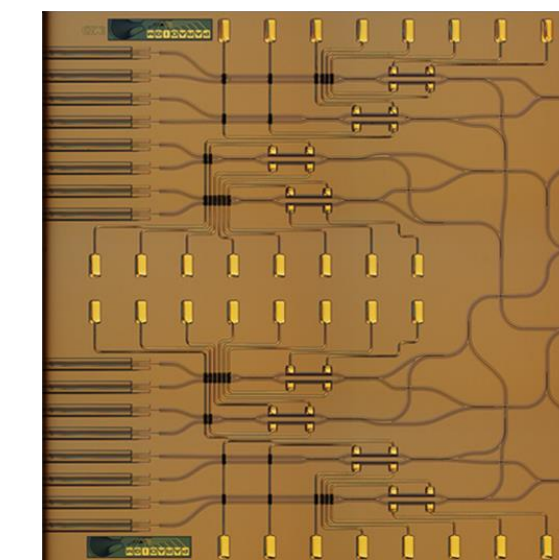
Spectrometer for FBG sensor interrogator



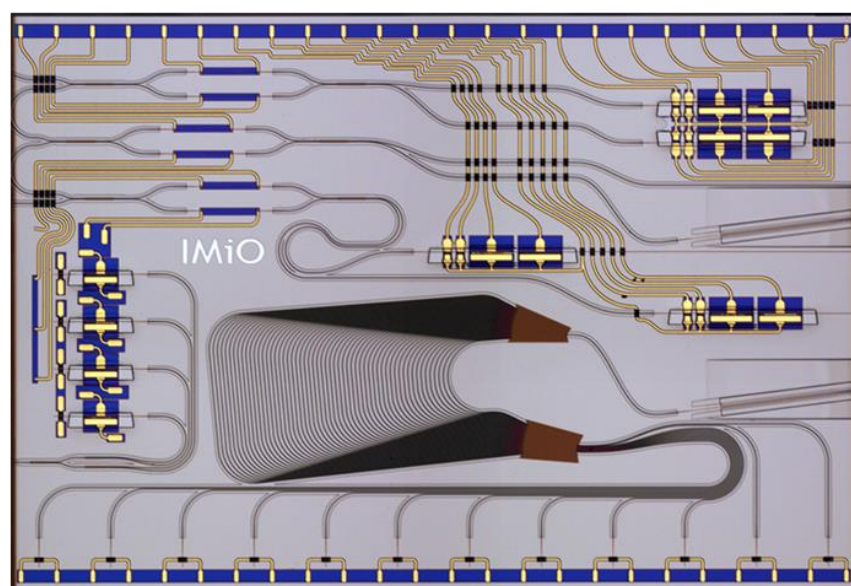
Discretely tunable laser



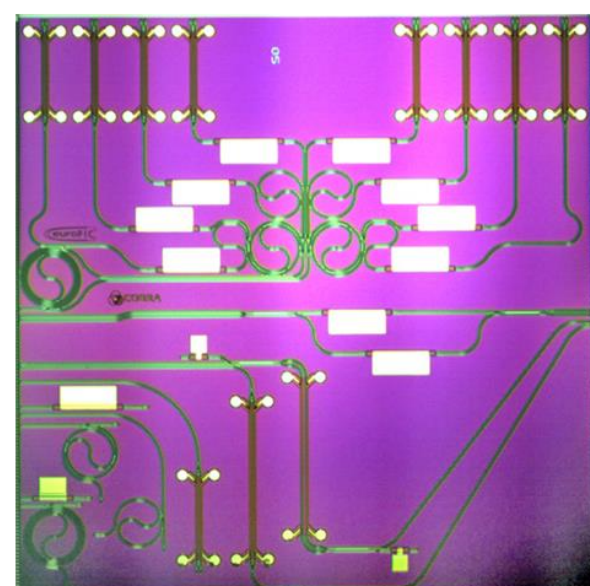
Photonic data readout units



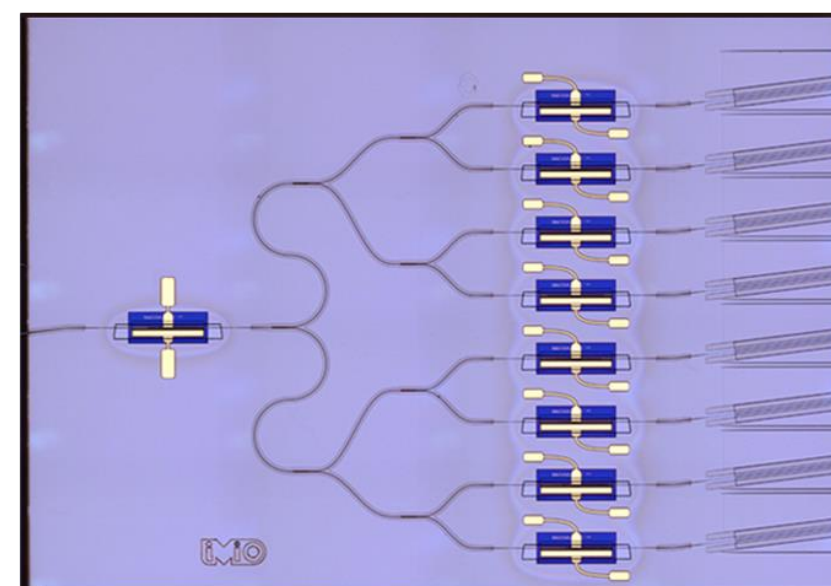
2x8 optical switch for fiber-optic access systems



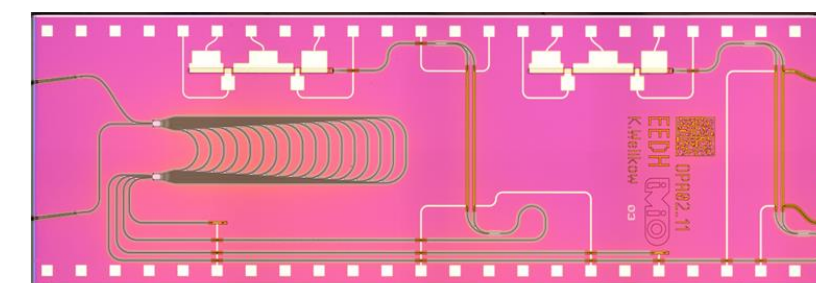
FBG interrogator unit



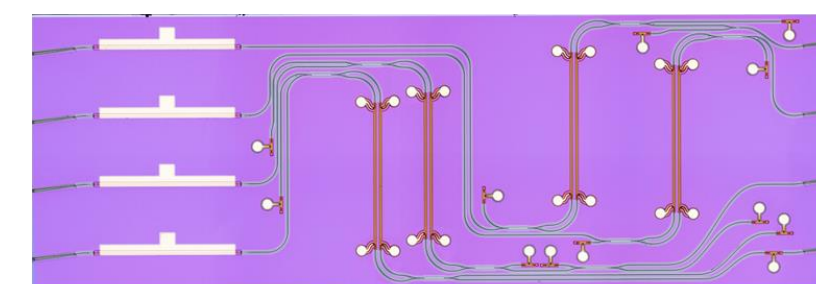
Optical time division multiplexer



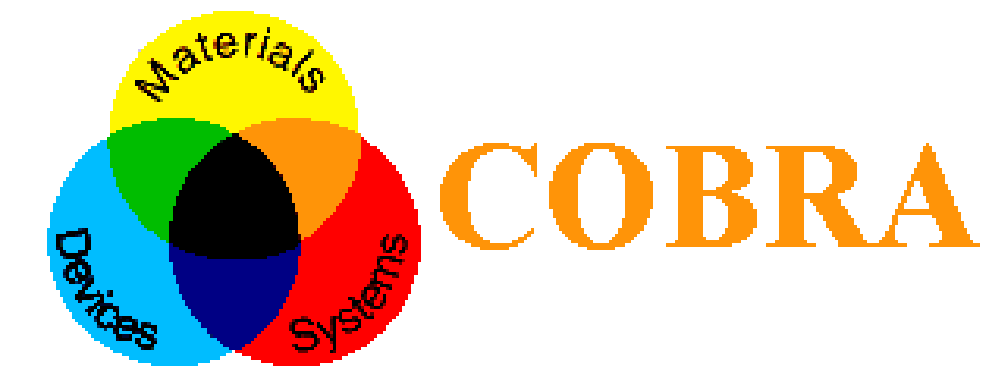
Lossless power splitter



Photonic transceiver for metrology applications



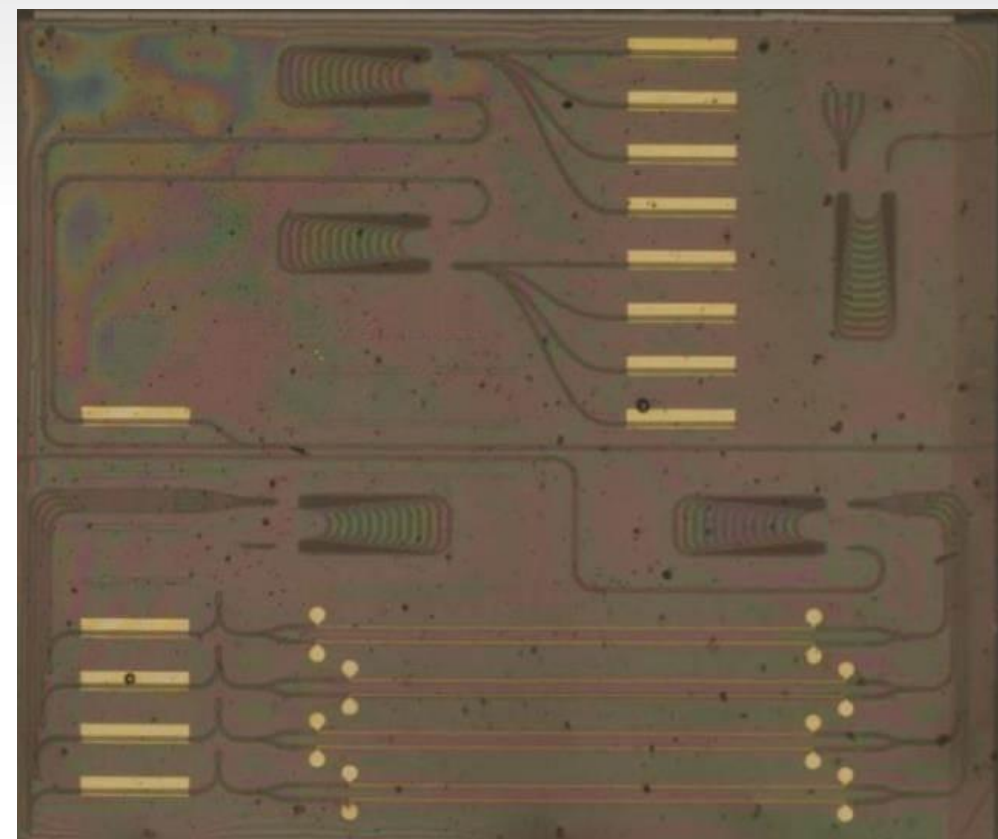
Photonic integrated transceiver for data readout units



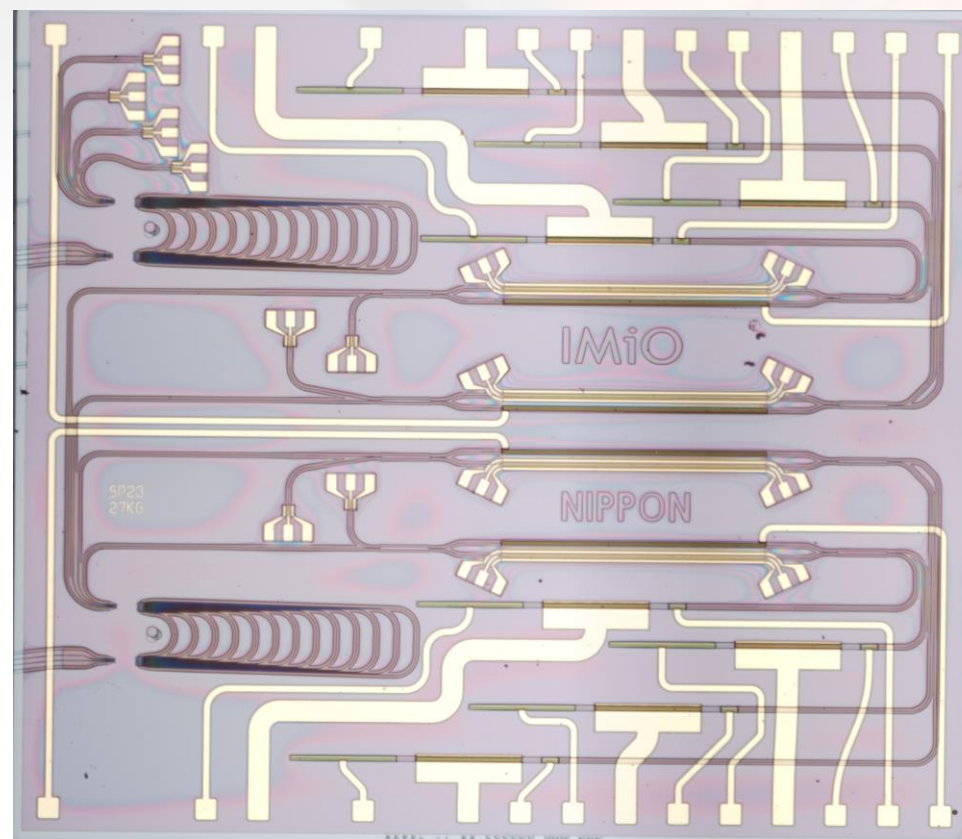
Multi-wavelength transmitters for telecom and datacom

Four generations of ASPICs designed, developed and tested (TRL6)

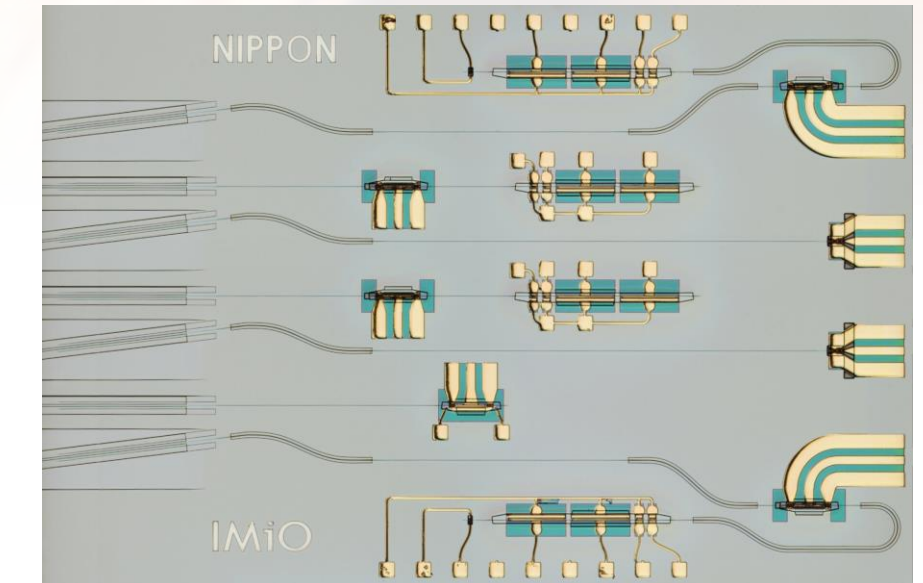
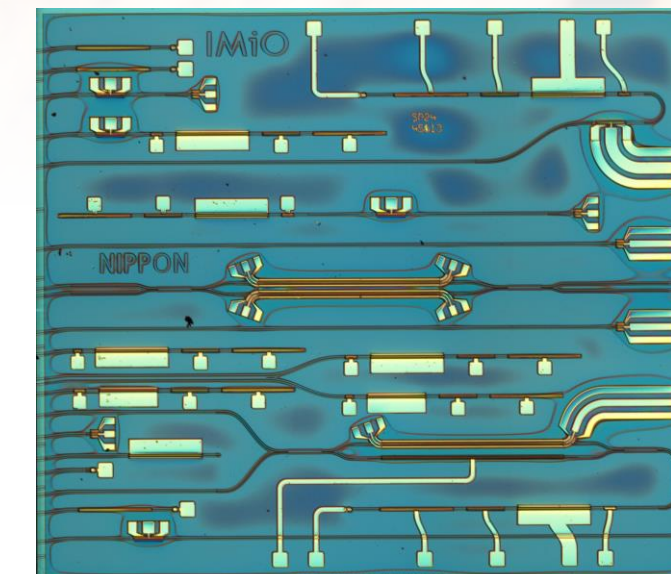
1st



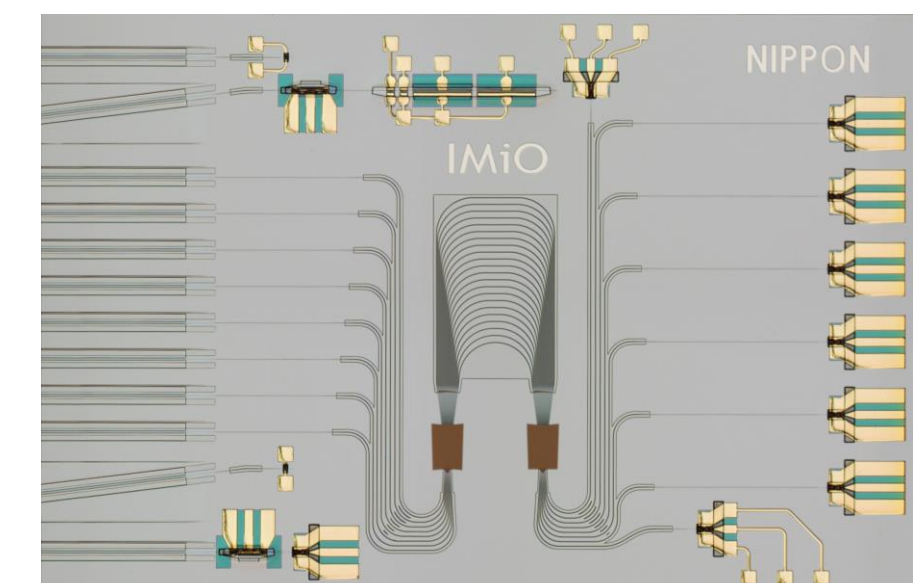
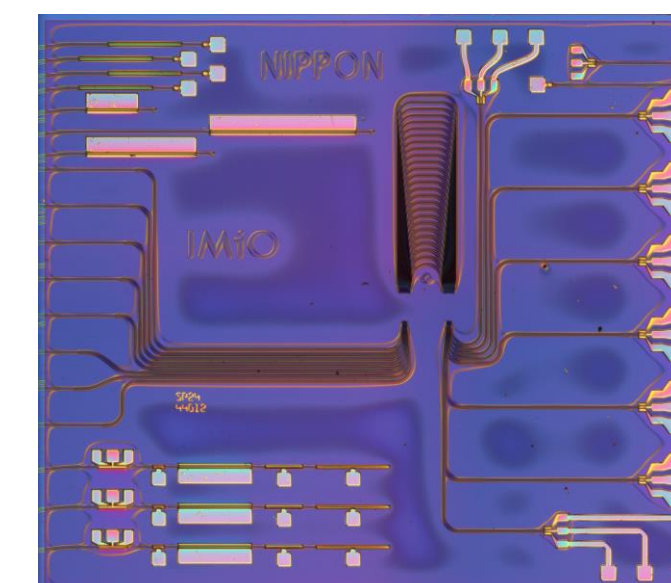
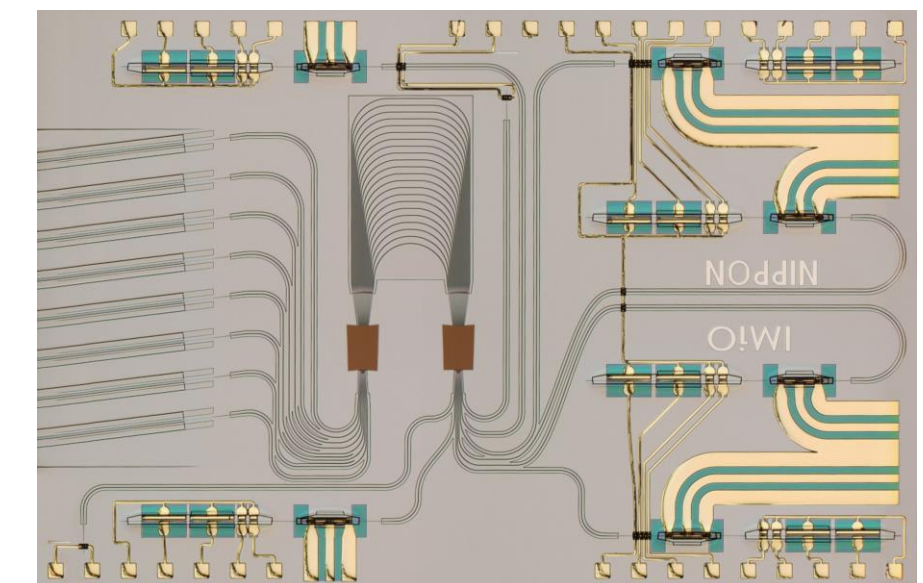
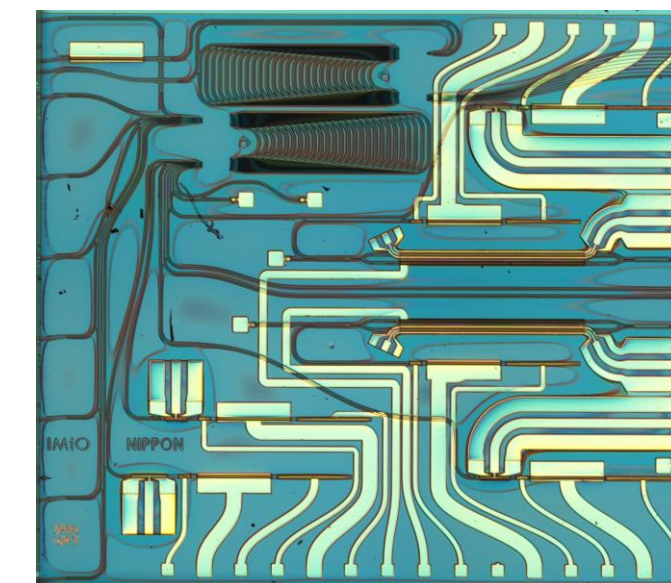
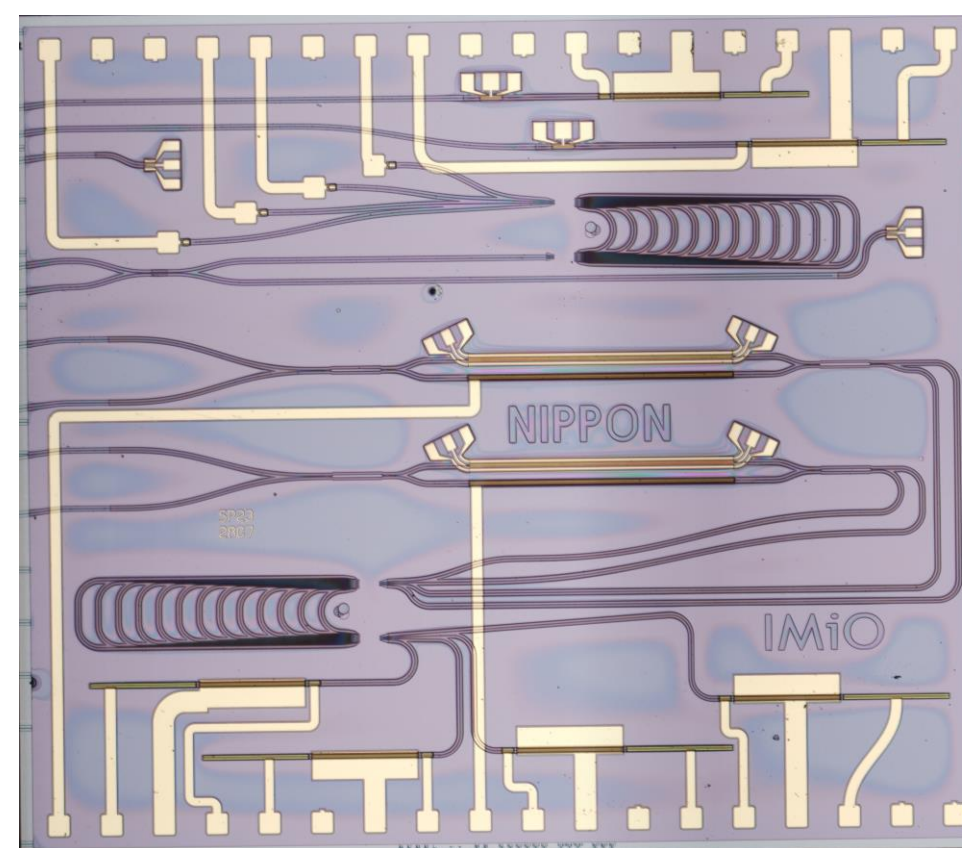
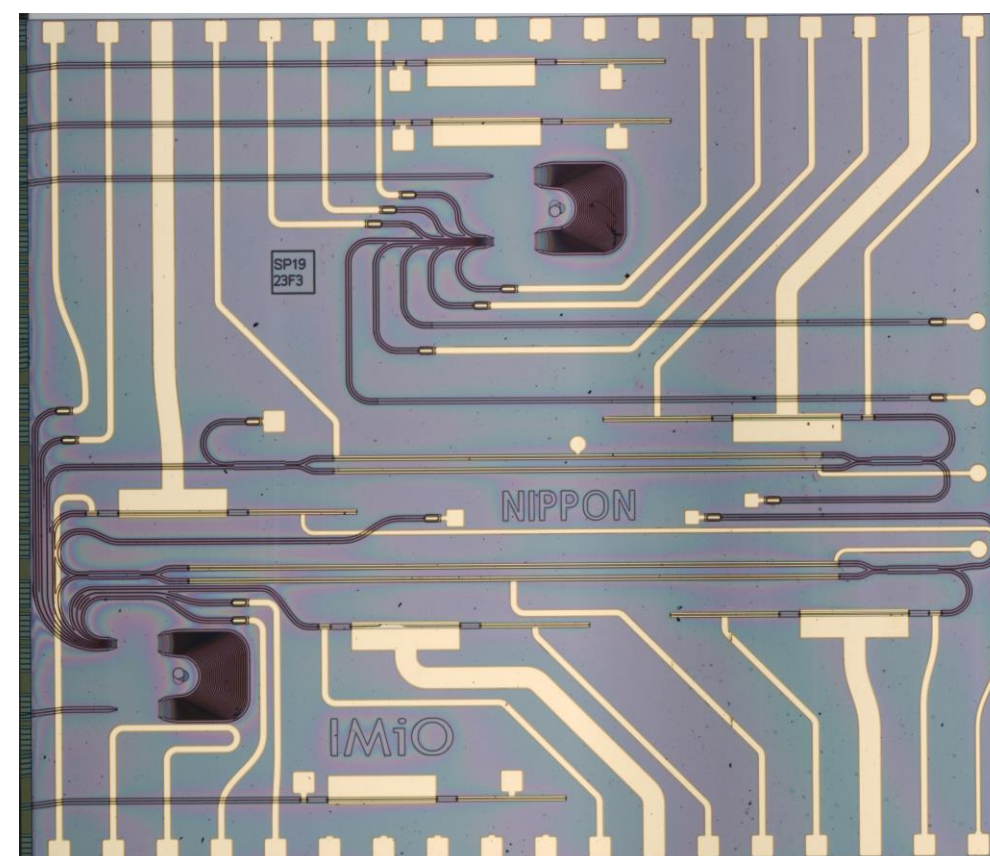
3rd



4th

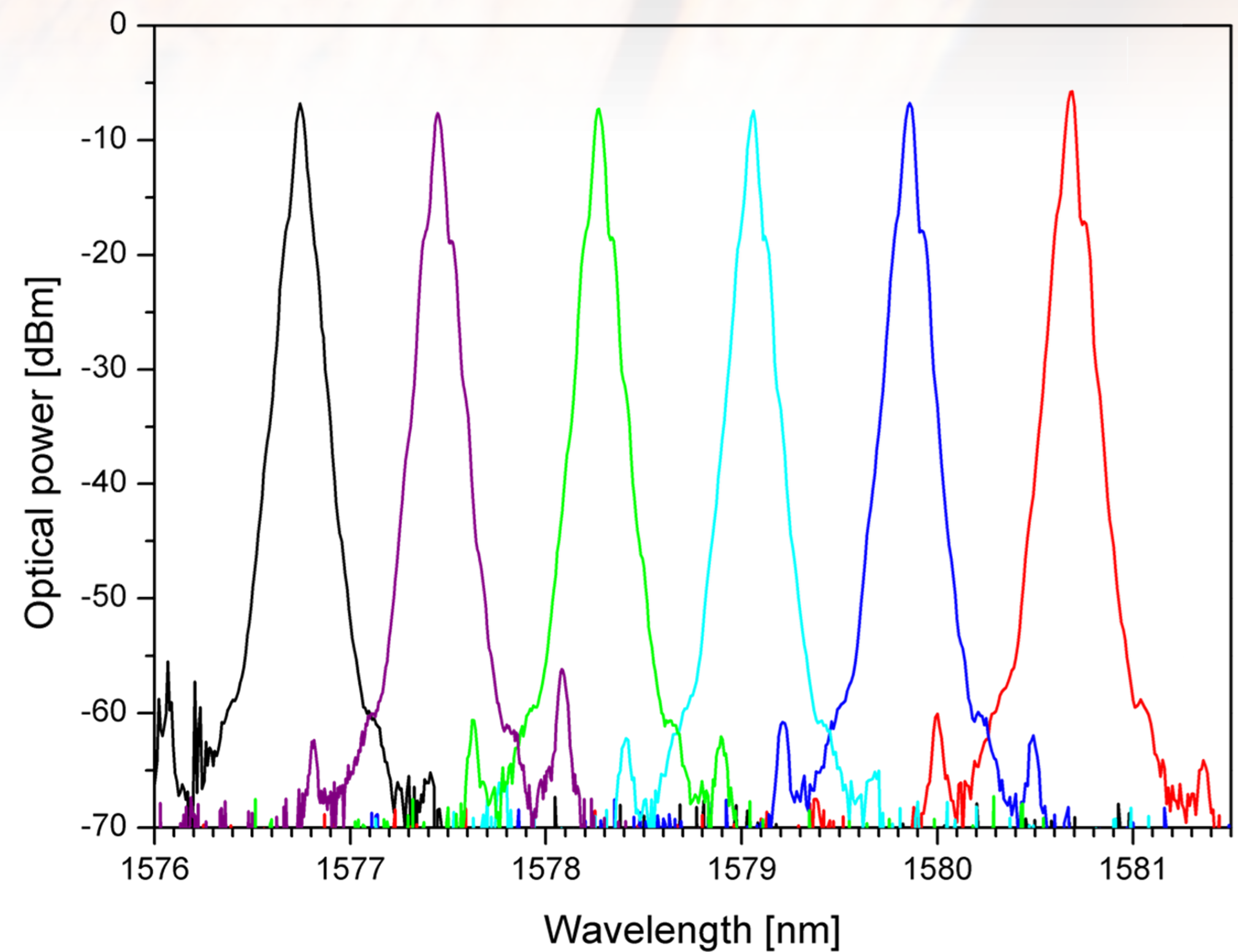
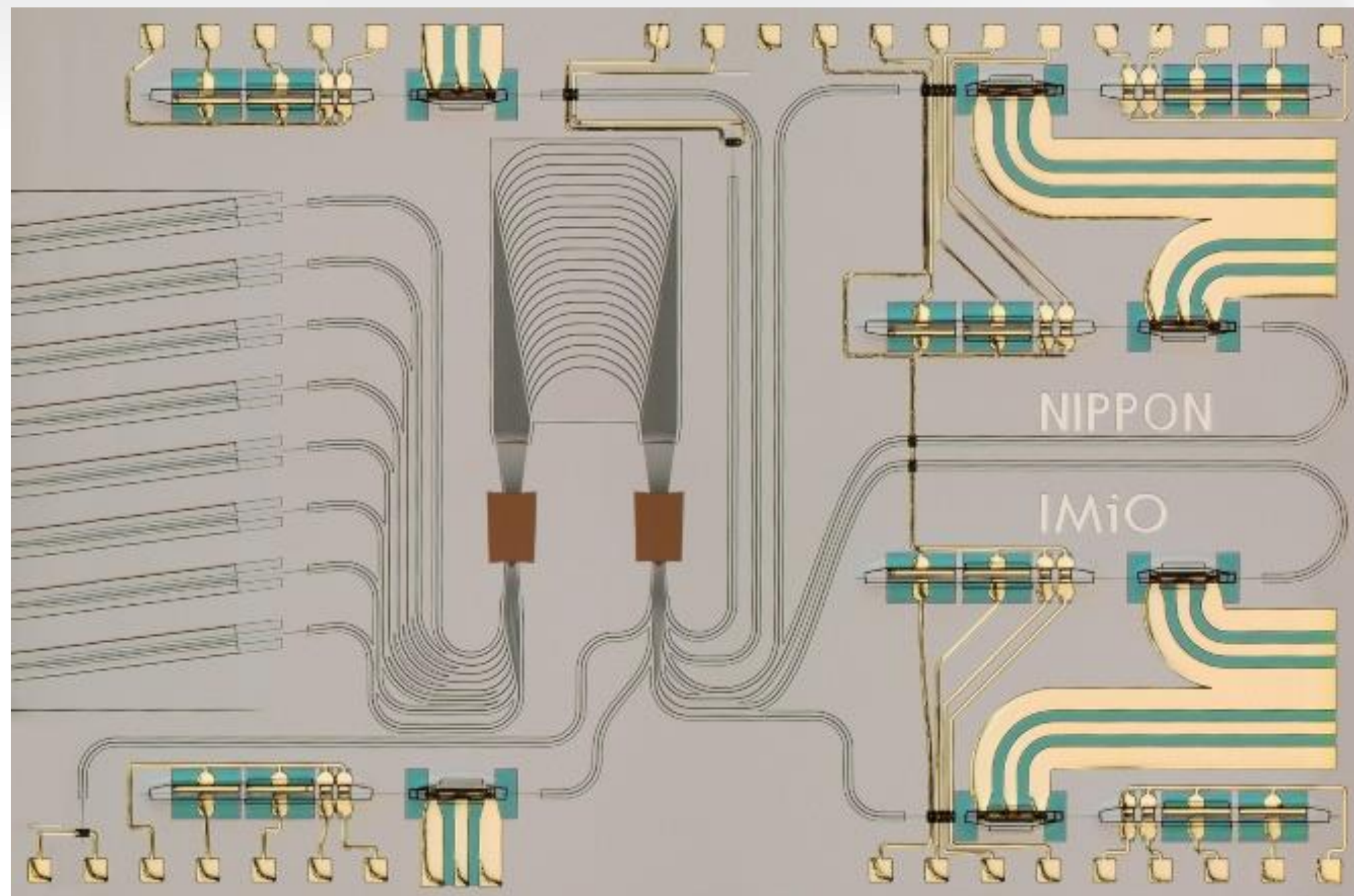


2nd



Multi-wavelength transmitters for telecom and datacom

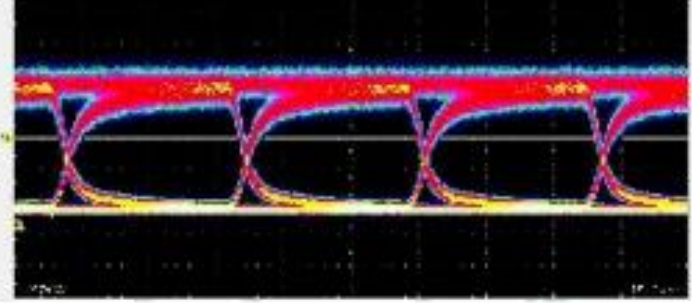
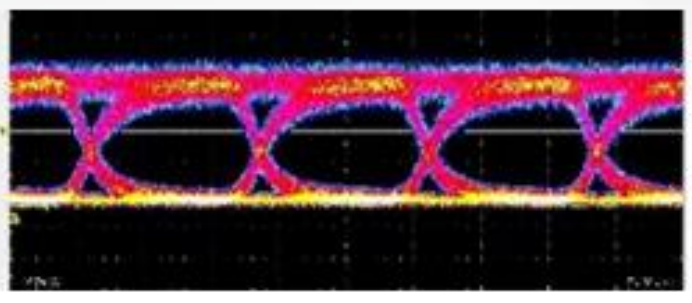
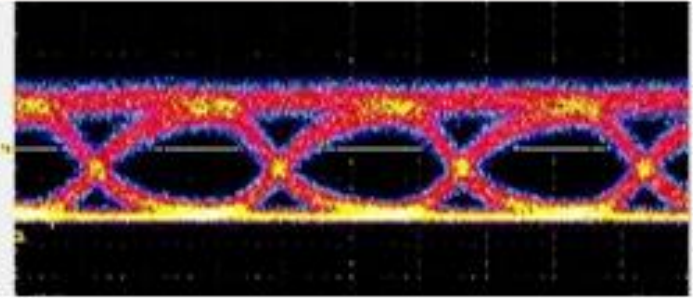
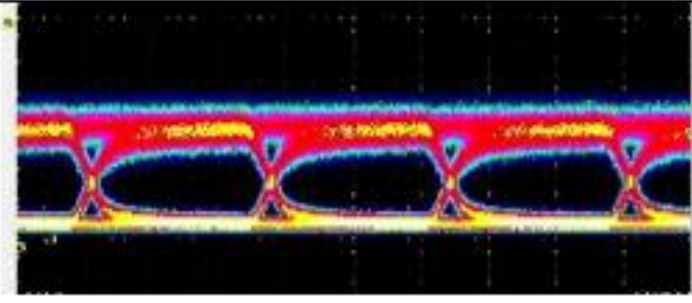
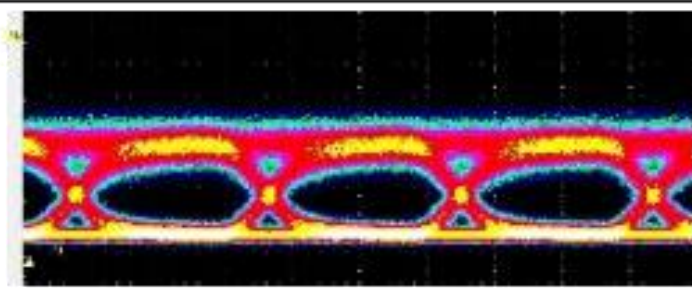
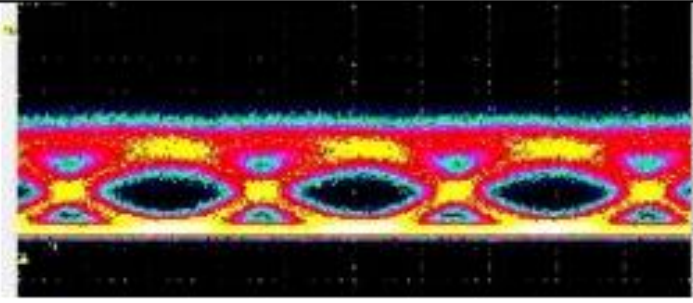
Four generations of ASPICs designed, developed and tested (TRL6)

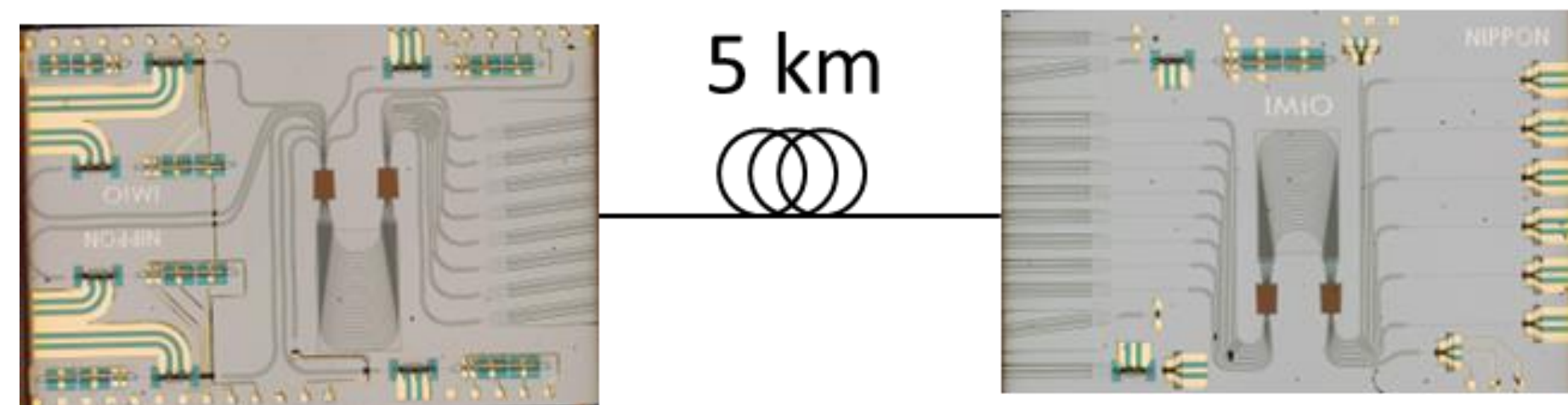
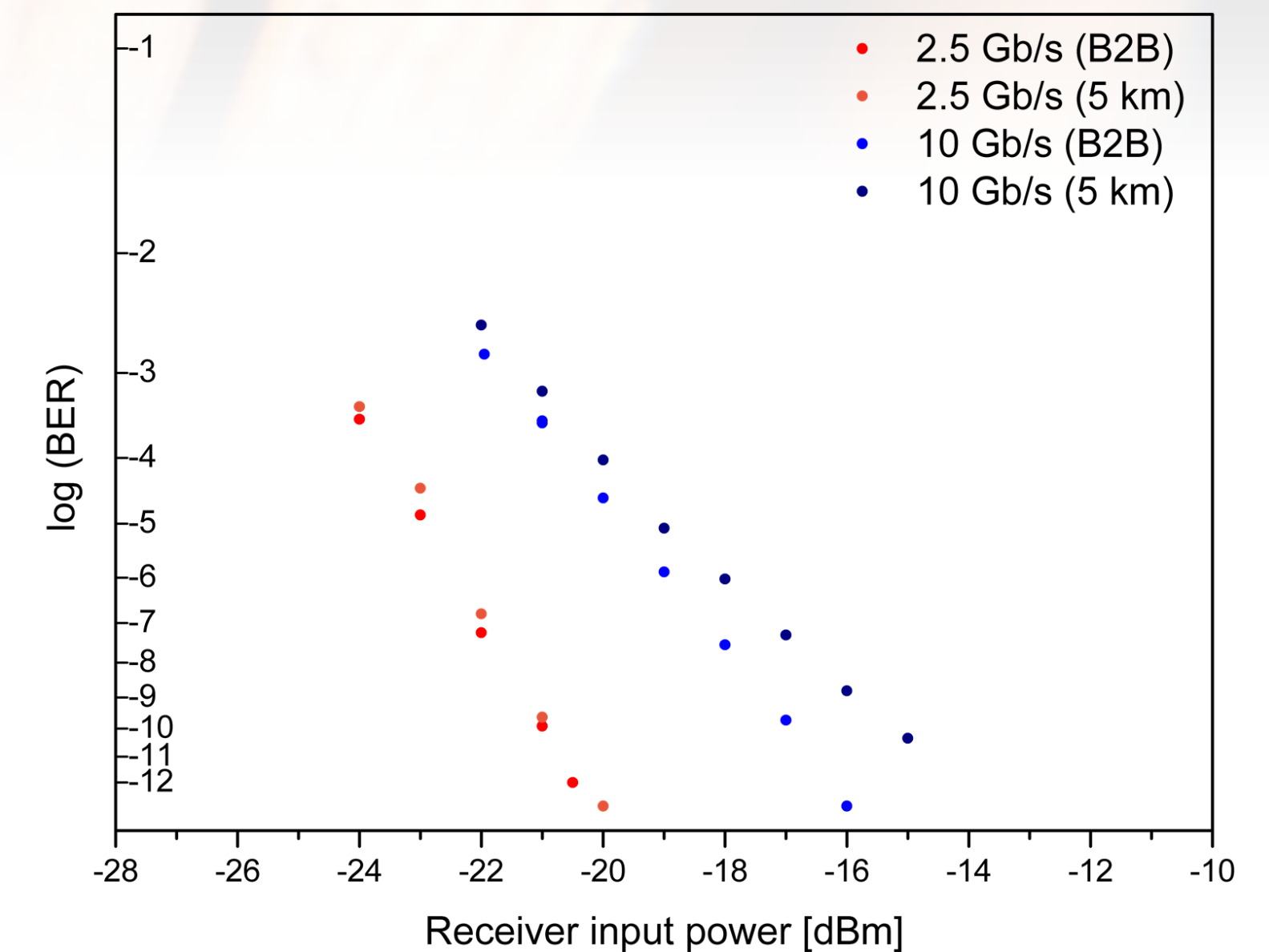


- 6 channels, L-band
- $\Delta\lambda = 0.8$ nm (100 GHz grid)
- output power 0.2 mW
- single mode operation, SMSR > 40 dB

Multi-wavelength transmitters for telecom and datacom

Four generations of ASPICs designed, developed and tested (TRL6)

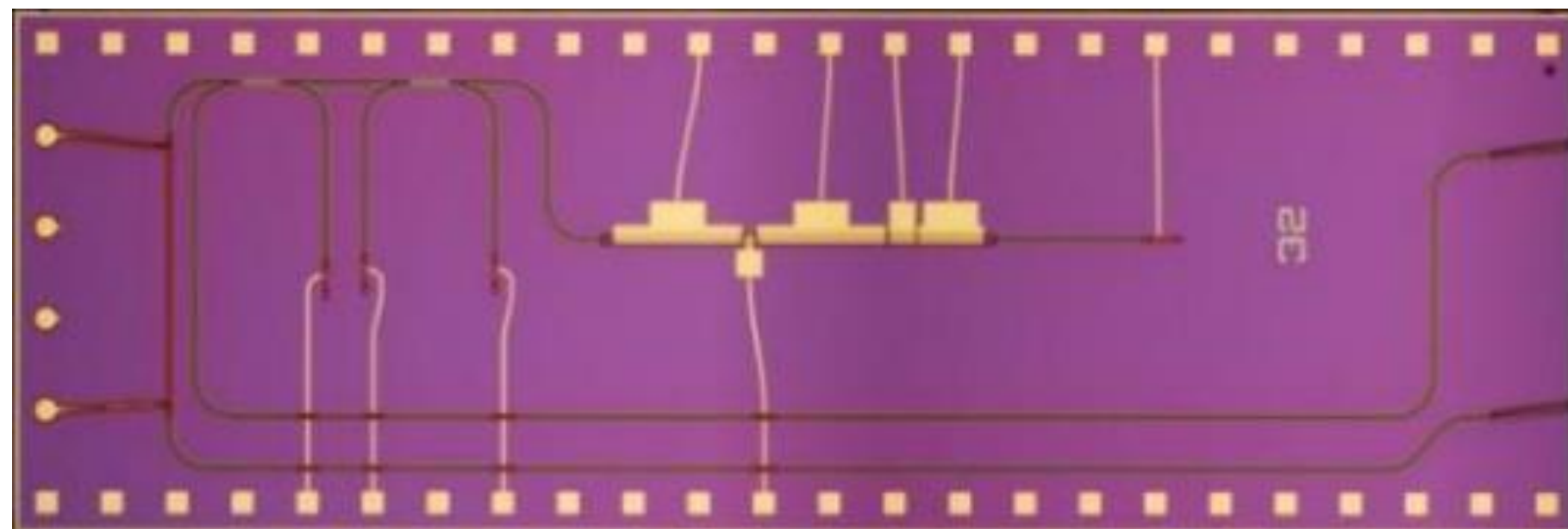
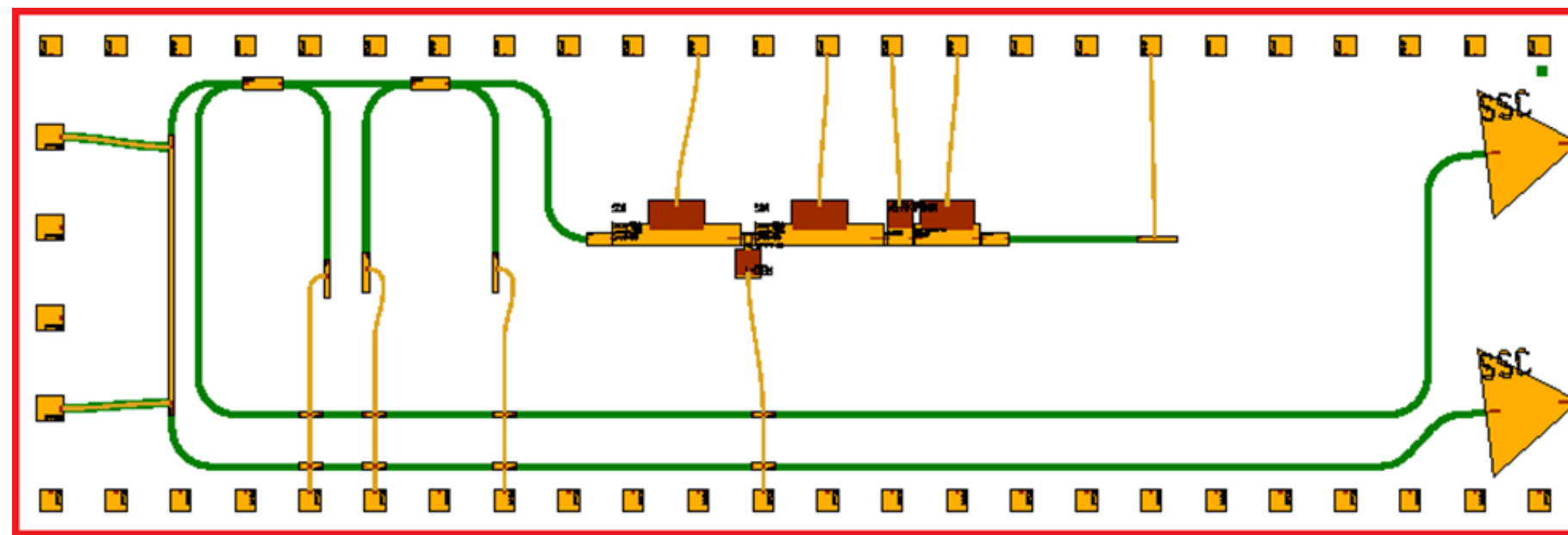
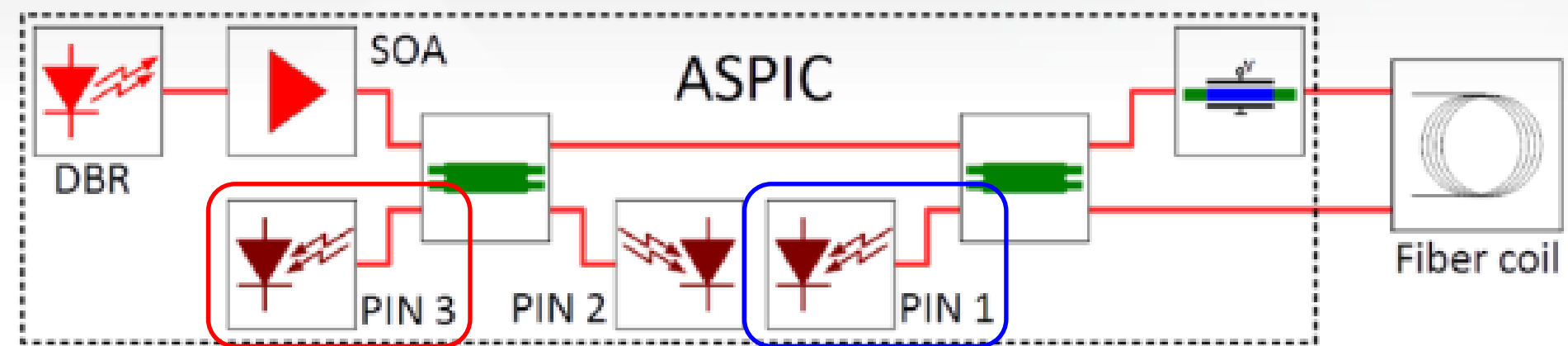
	2.5 Gb/s	5 Gb/s	10 Gb/s
B2B	 ER = 10 dB QF = 9	 ER = 9 dB QF = 8	 ER = 8 dB QF = 6
5 km	 ER = 7 dB QF = 6	 ER = 7 dB QF = 6	 ER = 6 dB QF = 5



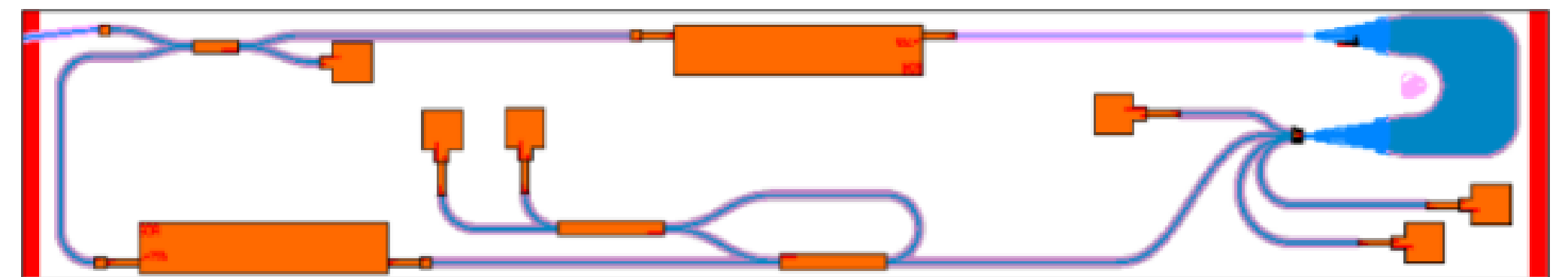
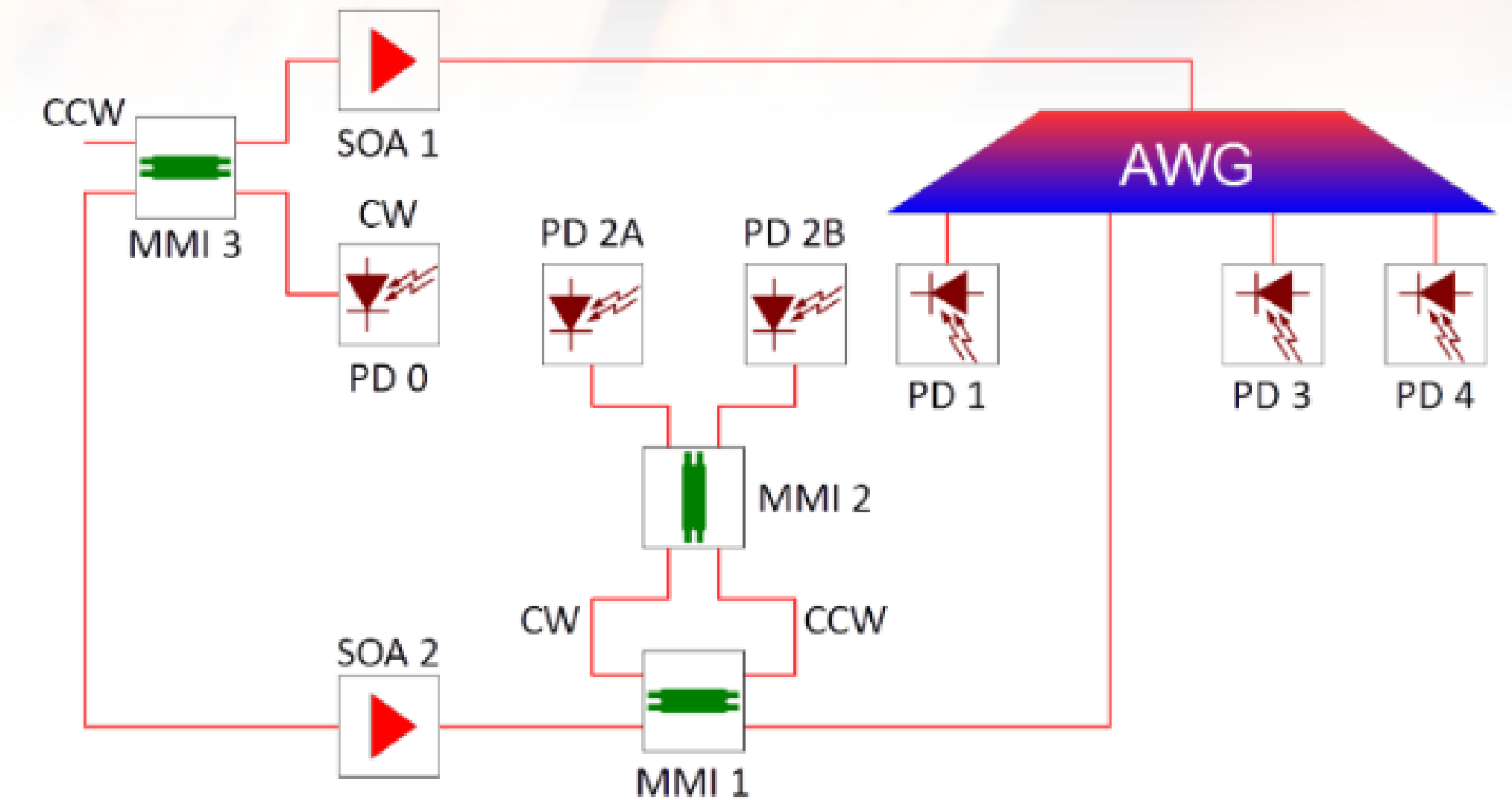
- open eye-diagrams for modulation speed up to 10 Gb/s and distance up to 5 km
- error-free operation confirmed

Integrated optical gyroscopes

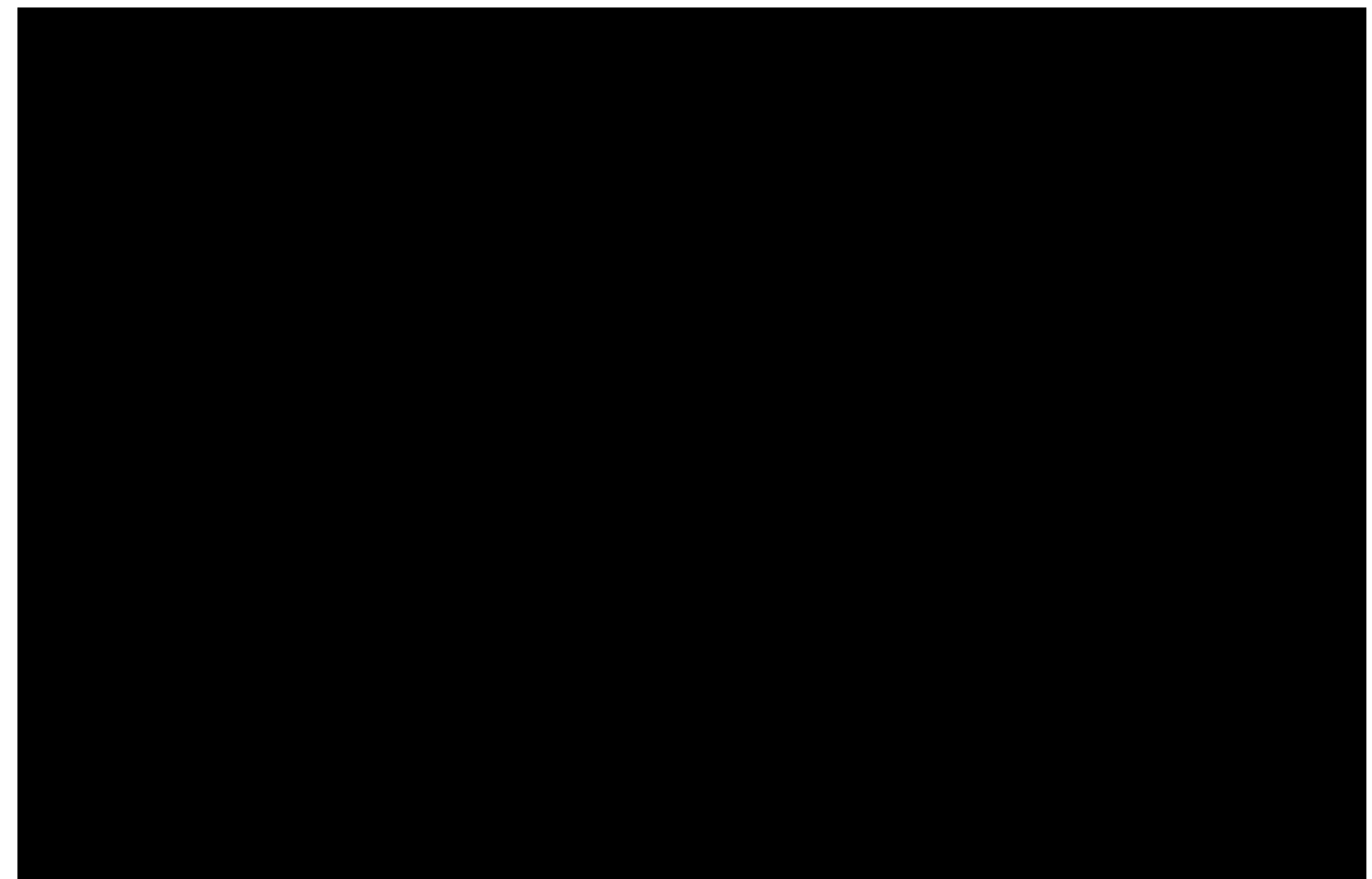
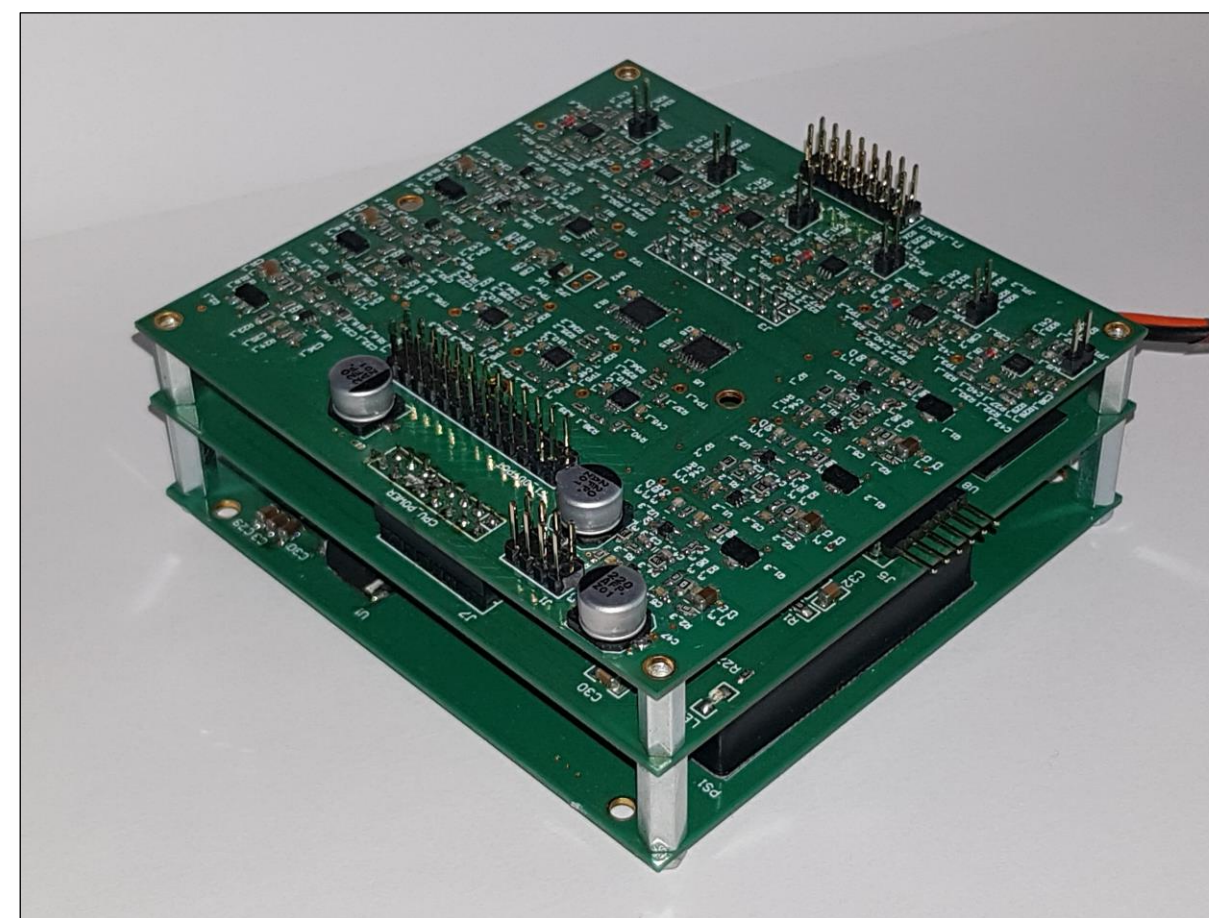
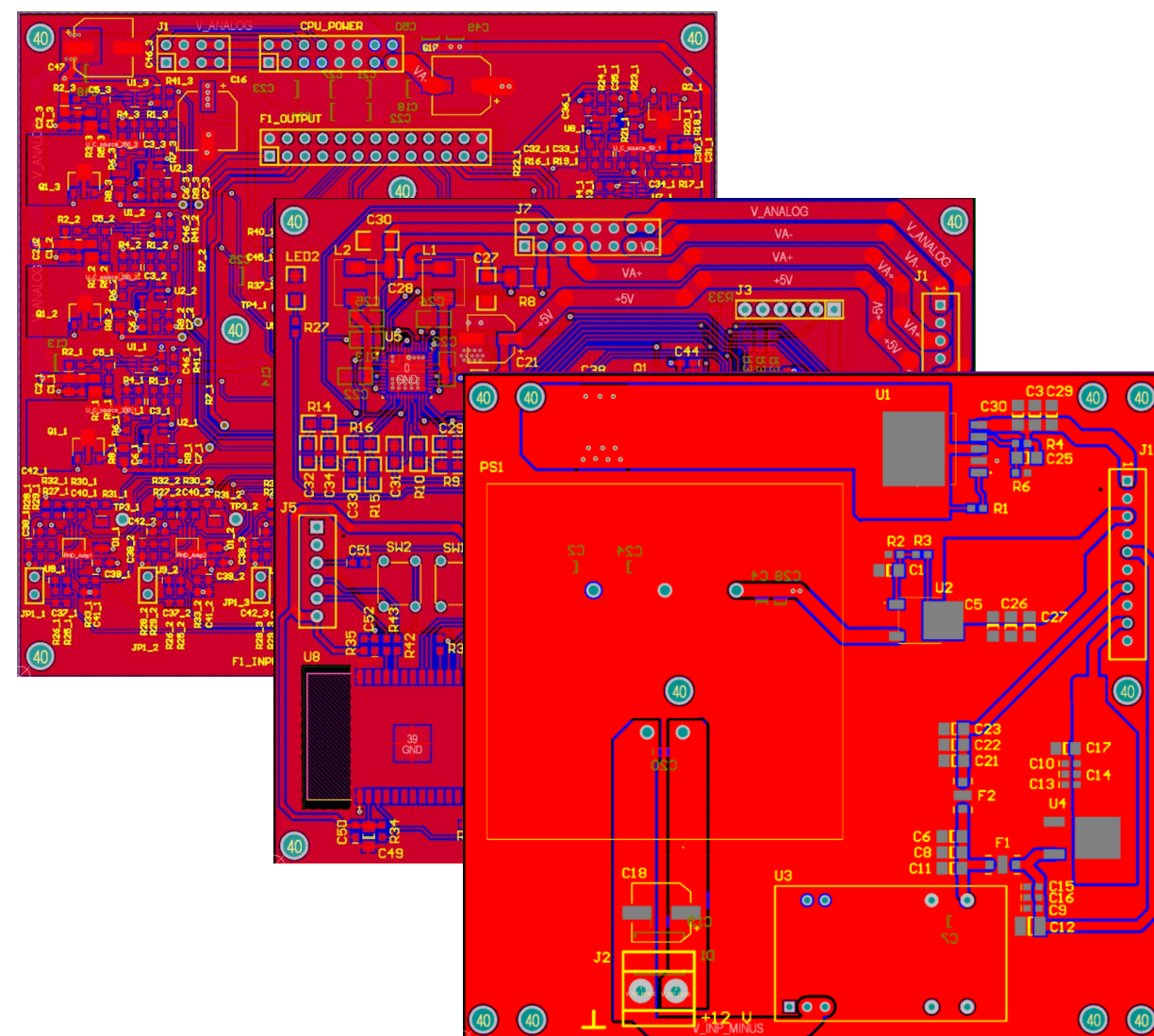
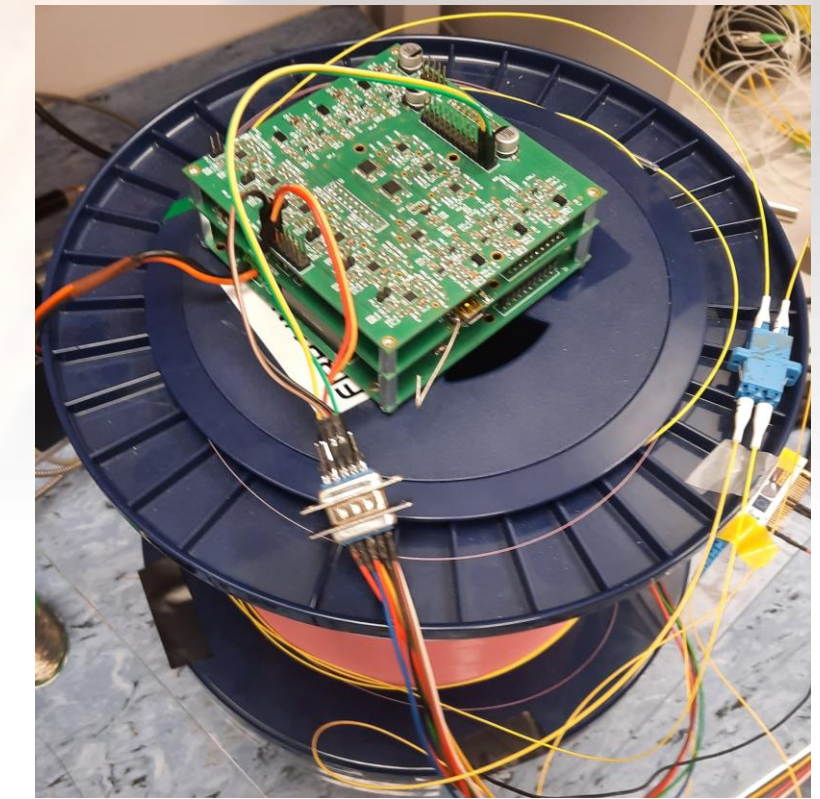
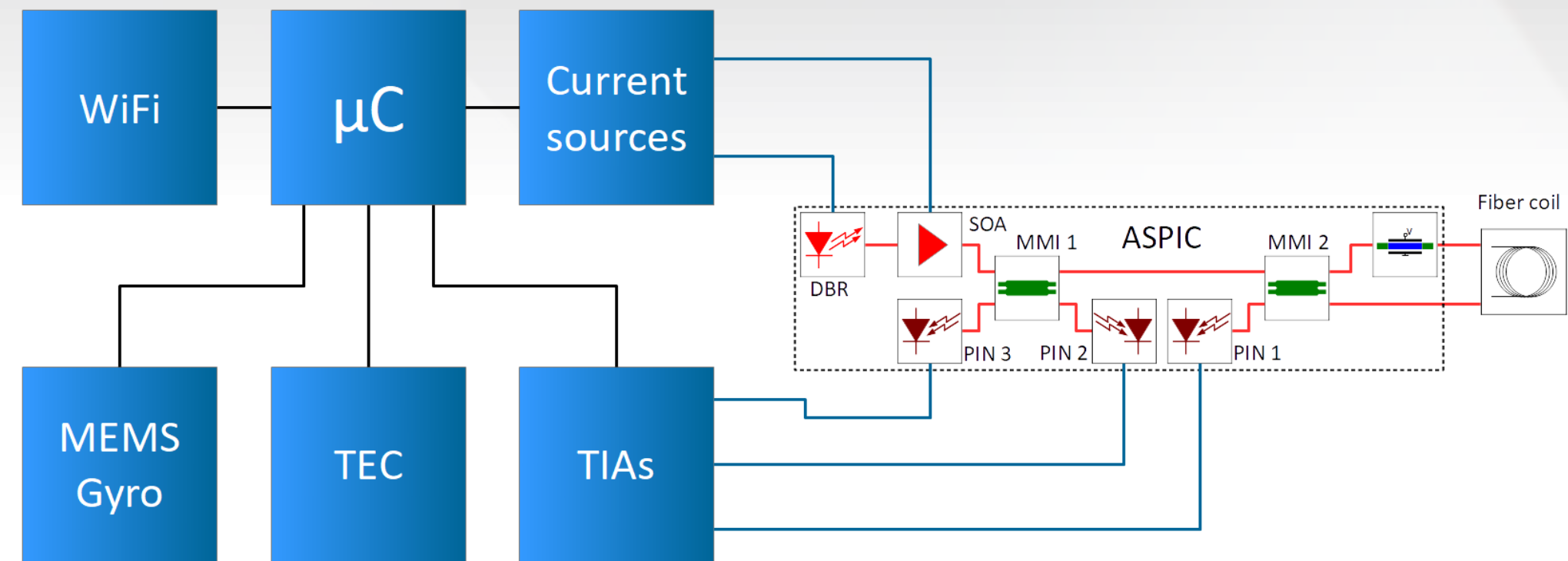
ASPIC-based interrogator for interferometric fiber-optic gyroscope (iFOG)



ASPIC-based single-mode ring laser for ring laser gyroscope (RLG)

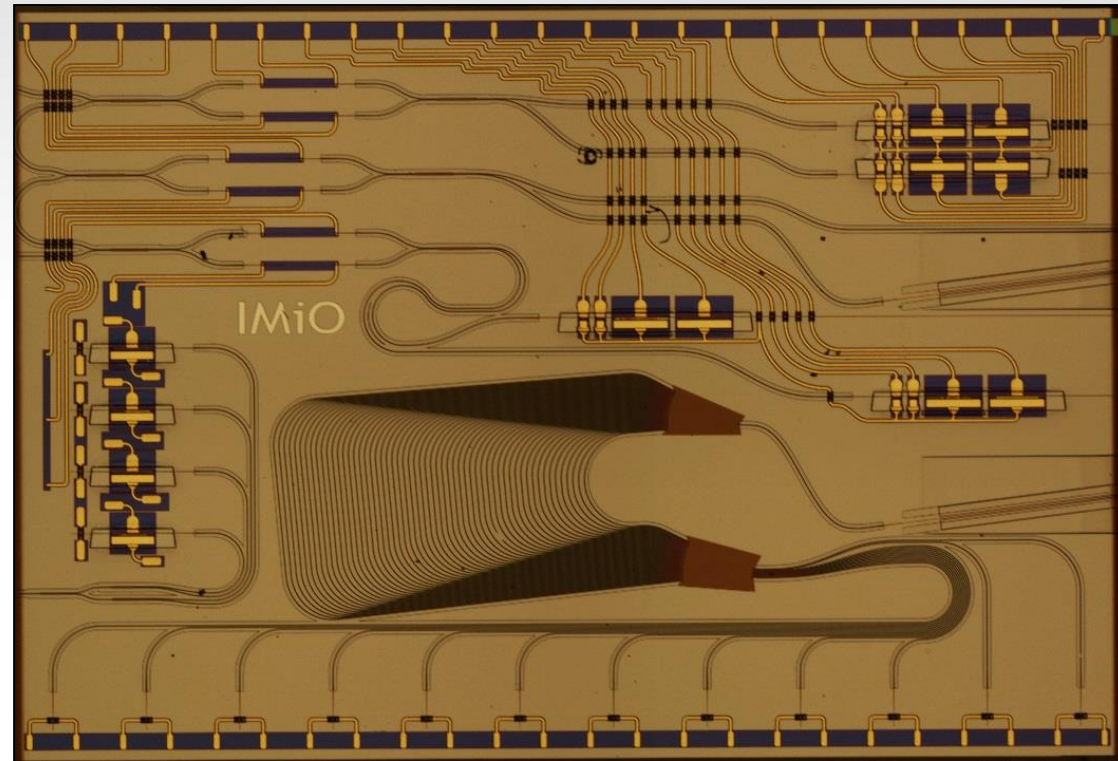


IFOG system demonstrator – gyroscope experiments

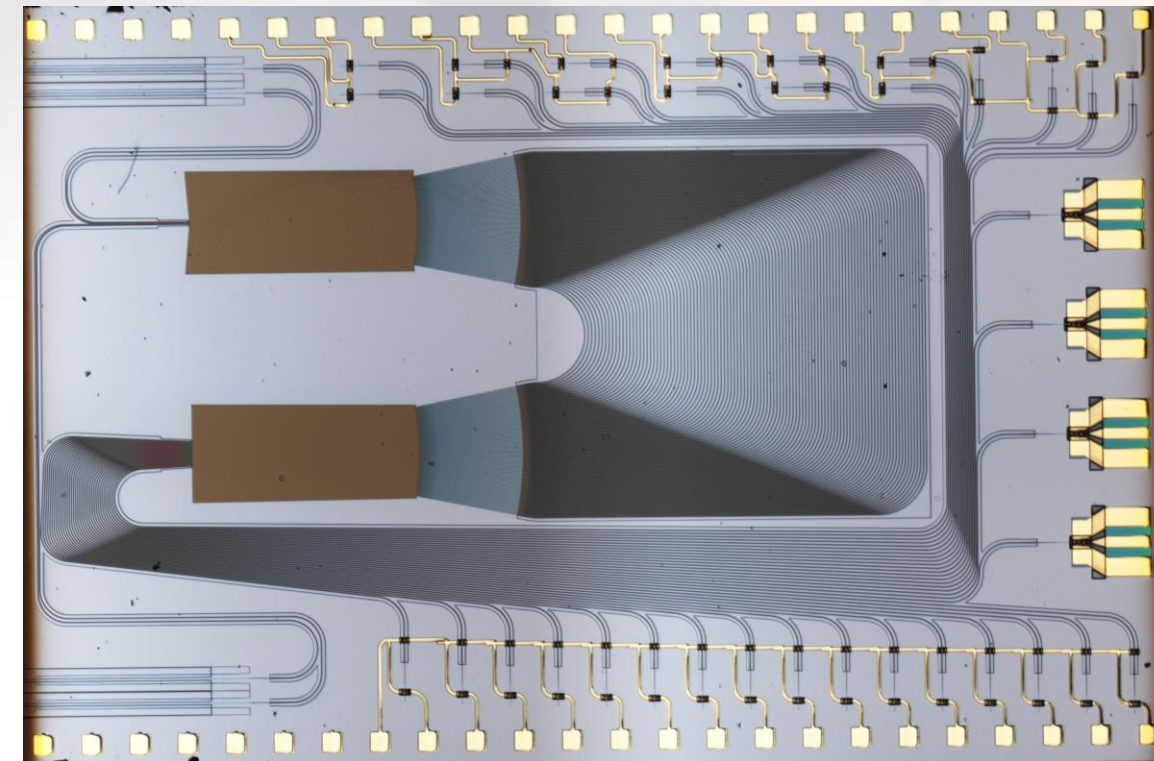


Integrated interrogators of fiber Bragg gratings

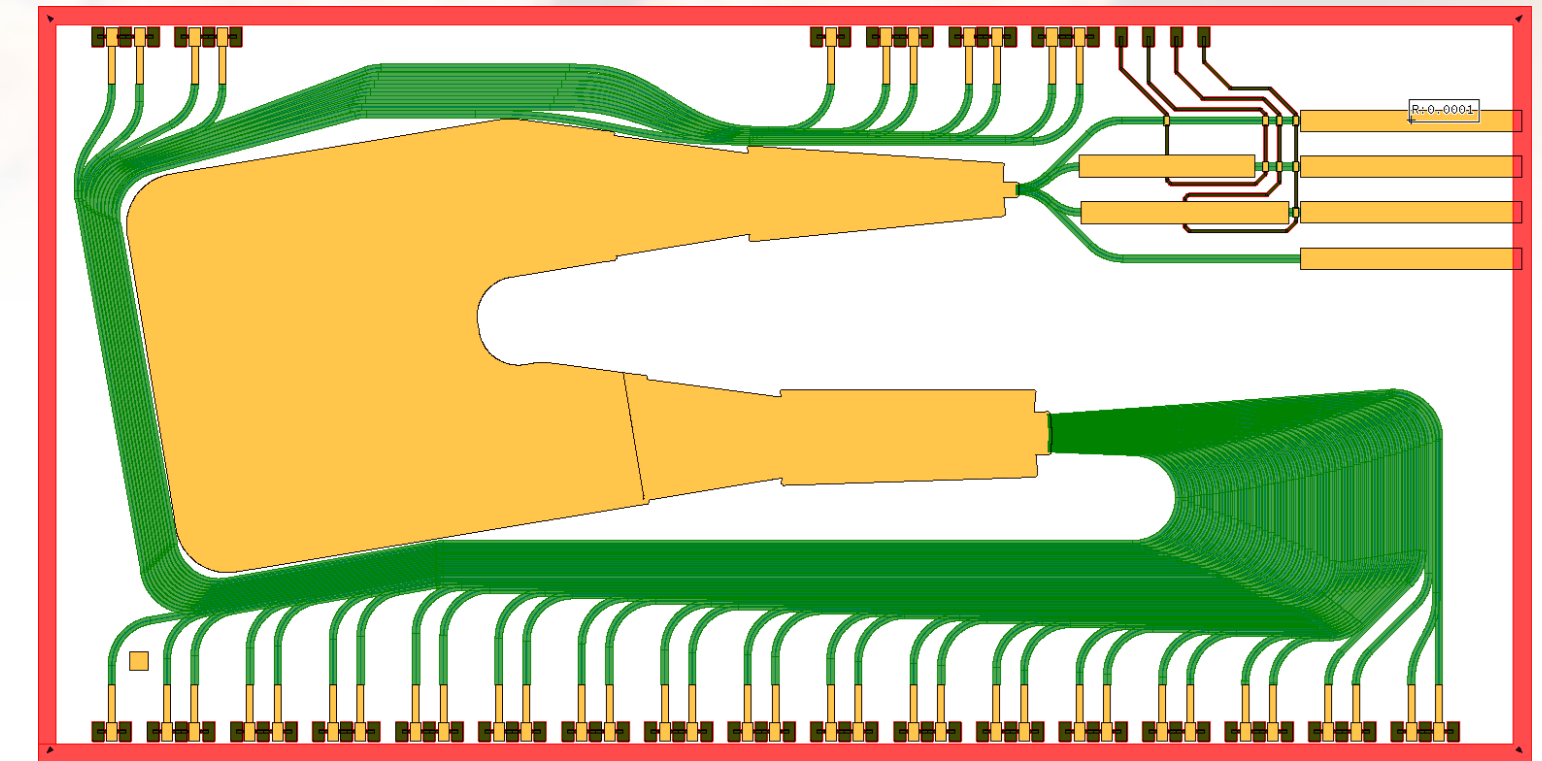
Line of AWG-based interrogators (TRL6/TRL7)



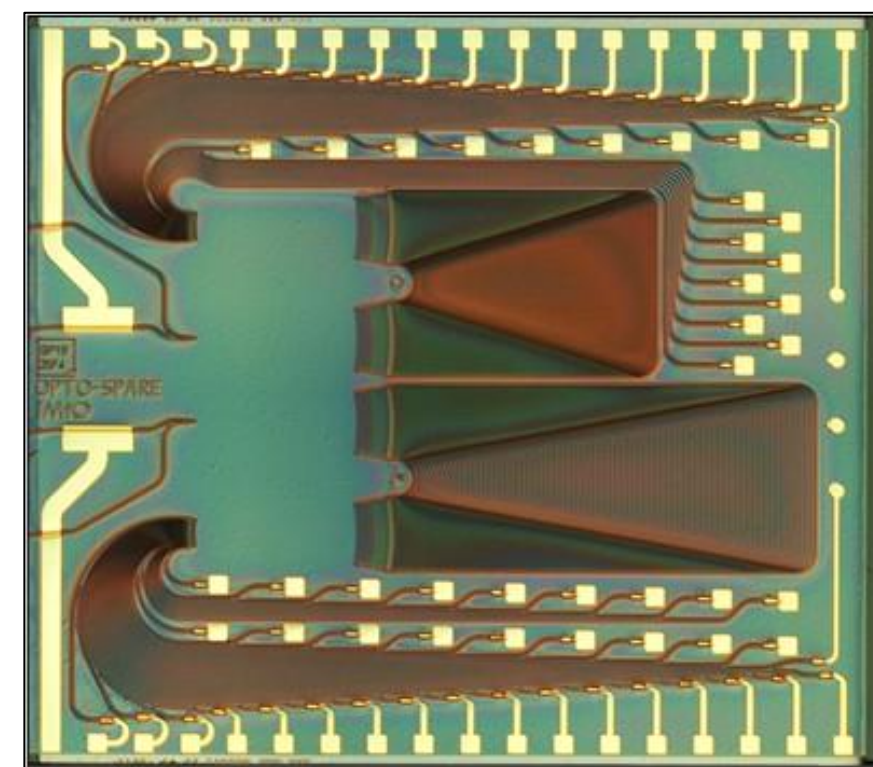
- 12 channels
- $\Delta f = 100$ GHz
- foundry: Heinrich-Hertz Institute



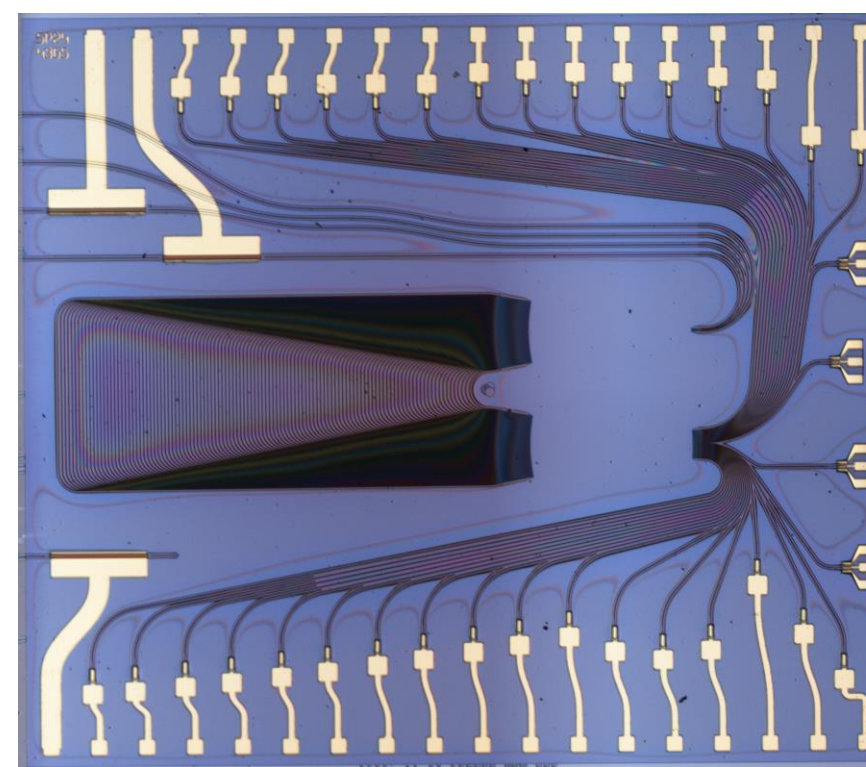
- 36 channels
- $\Delta f = 50$ GHz
- foundry: Heinrich-Hertz Institute



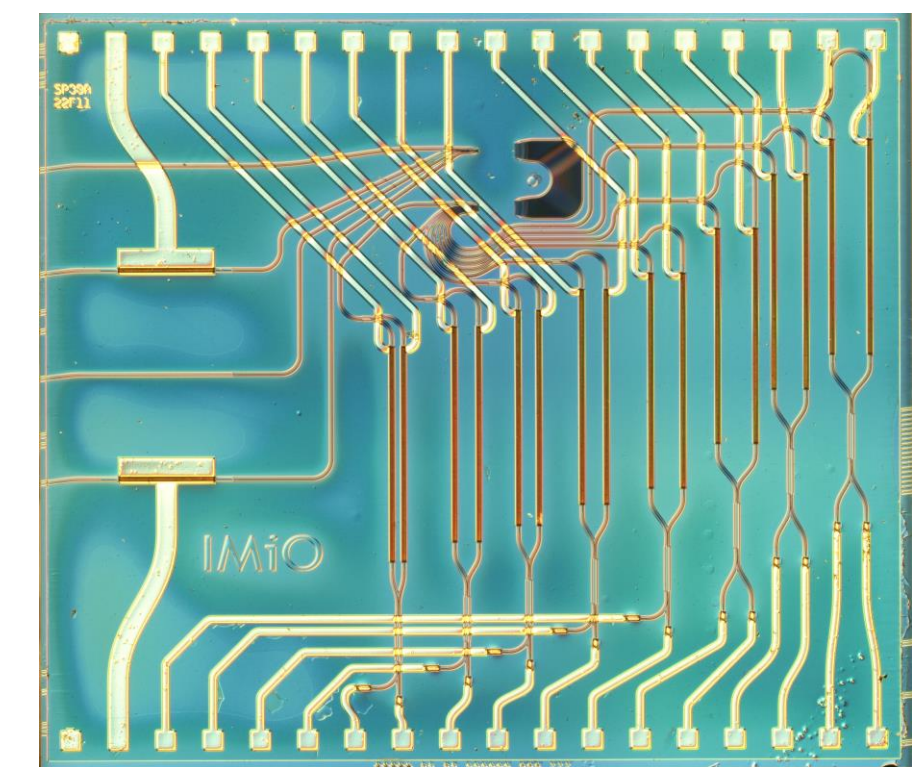
- 44 channels
- $\Delta f = 50$ GHz
- foundry: Heinrich-Hertz Institute



- 36 channels
- $\Delta f = 50$ GHz
- foundry: SMART Photonics



- 36 channels
- $\Delta f = 50$ GHz
- foundry: SMART Photonics



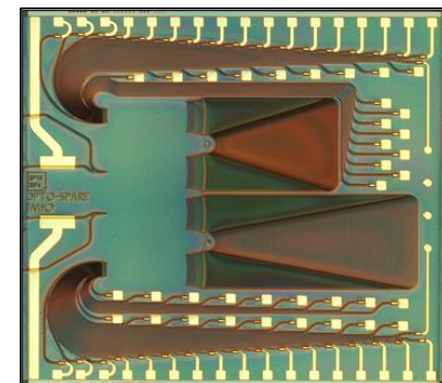
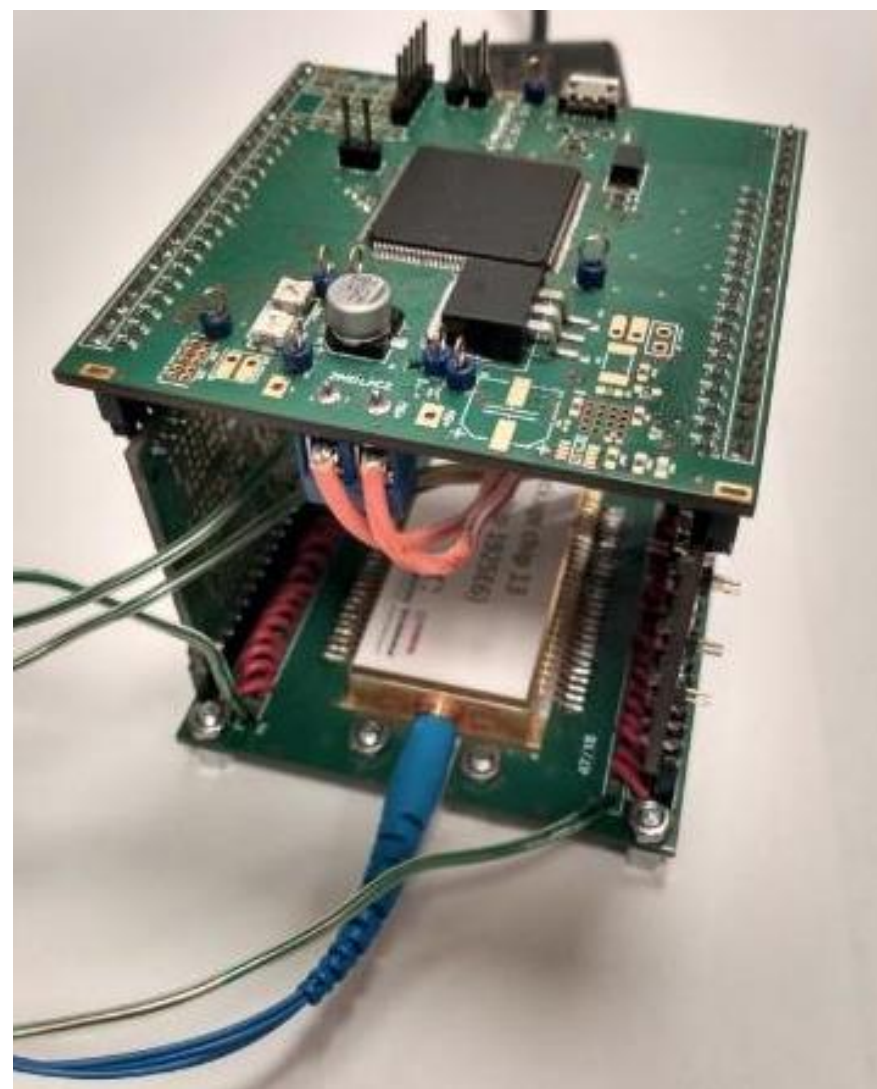
- AMZI-based interrogator
- foundry: SMART Photonics

Integrated interrogators of fiber Bragg gratings

Line of AWG-based interrogators (TRL6/TRL7)

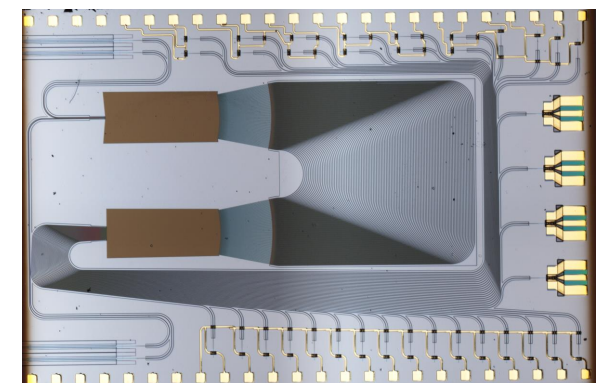
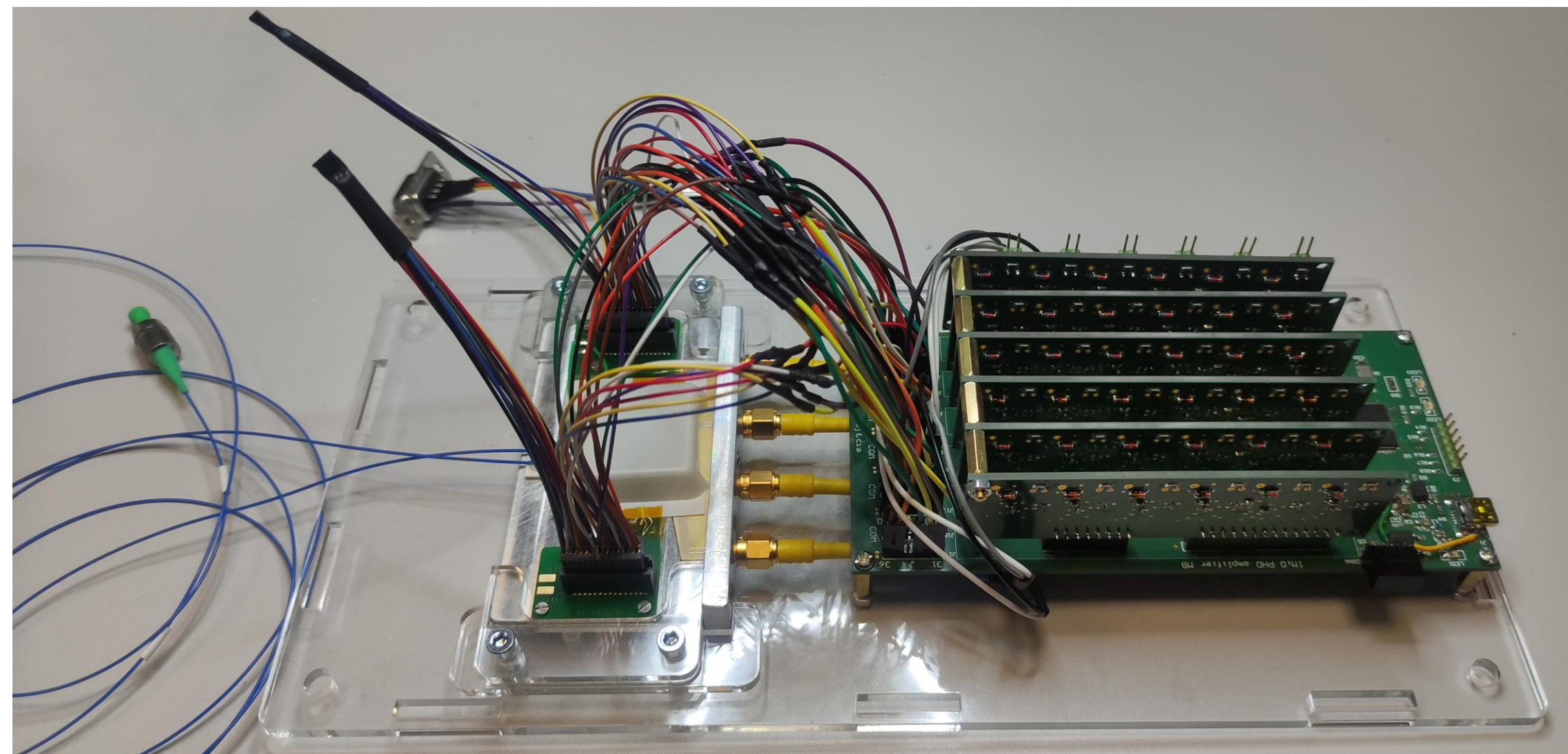
Demonstrators equipped with custom-made driving electronic systems

- micro-controller
- analog frontend: an array of transimpedance amplifier
- adjustable sampling rate 10 Hz – 10 kHz
- temperature control
- USB interface



ASPIC installed

- 18 channels
- $\Delta f = 50$ GHz
- foundry: SMART Photonics



ASPIC installed

- 36 channels
- $\Delta f = 50$ GHz
- foundry: Heinrich Hertz Institute

Integrated interrogators of fiber Bragg gratings

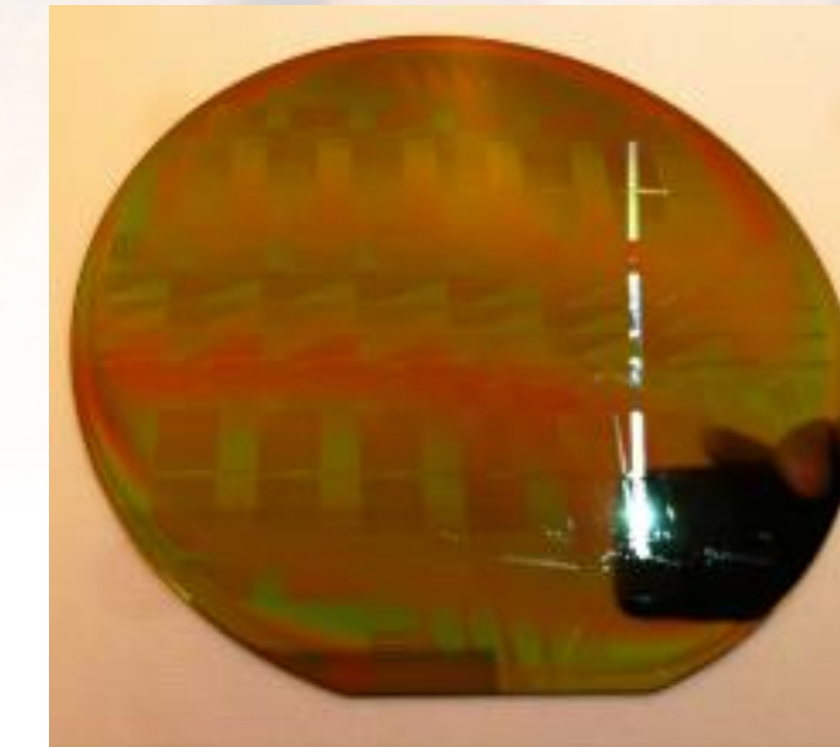
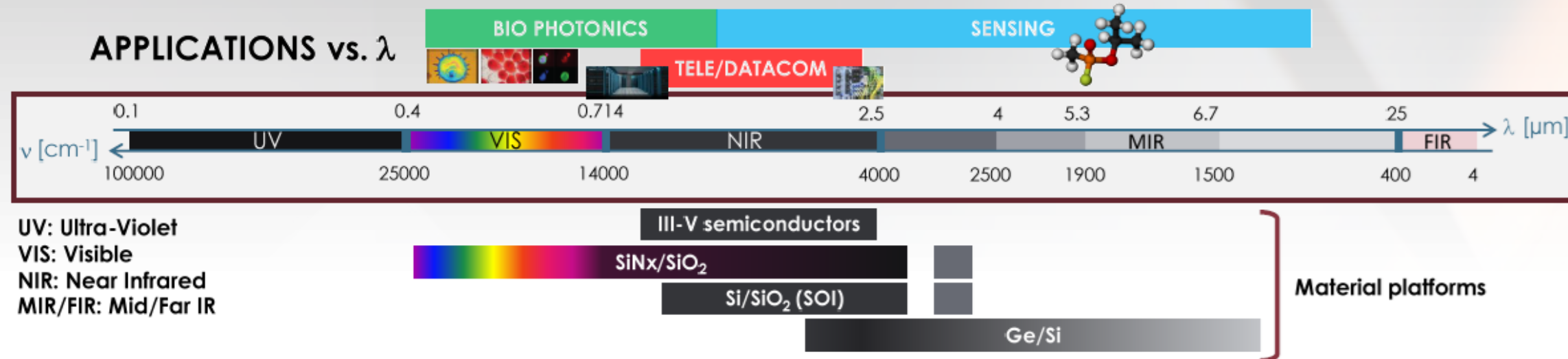




PICs technology in Poland – silicon nitride

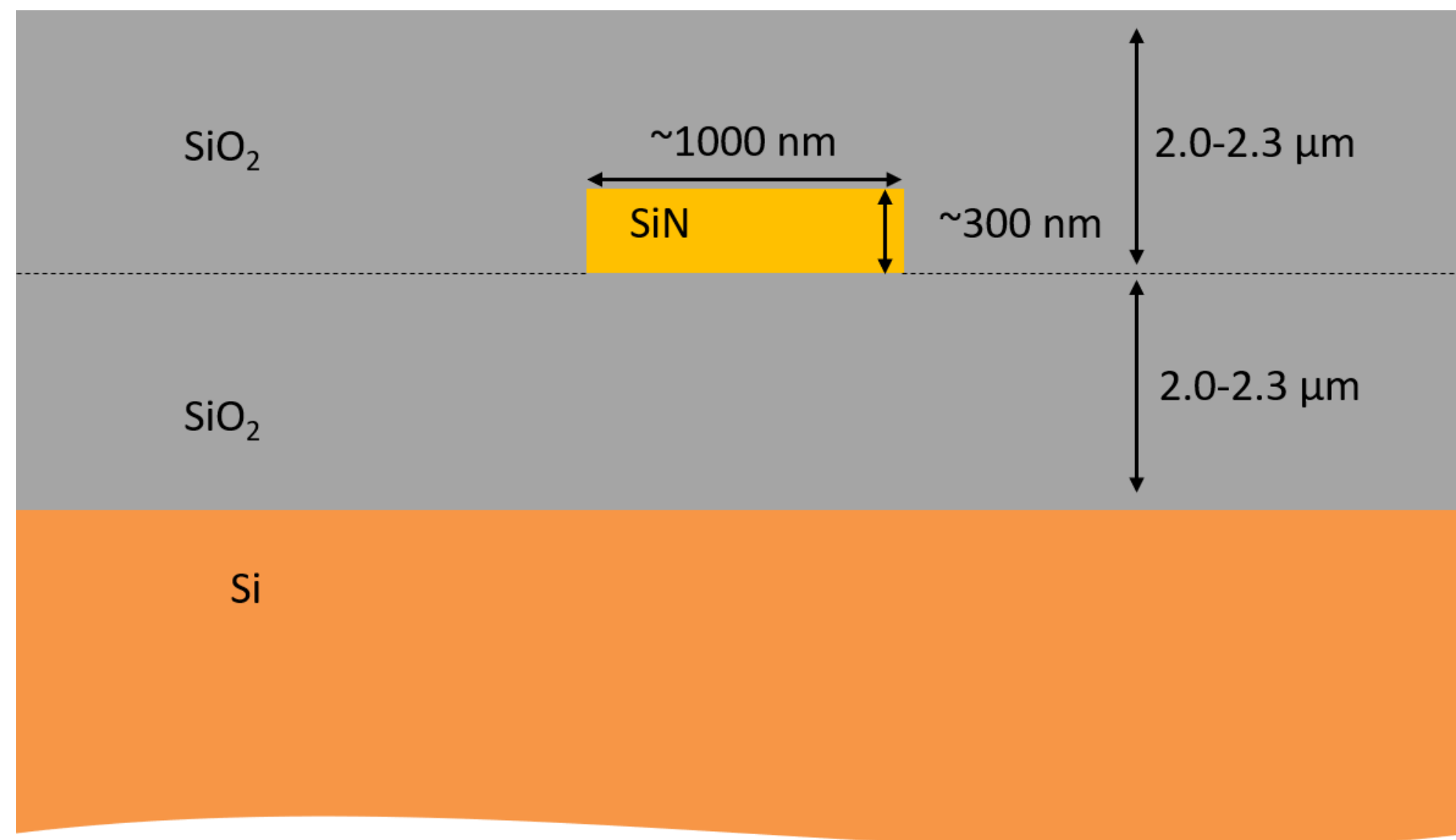


Silicon nitride technology at WUT CEZAMAT

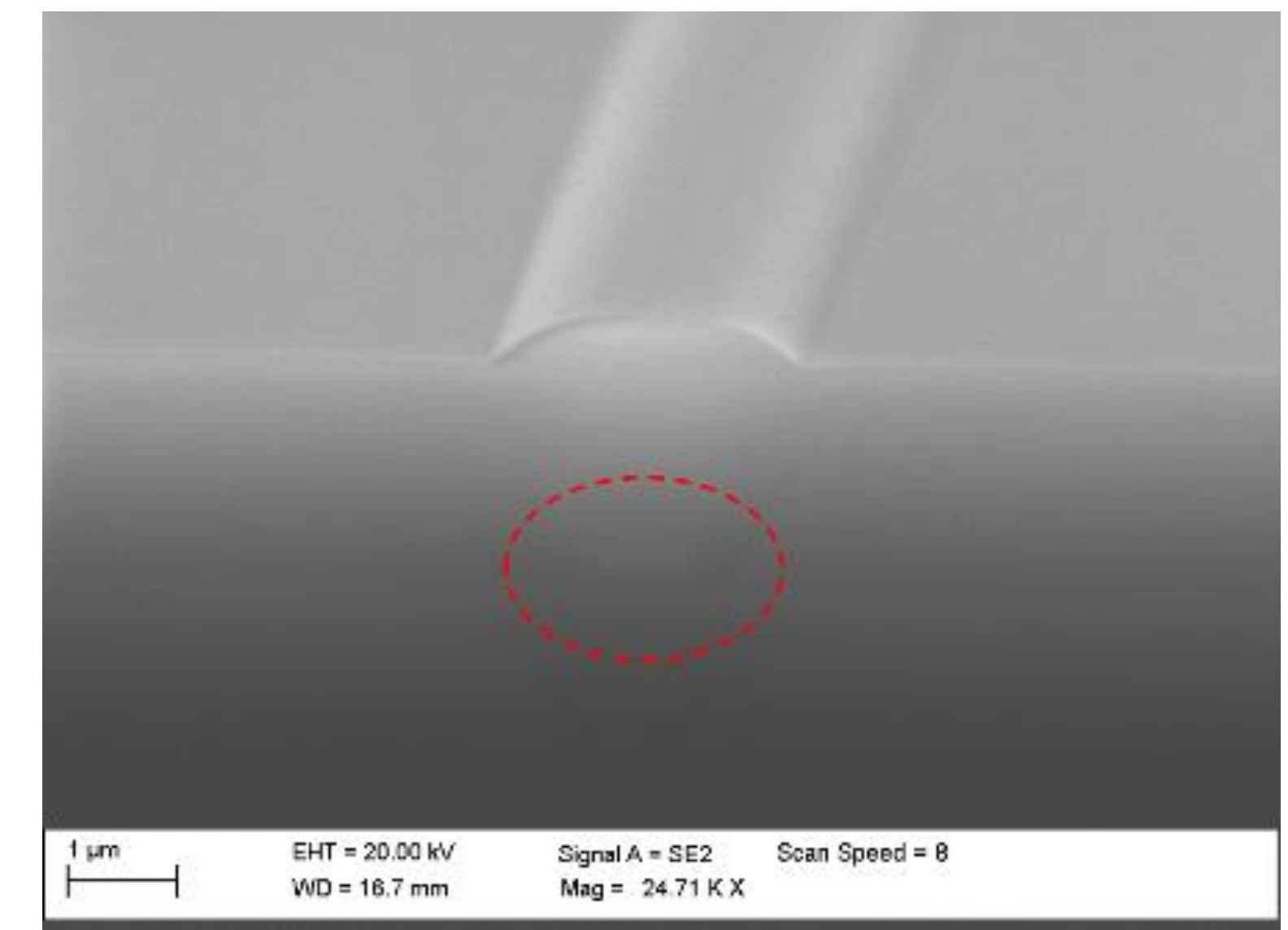


P. Munoz et al., „Silicon Nitride Photonic Integration Platforms for Visible, Near-Infrared and Mid-Infrared Applications”, Sensors. 2017;17:2088. doi: 10.3390/s17092088

Waveguide cross-section



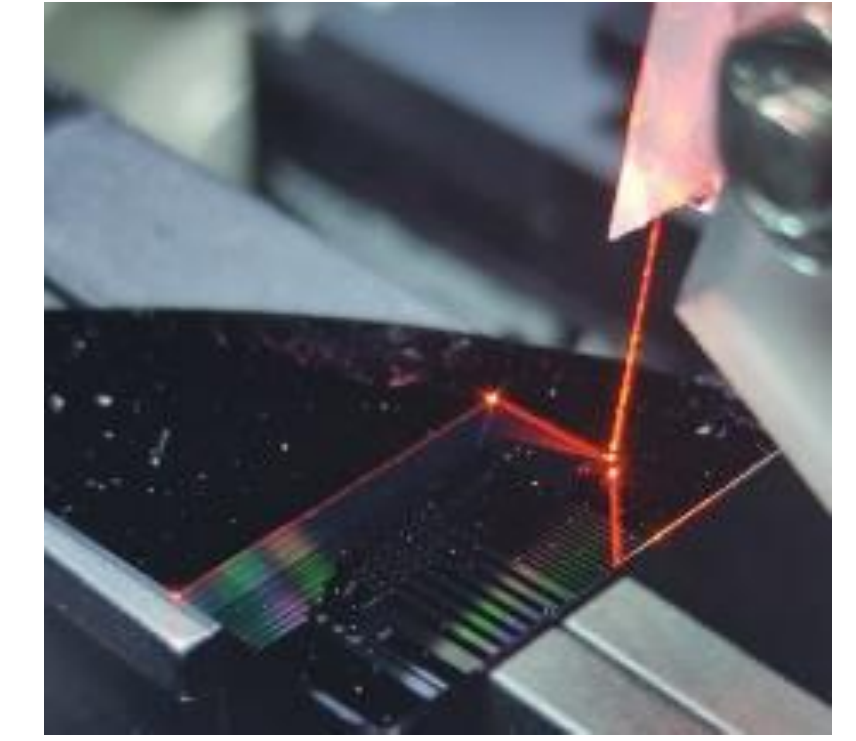
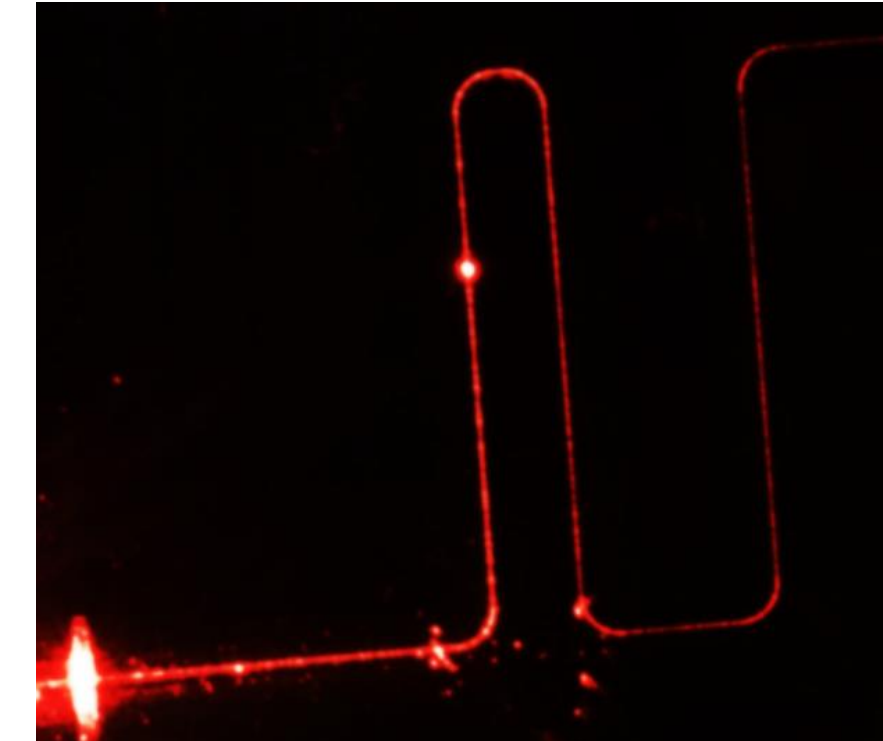
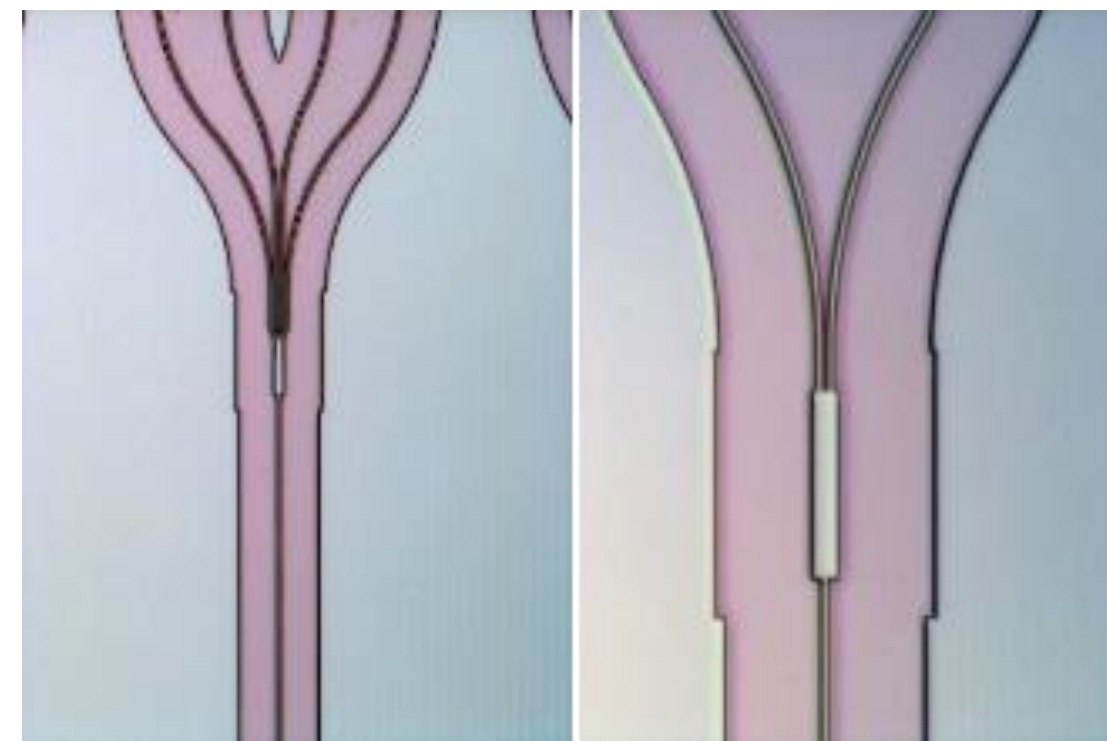
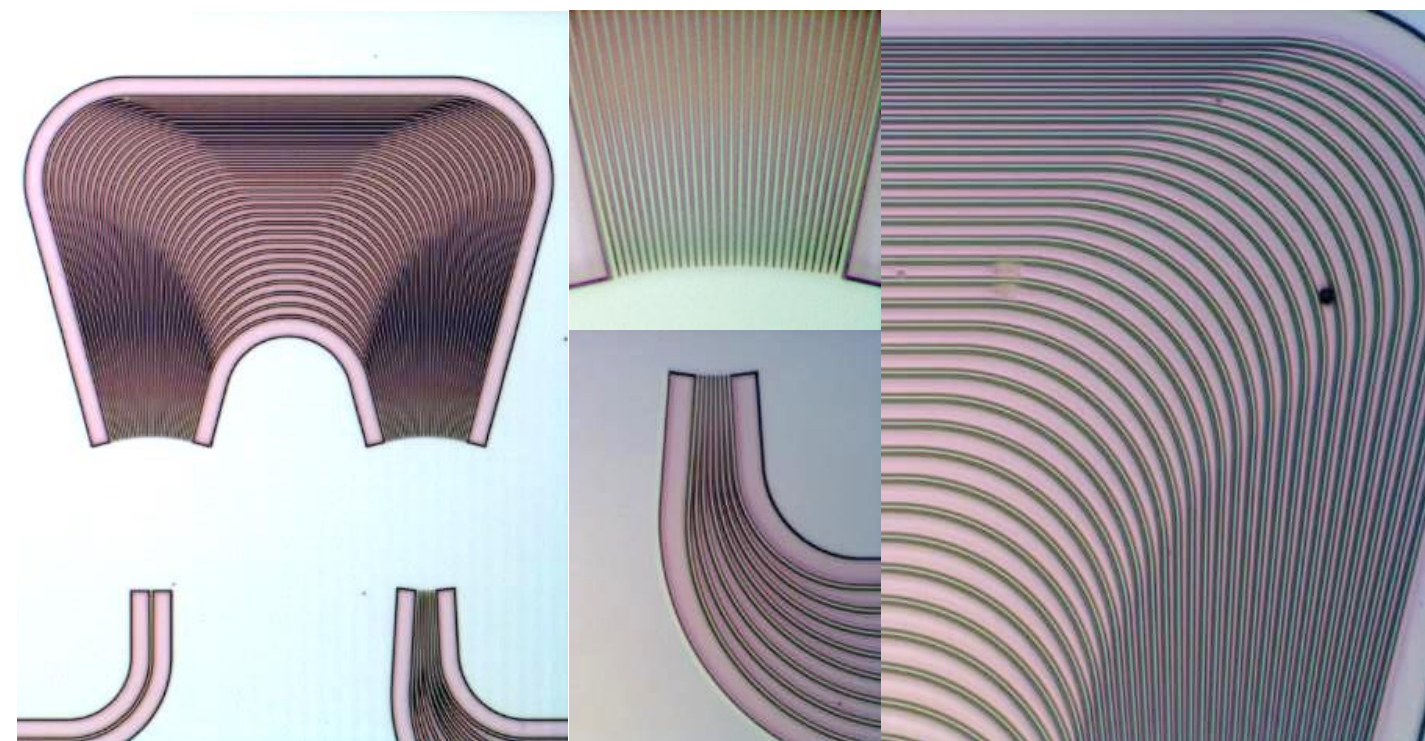
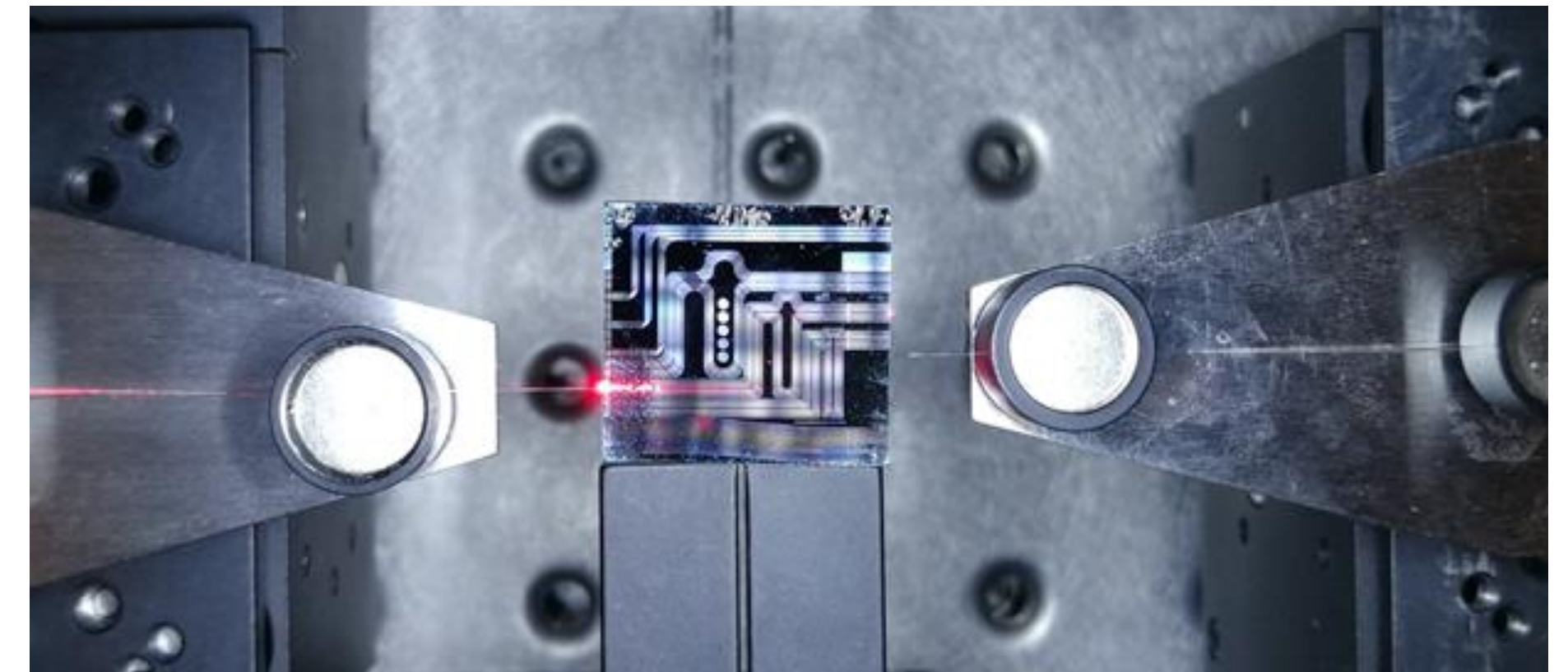
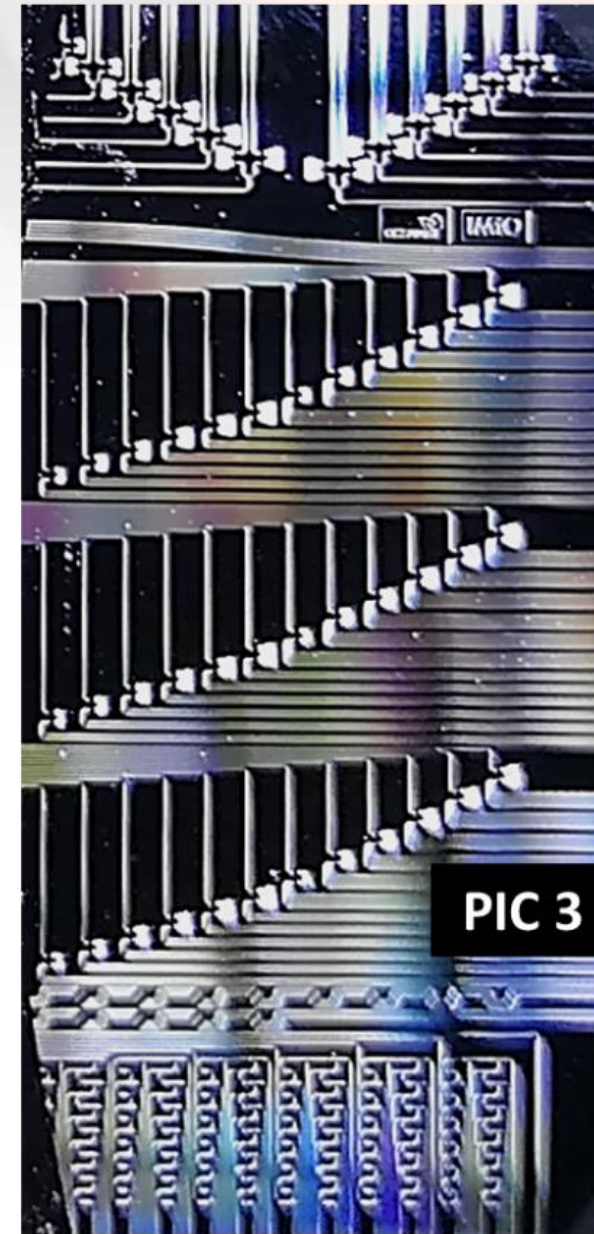
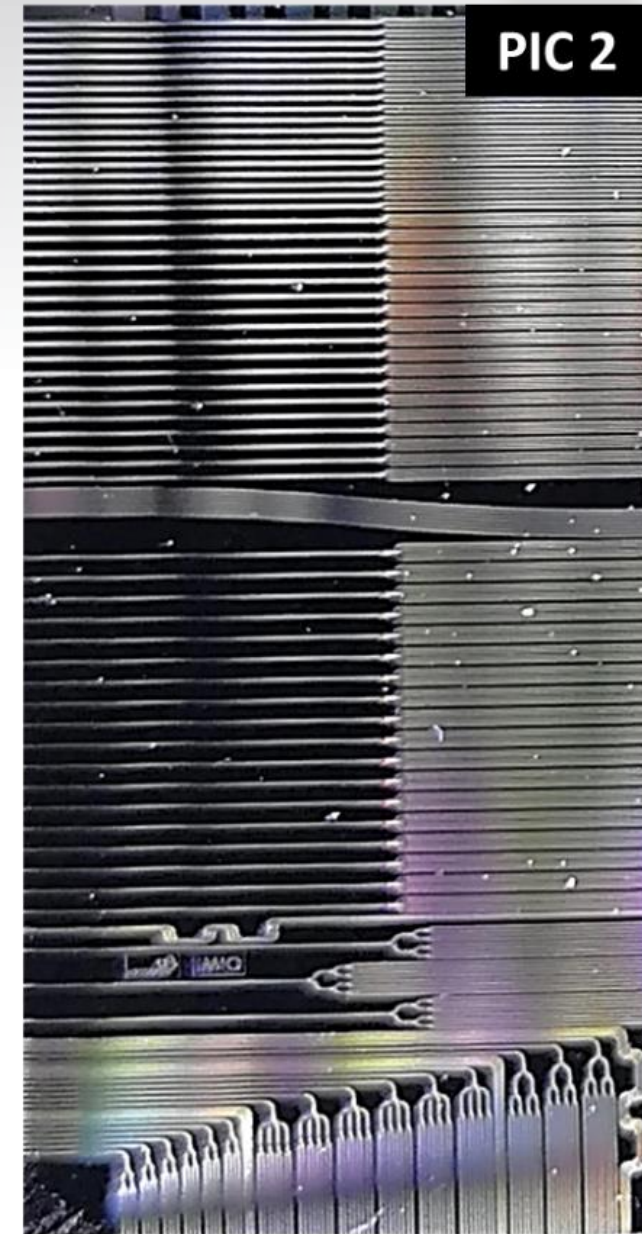
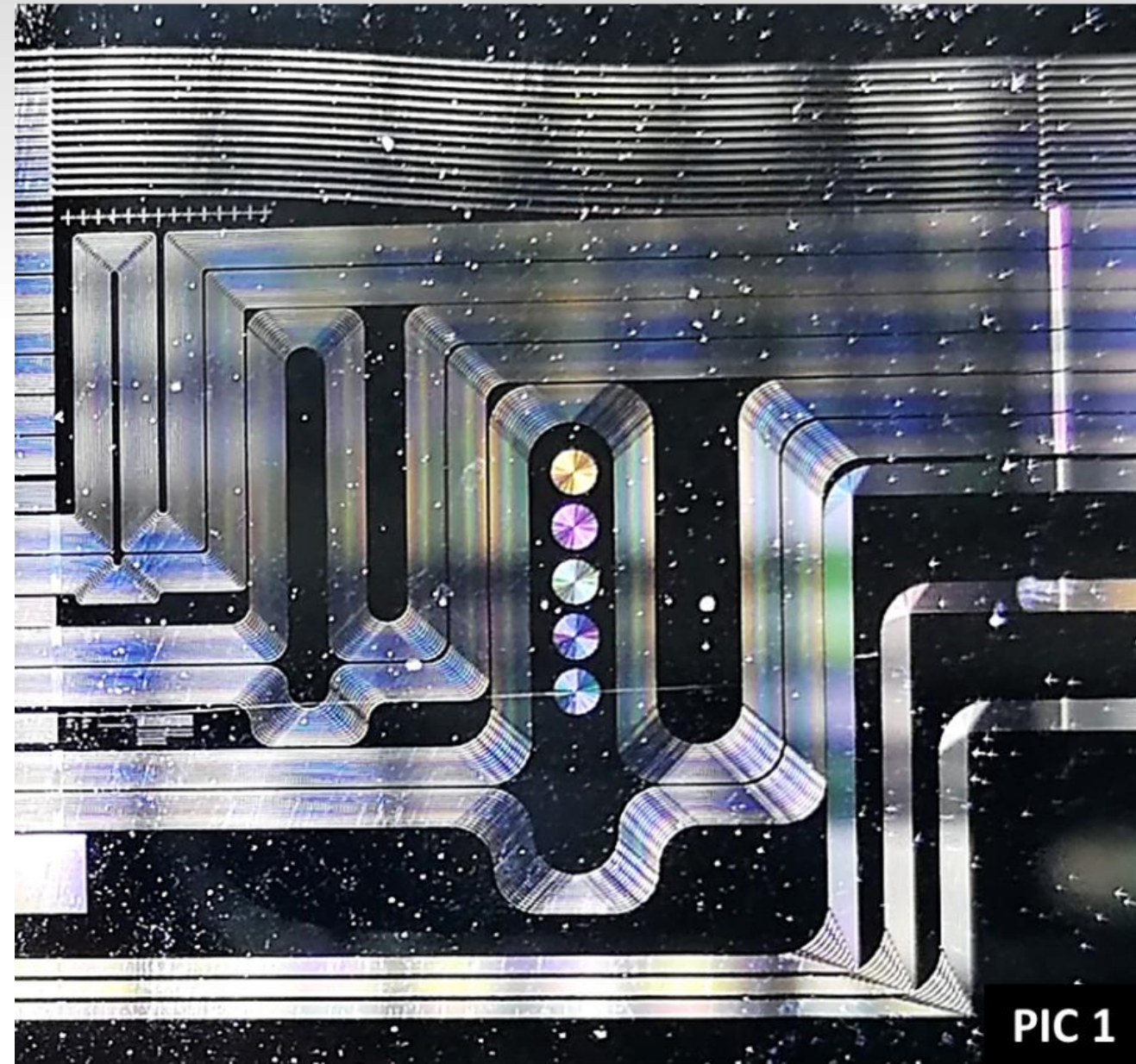
SEM image of fabricated waveguides



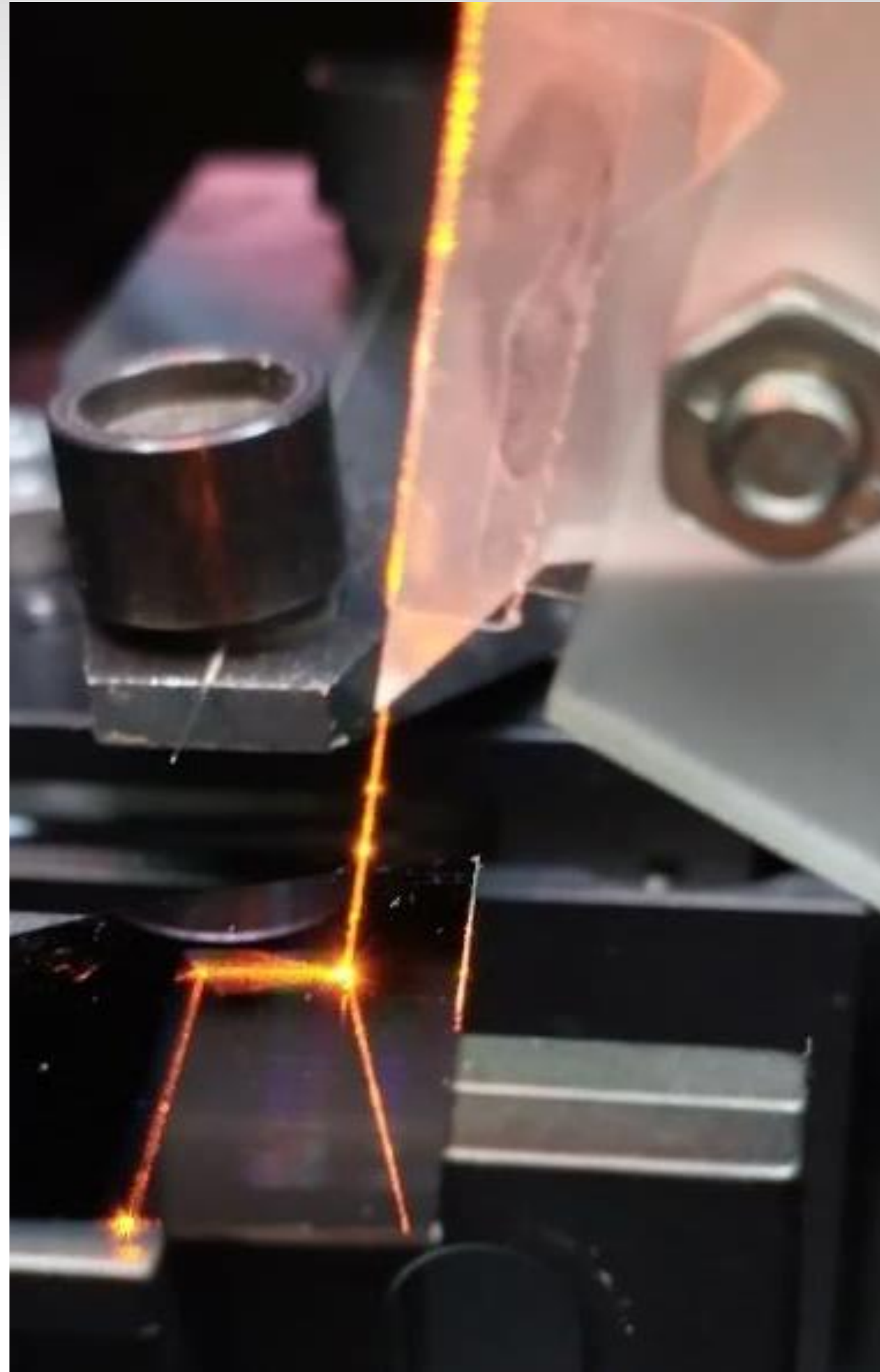
Silicon nitride technology at WUT CEZAMAT

Passive waveguides:

- attenuation between 1.7 and 3.7 dB/cm
- average loss (90° bend, 100 μm radius) 0.2 dB

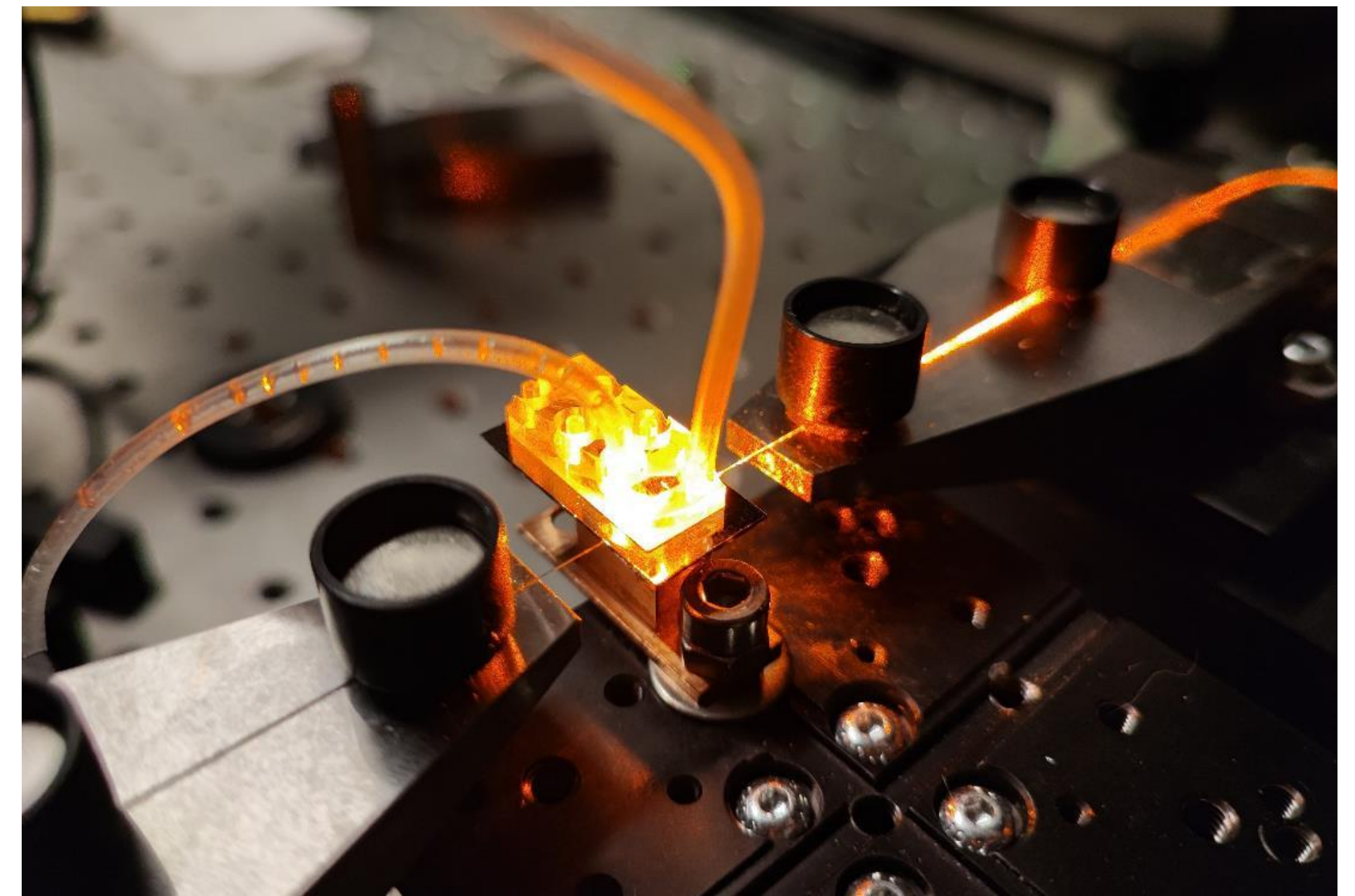


Silicon nitride technology at WUT CEZAMAT



SiN waveguides

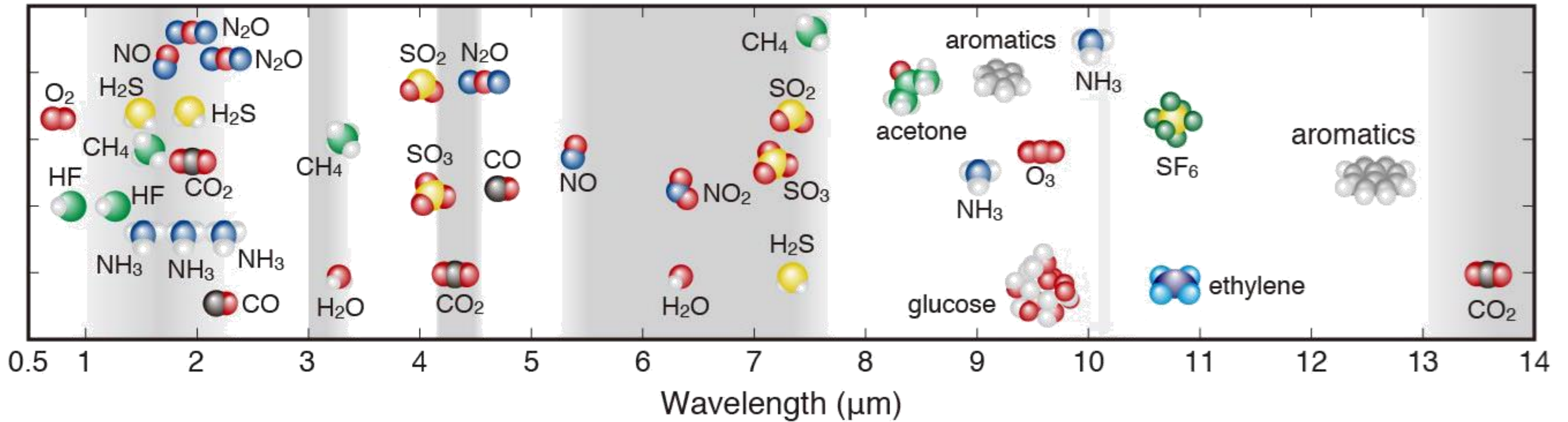
- optical interface – butt coupling and grating coupling
- integrated structures with microfluidics interface for sensing applications





Toward mid-infrared spectral range – MIRPIC platform

Nearly all chemical vapors have a unique “molecular fingerprints” in mid-infrared





Environment protection



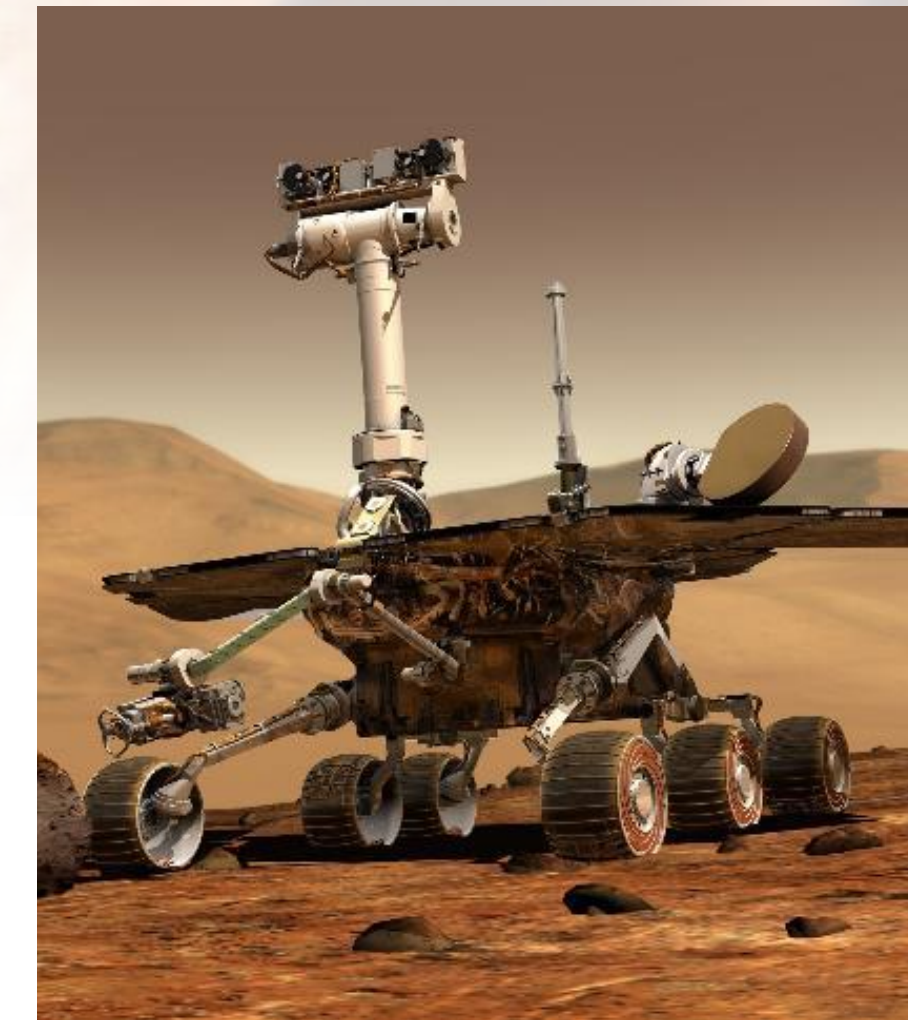
Greenhouse gases emission monitoring



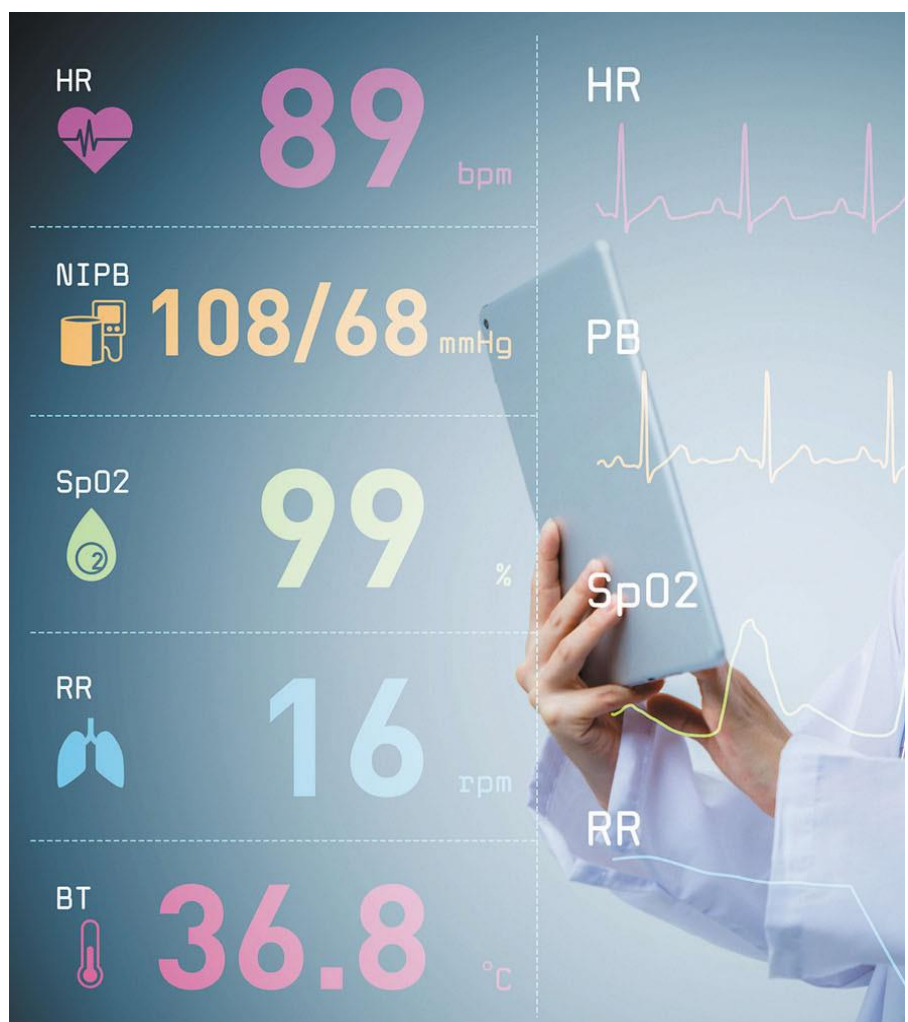
Modern agriculture



Automotive



Special applications



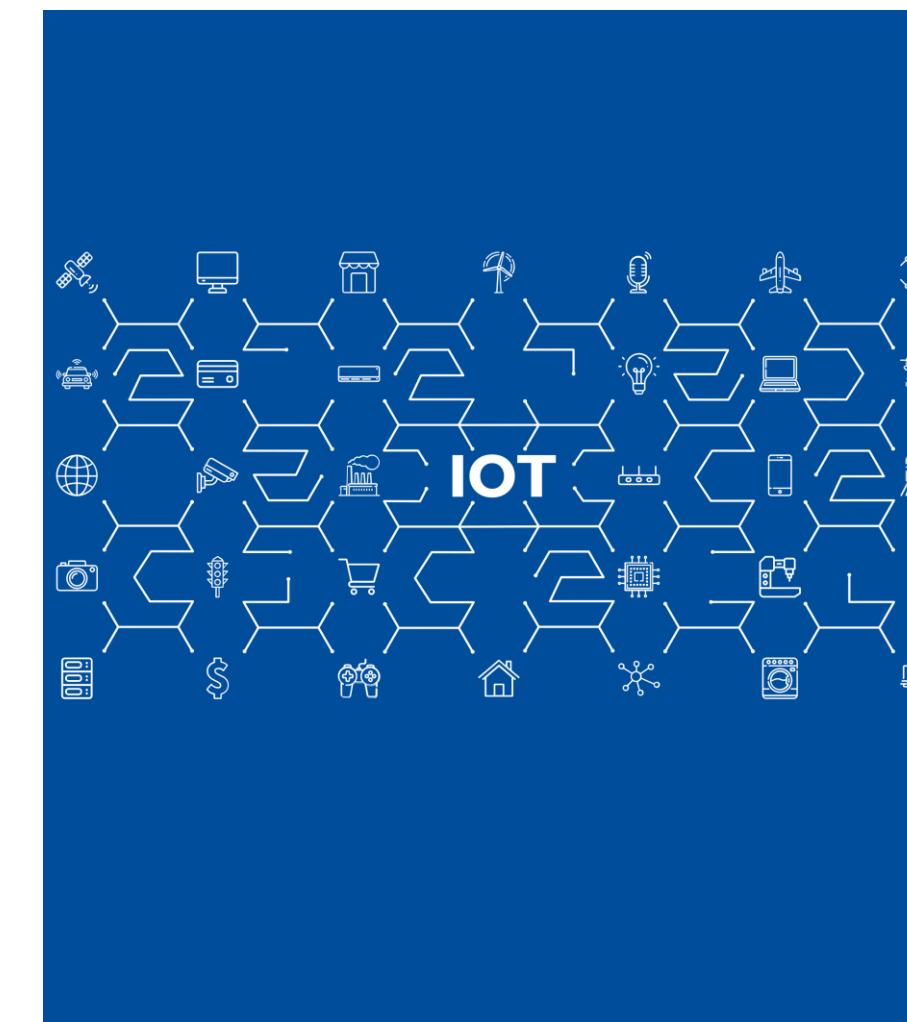
Medicine



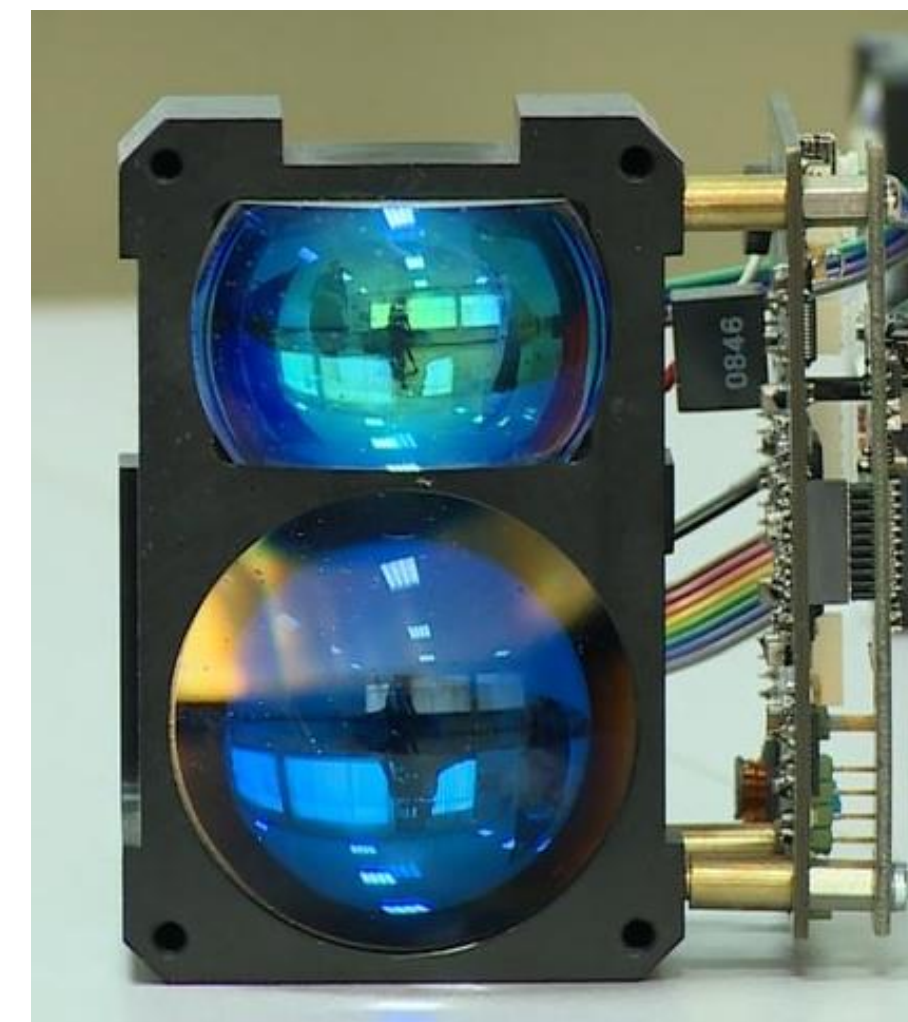
Security and safety



Defense



Internet of Things



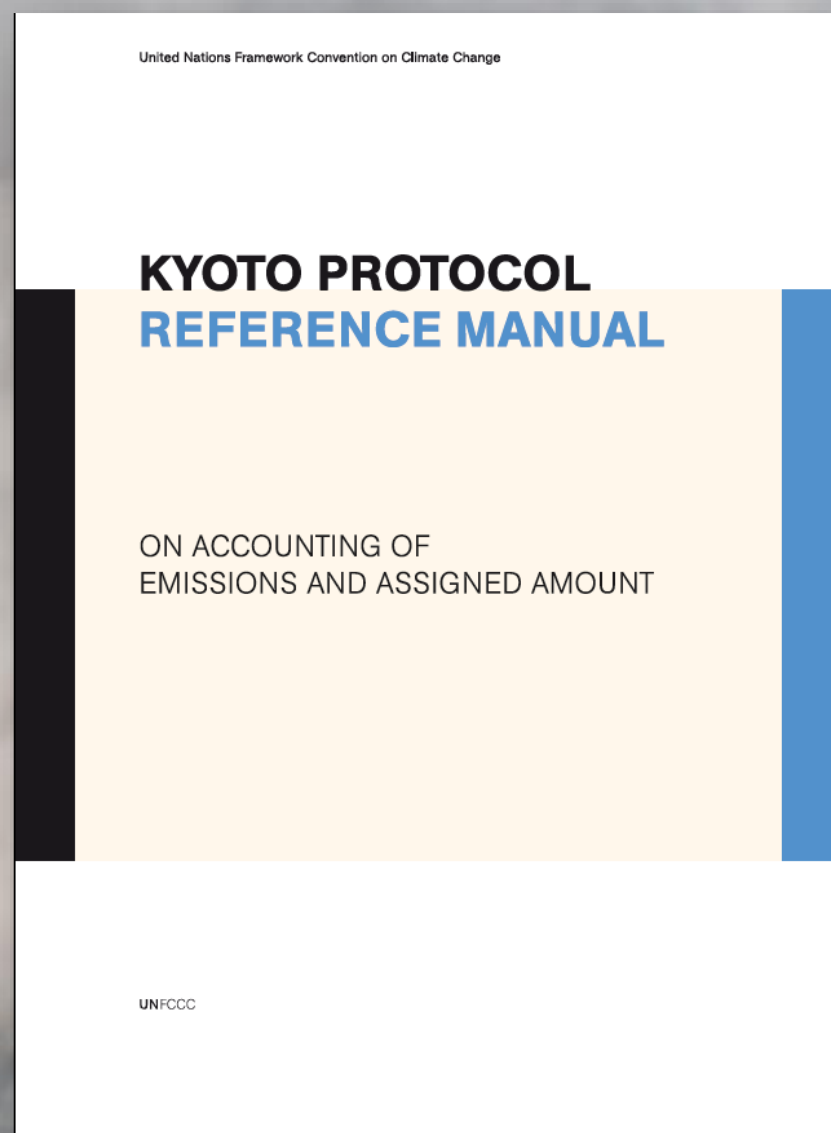
FSO Communication



Environment

"Photonic sensing technologies are a critical element in (...) environmental hazard monitoring"

- air quality/pollution monitoring
- water quality/pollution monitoring, including detection of chemical and micro-biological risks
- soil quality monitoring
- indoor monitoring (schools, hospitals, offices, private houses)



Greenhouse gases monitoring

Kyoto Protocol:

„The Parties included in Annex I shall, individually or jointly, ensure that their aggregate anthropogenic **carbon dioxide equivalent emissions of the greenhouse gases listed in Annex A** do not exceed their assigned amounts...”

	Greenhouse gas (Annex A of the Kyoto Protocol)	Chem. form.	Absorption lines in MIR [μm]
1	Carbon dioxide	CO_2	4.3
2	Methane	CH_4	2.3, 3.3, 7.5
3	Nitrous oxide	N_2O	2.9, 3.9, 4.5, 7.7
4	Chlorofluorocarbons (HFCs)	CCl_xF_y	13.7
5	Perfluorocarbons (PFCs)	CF_x	7.8
6	Sulfur hexafluoride	SF_6	10.6





Agriculture & food industry

Growing demand for safer, healthier and higher quality food with smaller carbon footprint

- monitoring of the quality of air, water and soil
 - monitoring of microorganisms in plants
 - reduction of the use of fertilizers/pesticides
 - prevention of soil degradation
 - monitoring of food quality at every stage of production and distribution
 - smart sensors for packages
 - reduction of food wasting
-
- market growth of precision farming equipment and services from 3.3 billion USD in 2016 to 5.9 billion USD in 2021

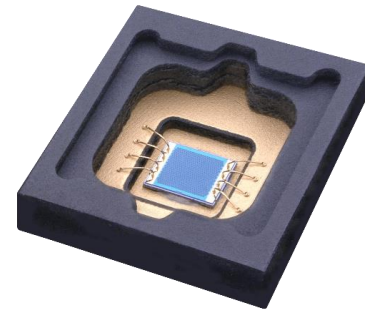
Constantly increasing number of sensors installed in modern cars, buses and trucks (including autonomous)

- monitoring of classical (combustion) and next generation (electric) engines
- in-cabin sensors
- advanced driver assistance systems (ADAS)
- thermographic cameras
- new generation LIDARs

- market growth additionally stimulated by new EU regulations
- market volume up to tens of million of units per year



Autonomous motor vehicles



Advanced driver-assistance systems ADAS



Driver monitoring systems



Gesture-based control systems

Cabin monitoring (CO2, pollution, alcohol)

HR



89

bpm

NIPB



108/68

mmHg

SpO2



99

%

RR



16

rpm

BT



36.8

°C

HR



PB



SpO2



RR



Photonics provides vital components to medical technologies for the instant diagnosis of major diseases...

- breath analysis (O₂, CO₂, NO, H₂S, NH₃ and other gases, inflammation and cancer markers)
- body fluids analysis
- sweat analysis

- mobile and wearable biosensors
- smart health systems
- contactless monitoring of infants/elderly people

- nearly 10% of European GDP in 2021
- photonics in healthcare is assumed to reach 50 billion EUR worldwide
- a rapidly expanding sector



Security and Safety

Growing demand for fast and contactless detection of potential threats to people and critical infrastructure

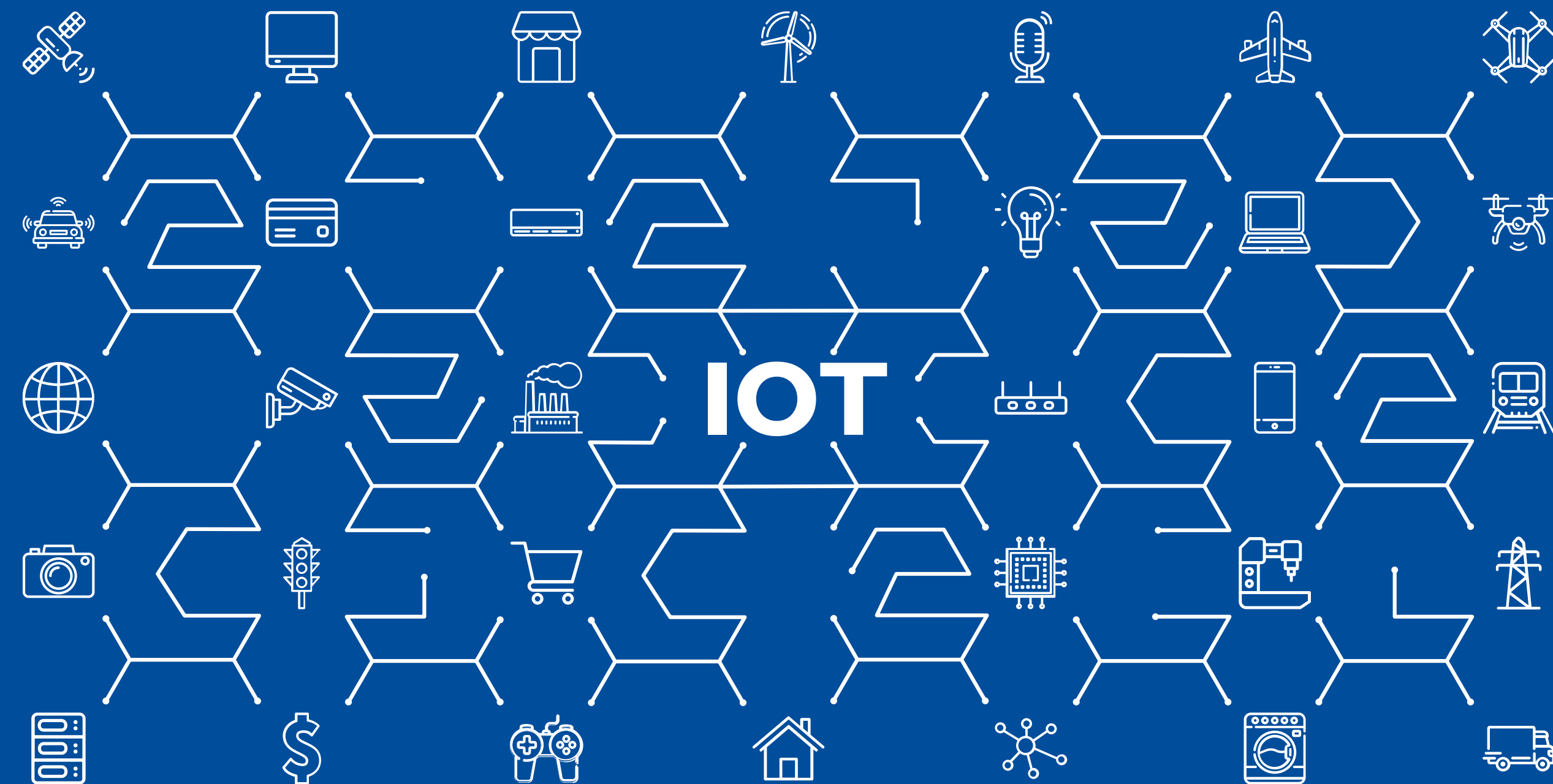
- detection of explosive materials
- detection of toxic and flammable gases
- detection of drugs and other prohibited chemicals
- chemical & microbiological contaminations
- testing and analysis of biological and chemical samples
- identification of silent virus carriers
- food security

Internet of Things

Billions of physical devices around the world connected to the internet

- indoor monitoring - public offices/private houses (air/water quality/contamination)
- home appliance sensors (gas/liquid analysis)
- furnace monitoring in private houses (CO₂, CO, SO₂)
- mobile/wearable sensors (medicine, sports)
- industrial processing monitoring
- large-area sensor networks in cities

A rapidly expanding sector, 6300 IoT start-ups in May 2020 (globally), prediction of up 75 billion devices installed by 2025*



MIR photonics in Poland

VIGO
PHOTONICS



Epiwafers



Infrared photon detectors



Infrared detection modules

VIGO Photonics S.A. is a **photonic semiconductors** company.

The **sole European provider of photon mid-infrared detectors**, competing with Asian and US companies.

Manufacturer of **high-quality epi-wafers for photonic and microelectronic** applications based on advanced compound materials (III-V & II-VI).

On the road to **Mid-IR Photonic Integrated Circuits foundry**



35

YEARS ON THE MARKET



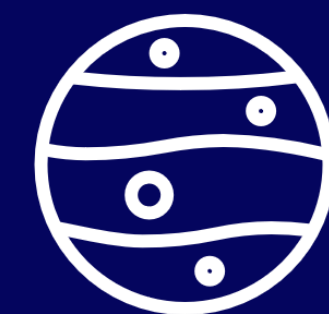
220

EMPLOYEES



6500 m²

PRODUCTION AREA



6

DETECTORS ON MARS

MIRPIC

PHOTONIC INTEGRATED CIRCUITS TECHNOLOGIES FOR MID INFRARED

VIGO
PHOTONICS



started in April 2021

AIM

Development of the technology of manufacturing application-specific photonic integrated circuits (ASPIC) for MIR spectral range, providing the foundation for the first Polish PICs foundry

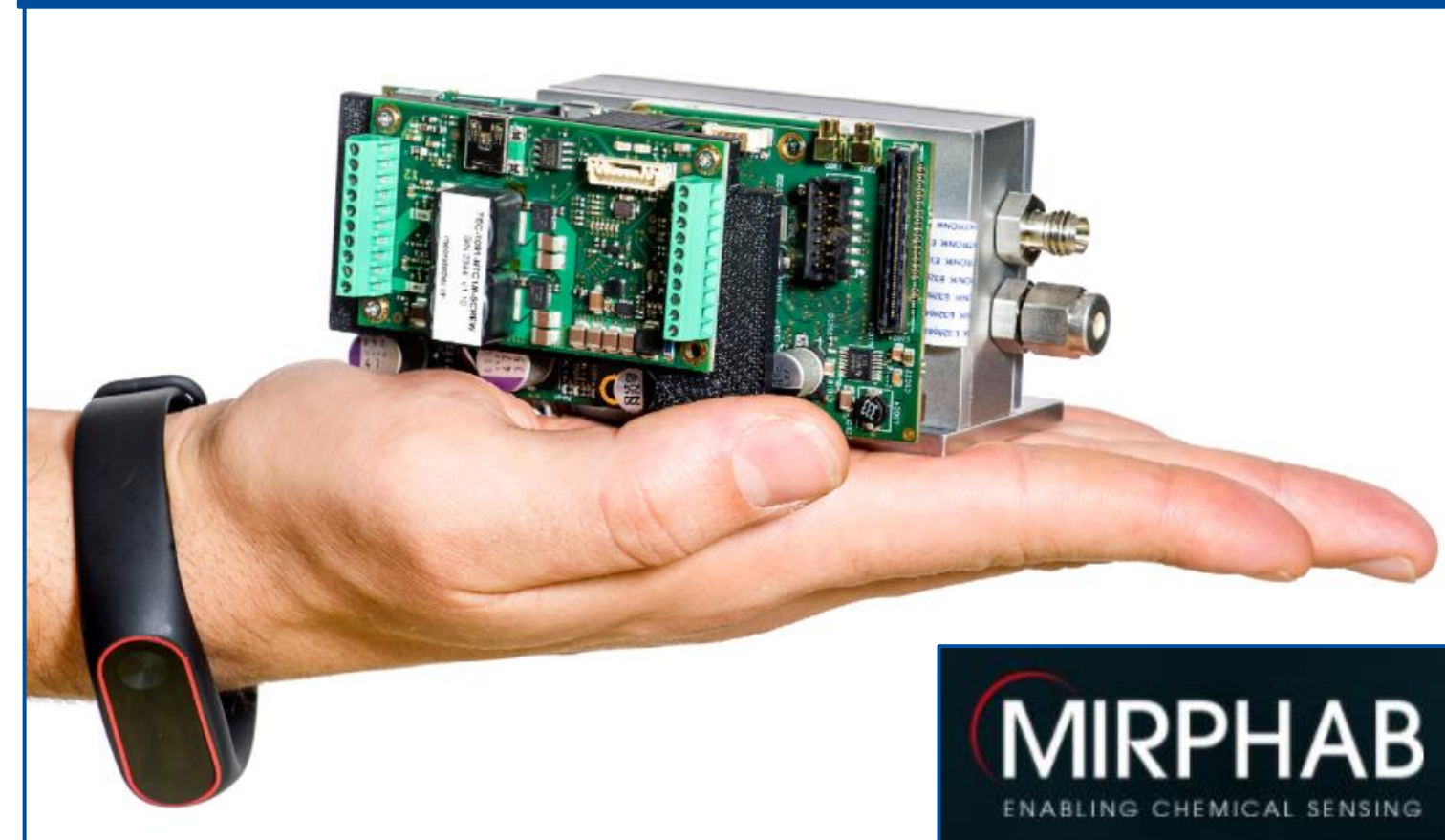
- **product innovation** – unique ASPICs for MIR spectra range (3.0-5.5 μm)
- **know-how** – design, development, and integration of fundamental building blocks, mastering key technologies
- **solid foundation** for the first Polish PICs foundry

yesterday



THE KEY ELEMENT of VIGO Photonics STRATEGY!

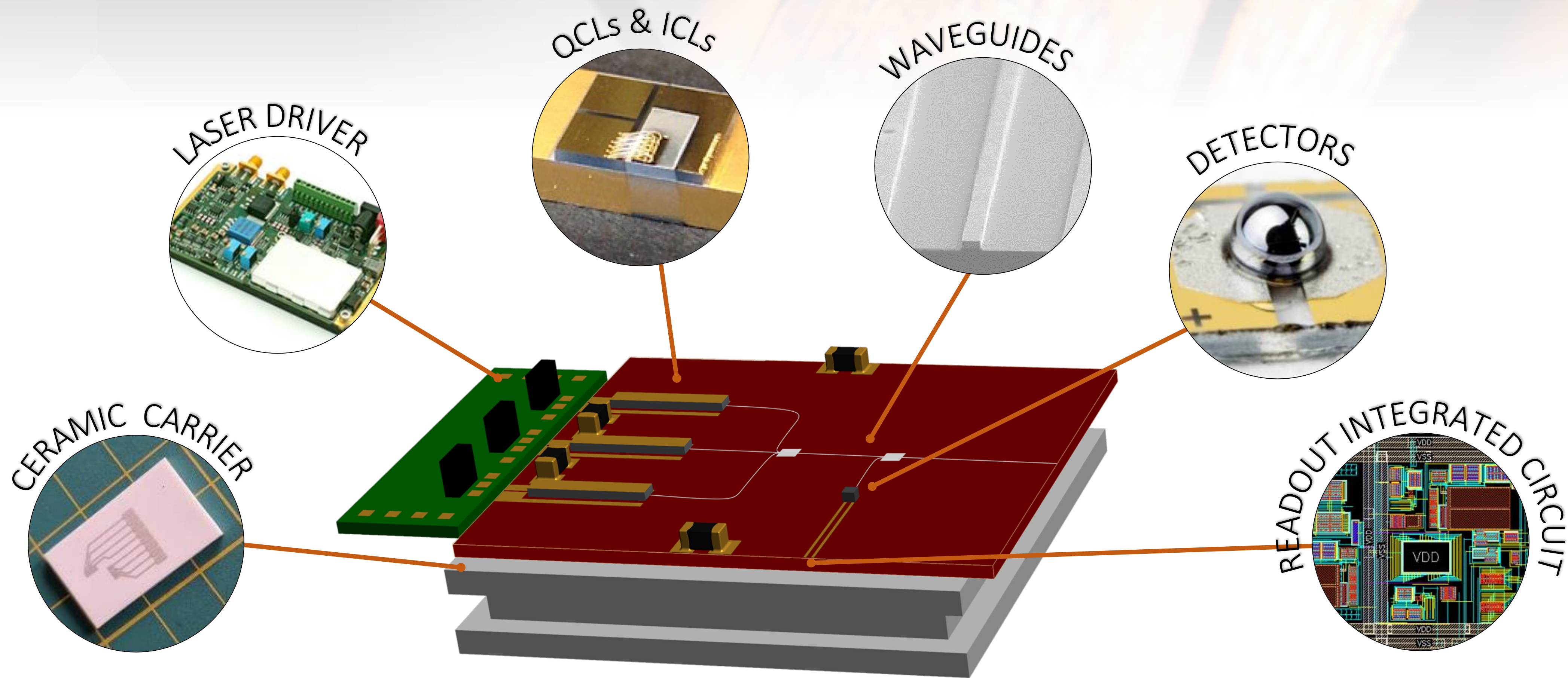
today

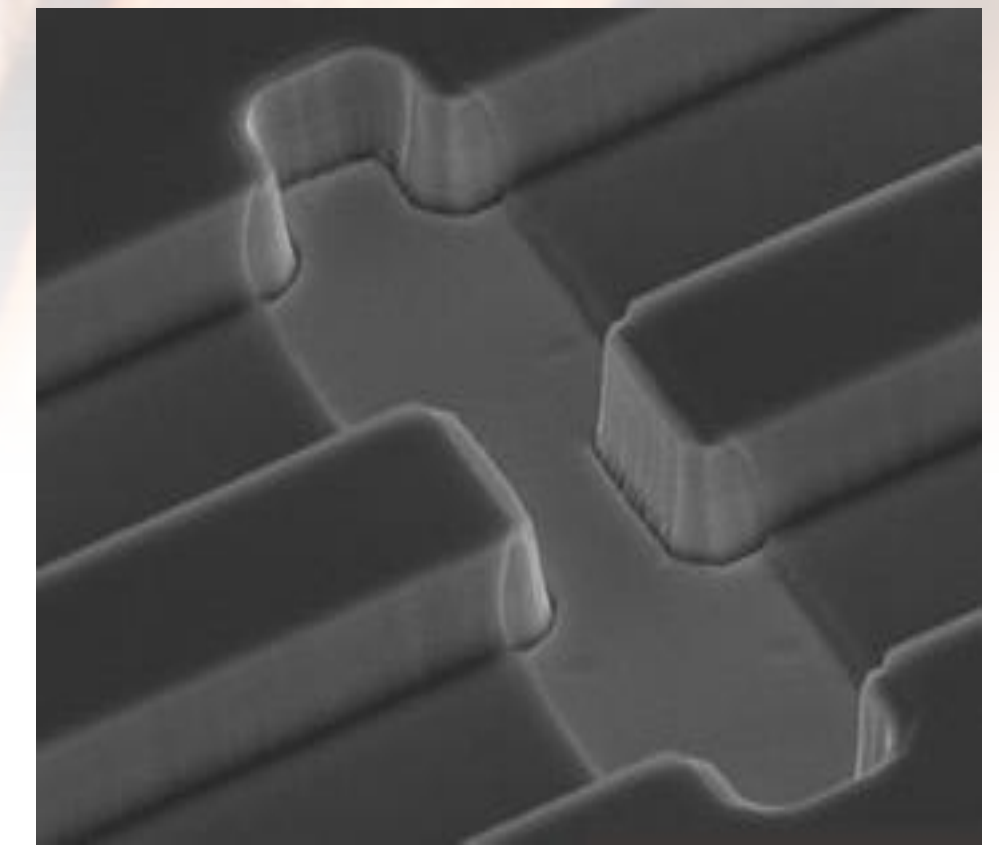
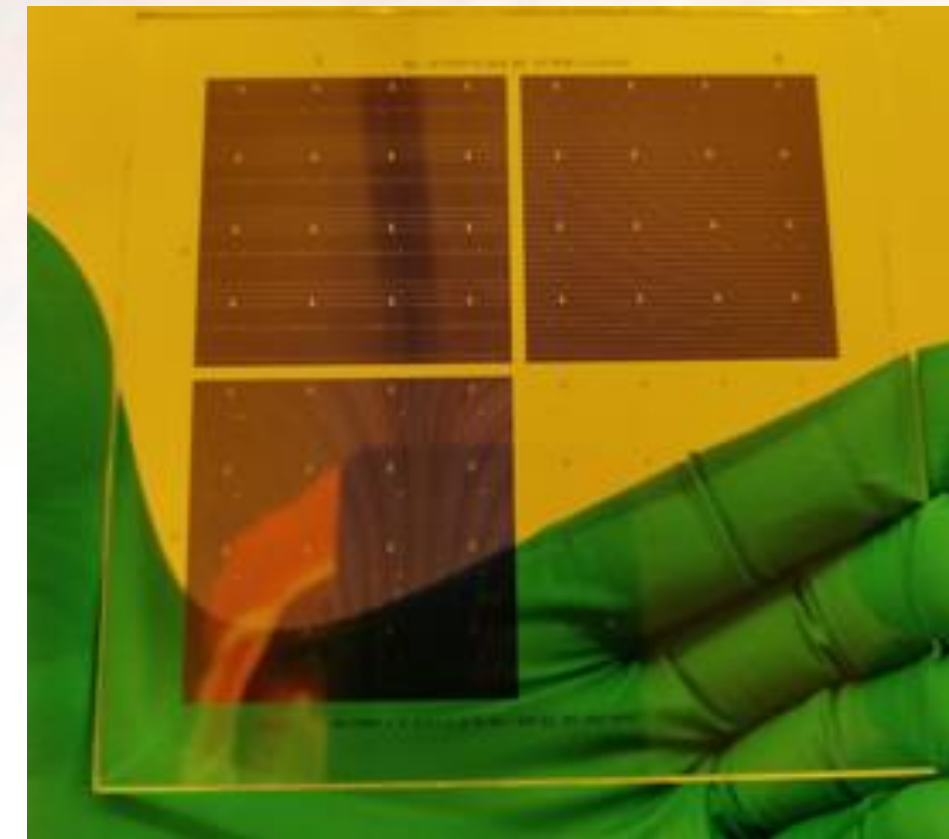
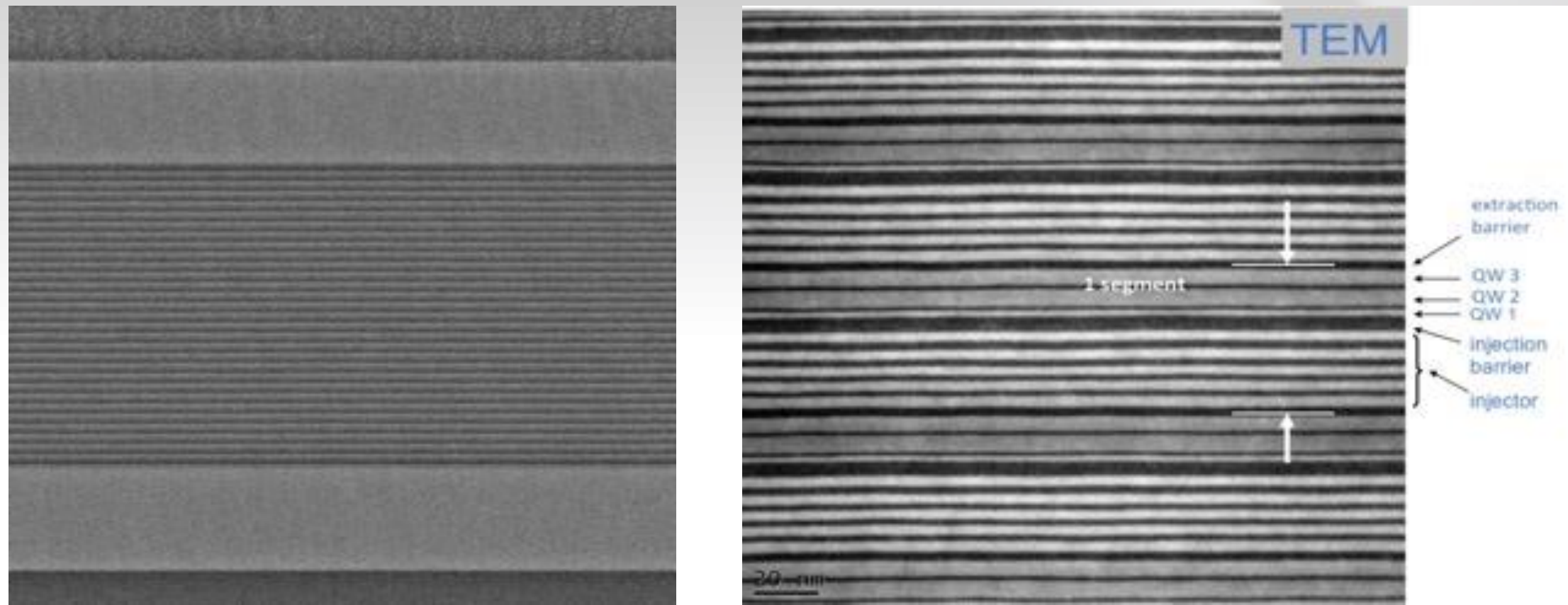


tomorrow

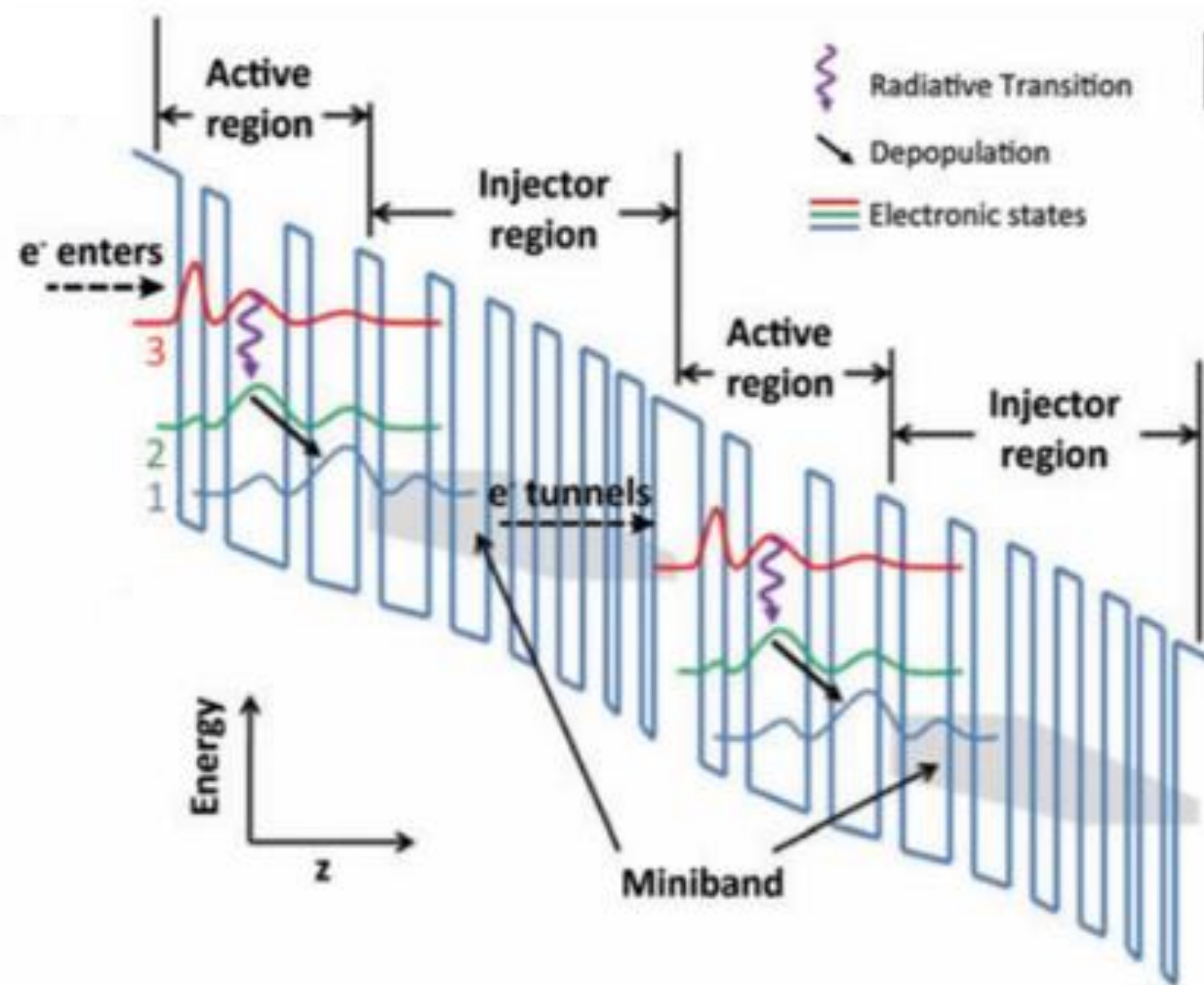


MIRPIC technology platform

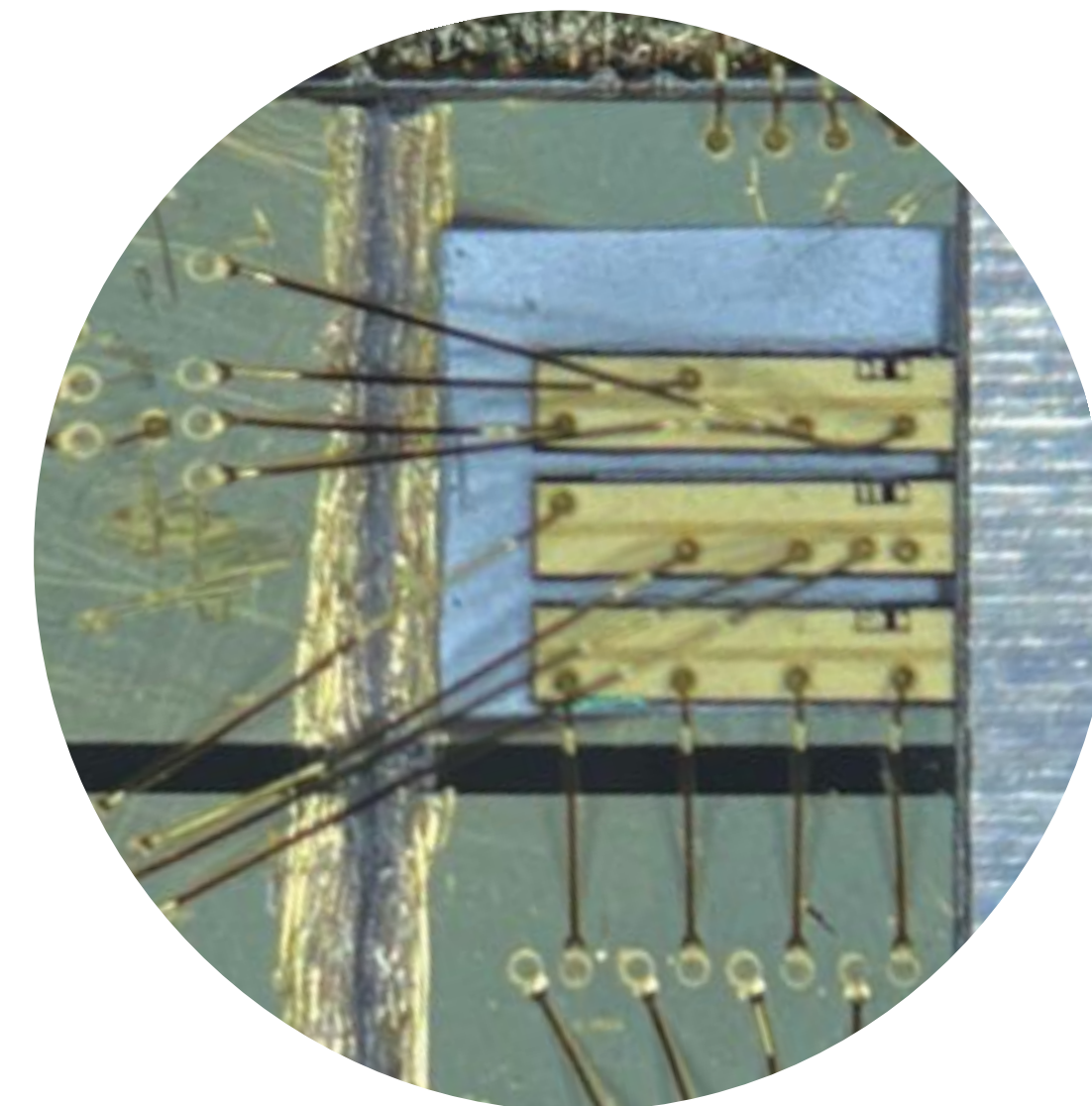




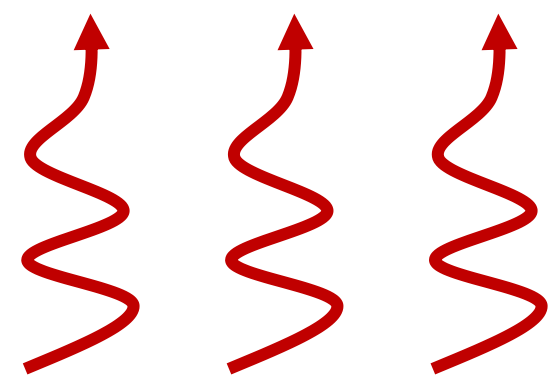
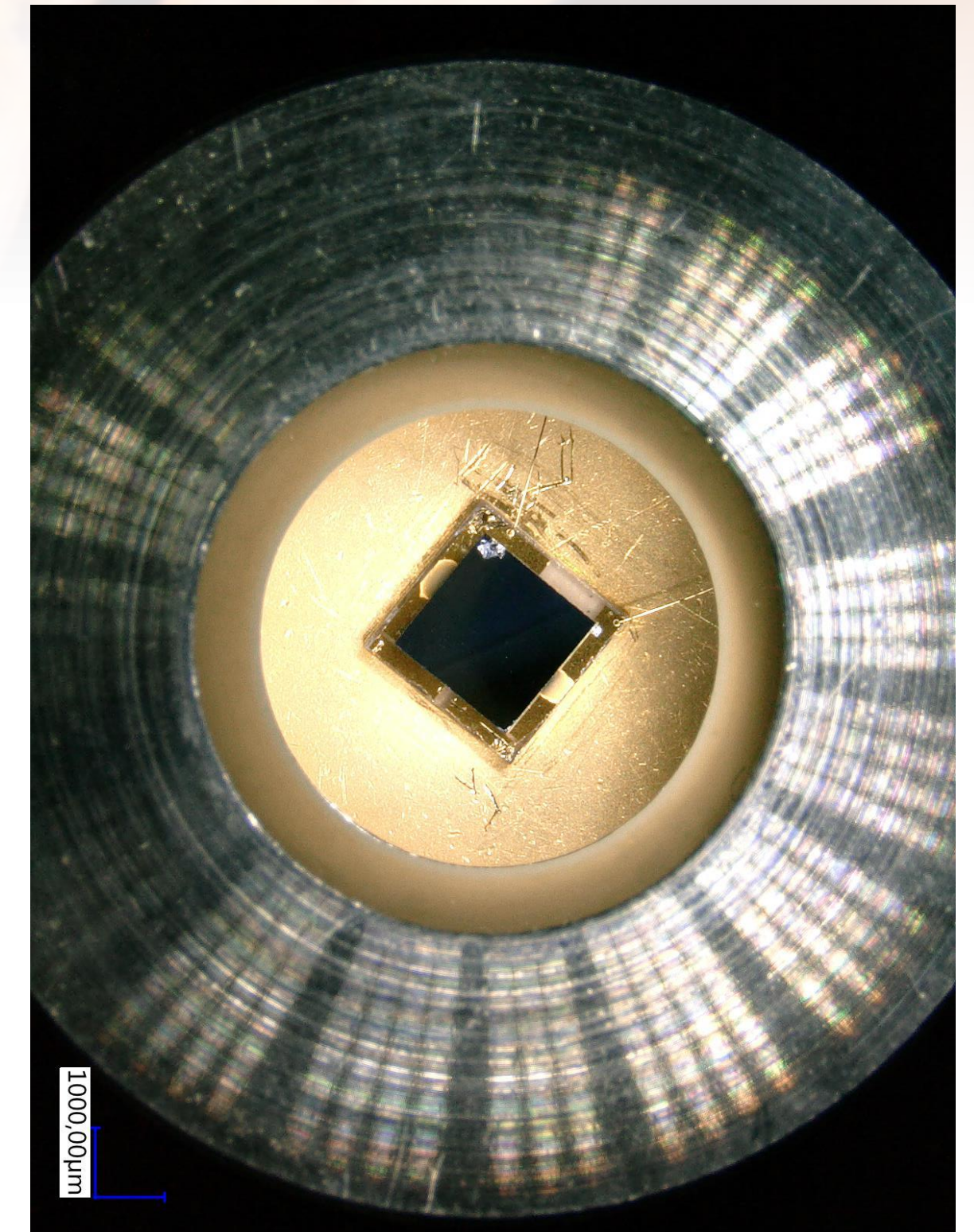
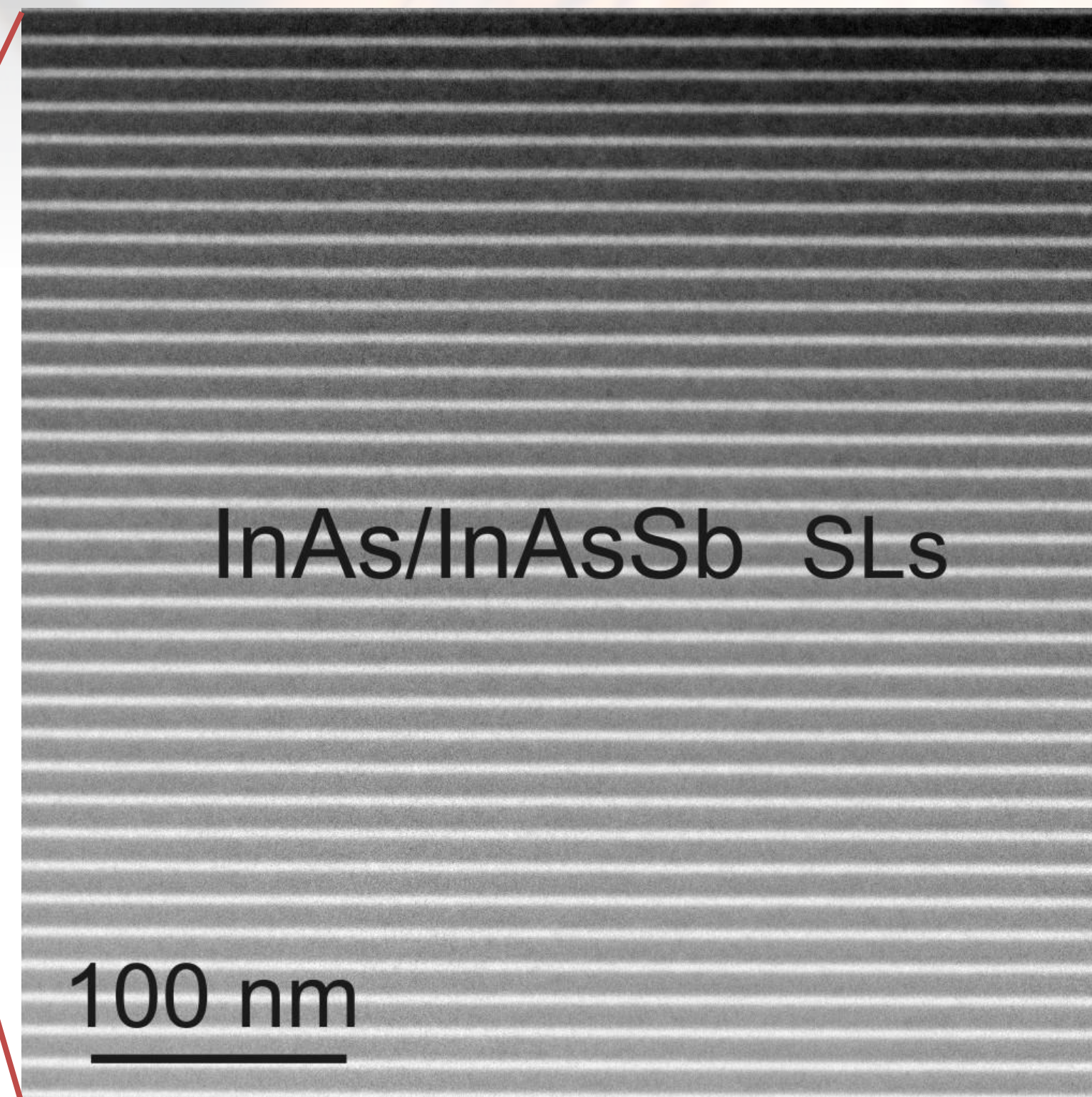
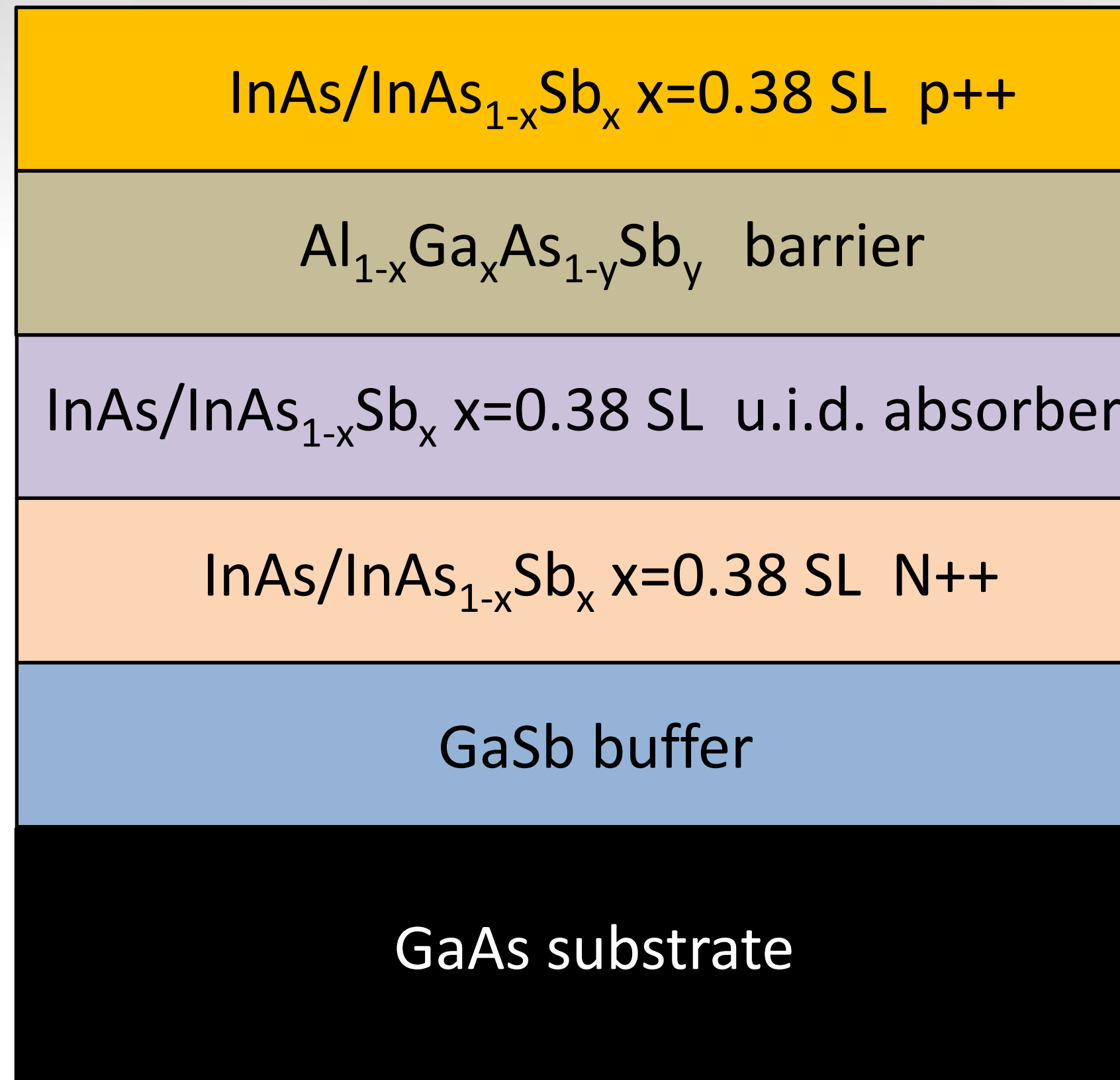
growth technology



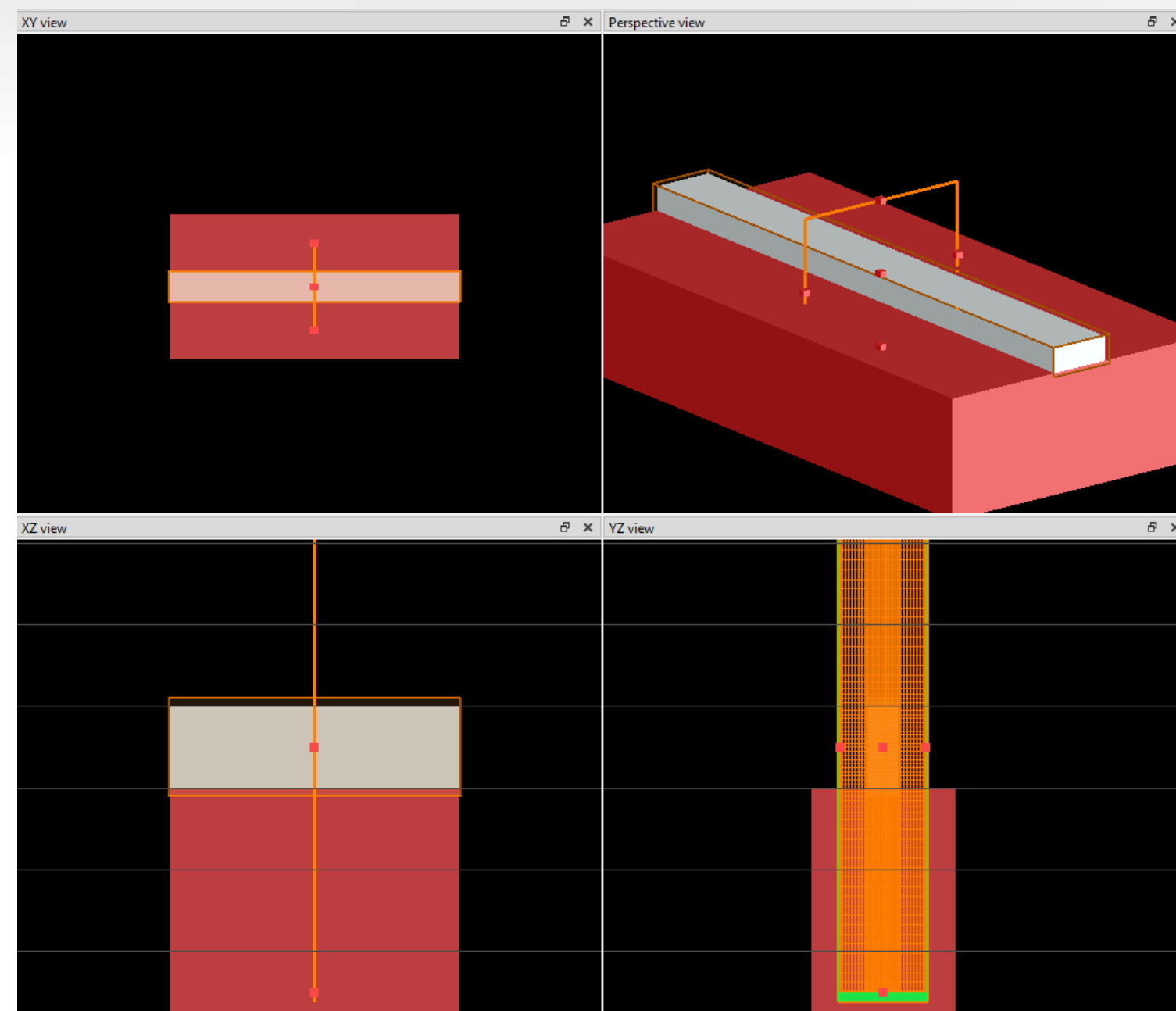
processing technology



Detectors – antimonide super-lattice

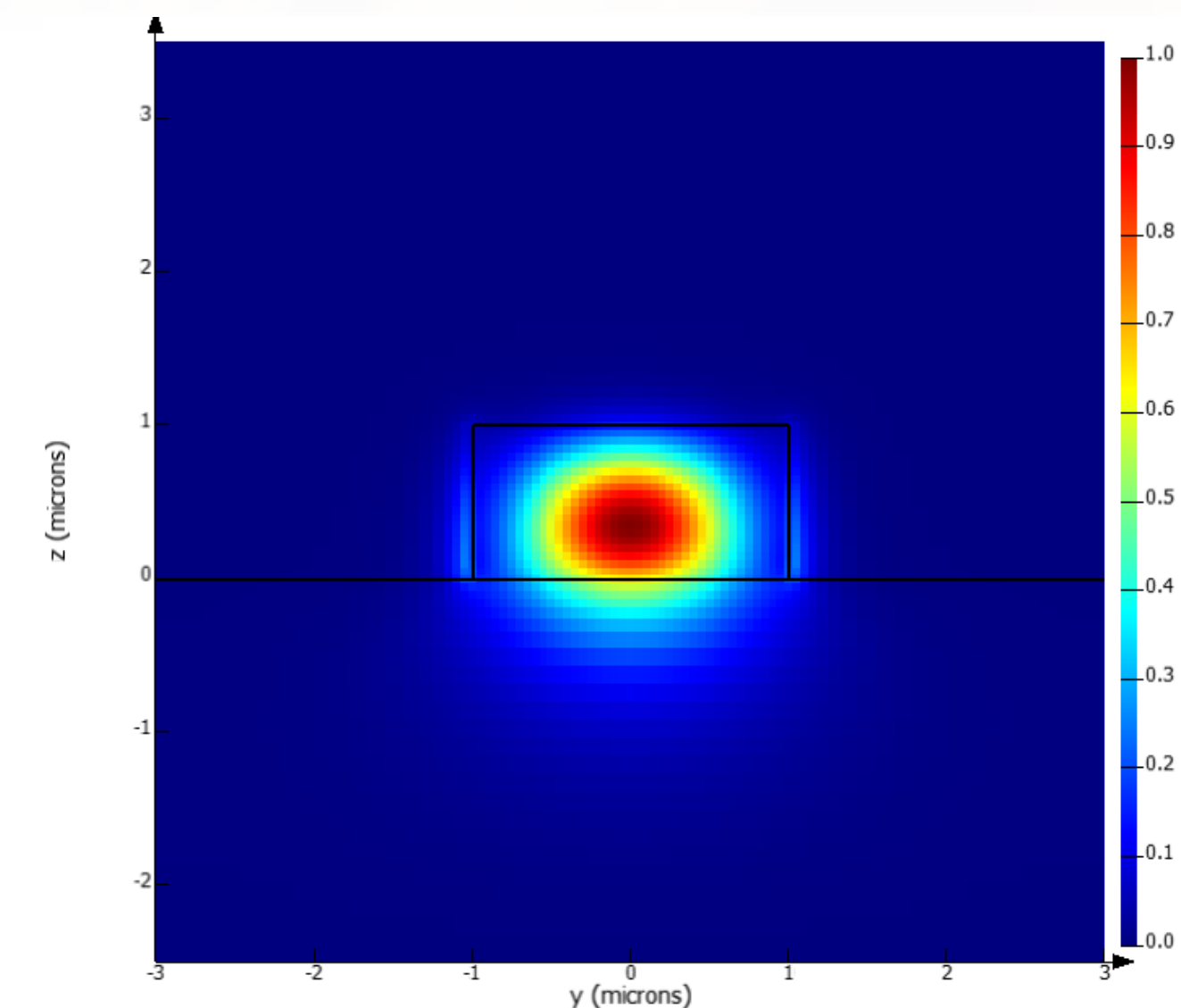


Ge-on-Si technology – modeling of passive waveguides



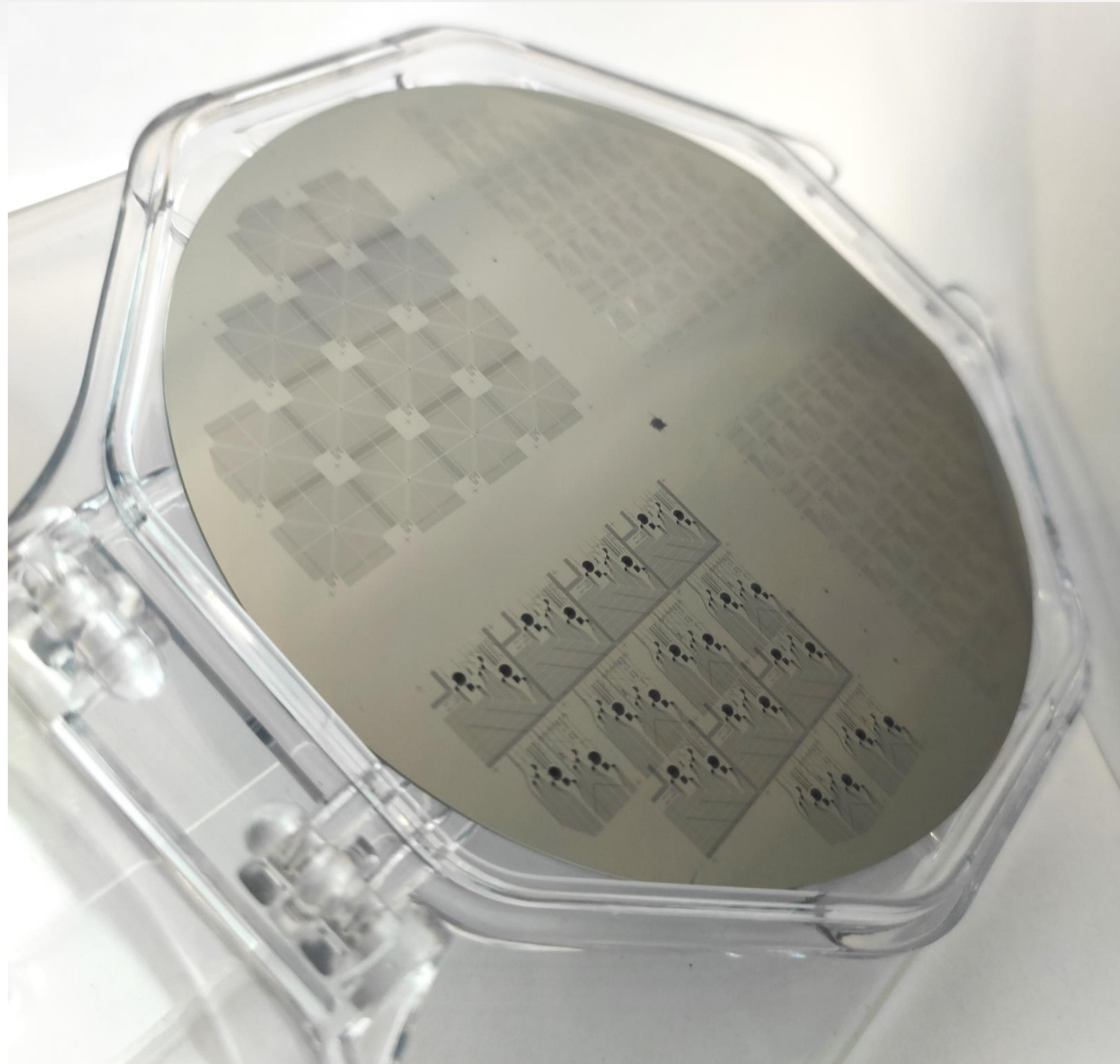
$\lambda = 5.5 \mu\text{m}$
 $W = 2 \mu\text{m}$
 $d = 1 \mu\text{m}$

TE fundamental mode

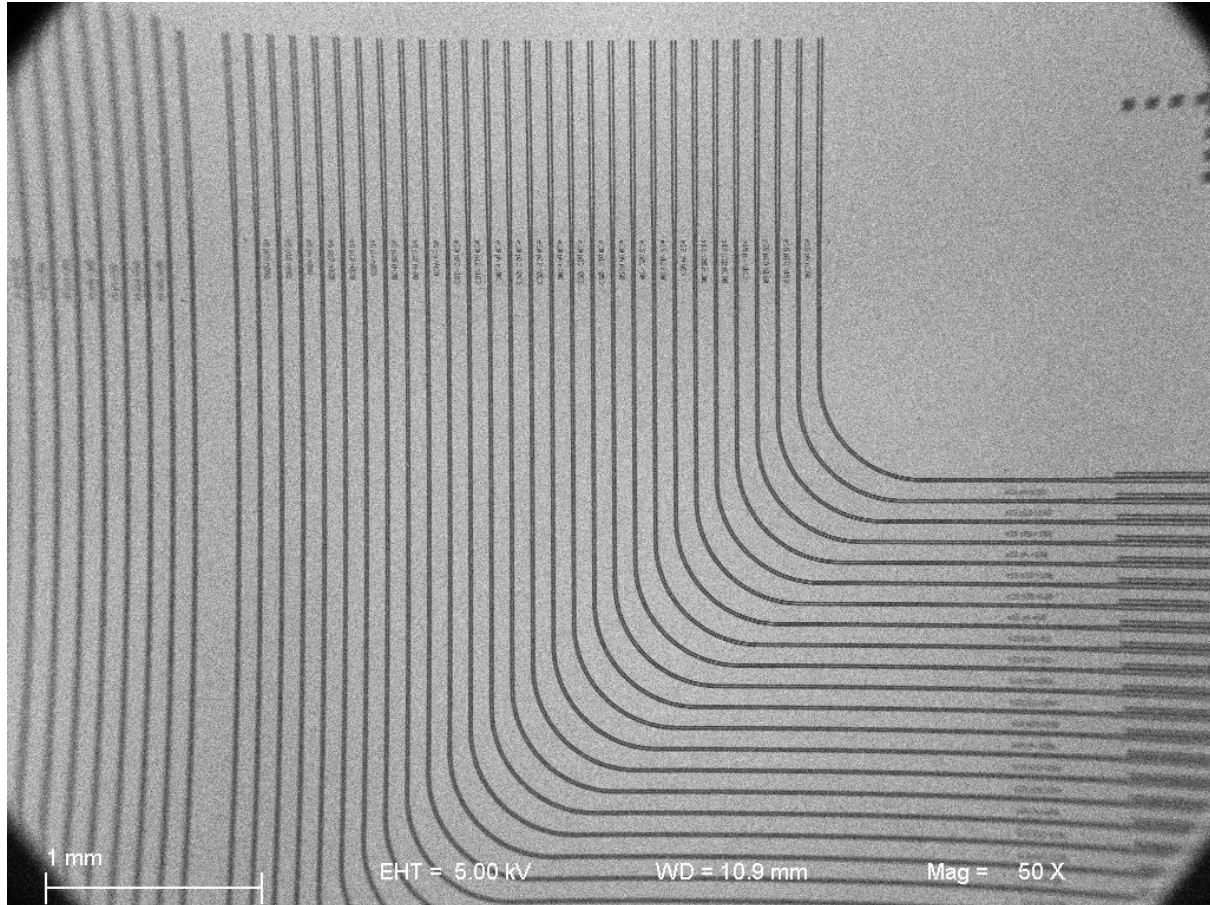
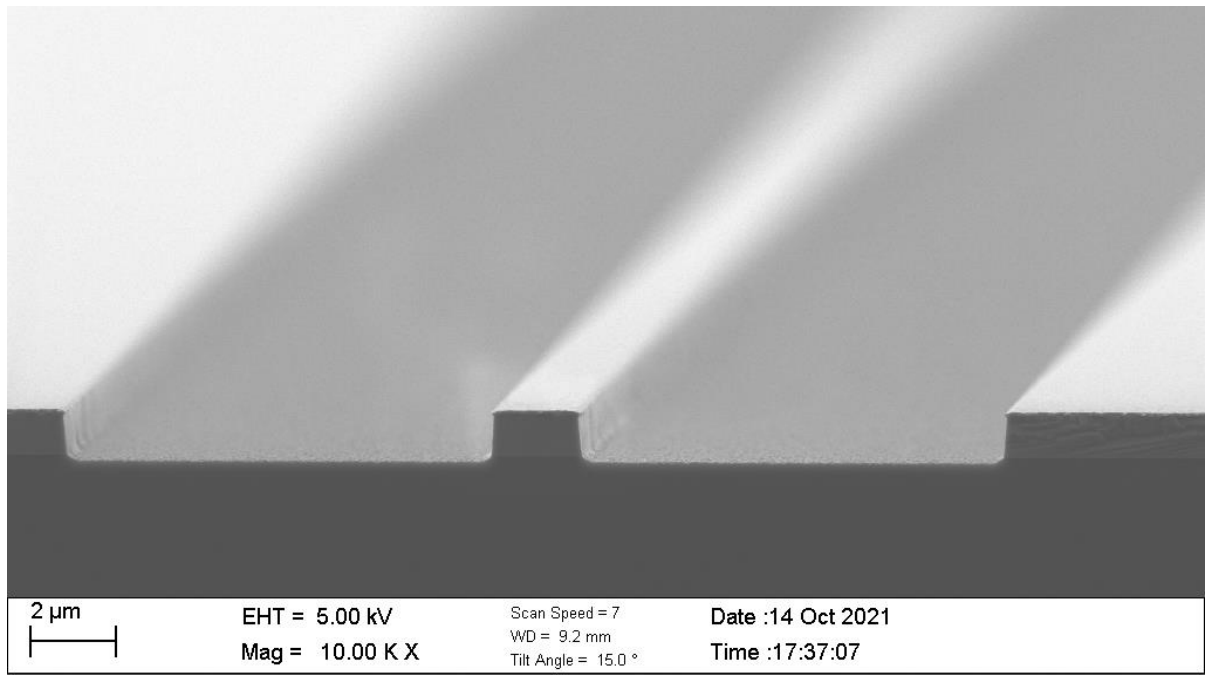


$d = 1 \mu\text{m}$	TM0 or TE0	TM0 + TE0	Multimode
$W [\mu\text{m}]$ for $\lambda = 3.0 \mu\text{m}$	0.7 – 0.9	0.9 – 1.5	> 1.50
$W [\mu\text{m}]$ for $\lambda = 5.5 \mu\text{m}$	1.8 – 2.2	2.2 – 3.8	> 3.80

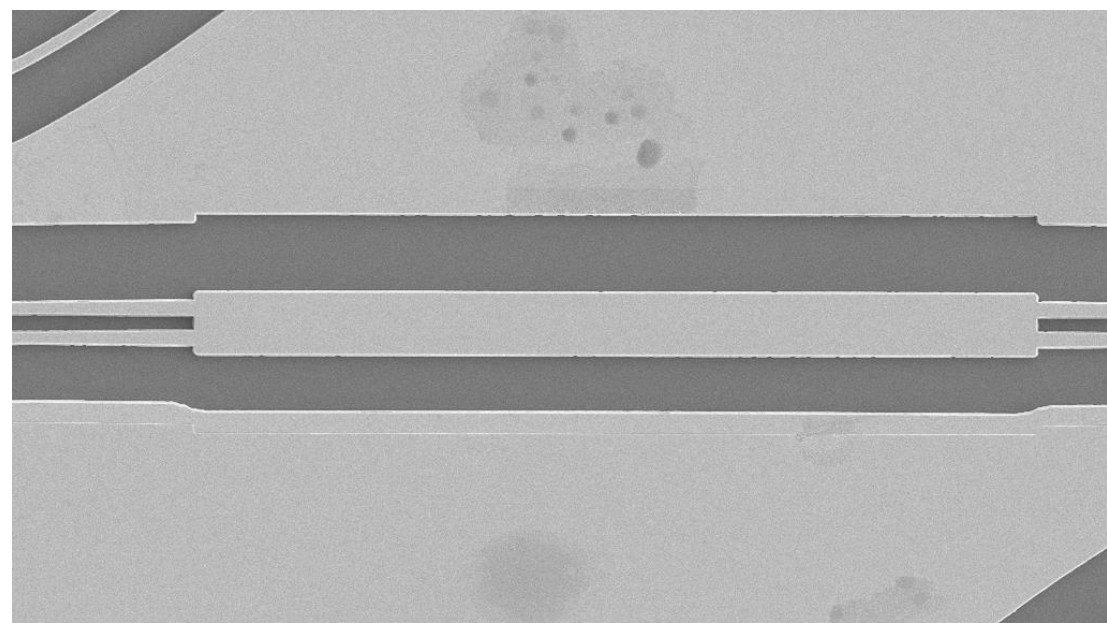
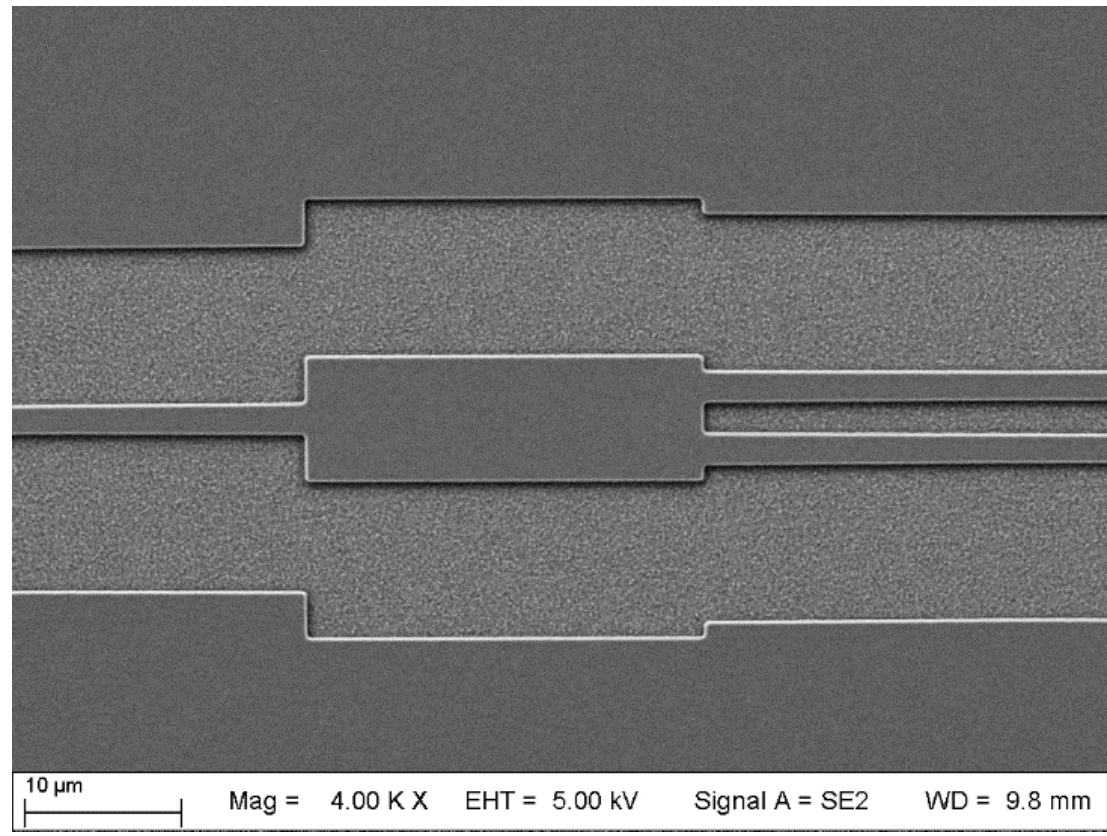
Ge-on-Si technology – waveguides and waveguiding components



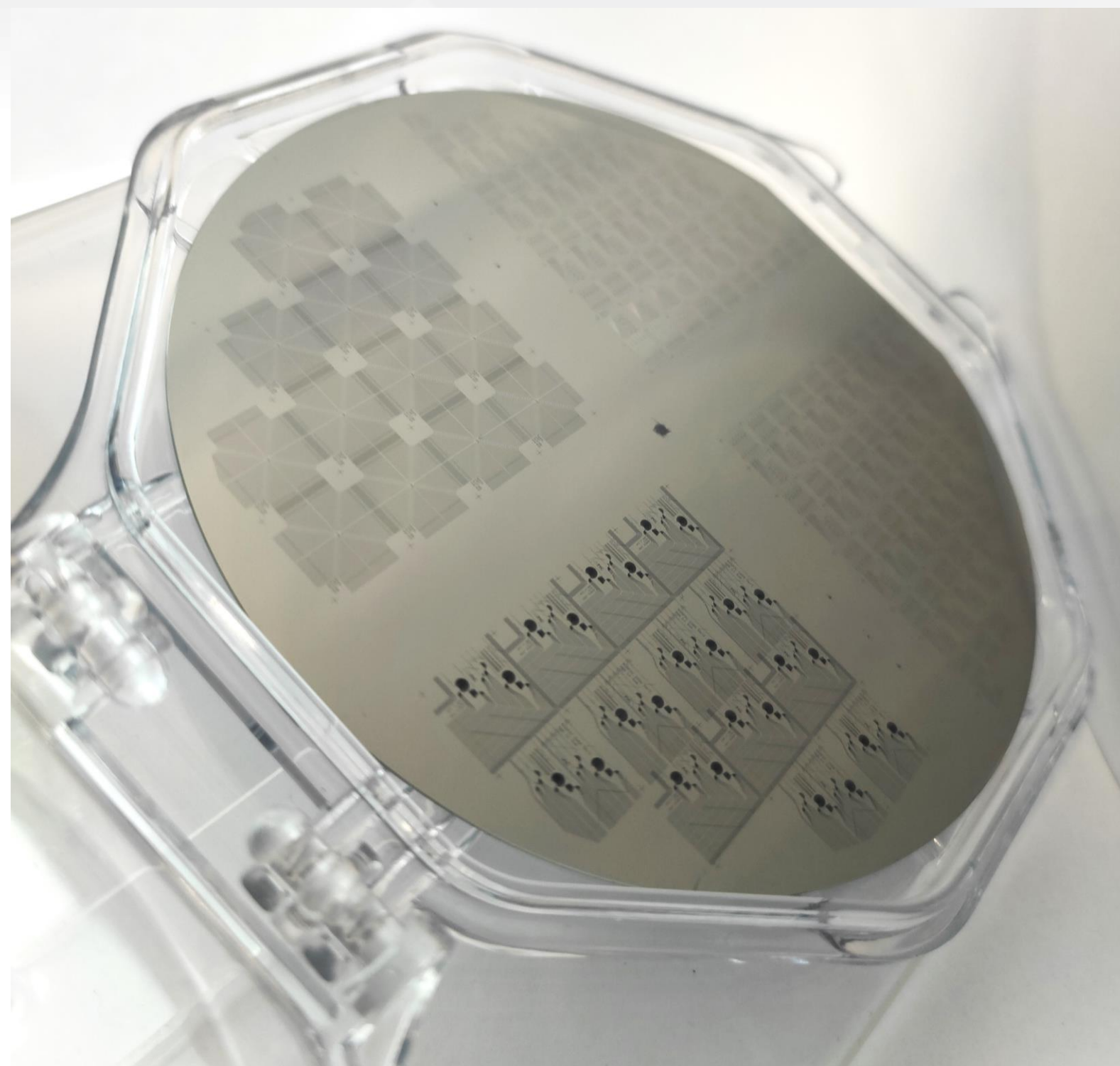
Waveguides, tapers and bends



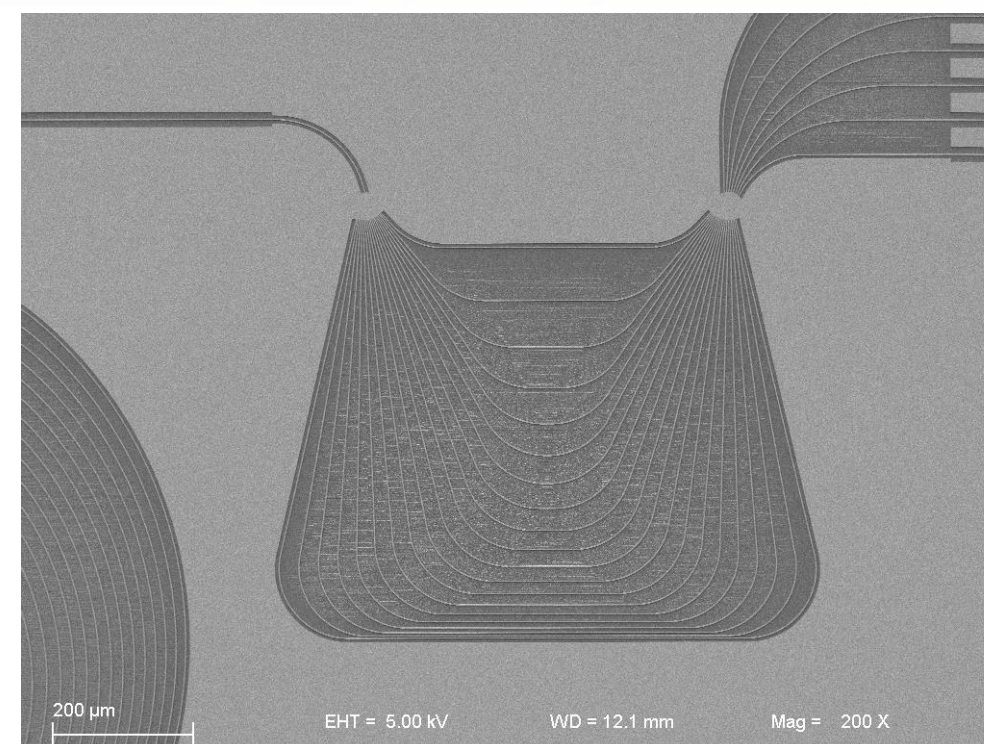
Multi-mode interference (MMI) couplers



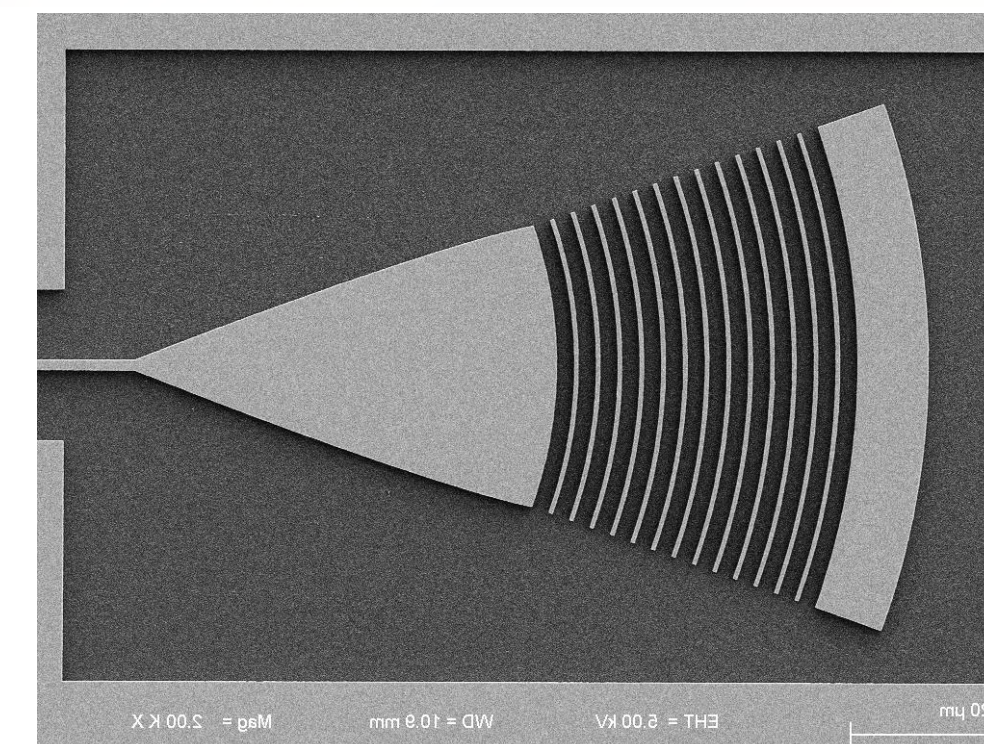
Ge-on-Si technology – waveguides and waveguiding components



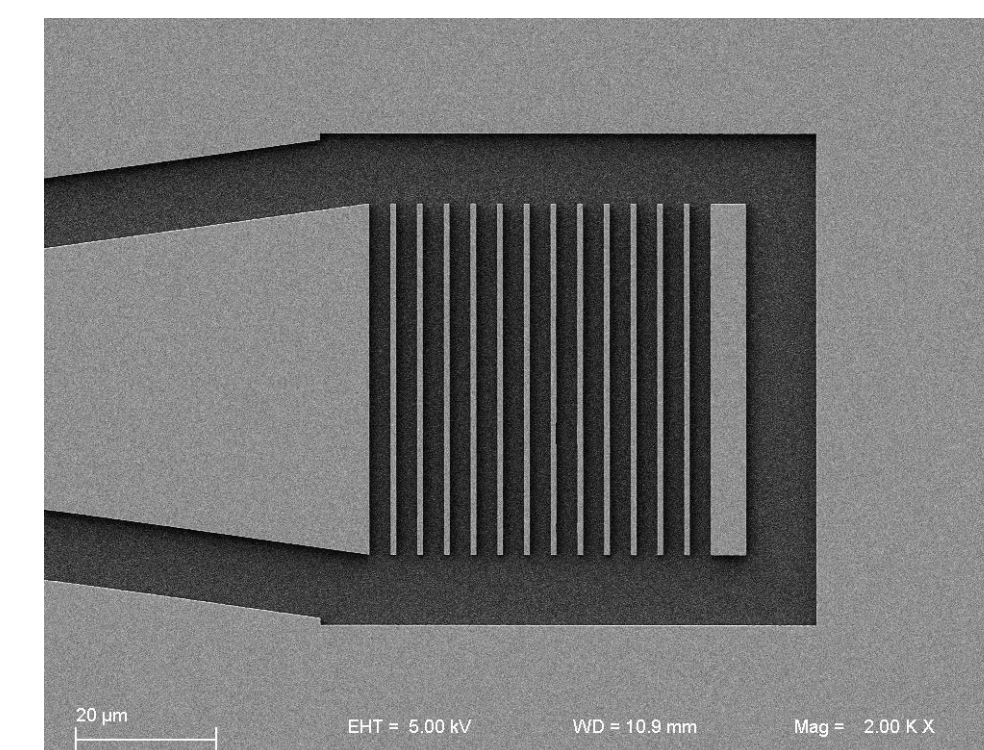
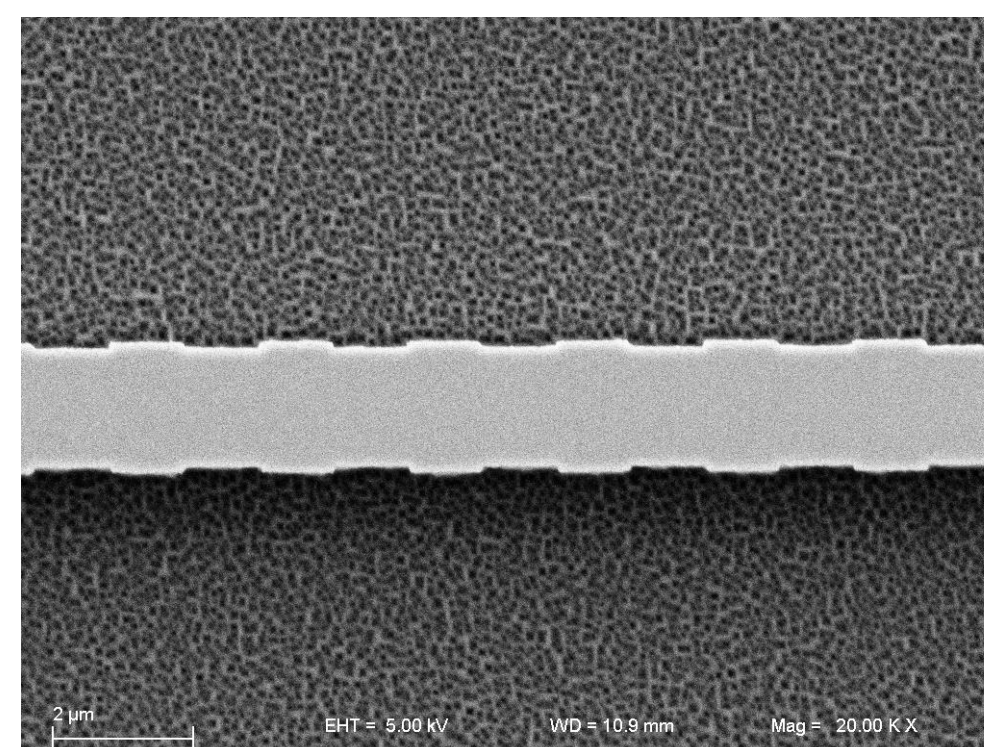
Arrayed waveguide gratings (AWG)



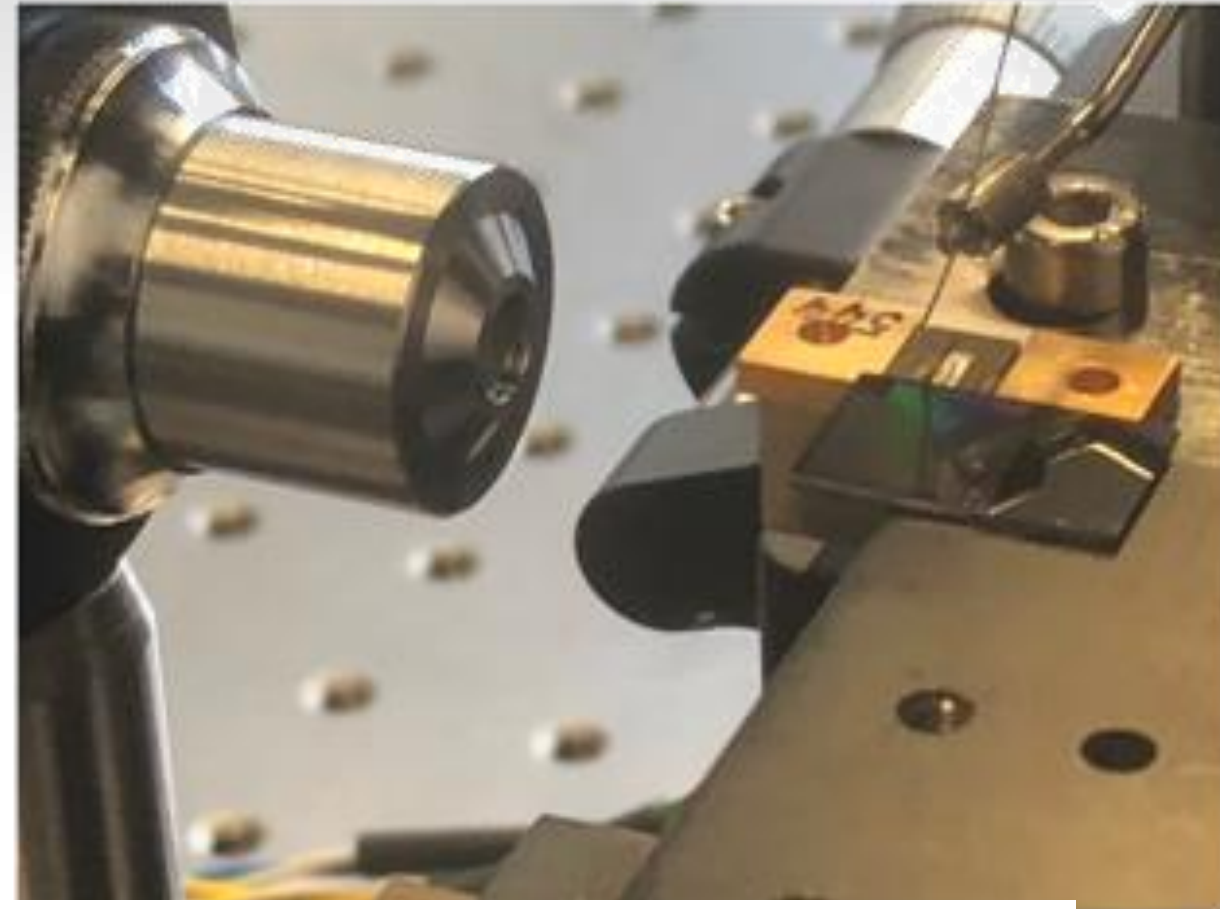
Grating couplers



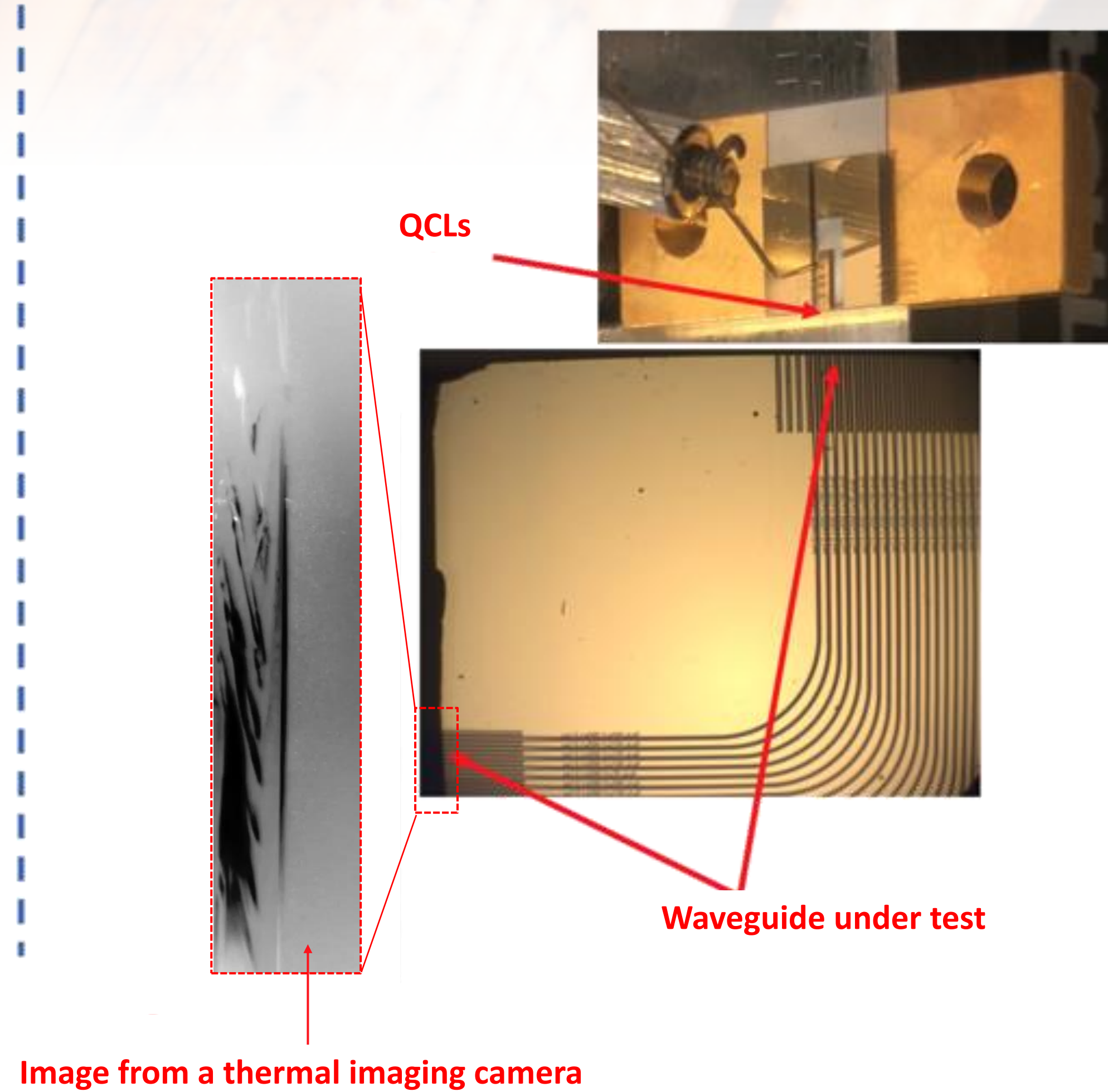
Distributed Bragg reflectors (DBR)



Coupling QCL lasers with germanium waveguides - first trials



Measurement setup

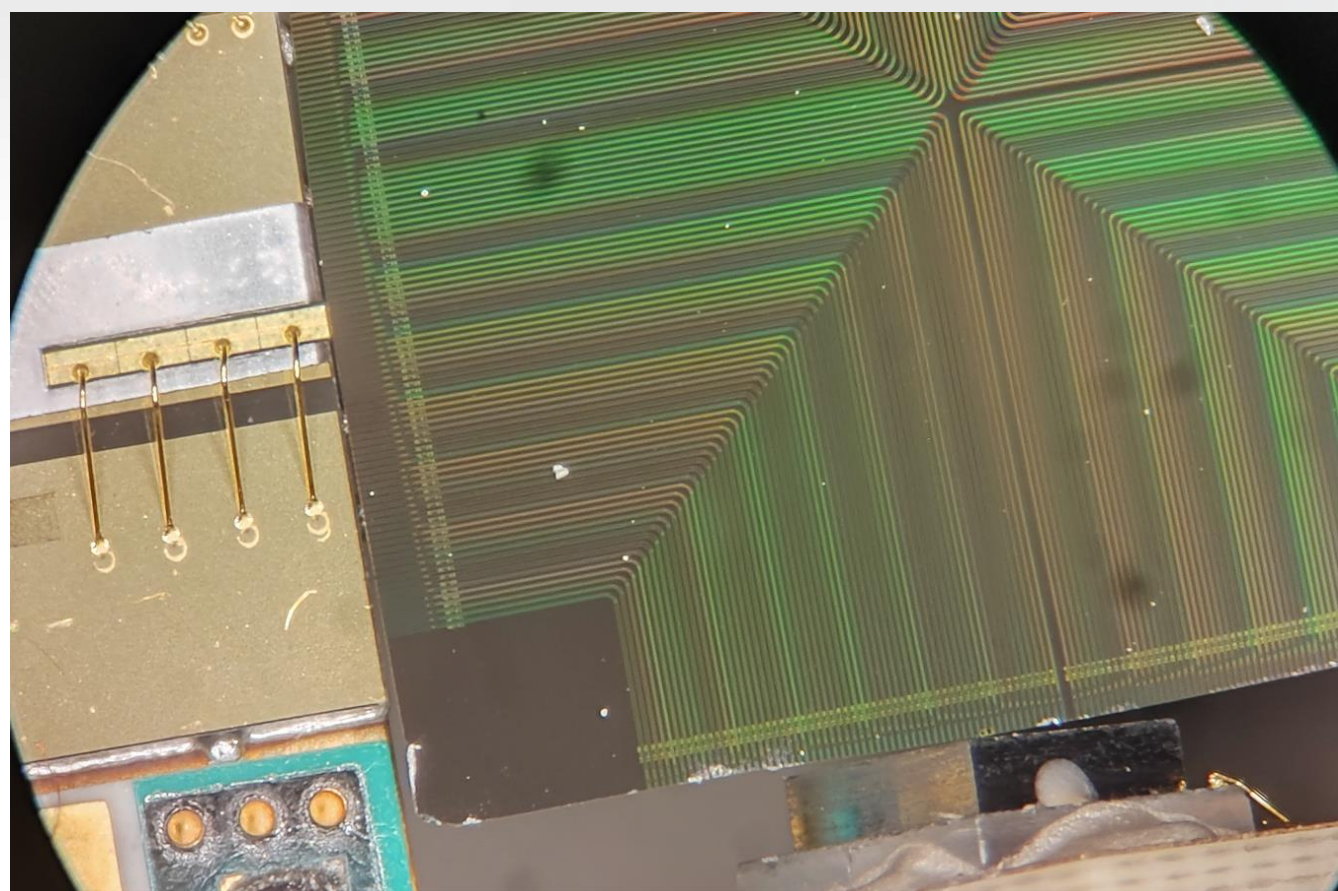


Confirmed signal transmission

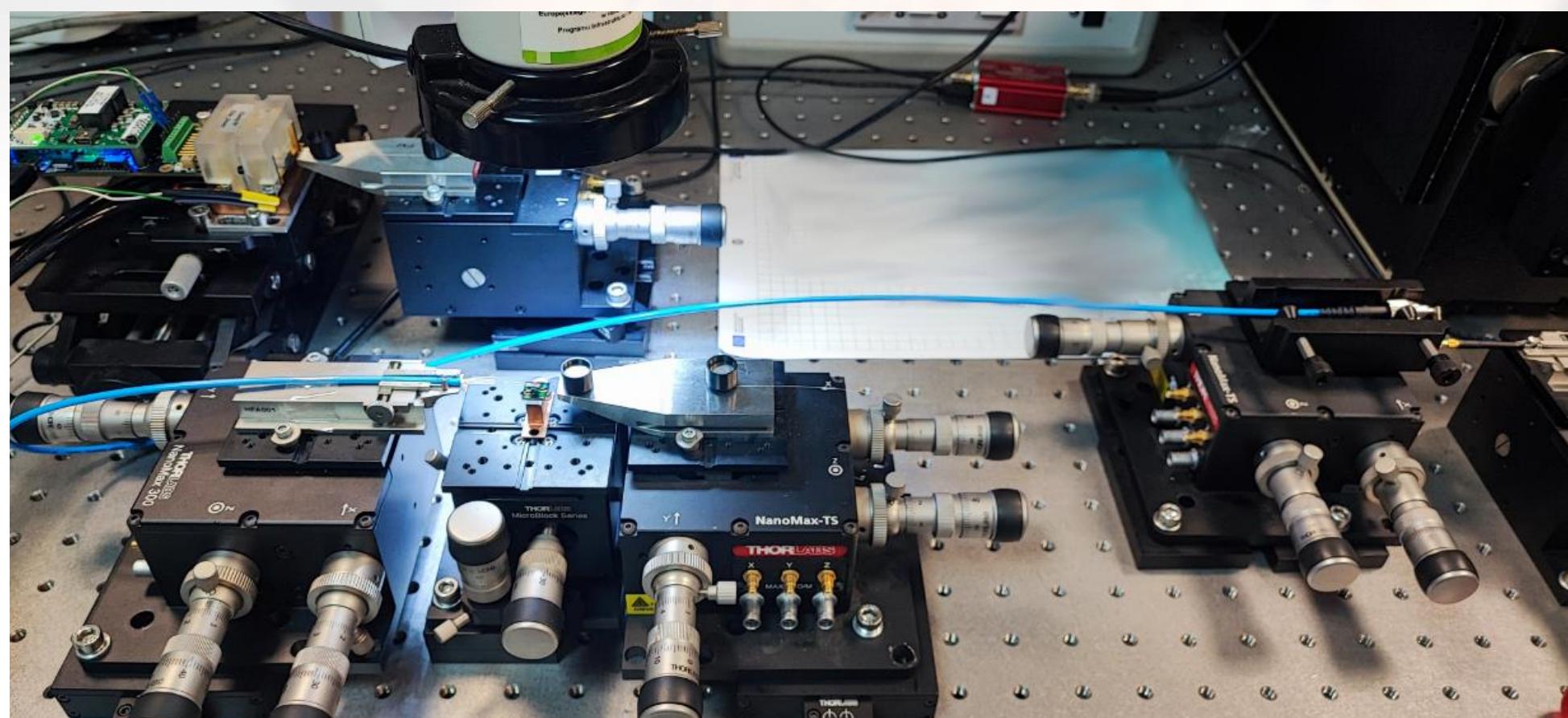
$$\lambda_1 = 4.7 \mu\text{m}$$

$$\lambda_2 = 5.2 \mu\text{m}$$

Ge-on-Si technology – characterization of waveguides and passive components



Characterization setup I
Light source: QCLs (3.7 - 5.2 μm)
Detector: InAs/InAsSb superlattice
Direct butt-coupling



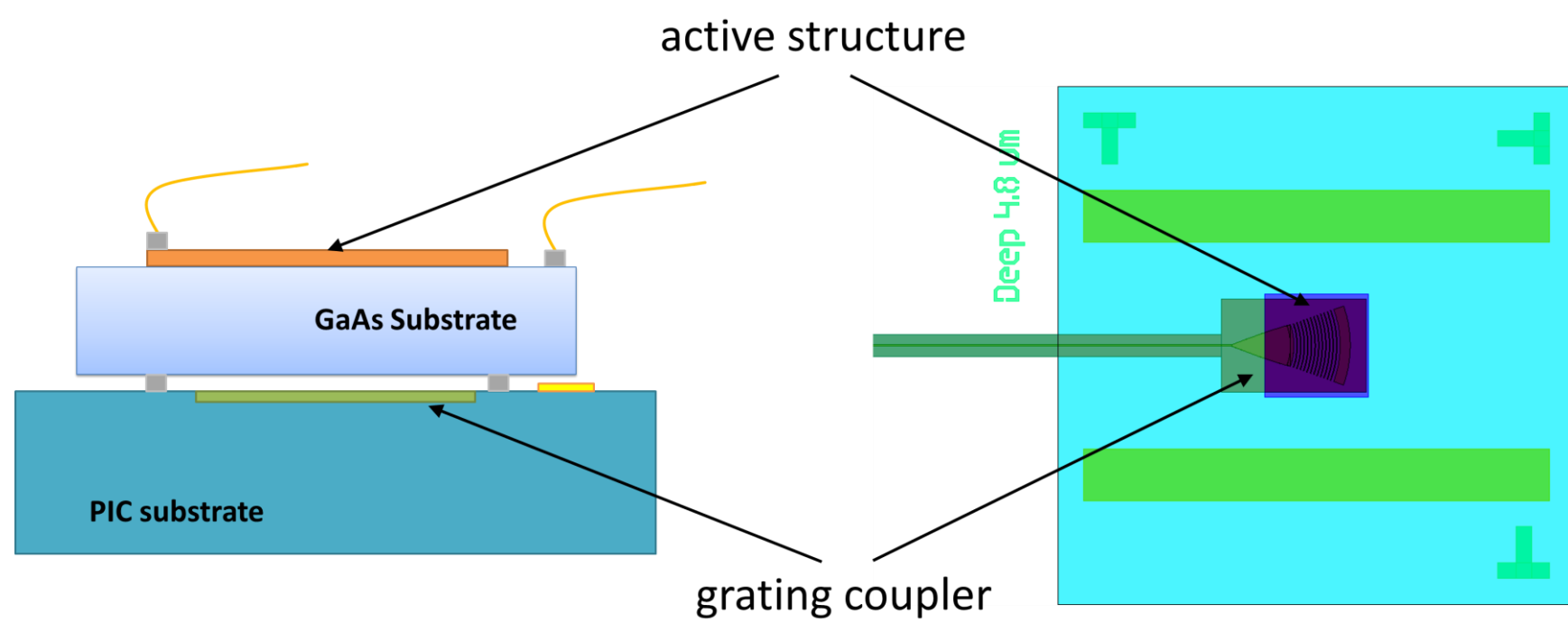
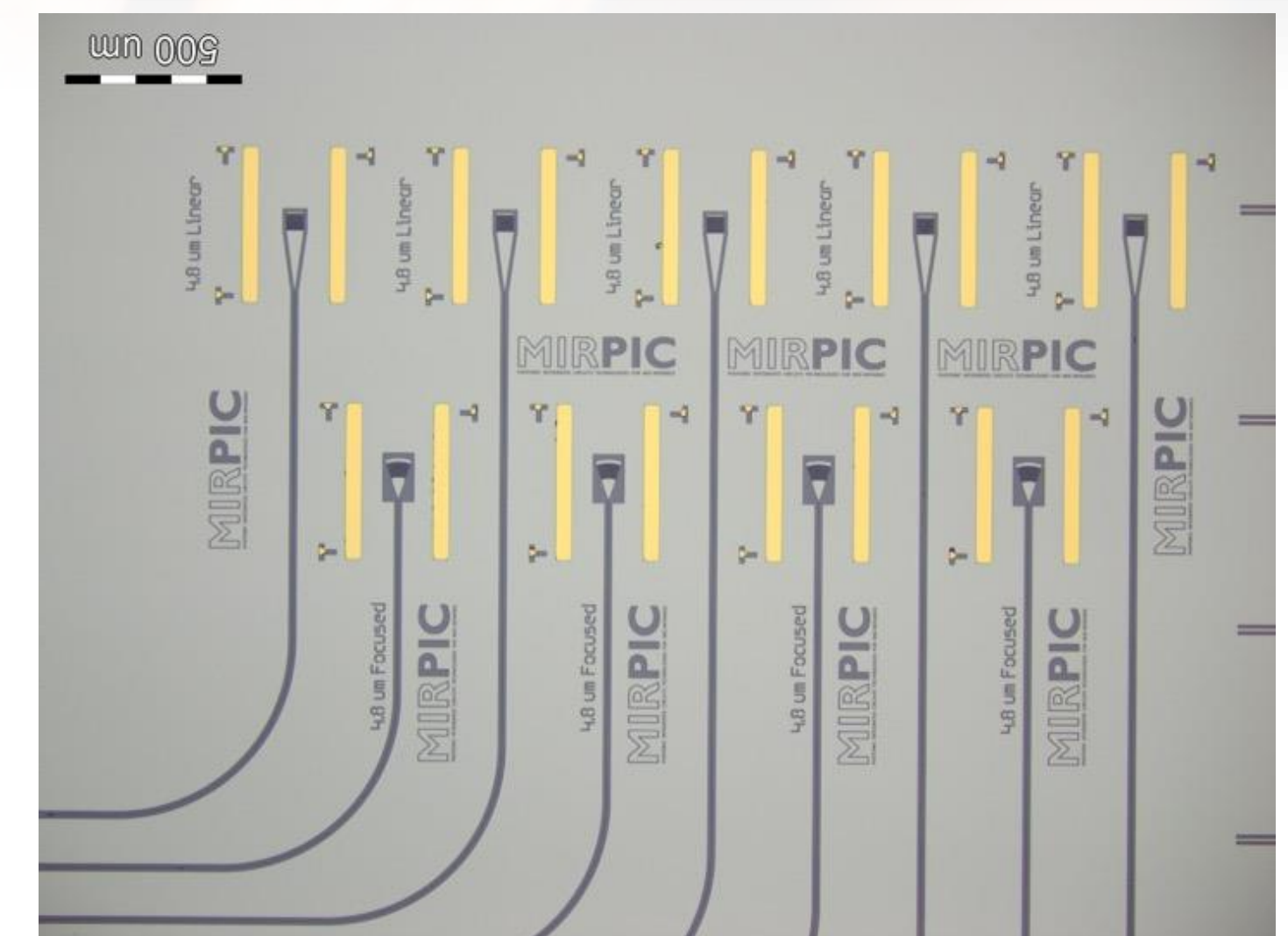
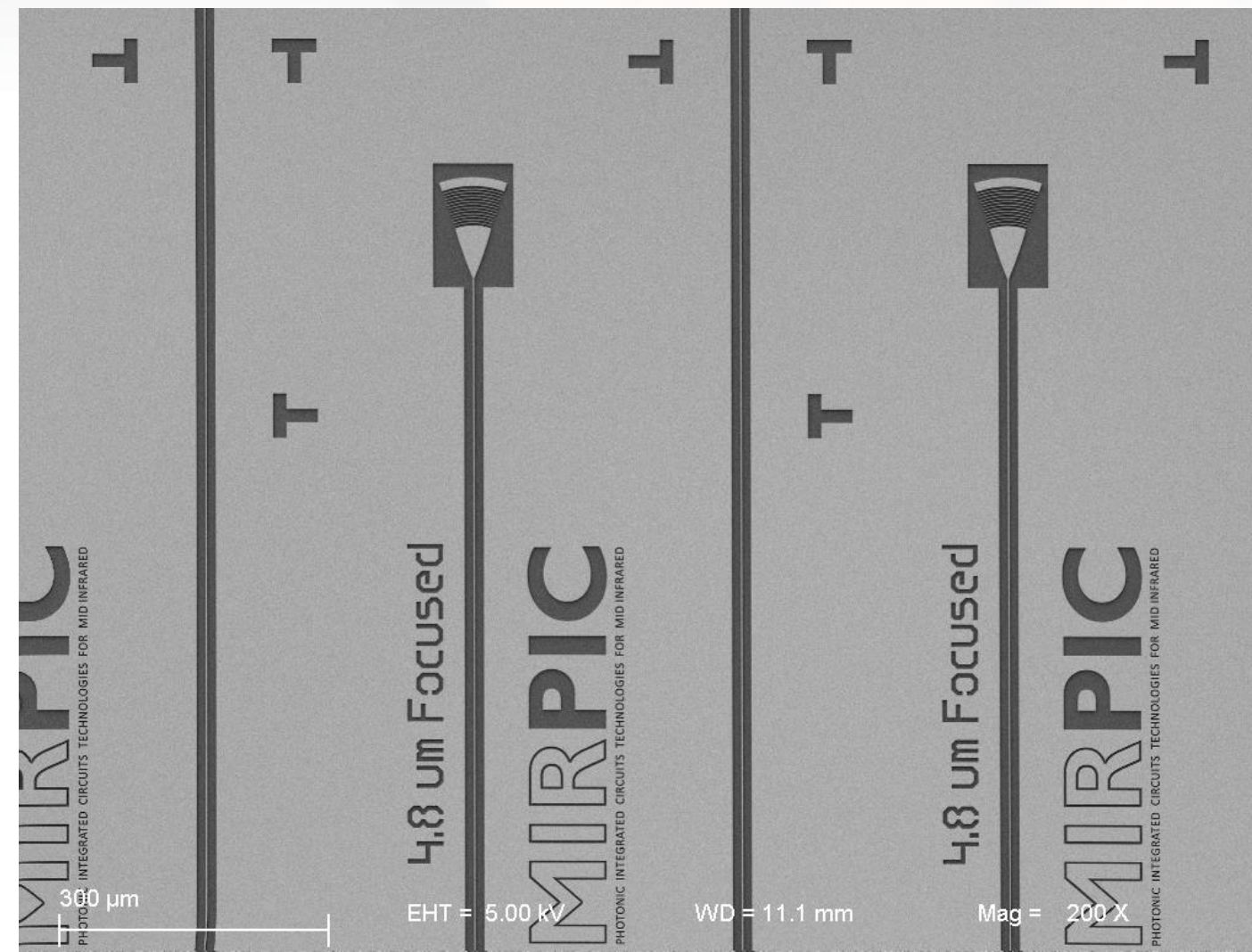
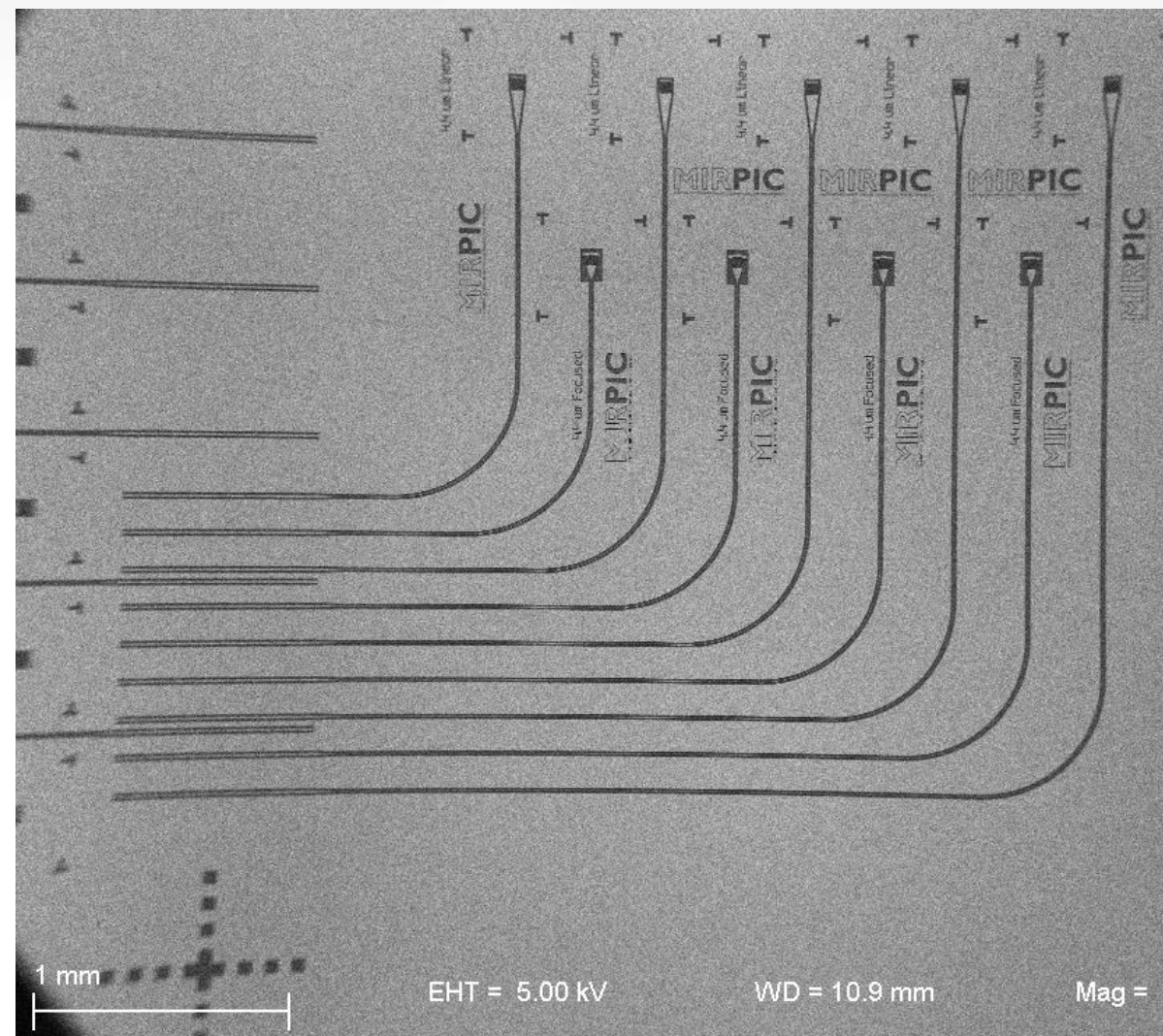
Characterization setup II
Light source: QCLs (3.7 - 5.2 μm)
Detector: InAs/InAsSb superlattice
Coupling through InF₃/ZBLAN
single-mode and multi-mode fibers

Ge-on-Si material platform; waveguides H = 2.0 μm , W = 1.6 μm

Bending radius [μm]	Attenuation [dB/cm] (number of measurements)	Attenuation [dB/ 90° bend] (number of measurements)
100	2.79 \pm 0.57 (10)	0.13 \pm 0.09 (8)
200	2.52 \pm 0.11 (8)	0.17 \pm 0.09 (10)
300	2.52 \pm 0.16 (20)	0.39 \pm 0.08 (19)
500	2.11 \pm 0.46 (11)	0.17 \pm 0.10 (14)

Waveguide attenuation below 3.0 dB/cm!

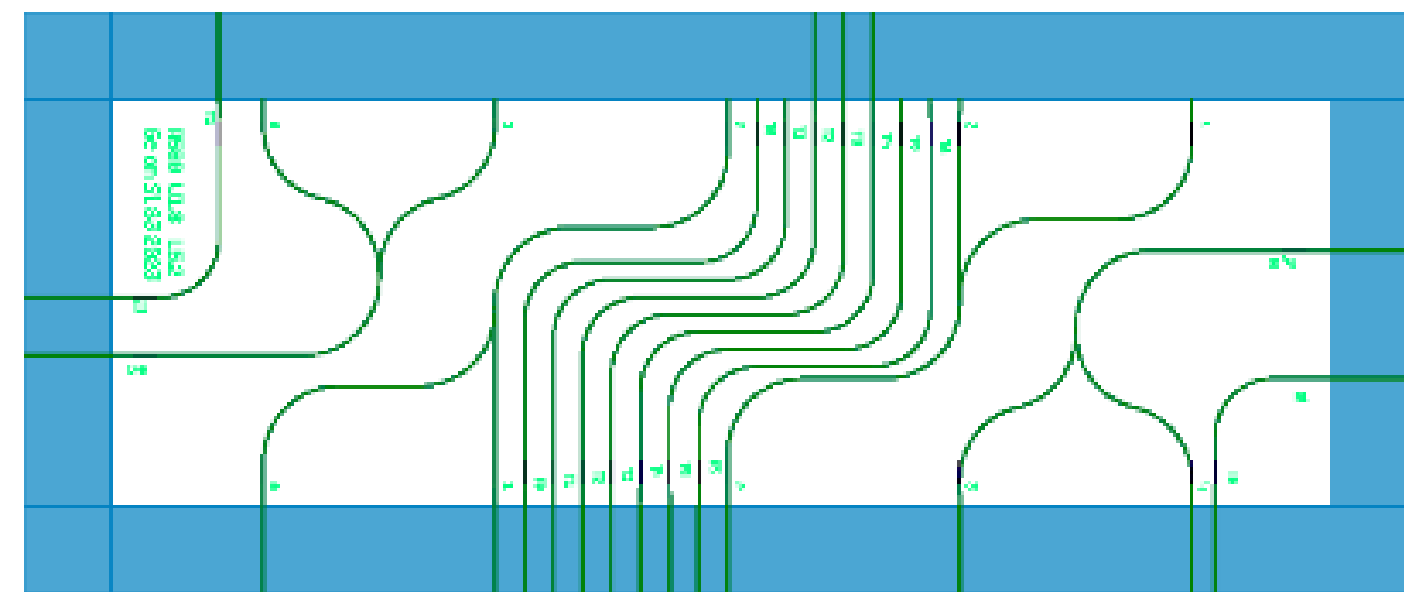
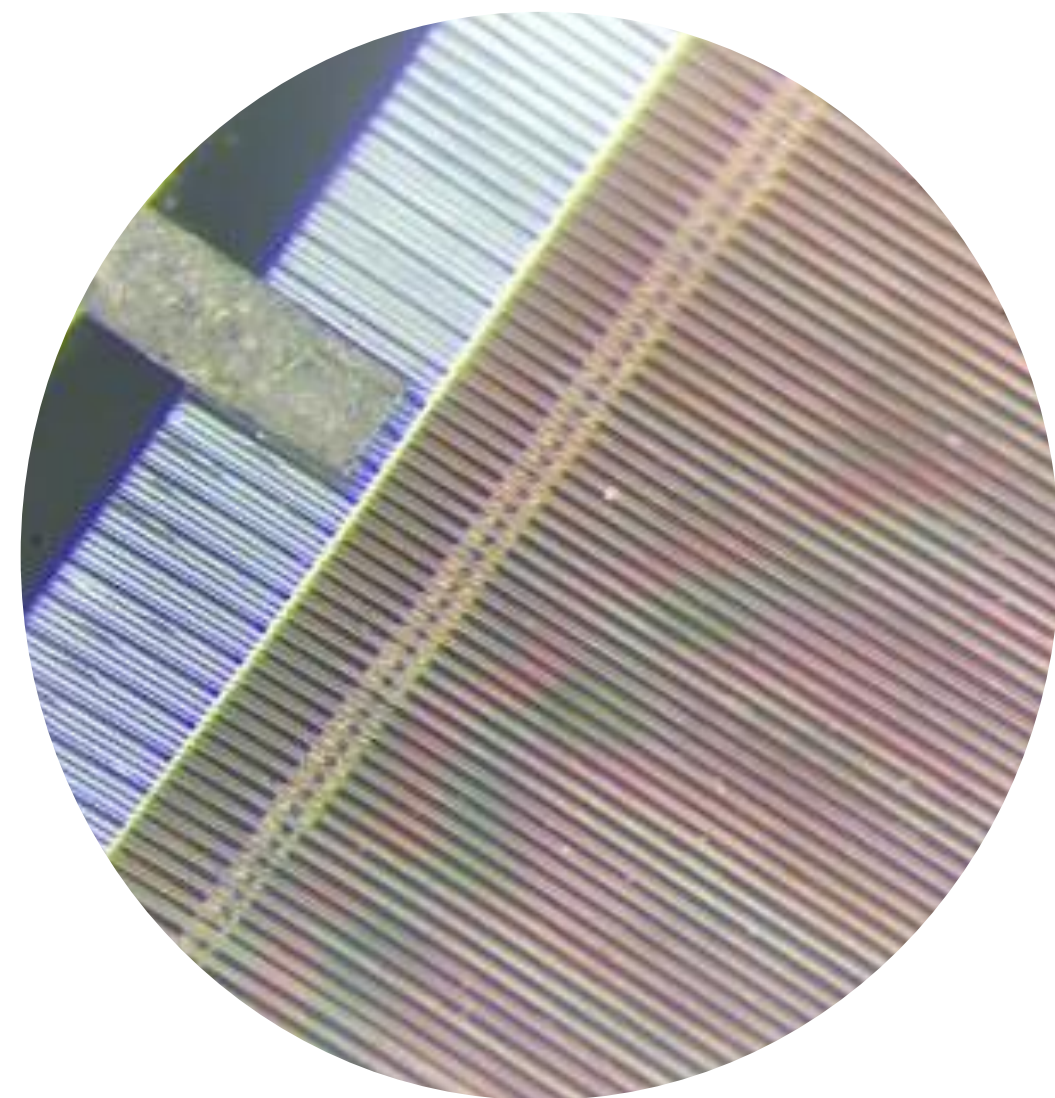
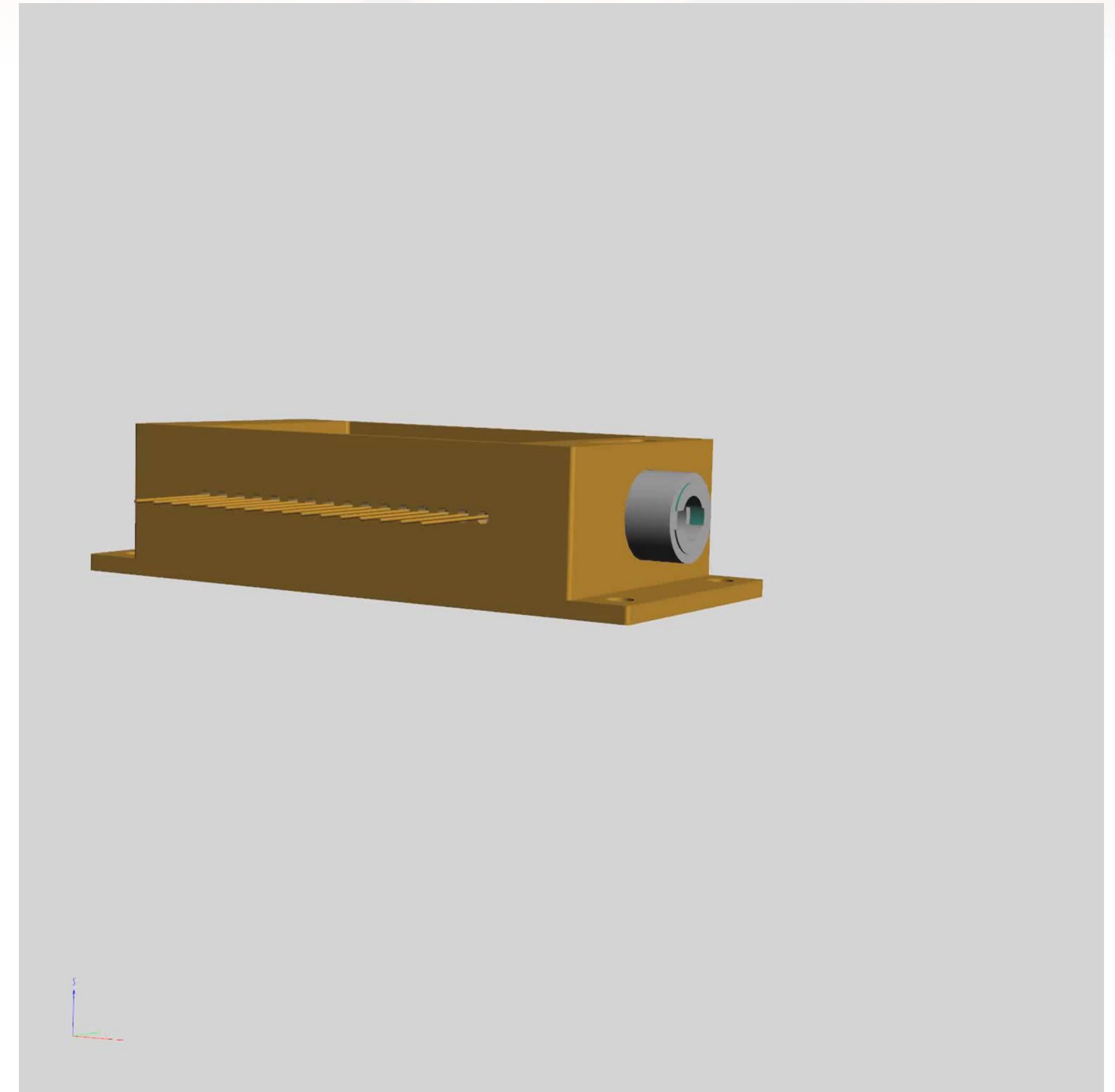
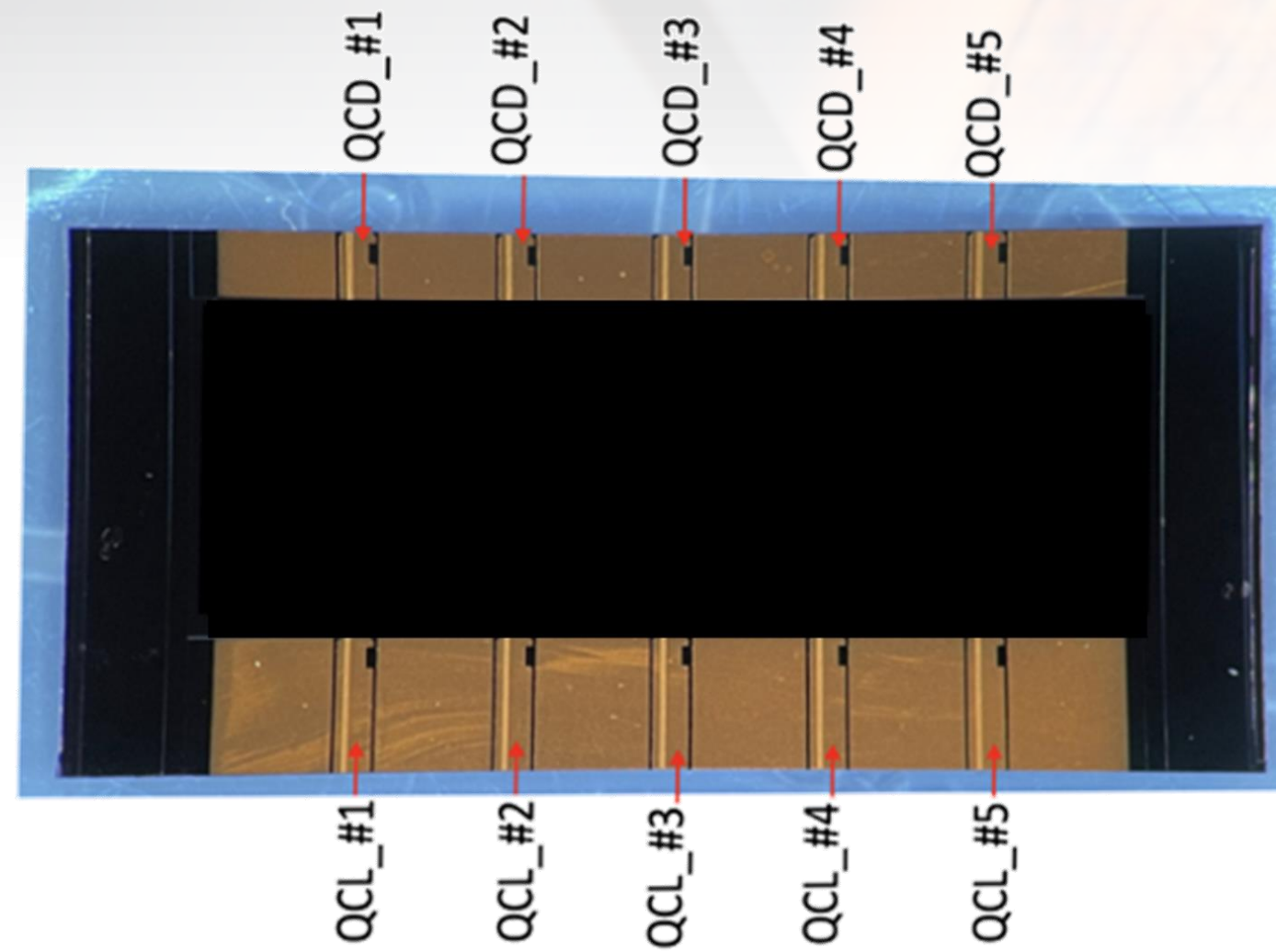
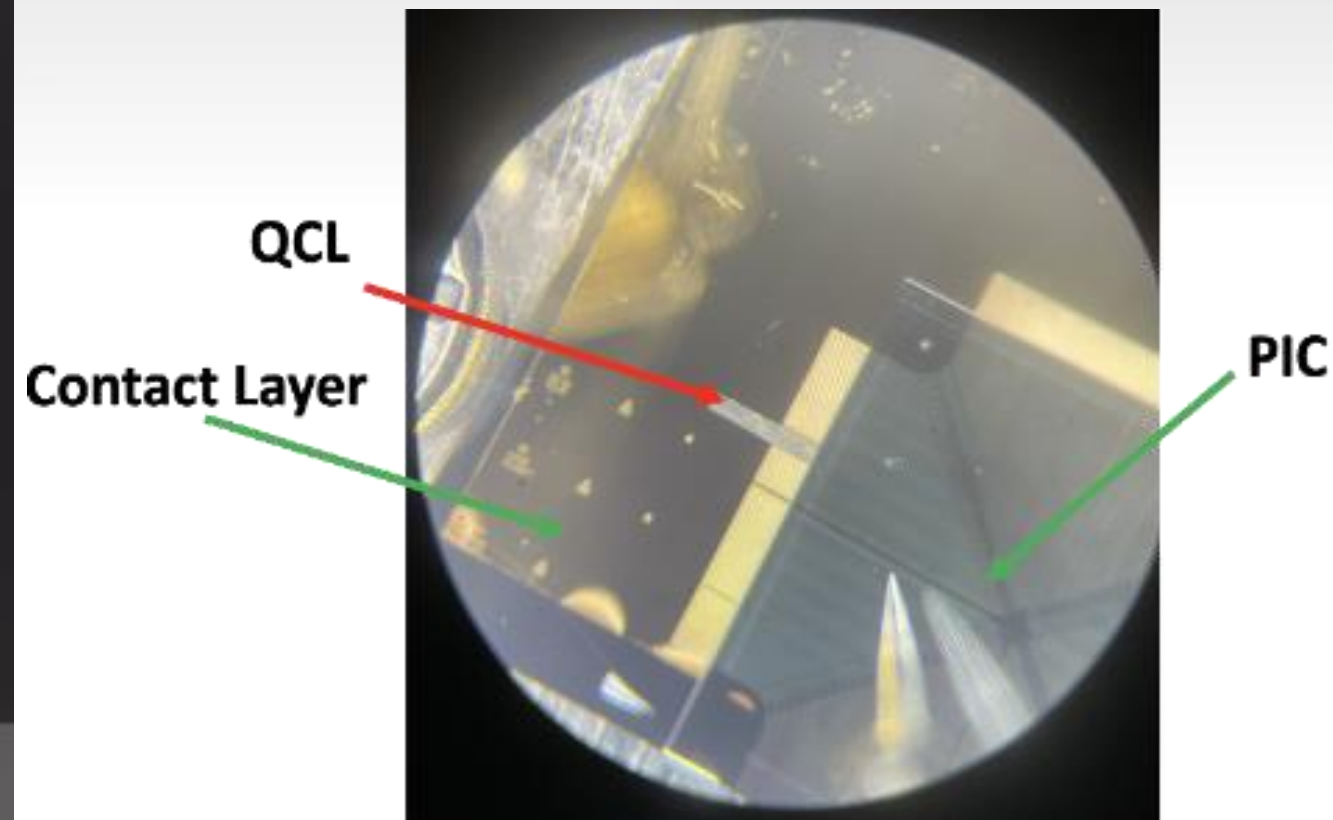
Integration with passive photonic circuits (Ge-on-Si)

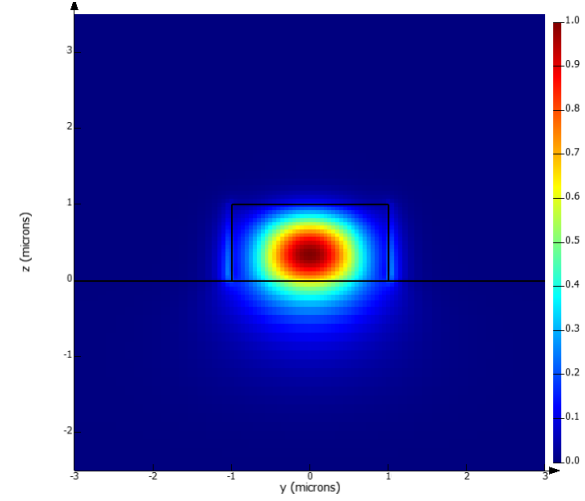
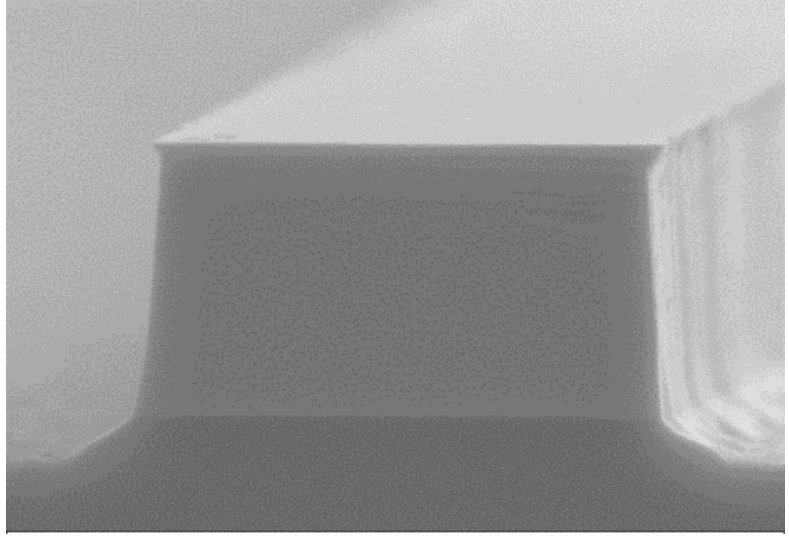
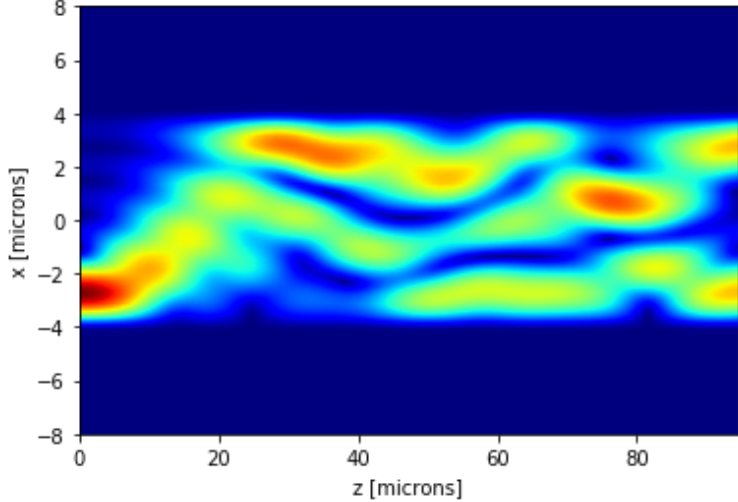
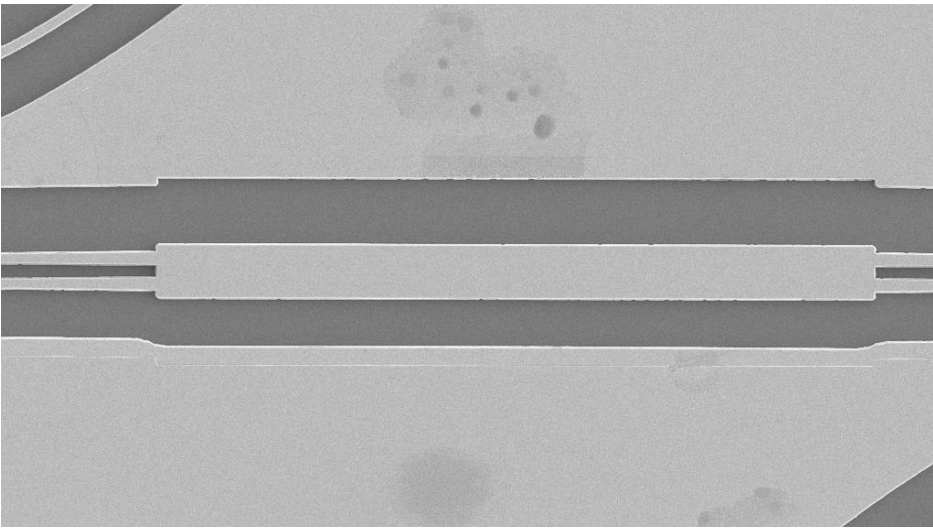
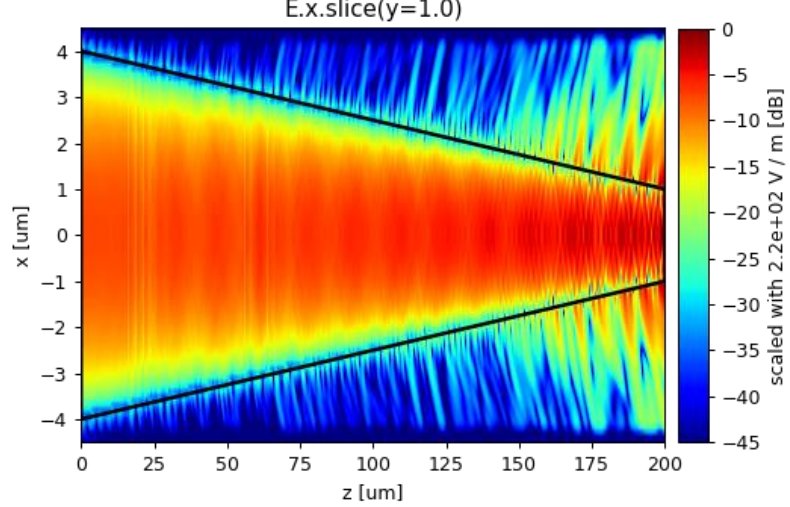
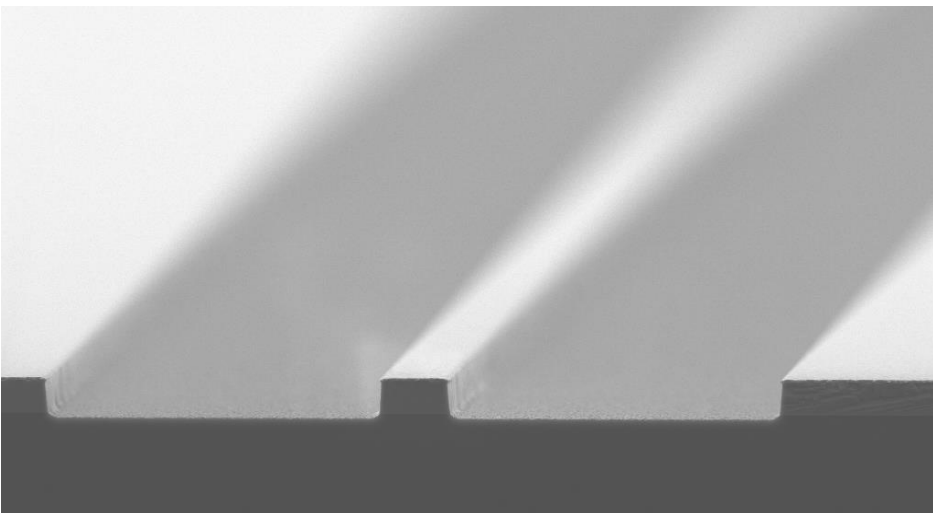


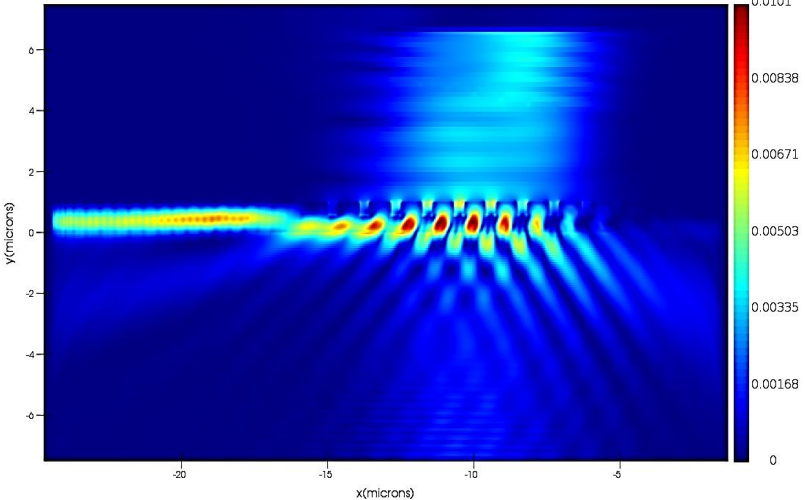
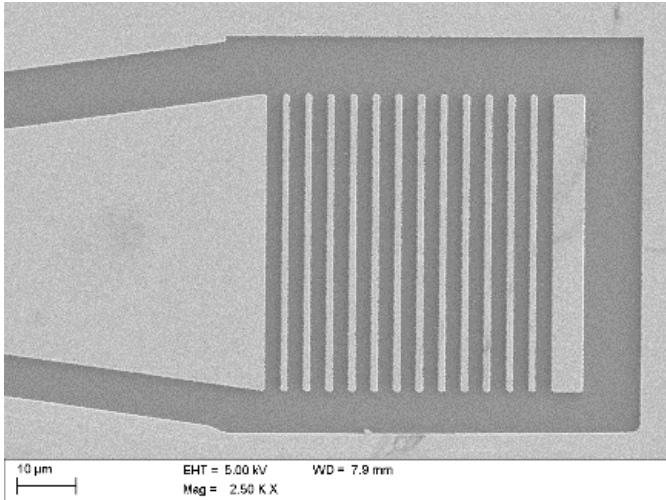
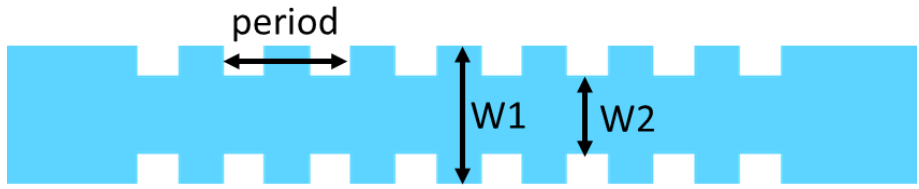
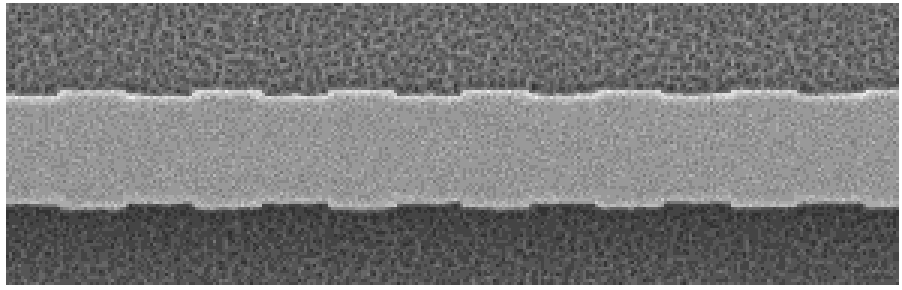
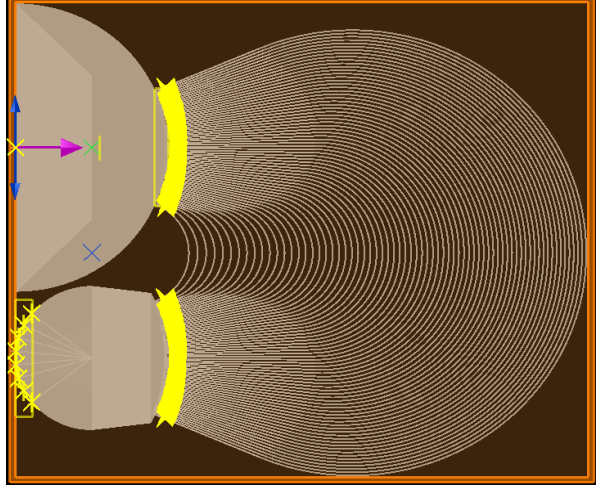
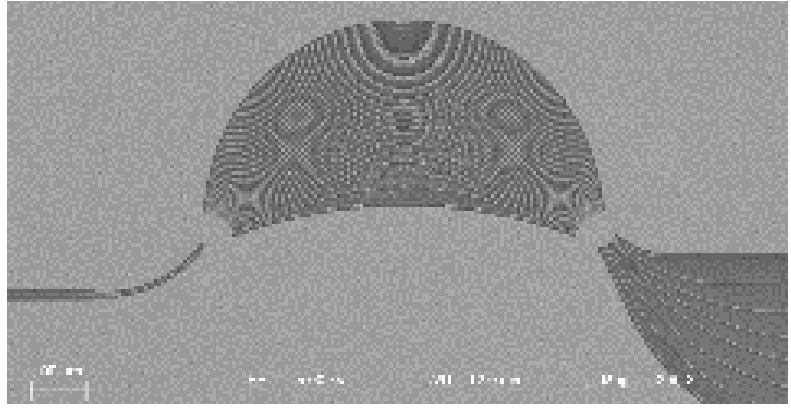
First flip-chip integration tests in progress.

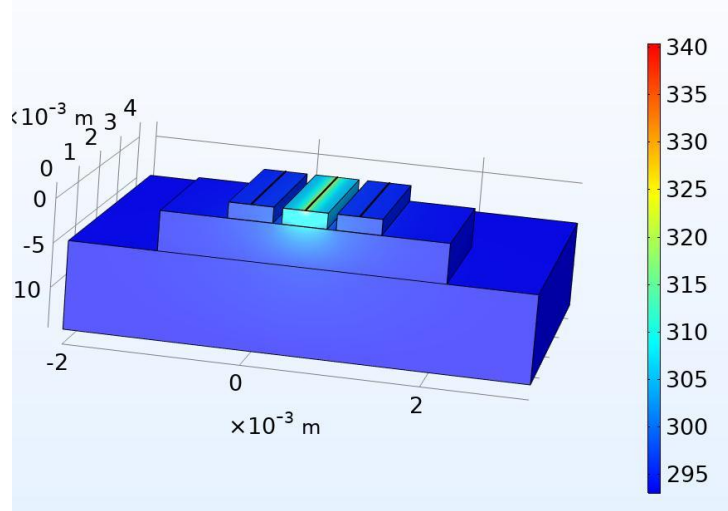
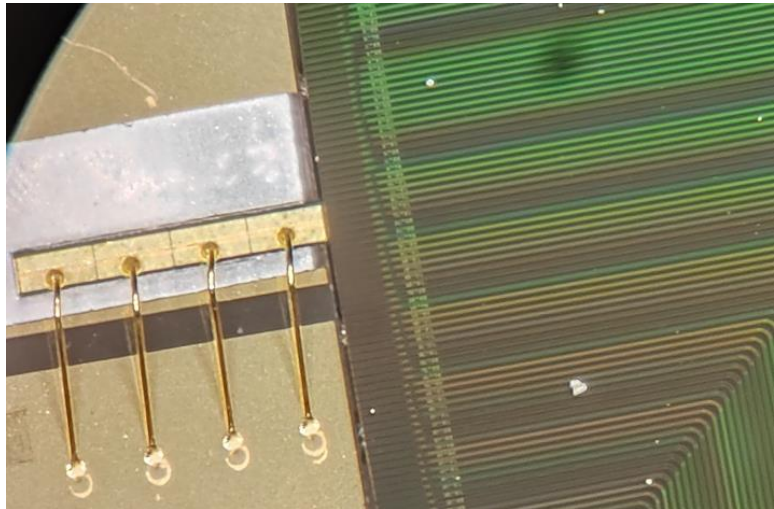
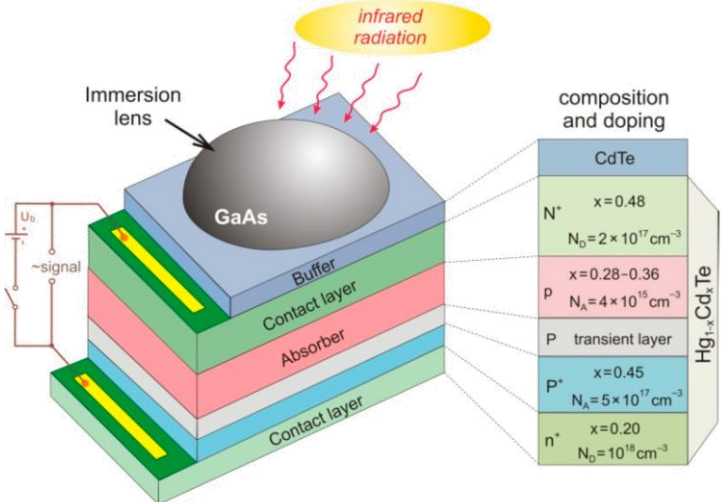
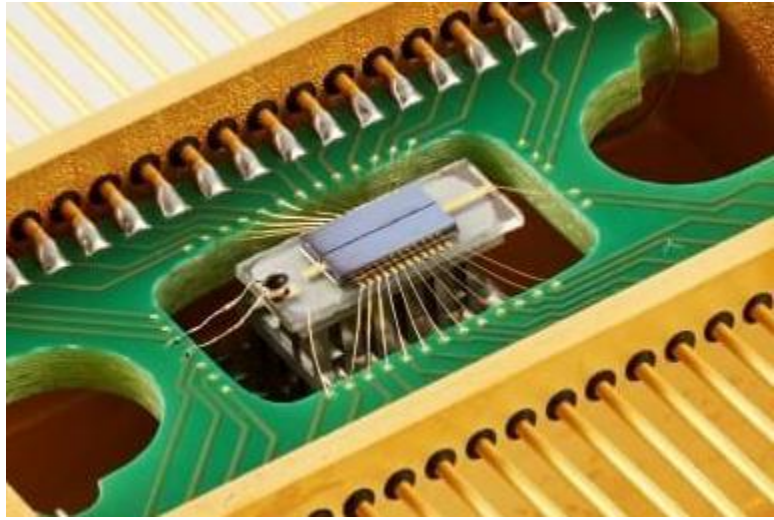
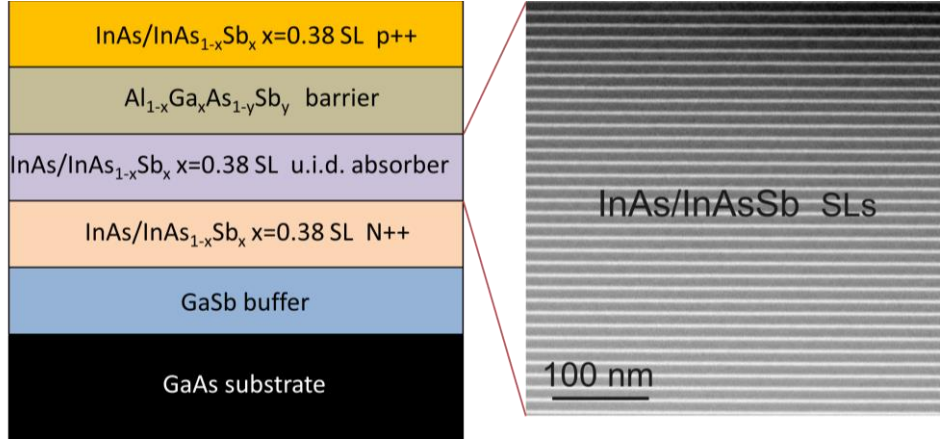
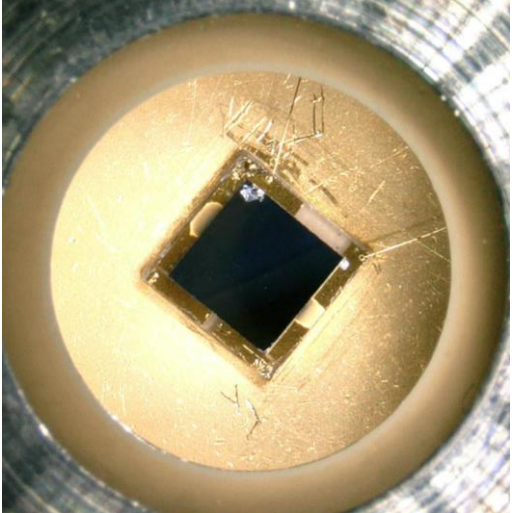
QCLs-waveguides integration experiments

packaging concept



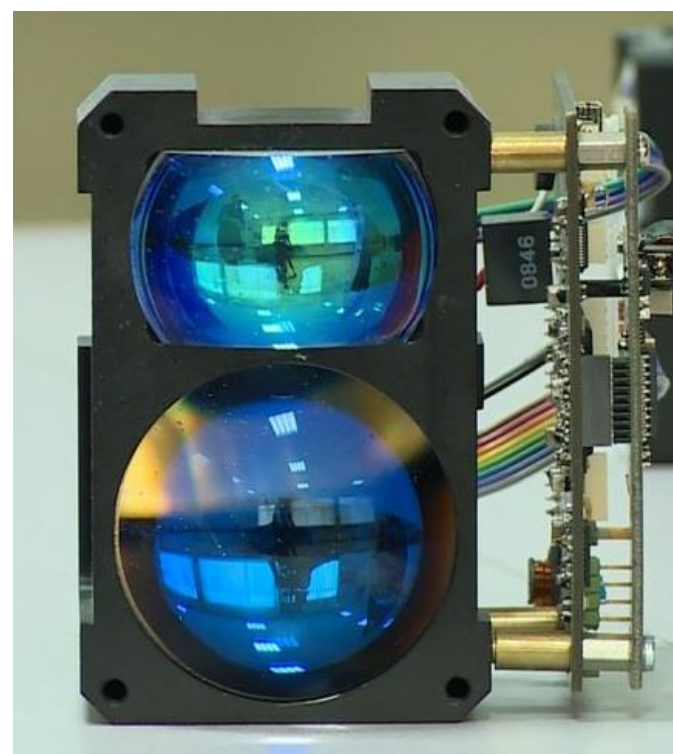
component	design	structure	parameters
<p>Waveguide WG</p>			<ul style="list-style-type: none"> ■ attenuation 2-3 dB/cm ■ spectral range 3.0 – 5.5 μm ■ minimum bending radius 500 μm ■ minimum WG width 0.8 μm ■ Ge layer thickness 1 μm and 2 μm
<p>Multi-Mode Interference (MMI) coupler</p>			<ul style="list-style-type: none"> ■ spectral range 3.0 – 5.5 μm ■ excess loss below 0.8 dB ■ 1x2, 2x2 and 1x4 configuration ■ asymmetric splitting ratio available
<p>Spot-Size Converter SSC</p>			<ul style="list-style-type: none"> ■ spectral range 3.0 – 5.5 μm ■ transmission 90% ■ lateral taper ($w_{\text{out}} = 8 \mu\text{m}$)

component	design	structure	parameters
<p>Grating Coupler GC</p>			<ul style="list-style-type: none"> ■ spectral range: 3.0 – 5.5 μm ■ transmission above 15%
<p>Distributed Bragg Reflector DBR</p>			<ul style="list-style-type: none"> ■ Bragg wavelength: 3.0 – 5.5 μm ■ reflectivity above 80% ■ tailored spectral width ■ side lobe suppression above 10 dB
<p>Arrayed Waveguide Grating AWG</p>			<ul style="list-style-type: none"> ■ spectral range: 3.0 – 5.5 μm ■ insertion loss below 4 dB ■ arbitrary λ_c, $\Delta\lambda$ and FSR

component	design	structure	parameters																						
<p>QCL laser</p>			<ul style="list-style-type: none"> ▪ spectral range 4.4 – 5.2 μm ▪ pulse power 500 mW ▪ pulse duration 0.2 – 1.0 μs ▪ $I_{\text{th}} < 3.0 \text{ A}$ ▪ $U < 18.0 \text{ V}$ 																						
<p>MCT detector</p>	 <table border="1" data-bbox="1372 1095 1499 1346"> <thead> <tr> <th colspan="2">composition and doping</th> </tr> </thead> <tbody> <tr> <td>CdTe</td> <td></td> </tr> <tr> <td>N^+</td> <td>$x=0.48$</td> </tr> <tr> <td></td> <td>$N_D=2 \times 10^{17} \text{ cm}^{-3}$</td> </tr> <tr> <td>$P$</td> <td>$x=0.28-0.36$</td> </tr> <tr> <td></td> <td>$N_A=4 \times 10^{17} \text{ cm}^{-3}$</td> </tr> <tr> <td>$P$</td> <td>transient layer</td> </tr> <tr> <td>P^+</td> <td>$x=0.45$</td> </tr> <tr> <td></td> <td>$N_D=5 \times 10^{17} \text{ cm}^{-3}$</td> </tr> <tr> <td>$n^+$</td> <td>$x=0.20$</td> </tr> <tr> <td></td> <td>$N_D=10^{19} \text{ cm}^{-3}$</td> </tr> </tbody> </table>	composition and doping		CdTe		N^+	$x=0.48$		$N_D=2 \times 10^{17} \text{ cm}^{-3}$	P	$x=0.28-0.36$		$N_A=4 \times 10^{17} \text{ cm}^{-3}$	P	transient layer	P^+	$x=0.45$		$N_D=5 \times 10^{17} \text{ cm}^{-3}$	n^+	$x=0.20$		$N_D=10^{19} \text{ cm}^{-3}$		<ul style="list-style-type: none"> ▪ spectral range 2 – 14 μm ▪ detectivity (room temperature) $5 \cdot 10^{10} - 5 \cdot 10^7 \text{ cmHz}^{1/2}\text{W}^{-1}$ ▪ bandwidth up to 2 GHz
composition and doping																									
CdTe																									
N^+	$x=0.48$																								
	$N_D=2 \times 10^{17} \text{ cm}^{-3}$																								
P	$x=0.28-0.36$																								
	$N_A=4 \times 10^{17} \text{ cm}^{-3}$																								
P	transient layer																								
P^+	$x=0.45$																								
	$N_D=5 \times 10^{17} \text{ cm}^{-3}$																								
n^+	$x=0.20$																								
	$N_D=10^{19} \text{ cm}^{-3}$																								
<p>SL antimonide detector</p>			<ul style="list-style-type: none"> ▪ spectral range 1.7 – 13 μm ▪ detectivity (room temperature) $5 \cdot 10^{10} - 7 \cdot 10^7 \text{ cmHz}^{1/2}\text{W}^{-1}$ ▪ bandwidth up to 5 GHz ▪ ROHS compliant 																						

- QCLs and detectors integrated with waveguides (in progress)
- First MIRPICs packaged (end of 2024)
- Line-up of technology demonstrators (on the roadmap)

**FSOC
transmitter**



Dec. 2024

**Gas
analyzer**



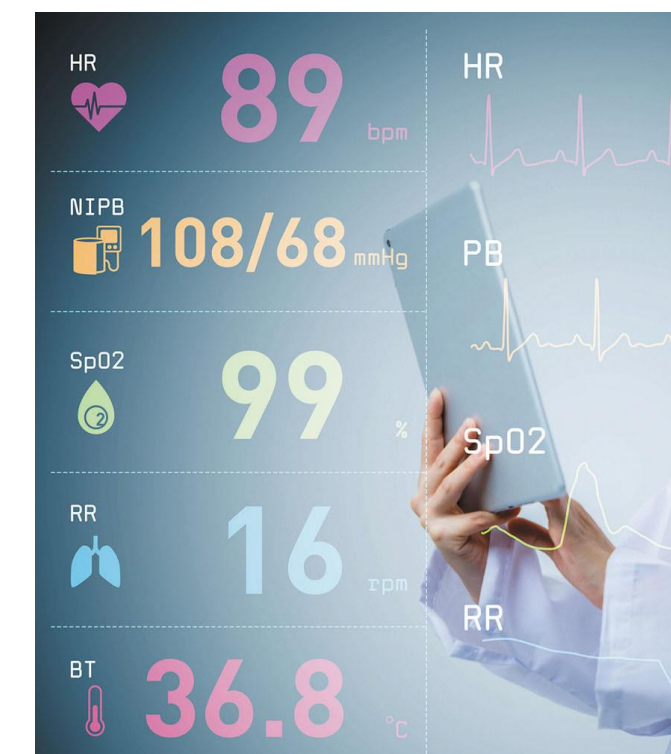
Dec. 2025

**Driver condition
monitoring**



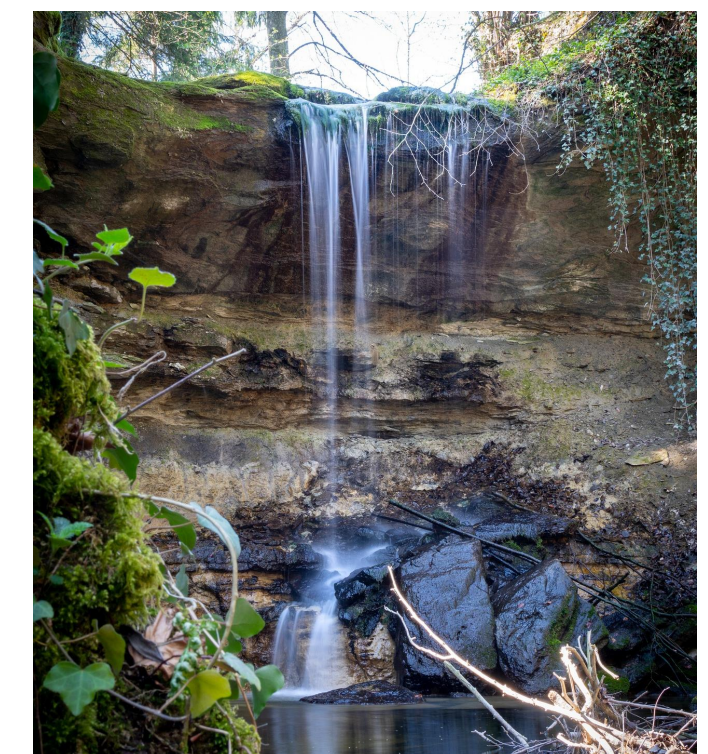
June 2026

**Breath
analyzer**



June 2026

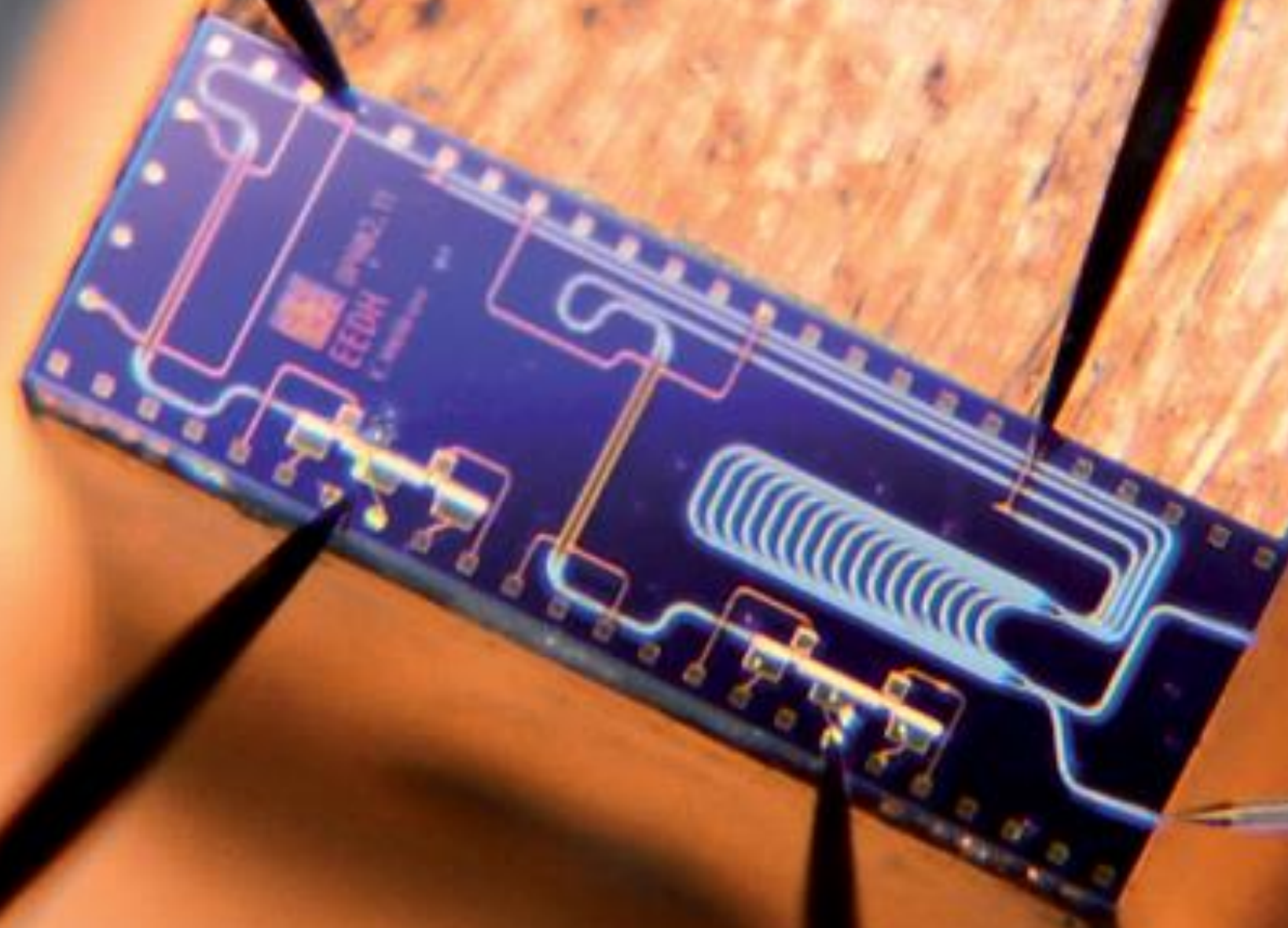
**Water quality
monitoring**



March 2027



From MIRPIC to HyperPIC



IPCEI – Important Projects of Common European Interest

The context



https://commission.europa.eu/strategy-and-policy/priorities-2019-2024/europe-fit-digital-age/european-chips-act_en

Growing global demand for semiconductors

Digital sovereignty – EC proposes Chips Act to confront semiconductor shortages and strengthen Europe's technological leadership.

European Commission
EUROPEAN CHIPS ACT
February 2022
#EUChipsAct #DigitalEU

Our aim is to jointly create a state-of-the-art European chip ecosystem, including production. We need to link together our world-class research, design and testing capacities. We need to coordinate EU and national investment along the value chain. This is not just a matter of our competitiveness. This is also a matter of tech sovereignty.

Ursula von der Leyen
President of the European Commission, 2021 State of the Union address

Semiconductor chips are the essential building blocks of digital products we use constantly ranging from smartphones and computers, to appliances in our homes, lifesaving medical equipment, communication, energy, industrial automation etc. Chips are everywhere.

In 2020, more than **1 trillion microchips** were manufactured around the world, about **130 chips for every person on earth**.

World shortage since 2020

- Higher prices
- Lengthier delivery for consumer electronics and life-saving equipment
- Car

Europe is strong in some specific areas

- Semiconductor research: World leading techniques behind most advanced chips
- Chip manufacturing equipment: central equipment for all advanced chips
- Silicon wafer: mirror-like material essential for manufacturing semiconductors

However, **the EU has only roughly 10% of global market share** and is heavily dependent on imports.

The EU aims to play a leading role in the design and manufacturing of the next generation of microchips, down to 2 nanometers nodes and below. A nanometer is how much a fingernail grows per second.

Current state of art in chips: engraving at 5 nanometres

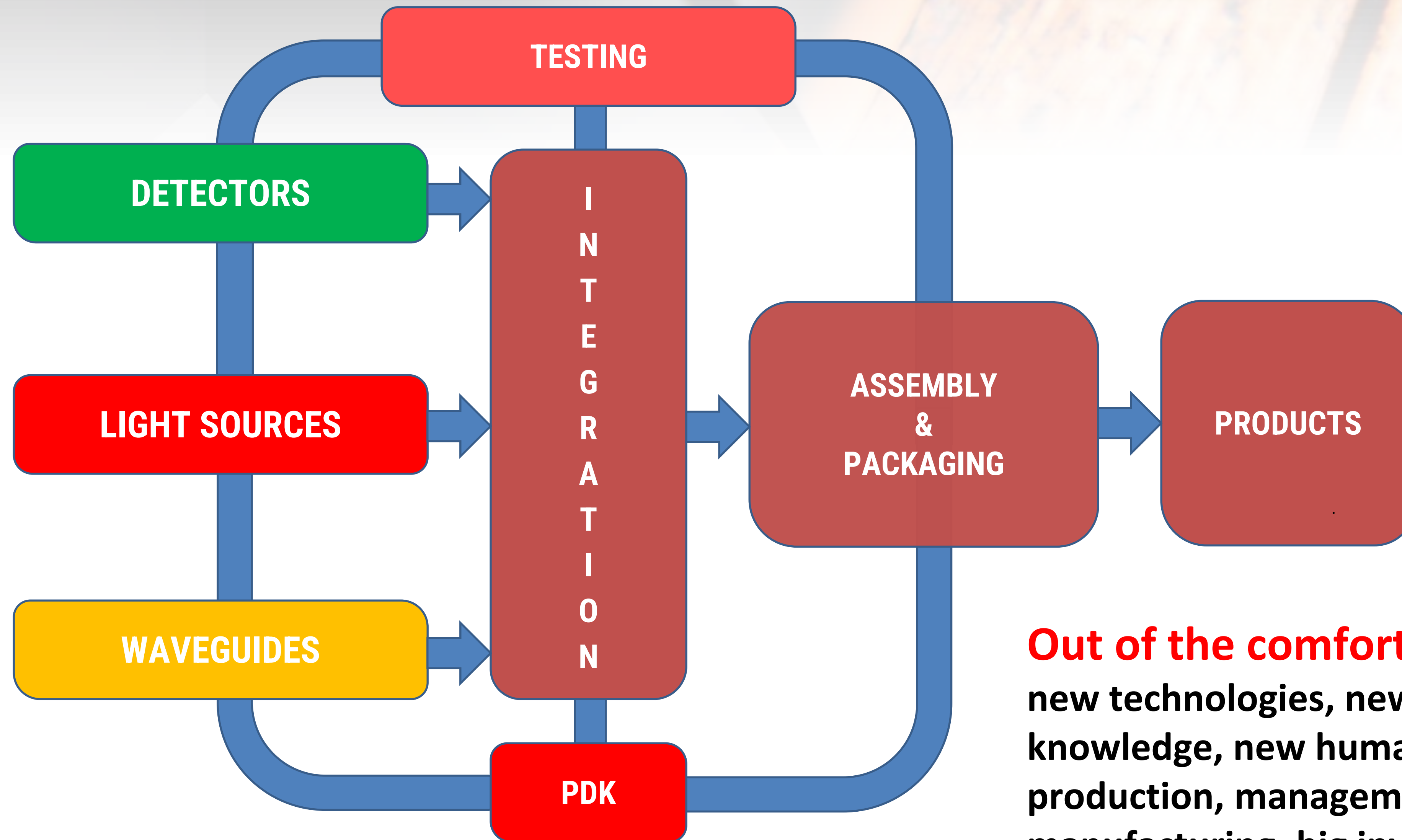
2022: 3 nanometres semiconductor goes into production. 2 nanometres and below are expected in 2024.



THE EU CHIPS ACT & TECHNOLOGICAL SOVEREIGNTY



HyperPIC proposal within IPCEI mechanism



Out of the comfort zone:

new technologies, new infrastructure, new knowledge, new human capital (R&D, production, management), new approach to manufacturing, big investments (IPCEI)

HyperPIC proposal within IPCEI mechanism

HyperPIC R&D partners

1. VIGO Photonics
2. Warsaw University of Technology
3. Institute of Microelectronics and Photonics SBŁ
4. Universitat Politecnica de Valencia
5. Eindhoven University of Technology
6. Politecnico di Milano
7. Tyndall National Institute
8. Silicon Austria Labs
9. Photon IP
10. Ficontec
11. KDPOF
12. TRUMPF Photonic Components
13. ams Osram



HyperPIC proposal within IPCEI mechanism

State aid: Commission approves up to €8.1 billion of public support by fourteen Member States for an Important Project of Common European Interest in microelectronics and communication technologies



The first workstream "Sense" will focus on **developing novel sensors** able to collect relevant analogue signals from our environment and translate them into digital data. **Vigo, a Polish SME**, will develop sensors in highly compact integrated circuits, replacing the current complex and large systems.

Page 1 of 1

Top

Quote(s)

Print friendly pdf

Contacts for media

innovation and the first industrial deployment of microelectronics and communication technologies across the value chain.

The project, called "IPCEI ME/CT", was jointly prepared and notified by fourteen Member States: Austria, Czechia, Finland, France, Germany, Greece, Ireland, Italy, Malta, the Netherlands, Poland, Romania, Slovakia and Spain.

Total budget: ca. 253.4 mln EUR
Public aid: ca. 102.9 mln EUR

IPCEI – Important Projects of Common European Interest

Contract between VIGO and NCBR signed on 14th May 2024

HyperPIC – Fotoniczne układy scalone do zastosowań w średniej podczerwieni

HyperPIC – Photonic integrated circuits for applications in mid-infrared





Instead of summary



Instead of summary

Every journey begins with a first step...

Every journey begins with a first step...

**HyperPIC is a very long journey,
big challenge, a unique opportunity, and a big adventure!**

Join the adventure!

